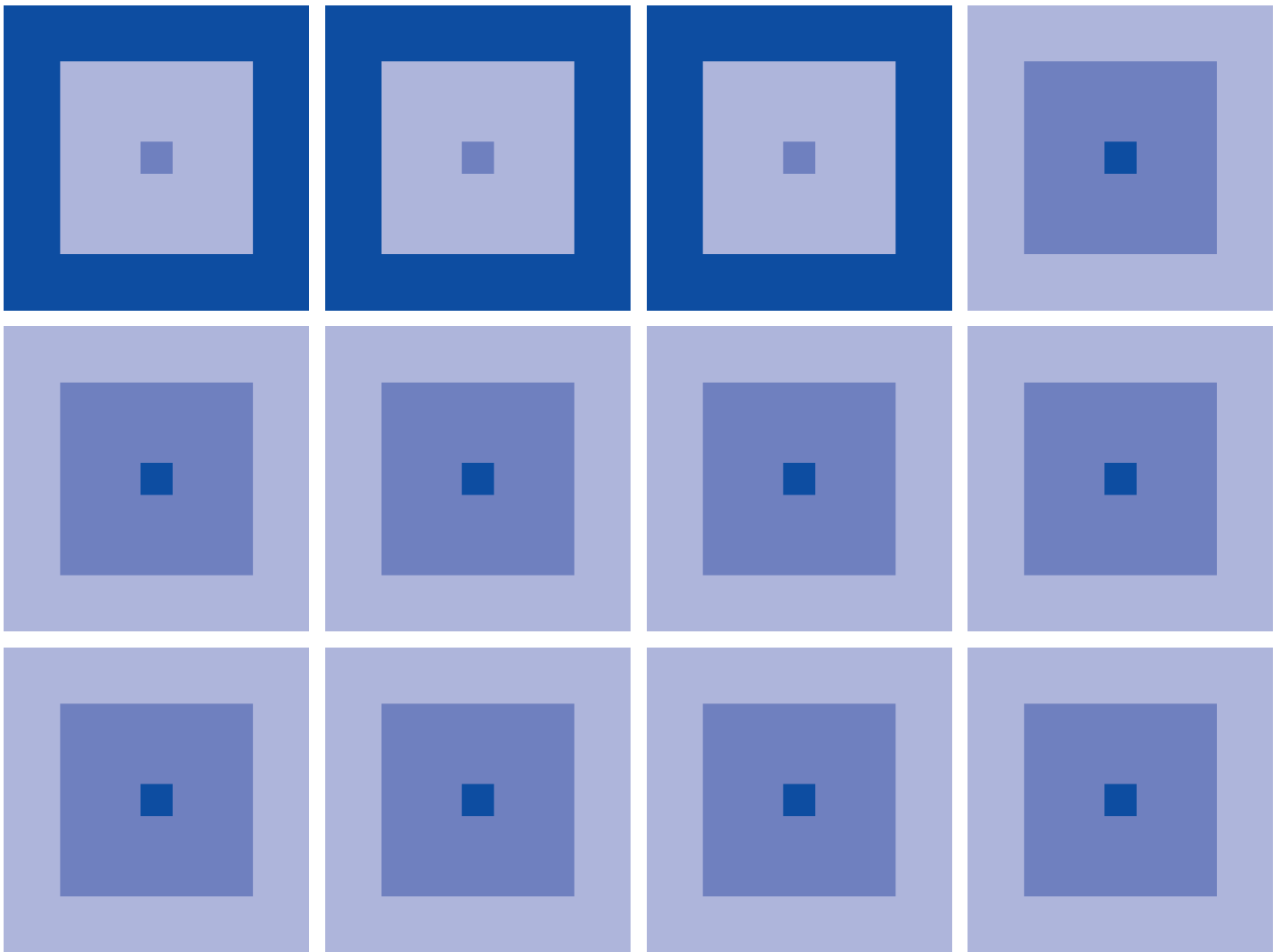


POWER SUPPLY IC
S1F70000 Series
Technical Manual



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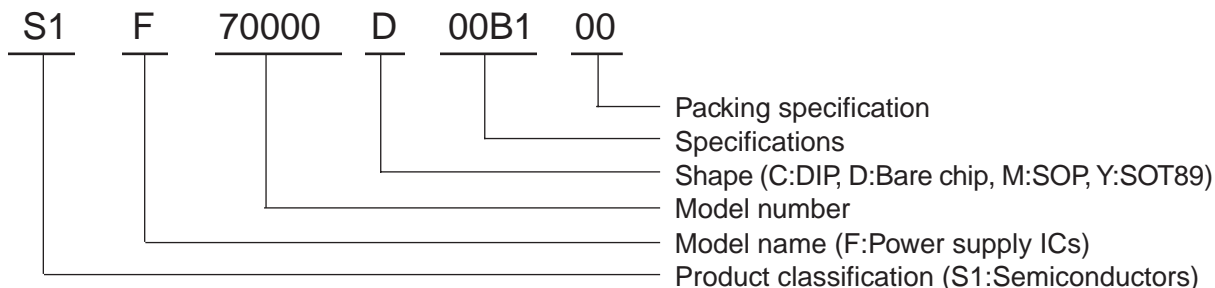
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The information of the product number change

Starting April 1, 2001 the product number has been changed as listed below. To order, please use the new product number. For further information, please contact Epson sales representative.

Configuration of product number

●DEVICES (Example : S1F70000D00B100)



Comparison table between new and previous number

Previous number	New number	Previous number	New number
SCI7660M0B	S1F76600M0B0	SCI7530M0B	S1F75300M0B0
SCI7660C0B	S1F76600C0B0	SCI7721Y*A	S1F77210Y1*0
SCI7662M0A	S1F76620M0A0	SCI7721Y*B	S1F77210Y2*0
SCI7662D0A	S1F76620D0A0	SCI7720Y*A	S1F77200Y1*0
SCI7661M0B	S1F76610M0B0	SCI7722YDB	S1F77220Y2D0
SCI7661M0B	S1F76610M0B0		
SCI7661M0B	S1F76610M2B0		
SCI7661C0B	S1F76610C0B0		
SCI7654M0A	S1F76540M0A0		
SCI7654C0A	S1F76540C0A0		
SCI7664M0A	S1F76640M0A0		
SCI7664D0A	S1F76640D0A0		
SCI7810Y*B	S1F78100Y2*0		
SCI7910Y*A	S1F79100Y1*0		
SCI7631MLA	S1F76310M1L0		
SCI7631MBA	S1F76310M1B0		
SCI7631MKA	S1F76310M1K0		
SCI7631MAA	S1F76310M1A0		
SCI7638MHA	S1F76380M1H0		
SCI7638MLA	S1F76380M1L0		
SCI7633MBA	S1F76330M1B0		
SCI7110M0A	S1F71100M0A0		
SCI7120M0A	S1F71200M0A0		
SCI7120M0B	S1F71200M0B0		
SCI7530M0A	S1F75300M0A0		

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Introduction

This book describes SEIKO EPSON's full lineup of power supply ICs and includes a complete set of product specifications. Also included are sections on quality assurance and packaging.

We suggest that you use the selector guide beginning on the following page to choose the IC or IC series that most closely matches your application. Then you can

use the detailed product descriptions in subsequent sections to confirm device specifications and characteristics.

Please contact your local SEIKO EPSON sales representative for further information or assistance on these or other products.

Selection Guide

DC/DC Converter

Product	Features	Package
S1F76600M0B0	<ul style="list-style-type: none"> Supply voltage conversion IC. It effectively converts input voltage V_{DD} into $-V_{DD}$ or $2V_{DD}$ Output current : Max. 30mA at $-5V$ Power conversion efficiency: Typ. 95% 	SOP4-8pin
S1F76600C0B0		DIP-8pin
S1F76620M0A0	<ul style="list-style-type: none"> Supply voltage conversion IC. It effectively converts input voltage V_{DD} into $-V_{DD}$ or $2V_{DD}$ Output current : Max. 30mA at $5V$ Power conversion efficiency: Typ. 95% 	SOP4-8pin

DC/DC Converter and Voltage Regulator

Product	Features	Package
S1F76610M0B0	<ul style="list-style-type: none"> On-chip voltage regulator. It effectively converts input voltage V_{DD} into $-V_{DD}/-2V_{DD}$ or $2V_{DD}/3V_{DD}$ Output current : Max. 20mA at $-5V$ Power conversion efficiency: Typ. 95% Three temperature gradients for LCD panel power. 	SOP5-14pin
S1F76610M2B0		SSOP2-16pin
S1F76610C0B0		DIP-14pin
S1F76540M0A0	<ul style="list-style-type: none"> On-chip voltage regulator. It effectively converts input voltage V_{DD} into $-2V_{DD}/-3V_{DD}/-4V_{DD}$. Low current Consumption : Typ. 130μA at $-5V$, 4-time boosting Power conversion efficiency: Typ. 95% Three temperature gradients for LCD panel power. 	SSOP2-16pin
S1F76540C0A0		DIP-16pin
S1F76640M0A0	<ul style="list-style-type: none"> On-chip voltage regulator. It effectively converts input voltage V_{DD} into $2V_{DD}/3V_{DD}/4V_{DD}$. Output current : Max. 20mA at $5V$ Power conversion efficiency: Typ. 95% Three temperature gradients for LCD panel power. 	SSOP2-16pin

Voltage regulator

Product	Features	Package
S1F78100Y2A0	<ul style="list-style-type: none"> 6.00V positive output voltage regulator. Low operating current (Typ. 3.0μA). Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin
S1F78100Y2B0	<ul style="list-style-type: none"> 5.00V positive output voltage regulator. Low operating current (Typ. 3.0 μA). Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin
S1F78100Y2M0	<ul style="list-style-type: none"> 4.50V positive output voltage regulator. Low operating current (Typ. 3.0 μA). Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin
S1F78100Y2P0	<ul style="list-style-type: none"> 4.00V positive output voltage regulator. Low operating current (Typ. 3.0 μA). Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin
S1F78100Y2K0	<ul style="list-style-type: none"> 3.90V positive output voltage regulator. Low operating current (Typ. 3.0 μA). Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin
S1F78100Y2N0	<ul style="list-style-type: none"> 3.50V positive output voltage regulator. Low operating current (Typ. 3.0 μA). Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin
S1F78100Y2T0	<ul style="list-style-type: none"> 3.30V positive output voltage regulator. Low operating current (Typ. 3.0 μA). Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin
S1F78100Y2C0	<ul style="list-style-type: none"> 3.20V positive output voltage regulator. Low operating current (Typ. 3.0 μA). Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin

Selection Guide

Product	Features	Package
S1F78100Y2D0	<ul style="list-style-type: none"> • 3.00V positive output voltage regulator. • Low operating current (Typ. 3.0 μA). • Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin
S1F78100Y2R0	<ul style="list-style-type: none"> • 2.80V positive output voltage regulator. • Low operating current (Typ. 3.0 μA). • Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin
S1F78100Y2L0	<ul style="list-style-type: none"> • 2.60V positive output voltage regulator. • Low operating current (Typ. 3.0 μA). • Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin
S1F78100Y2F0	<ul style="list-style-type: none"> • 2.20V positive output voltage regulator. • Low operating current (Typ. 3.0 μA). • Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin
S1F78100Y2G0	<ul style="list-style-type: none"> • 1.80V positive output voltage regulator. • Low operating current (Typ. 3.0 μA). • Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin
S1F78100Y2H0	<ul style="list-style-type: none"> • 1.50V positive output voltage regulator. • Low operating current (Typ. 3.0 μA). • Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin
S1F79100Y1B0	<ul style="list-style-type: none"> • -5.00V negative output voltage regulator. • Low operating current (Typ. 4.0 μA). • Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin
S1F79100Y1P0	<ul style="list-style-type: none"> • -4.00V negative output voltage regulator. • Low operating current (Typ. 4.0 μA). • Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin
S1F79100Y1D0	<ul style="list-style-type: none"> • -3.00V negative output voltage regulator. • Low operating current (Typ. 4.0 μA). • Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin
S1F79100Y1G0	<ul style="list-style-type: none"> • -1.80V negative output voltage regulator. • Low operating current (Typ. 4.0 μA). • Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin
S1F79100Y1H0	<ul style="list-style-type: none"> • -1.50V negative output voltage regulator. • Low operating current (Typ. 4.0 μA). • Input voltage stability (Typ. 0.1%/V). 	SOT89-3pin

DC/DC Switching Regulator

Product	Features	Package
S1F76310M1A0	<ul style="list-style-type: none"> • Step-up switching regulator (from 1.5V to 5.0V). • Low operating voltage (Min. 0.9V). • Low operating current (Typ. 10μA). • High precision voltage detection function and battery backup function. • Built-in CR oscillator circuit. • Power-on clear function. 	SOP3-8pin
S1F76310M1K0	<ul style="list-style-type: none"> • Step-up switching regulator (from 1.5V to 3.5V). • Low operating voltage (Min. 0.9V). • Low operating current (Typ. 8μA). • High precision voltage detection function and battery backup function. • Built-in CR oscillator circuit. • Power-on clear function. 	SOP3-8pin
S1F76310M1B0	<ul style="list-style-type: none"> • Step-up switching regulator (from 1.5V to 3.0V). • Low operating voltage (Min. 0.9V). • Low operating current (Typ. 8μA). • High precision voltage detection function and battery backup function. • Built-in CR oscillator circuit. • Power-on clear function. 	SOP3-8pin

Selection Guide

Product	Features	Package
S1F76310M1L0	<ul style="list-style-type: none"> Step-up switching regulator (from 1.5V to 2.4V). Low operating voltage (Min. 0.9V). Low operating current (Typ. 7μA). High precision voltage detection function and battery backup function. Built-in CR oscillator circuit. Power-on clear function. 	SOP3-8pin
S1F76380M1H0	<ul style="list-style-type: none"> Step-up switching regulator (from 1.5V to 2.2V). Low operating voltage (Min. 0.9V). Low operating current. (Typ. 7μA). Built-in CR oscillator circuit. High precision voltage detection. Output voltage response compensation. Temperature characteristics of output voltage for LCD panel (-4.5mV/C). 	SOP3-8pin
S1F76380M1L0	<ul style="list-style-type: none"> Step-up switching regulator (from 1.5V to 2.4V). Low operating voltage (Min. 0.9V). Low operating current. (Typ. 7μA). Built-in CR oscillator circuit. High precision voltage detection. Output voltage response compensation. Temperature characteristics of output voltage for LCD panel (-4.0mV/C). 	SOP3-8pin
S1F76330M1B0	<ul style="list-style-type: none"> Step-up switching regulator (from 1.5V to 3.0V). Low operating voltage (Min. 0.9V). Low operating current. (Typ. 5μA). Built-in crystal oscillator circuit. Equipped with crystal oscillator output pin. 	SOP3-8pin
S1F71100M0A0	<ul style="list-style-type: none"> Step-down switching regulator (from 3.3V ~ 12.0V to 3.3V). Power off current : 1μA Frequency fixing (200kHz) PWM. Soft start function. Overcurrent protection function, Low-voltage protection function. 	SOP4-8pin
S1F71200M0A0	<ul style="list-style-type: none"> Step-up/down switching regulator (from 2.5V ~ 12.0V to 5.0V). Power off current : 1μA Frequency fixing (200kHz) PWM. Soft start function. Overcurrent protection function. 	SSOP2-16pin
S1F71100M0B0	<ul style="list-style-type: none"> Step-up/down switching regulator (from 2.5V ~ 12.0V to 3.3V). Power off current : 1μA Frequency fixing (200kHz) PWM. Soft start function. Overcurrent protection function. 	SSOP2-16pin

DC/DC Switching Regulators & Voltage Follower

Product	Features	Package
S1F75300M0A0	<ul style="list-style-type: none"> Step-up switching regulator with built-in voltage follower (from 2.7V ~ 5.5V to 27V). Boosting efficiency (90%). 	SSOP1-20pin
S1F75300M0B0	<ul style="list-style-type: none"> Low current consumption : Typ. 200μA without load Step-up output voltage : Max. 30V Adjustable output voltage with the electronic volume. 	SSOP1-20pin

Voltage Detector

Product	Features	Package
S1F77210Y1L0	<ul style="list-style-type: none"> Voltage detection (Typ. 5.00V). Output format: COMS. Low operating power (Typ. 2.0 μA, $V_{DD} = 6.0V$). 	SOP89-3pin
S1F77210Y1K0	<ul style="list-style-type: none"> Voltage detection (Typ. 4.80V). Output format: COMS. Low operating power (Typ. 2.0 μA, $V_{DD} = 5.0V$). 	SOP89-3pin

Selection Guide

Product	Features	Package
S1F77210Y120	<ul style="list-style-type: none"> Voltage detection (Typ. 4.60V). Output format: COMS. Low operating power (Typ. 2.0 μA, $V_{DD} = 5.0V$). 	SOP89-3pin
S1F77210Y1J0	<ul style="list-style-type: none"> Voltage detection (Typ. 4.40V). Output format: COMS. Low operating power (Typ. 2.0 μA, $V_{DD} = 5.0V$). 	SOP89-3pin
S1F77210Y1M0	<ul style="list-style-type: none"> Voltage detection (Typ. 4.20V). Output format: COMS. Low operating power (Typ. 2.0 μA, $V_{DD} = 5.0V$). 	SOP89-3pin
S1F77210Y1T0	<ul style="list-style-type: none"> Voltage detection (Typ. 4.00V). Output format: COMS. Low operating power (Typ. 2.0 μA, $V_{DD} = 5.0V$). 	SOP89-3pin
S1F77210Y130	<ul style="list-style-type: none"> Voltage detection (Typ. 3.50V). Output format: COMS. Low operating power (Typ. 2.0 μA, $V_{DD} = 4.0V$). 	SOP89-3pin
S1F77210Y1H0	<ul style="list-style-type: none"> Voltage detection (Typ. 3.20V). Output format: COMS. Low operating power (Typ. 2.0 μA, $V_{DD} = 4.0V$). 	SOP89-3pin
S1F77210Y1G0	<ul style="list-style-type: none"> Voltage detection (Typ. 3.00V). Output format: COMS. Low operating power (Typ. 2.0 μA, $V_{DD} = 4.0V$). 	SOP89-3pin
S1F77210Y1R0	<ul style="list-style-type: none"> Voltage detection (Typ. 2.80V). Output format: COMS. Low operating power (Typ. 2.0 μA, $V_{DD} = 3.0V$). 	SOP89-3pin
S1F77210Y1F0	<ul style="list-style-type: none"> Voltage detection (Typ. 2.65V). Output format: COMS. Low operating power (Typ. 2.0 μA, $V_{DD} = 3.0V$). 	SOP89-3pin
S1F77210Y1E0	<ul style="list-style-type: none"> Voltage detection (Typ. 2.55V). Output format: COMS. Low operating power (Typ. 2.0 μA, $V_{DD} = 3.0V$). 	SOP89-3pin
S1F77210Y1S0	<ul style="list-style-type: none"> Voltage detection (Typ. 2.35V). Output format: COMS. Low operating power (Typ. 2.0 μA, $V_{DD} = 3.0V$). 	SOP89-3pin
S1F77210Y1P0	<ul style="list-style-type: none"> Voltage detection (Typ. 2.25V). Output format: COMS. Low operating power (Typ. 2.0 μA, $V_{DD} = 3.0V$). 	SOP89-3pin
S1F77210Y1C0	<ul style="list-style-type: none"> Voltage detection (Typ. 2.15V). Output format: COMS. Low operating power (Typ. 2.0 μA, $V_{DD} = 3.0V$). 	SOP89-3pin
S1F77210Y2F0	<ul style="list-style-type: none"> Voltage detection (Typ. 2.65V). Output format: COMS. Low operating power (Typ. 2.0 μA, $V_{DD} = 3.0V$). 	SOP89-3pin
S1F77210Y2C0	<ul style="list-style-type: none"> Voltage detection (Typ. 2.15V). Output format: COMS. Low operating power (Typ. 2.0 μA, $V_{DD} = 3.0V$). 	SOP89-3pin
S1F77200Y1T0	<ul style="list-style-type: none"> Voltage detection (Typ. 4.00V). Output format: N-ch open drain. Low operating power (Typ. 2.0 μA, $V_{DD} = 5.0V$). 	SOP89-3pin
S1F77200Y1F0	<ul style="list-style-type: none"> Voltage detection (Typ. 2.65V). Output format: N-ch open drain. Low operating power (Typ. 2.0 μA, $V_{DD} = 3.0V$). 	SOP89-3pin
S1F77200Y1C0	<ul style="list-style-type: none"> Voltage detection (Typ. 2.15V). Output format: N-ch open drain. Low operating power (Typ. 2.0 μA, $V_{DD} = 3.0V$). 	SOP89-3pin
S1F77200Y1N0	<ul style="list-style-type: none"> Voltage detection (Typ. 1.90V). Output format: N-ch open drain. Low operating power (Typ. 2.0 μA, $V_{DD} = 3.0V$). 	SOP89-3pin

Selection Guide

Product	Features	Package
S1F77200Y1B0	<ul style="list-style-type: none"> • Voltage detection (Typ. 1.15V). • Output format: N-ch open drain. • Low operating power (Typ. 1.5 μA, $V_{DD} = 1.5V$). 	SOP89-3pin
S1F77200Y1Y0	<ul style="list-style-type: none"> • Voltage detection (Typ. 1.10V). • Output format: N-ch open drain. • Low operating power (Typ. 1.5 μA, $V_{DD} = 1.5V$). 	SOP89-3pin
S1F77200Y1A0	<ul style="list-style-type: none"> • Voltage detection (Typ. 1.05V). • Output format: N-ch open drain. • Low operating power (Typ. 1.5 μA, $V_{DD} = 1.5V$). 	SOP89-3pin
S1F77200Y1V0	<ul style="list-style-type: none"> • Voltage detection (Typ. 0.95V). • Output format: N-ch open drain. • Low operating power (Typ. 1.5 μA, $V_{DD} = 1.5V$). 	SOP89-3pin
S1F77220Y2D0	<ul style="list-style-type: none"> • Voltage detection (Typ. 1.25V). • Output format: P-ch open drain. • Low operating power (Typ. 1.5 μA, $V_{DD} = 1.5V$). 	SOP89-3pin

1. DC/DC Converter

S1F7660 Series CMOS DC/DC Converter (Voltage Doubler)

DESCRIPTION

The S1F7660 Series is a highly efficient CMOS DC/DC converter for doubling an input voltage (from $-1.5V$ to $-8V$). This power-saving IC allows portable computers and similar hand-held equipment to operate from a single power supply, even when they incorporate LSIs that operate at voltages different from those of logic circuits, for example, LCD drivers and analog LSIs.

The S1F7660C0B0 is available in 8-pin plastic DIPs, and the S1F7660M0B0, in 8-pin plastic SOPs.

FEATURES

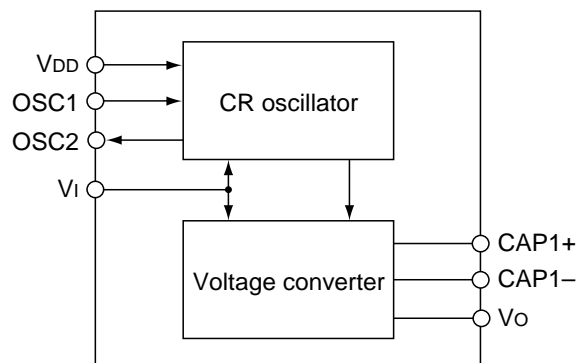
- 95% (Typ.) conversion efficiency
- Two output voltages, V_O , relative to V_{DD} and V_I
- 30mA maximum output current at 5V
- Connecting-in-series configuration obtains a higher output voltage ($V_I = -5V$, $V_O = -15V$ at two-in-series).
- Low operating voltage
- On-chip CR oscillator
- 8-pin plastic DIP and 8-pin plastic SOP

APPLICATIONS

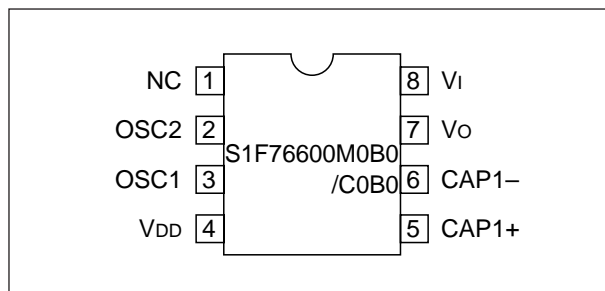
- Fixed-voltage power supplies for battery-operated equipment
- Power supplies for pagers, memory cards, calculators and similar hand-held equipment

- Fixed-voltage power supplies for medical equipment
- Fixed-voltage power supplies for communications equipment
- Uninterruptable power supplies

BLOCK DIAGRAM



PIN ASSIGNMENTS



PIN DESCRIPTIONS

Pin No.	Pin name	Description
1	NC	No connection
2	OSC2	Resistor connection. Open when using external clock
3	OSC1	Resistor connection. Clock input when using external clock
4	VDD	Positive supply (system Vcc)
5	CAP1+	Positive charge-pump connection
6	CAP1-	Negative charge-pump connection
7	Vo	$\times 2$ multiplier output
8	Vi	Negative supply (system ground)

S1F76600 Series

SPECIFICATIONS

Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Input voltage range	V_I	-10.0 to 0.5	V
Output voltage range	V_O	Min. -20.0	V
Power dissipation	P_D	300 (DIP)	mW
		150 (SOP)	
Operating temperature range	T_{opr}	-40 to +85	°C
Storage temperature range	T_{stg}	-65 to +150	°C
Soldering temperature(for 10s). See note.	T_{sol}	260	°C

Note:

Temperatures during reflow soldering must remain within the limits set out in LSI Device Precautions. Never use solder dip to mount S1F70000 series power supply devices.

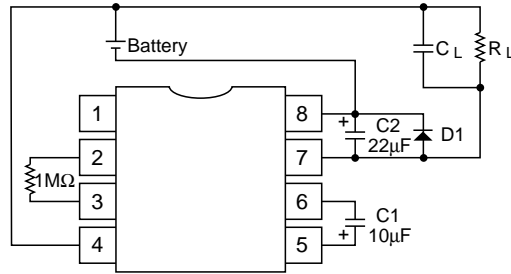
Recommended Operating Conditions

$V_{DD} = 0V$, $T_a = -40$ to $+85^\circ\text{C}$ unless otherwise noted

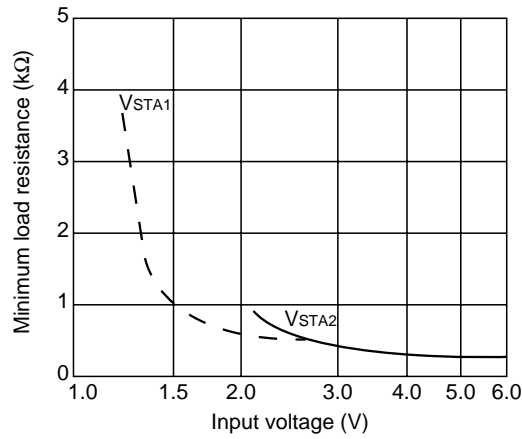
Parameter	Symbol	Condition	Rating			Unit
			Min.	Typ.	Max.	
Oscillator startup voltage	V_{STA}	ROSC = $1M\Omega$, $C_1/C_2 \leq 1/20$, $C_2 \geq 10\mu\text{F}$, $T_a = -20$ to $+85^\circ\text{C}$ See note 1.	—	—	-1.5	V
			—	—	-2.2	
Oscillator shutdown voltage	V_{STP}	ROSC = $1M\Omega$	-1.5	—	—	V
Load resistance	R_L		R_L min See note 2.	—	—	Ω
Output current	I_O		—	—	30.0	mA
Clock frequency	f_{osc}		10.0	—	30.0	kHz
CR oscillator network resistance	R_{osc}		680	—	2,000	k Ω
Capacitance	C_1, C_2		3.3	—	—	μF

Notes:

- The recommended circuit configuration for low-voltage operation (when V_I is between -1.2V and -2.2V) is shown in the following figure. Note that diode D1 should have a maximum forward voltage of 0.6V with 1.0mA forward current.
- R_L min can be varied depending on the input voltage.



3. R_L min is a function of V_I .



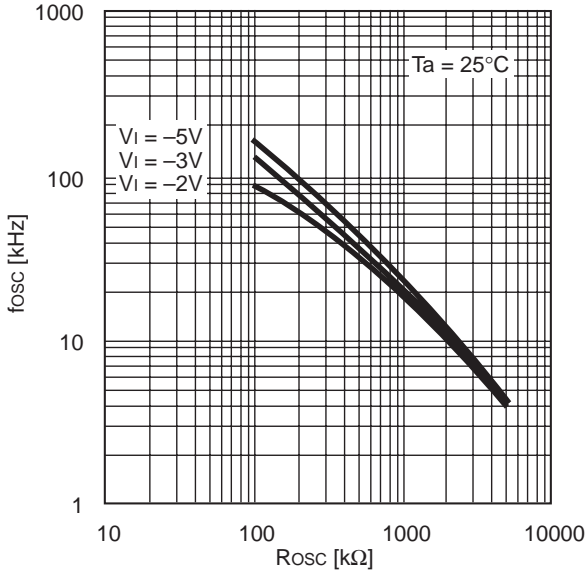
Electrical Characteristics

$V_{DD} = 0V$, $T_a = -40$ to $+85^\circ C$ unless otherwise noted

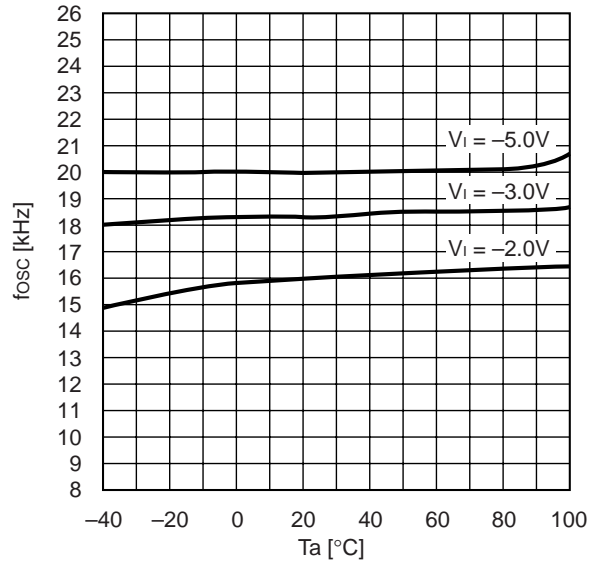
Parameter	Symbol	Condition	Rating			Unit
			Min.	Typ.	Max.	
Input voltage	V_I		-8.0	—	-1.5	V
Output voltage	V_O		-16.0	—	—	V
Multiplier current	I_{OPR}	$R_L = \infty$, $R_{OSC} = 1M\Omega$ $V_I = -5V$	—	20	30	μA
Quiescent current	I_Q	$R_L = \infty$, $V_I = -8V$	—	—	2.0	μA
Clock frequency	f_{OSC}	$R_{OSC} = 1M\Omega$, $V_I = -5V$	16	20	24	kHz
Output impedance	R_O	$I_O = 10mA$, $V_I = -5V$	—	75	100	Ω
Multiplication efficiency	P_{eff}	$I_O = 5mA$, $V_I = -5V$	90	95	—	%
OSC1 Input leakage current	I_{LKI}	$V_I = -8V$	—	—	2.0	μA

S1F76600 Series

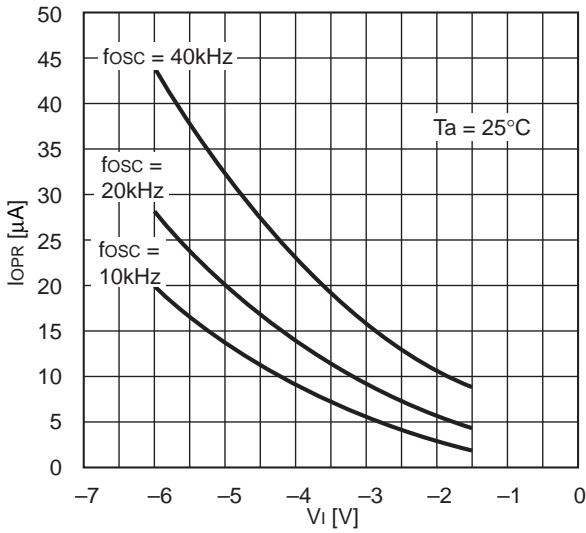
Typical Performance Characteristics



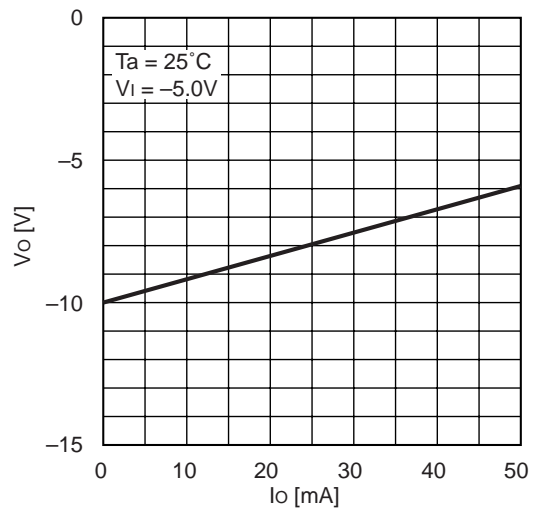
(1) Clock frequency vs. External resistance



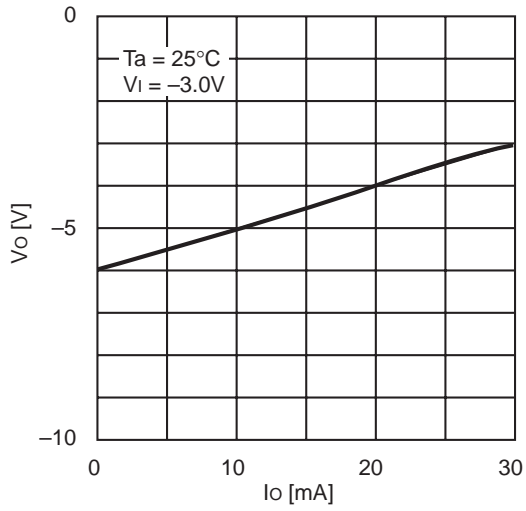
(2) Clock frequency vs. Ambient temperature



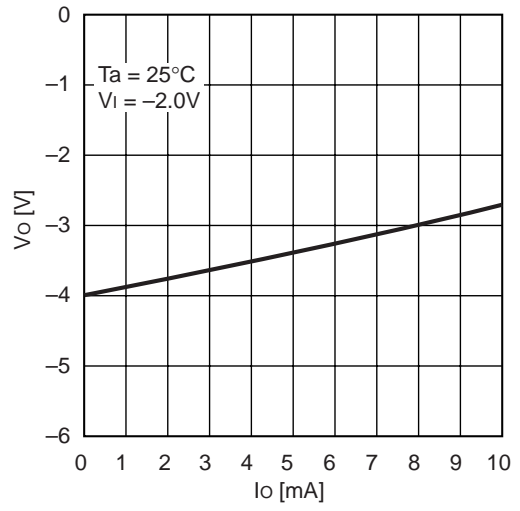
(3) Multiplier current vs. Input voltage



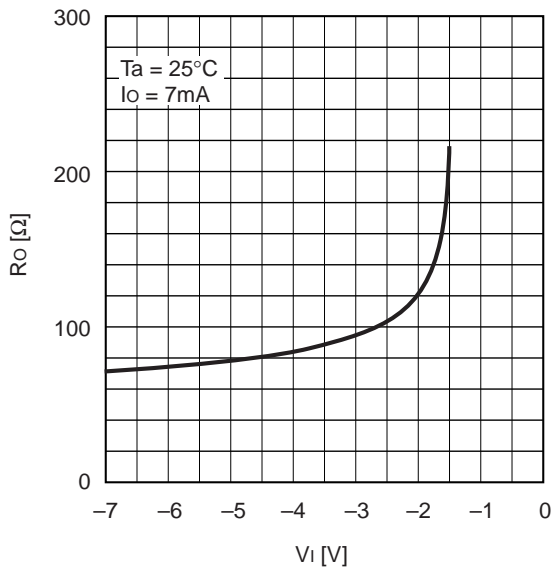
(4) Output voltage vs. Output current



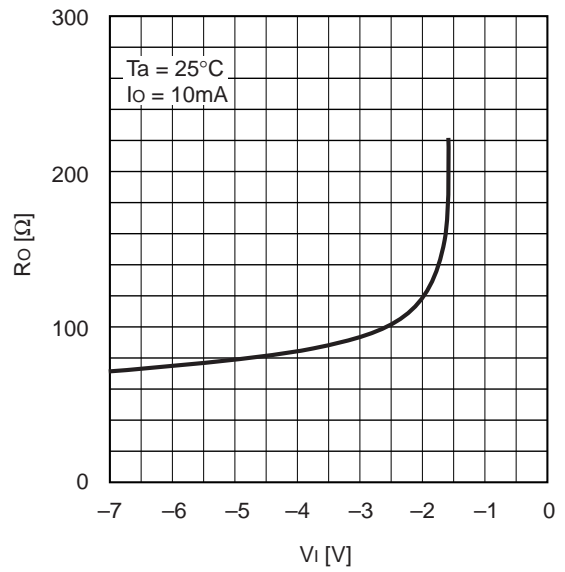
(5) Output voltage vs. Output current



(6) Output voltage vs. Output current

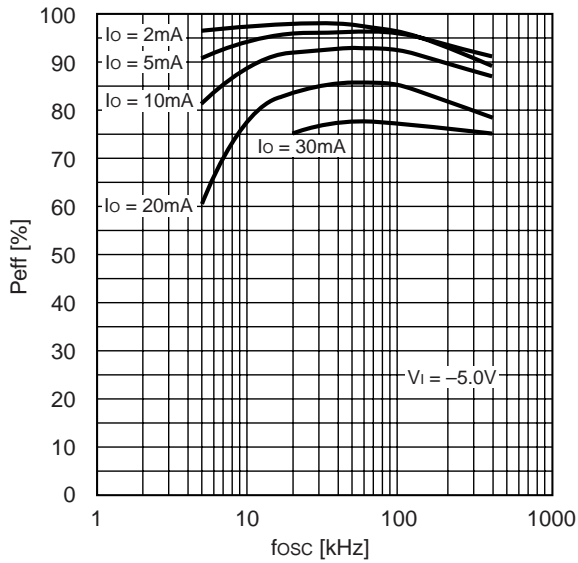


(7) Output impedance vs. Input voltage

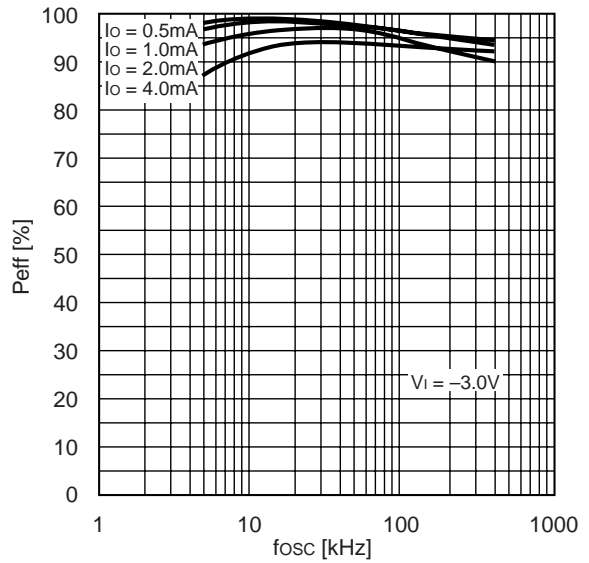


(8) Output impedance vs. Input voltage

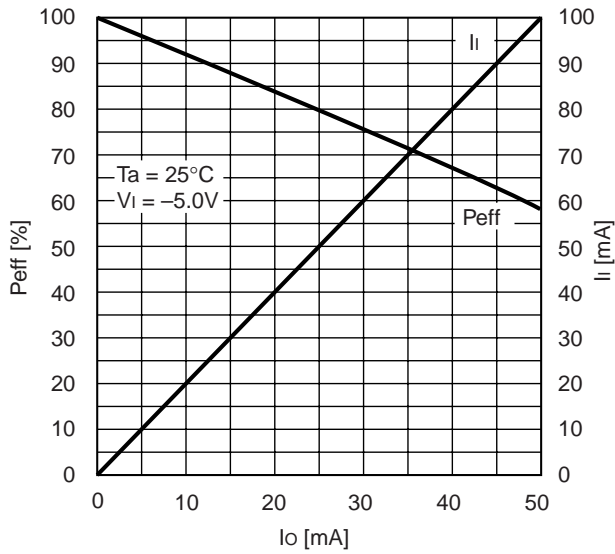
S1F76600 Series



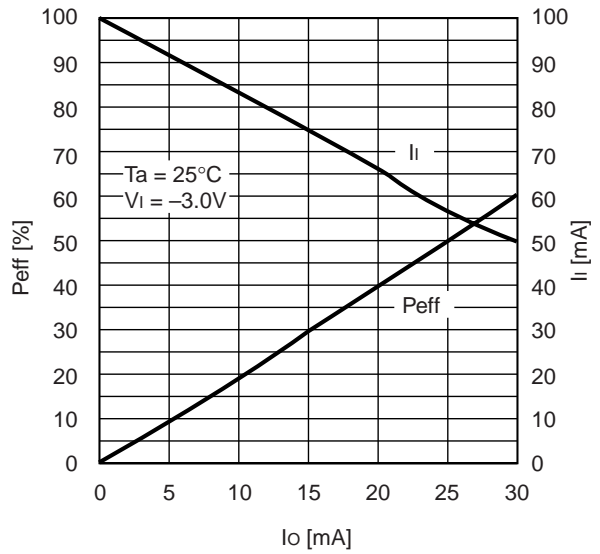
(9) Multiplication efficiency vs. Clock frequency



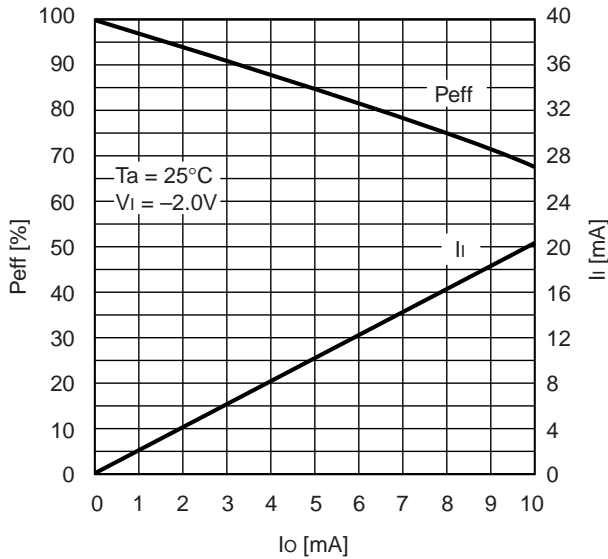
(10) Multiplication efficiency vs. Clock frequency



(11) Multiplication efficiency/input current vs. Output current



(12) Multiplication efficiency/input current vs. Output current

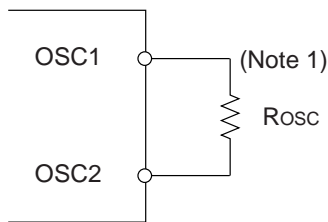


(13) Multiplication efficiency/input current vs. Output current

FUNCTIONAL DESCRIPTIONS

CR Oscillator

S1F76600 has a built-in CR oscillator as the internal oscillator, and an external oscillation resistor ROSC is connected between the pins OSC1 and OSC2 before operation.



Note 1

Since the oscillation frequency varies with wiring capacitance, make the cables between the terminals OSC1 and OSC2 and ROSC as short as possible.

When setting the external resistor ROSC, find ROSC suitable for fOSC that brings about the maximum efficiency from characteristics graph (9) and (10). The relations between ROSC and fOSC in characteristics graph (1) are expressed approximately with the following formula as

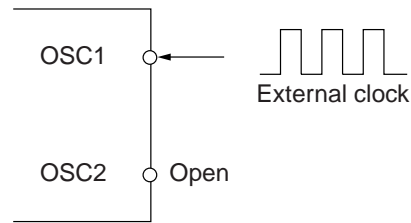
far as the straight portion ($500k\Omega < ROSC < 2M\Omega$) is concerned:

$$ROSC = A \cdot (1/fOSC)$$

(A : Constant, When GND is 0V and VDD is 5V, A is approximately 2.0×10^{10} (I/F).)

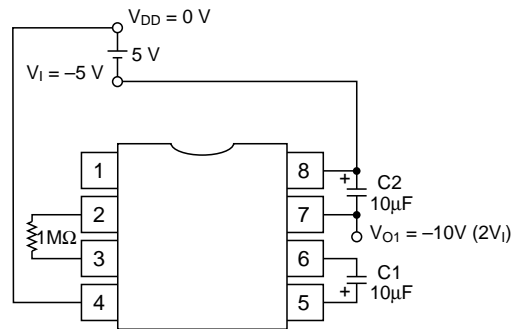
So, the ROSC value can be obtained from this formula. (Recommended oscillation frequency : 10kHz to 30kHz (ROSC : $2M\Omega$ to $680k\Omega$))

When the external clock operates, make the pin OSC2 open as shown below and input the 50% duty of the external clock from the pin OSC1.

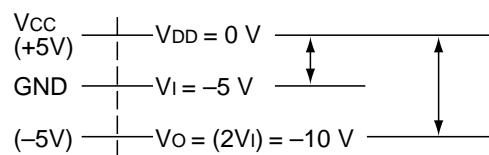


Voltage Multiplier

The voltage multiplier uses the clock signal from the oscillator to double the input voltage. This requires two external capacitors—a charge-pump capacitor, C1, between CAP1+ and CAP1-, and a smoothing capacitor, C2, between V1 and Vo.



Doubled potential levels

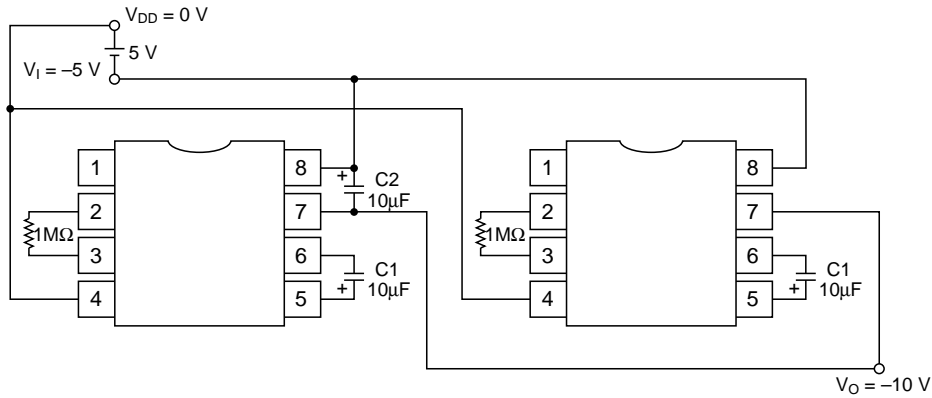


S1F7600 Series

TYPICAL APPLICATIONS

Parallel Connection

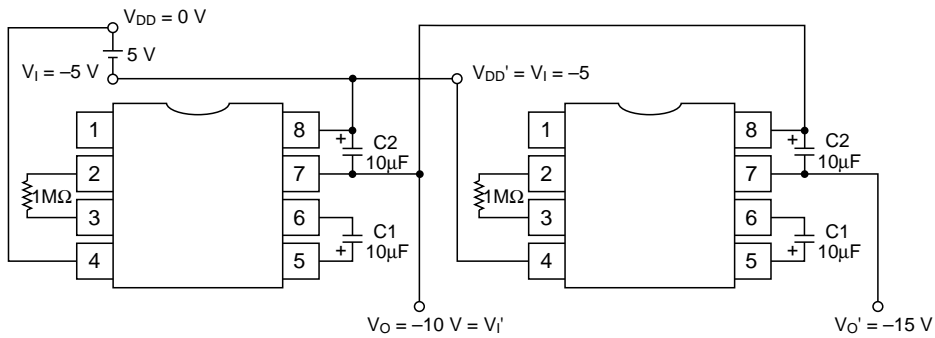
Connecting two or more chips in parallel reduces the output impedance by $1/n$, where n is the number of devices used.



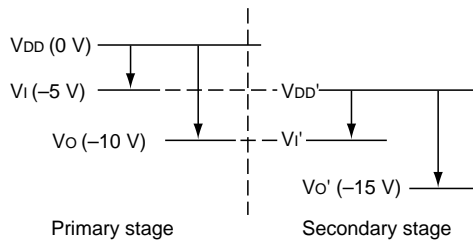
Serial Connection

Connecting two or more chips in series obtains a higher output voltage than can be obtained using a parallel

connection, however, this also raises the output impedance.

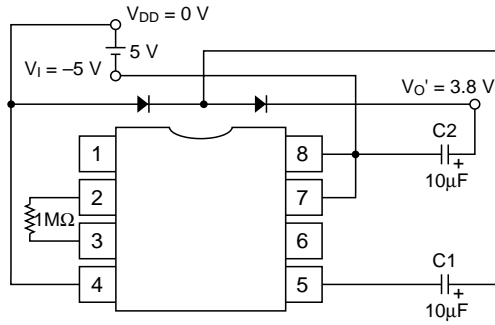


Potential levels



Positive Voltage Conversion

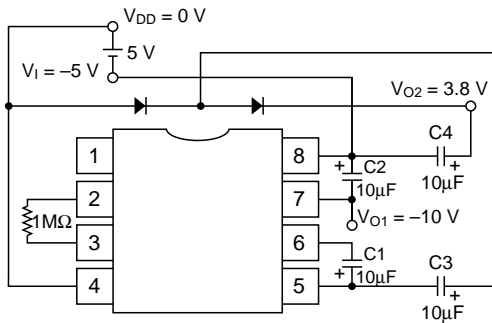
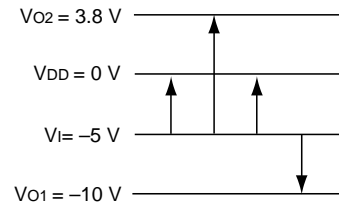
Diodes can be added to a circuit connected in parallel to make a negative voltage positive.



Simultaneous Voltage Conversion

Combining a multiplier circuit with a positive voltage conversion circuit generates both -10 and 3.8 V outputs from a single input.

Potential levels



S1F76620 Series

S1F76620 Series CMOS DC/DC Converter (Voltage Doubler)

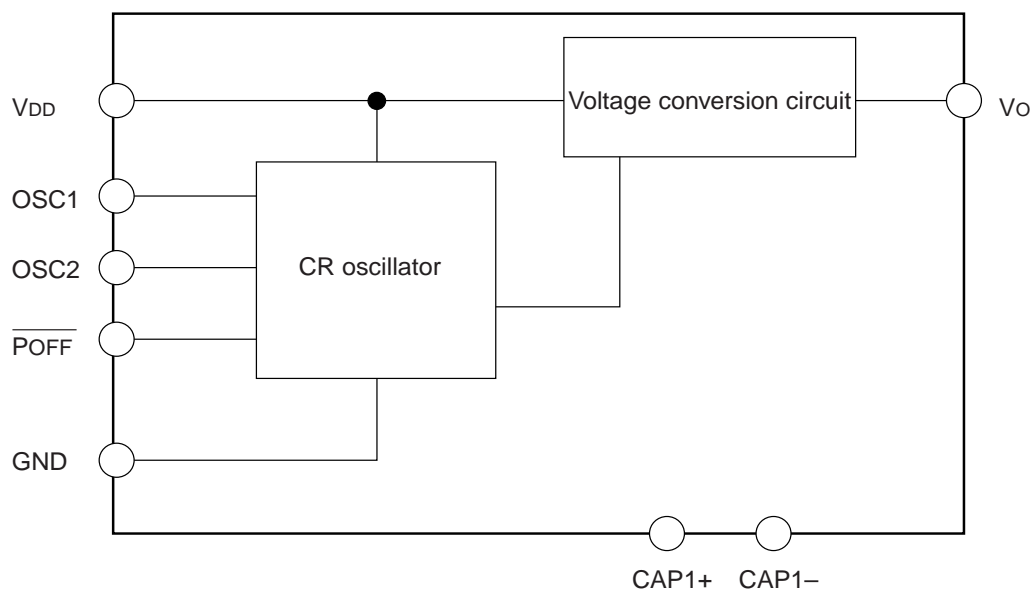
DESCRIPTION

S1F76620 is a high efficiency and low power consumption CMOS DC/DC converter. It enables to obtain 2 times step-up output (3.0 to 16V) from input voltage (1.5 to 8V). Also, S1F76620 enable to drive ICs (liquid crystal driver, analog IC, etc.), which require another power supply in addition to logic main power supply, with a single power supply, and it is suitable for micro power IC of hand-held computers, handy devices, etc. due to its small power consumption.

FEATURES

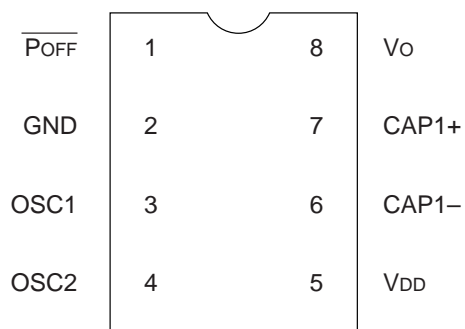
- (1) High efficiency and low power consumption CMOS DC/DC converter
- (2) Easy voltage conversion from input voltage V_{DD} (5V) to positive potential side or negative potential side
 - Input V_{DD} (5V) to output $-V_{DD}$ (-5V), $2V_{DD}$ (10V)
- (3) Output current : Max. 30mA ($V_{DD} = 5V$)
- (4) Power conversion efficiency : Typ. 95%
- (5) Possibility of series connection
(In 2-piece use, $V_{DD} = 5V$, $V_O = 15V$)
- (6) Low voltage operation : Suitable for battery drive
- (7) Built-in CR oscillator
- (8) SOP4-8pin S1F76620M0A0
Bare Chip S1F76620D0A0

BLOCK DIAGRAM



PIN DESCRIPTIONS

Pin Assignments



Pin Assignments of SOP4-8pin

Pin descriptions

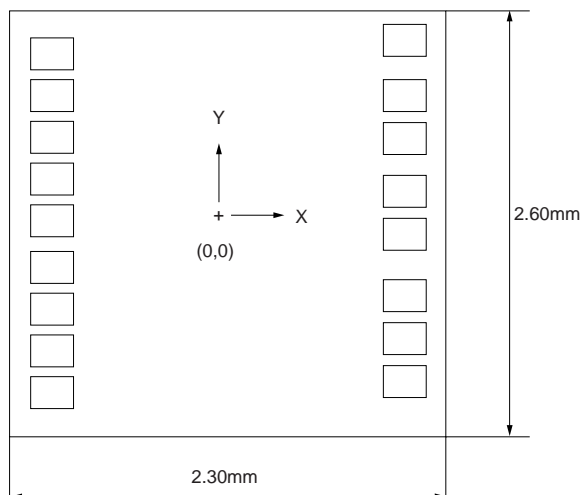
Pin No.	Pin name	Description
1	$\overline{\text{POFF}}$	Input pin for power off control.
2	GND (VSS)	Power pin. (Minus side, System GND)
3	OSC1	Oscillation resistor connection pin. Works as the clock input pin when the external clock operates.
4	OSC2	Oscillation resistor connection pin. Opens when the external clock operates.
5	VDD	Power pin. (Plus side, System VCC)
6	CAP1-	Pump up capacitor minus side connection pin for 2 times step-up.
7	CAP1+	Pump up capacitor plus side connection pin for 2 times step-up.
8	Vo	Output pin at the time of 2 times step-up.

S1F76620 Series

Pad Center Coordinates (S1F76620D0A0)

Pad No.	Pad name	Pad center coordinates X (μm)	Pad center coordinates Y (μm)	Description
1	(NC)	-984	1096	—
2	(NC)		788	—
3	POFF		580	Input pin for power off control
4	(NC)		390	—
5	(NC)		96	—
6	(NC)		-218	—
7	GND (Vss)		-510	Power input pin (Minus side)
8	OSC1		-802	Oscillation resistor connection pin
9	OSC2		-1094	Oscillation resistor connection pin
10	VDD	984	-1134	Power input pin (Plus side)
11	CAP1-		-892	Pump up capacitor minus side connection pin for 2 times step-up
12	CAP1+		-514	Pump up capacitor plus side connection pin for 2 times step-up
13	(NC)		182	—
14	VO		372	2 times step-up output pin
15	(NC)		750	—
16	(NC)		942	—
17	(NC)		1134	—

Chip External Shape



Pad Assignment

Pad aperture : $100\mu\text{m} \times 100\mu\text{m}$ Chip thickness : $400\mu\text{m}$

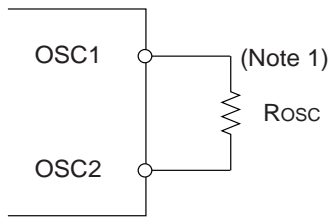
Note

Do not bond the NC pad.

FUNCTIONAL DESCRIPTIONS

CR Oscillator

S1F76620 has a built-in CR oscillator as the internal oscillator, and an external oscillation resistor ROSC is connected between the pins OSC1 and OSC2 before operation.



Note 1

Since the oscillation frequency varies with wiring capacitance, make the cables between the terminals OSC1 and OSC2 and ROSC as short as possible.

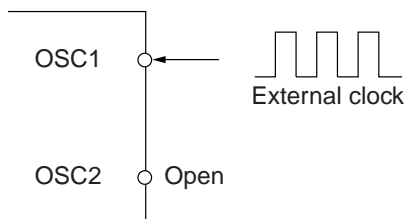
When setting the external resistor ROSC, find ROSC suitable for fOSC that brings about the maximum efficiency from characteristics graph (9) and (10). The relations between ROSC and fOSC in characteristics graph (1) are expressed approximately with the following formula as far as the straight portion (500kΩ < ROSC < 2MΩ) is concerned:

$$ROSC = A \cdot (1/fosc)$$

(A : Constant, When GND is 0V and VDD is 5V, A is approximately 2.0×10^{10} (I/F).)

So, the ROSC value can be obtained from this formula. (Recommended oscillation frequency : 10kHz to 30kHz (ROSC : 2MΩ to 680kΩ))

When the external clock operates, make the pin OSC2 open as shown below and input the 50% duty of the external clock from the pin OSC1.

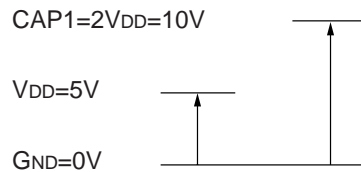


Voltage Conversion Circuit

The voltage conversion circuit uses clocks generated in the CR oscillator to double the input supply voltage VDD.

In case of 2 times step-up, 2 times voltage (2VDD) of the input voltage is obtained from the VO pin when a pump up capacitor is connected between CAP1+ and CAP2- and a smoothing capacitor is connected between VDD and VO outside.

When GND is 0 and VDD is 5, the relations between input/output and voltage are as shown below:



S1F76620 Series**ELECTRICAL CHARACTERISTICS****Absolute Maximum Ratings**

(Ta = -40 to +85°C)

Parameter	Symbol	Rating		Unit	Remarks
		Min.	Max.		
Input supply voltage	V _{IN}	-0.5	10.0	V	—
Input pin voltage	V _I	-0.5	V _{DD} + 0.5	V	OSC1, OSC2
Output voltage	V _O	—	20	V	—
Output supply voltage	V _{CAP+}	-0.5	V _{DD} + 0.5	V	CAP+
Output pin voltage	V _{CAP-}	-0.5	V _O + 0.5	V	CAP-
Allowable loss	P _D	—	300	mW	DIP-8pin
			150		SOP-8pin
Operating temperature	T _{opr}	-40	85	°C	—
Storage temperature	T _{stg}	-65	150	°C	—

Note 1

Under the conditions exceeding the above absolute maximum ratings, the IC may result in a permanent destruction. An operation for a long period under the conditions of the above absolute maximum ratings may deteriorate the reliability remarkably.

Note 2

All voltage values are based on GND being 0V.

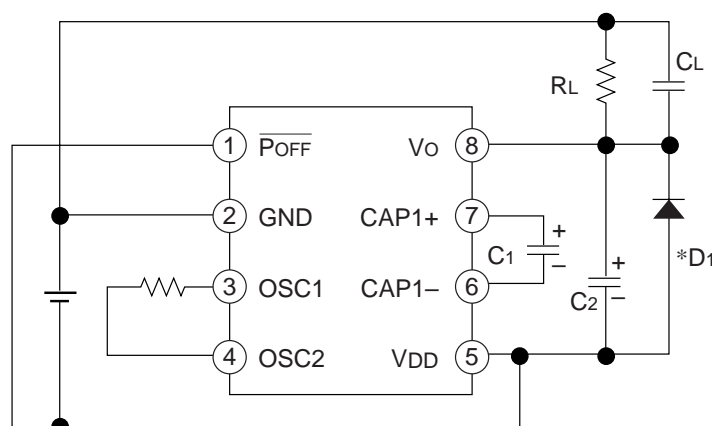
Recommended Operating Conditions

(Ta = -40 to +85°C)

Parameter	Symbol	Rating		Unit	Remarks
		Min.	Max.		
Step-up start operation	VSTA1	1.5	—	V	R _{OSC} = 1MΩ C ₂ ≥ 10μF C _L /C ₂ ≥ 1/20 See note 2.
	VSTA2	2.2	—	V	R _{OSC} = 1MΩ
Step-up stop voltage	VSTP	—	1.5	V	R _{OSC} = 1MΩ
Output load resistance	R _L	R _{Lmin} See note 3.	—	Ω	—
Output load current	I _O	—	30	mA	—
Oscillation frequency	f _{OSC}	10	30	kHz	—
External resistor for oscillation	R _{OSC}	680	2000	kΩ	—
Step-up capacitor	C ₁ , C ₂	3.3	—	μF	—

Note 1

All voltages are based on the GND being 0V.

Note 2The figure below shows the recommended circuit for operation with low voltages (V_{DD} = 1.5 to 2.2V):

* (DI (VF (IF=1mA) is recommended to be not more than 0.6V.)

Recommended Circuit

Note 3R_{Lmin} varies with input voltage. See Characteristics Graph (15).

S1F76620 Series

Electrical Characteristics

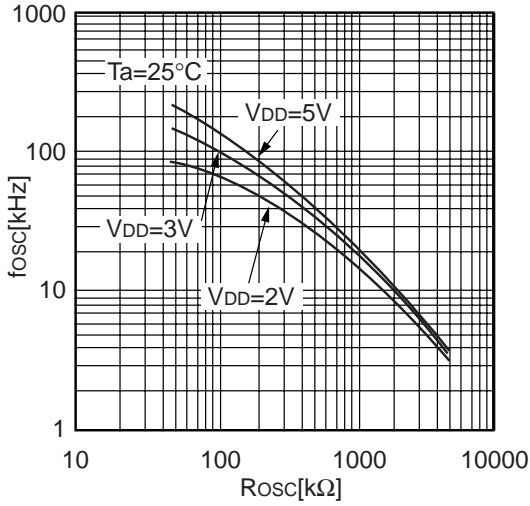
(V_{DD} = 5V, T_a = -40 to +85°C)

Parameter	Symbol	Rating			Unit	Remarks
		Min.	Typ.	Max.		
Input supply voltage	V _{DD}	1.8	—	8.0	V	—
Output voltage	V _O	—	—	16.0	V	—
Step-up circuit current consumption	I _{OPR}	—	35	50	μA	R _{osc} = 1MΩ
Static current	I _Q	—	—	1.0	μA	—
Oscillation frequency	f _{OSC}	16	20	24	kHz	R _{osc} = 1MΩ
Output impedance	R _O	—	85	130	Ω	I _o = 10mA
Step-up power conversion efficiency	P _{eff}	90	95	—	%	I _o = 5mA
Input leak current	I _{LKI}	—	—	1.0	μA	OSC1 pin

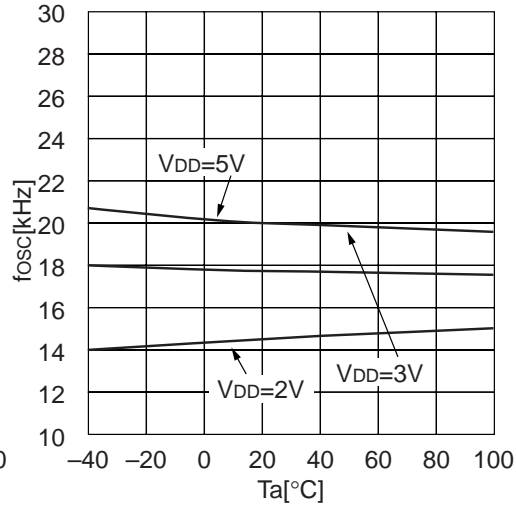
Note 1

All voltage values are based on GND being 0V.

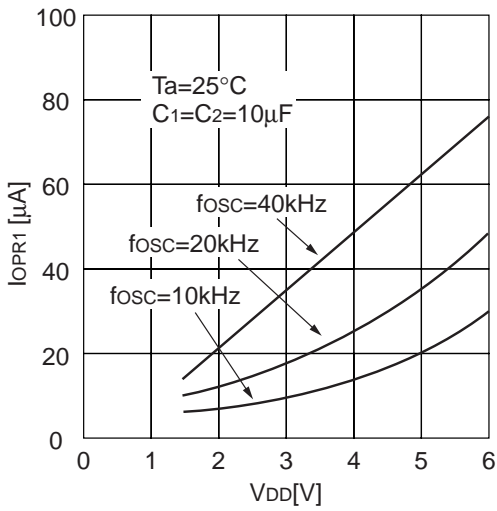
Characteristics Graph



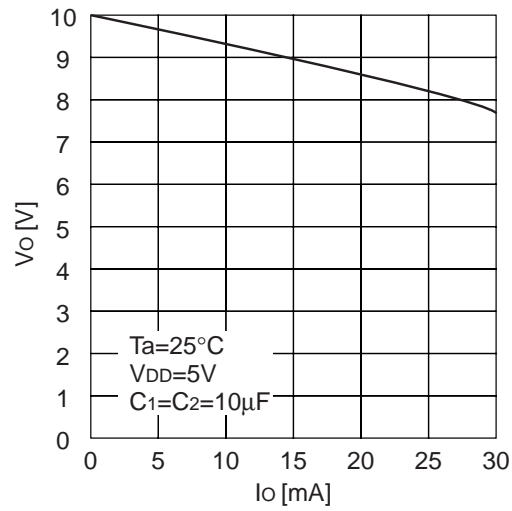
(1) Oscillation frequency vs. External resistance for oscillation



(2) Oscillation frequency vs. Temperature



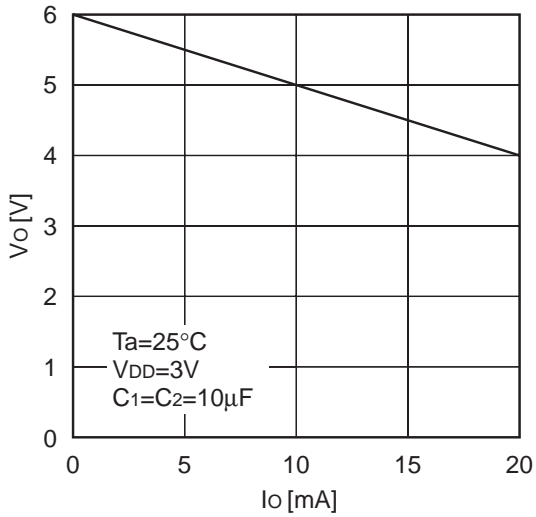
(3) Step-up circuit current consumption vs. Input current



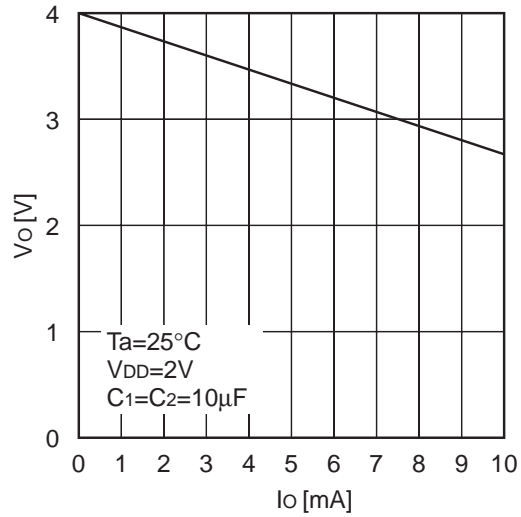
(4) Output voltage (Vo) vs. Output current 1

S1F76620 Series

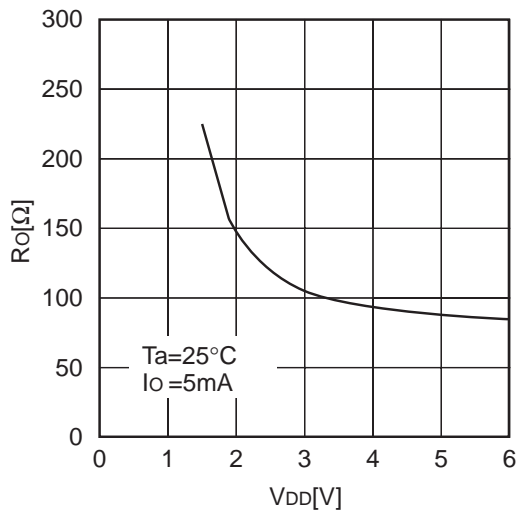
S1F76620 Series



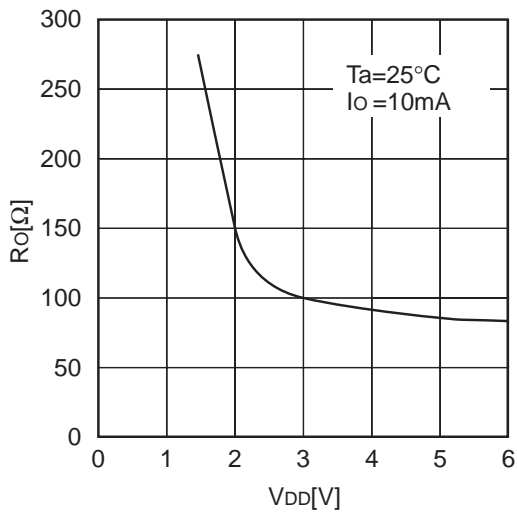
(5) Output voltage (Vo) vs. Output current 2



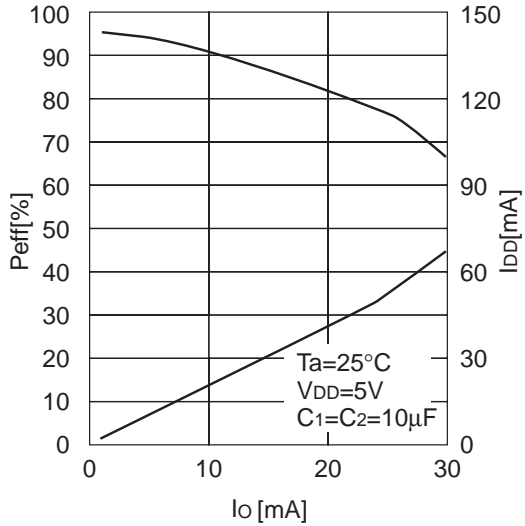
(6) Output voltage (Vo) vs. Output current 3



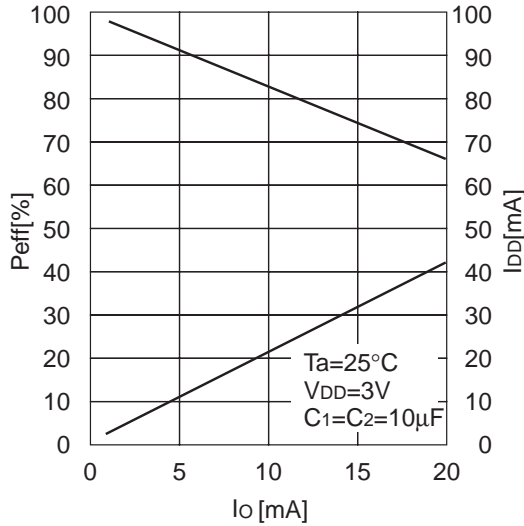
(7) Output impedance vs. Input current 1



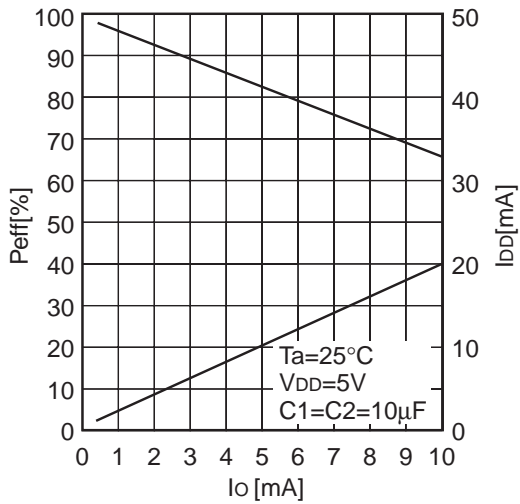
(8) Output impedance vs. Input voltage 2



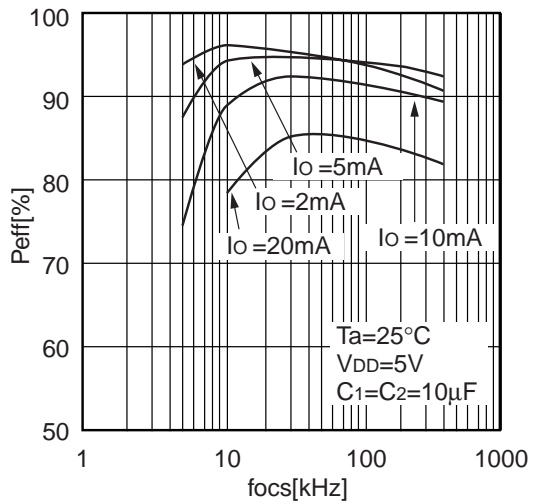
(9) Step-up power conversion efficiency vs. Output current 1
Input current vs. Output current 1



(10) Step-up power conversion efficiency vs. Output current 2
Input current vs. Output current 2

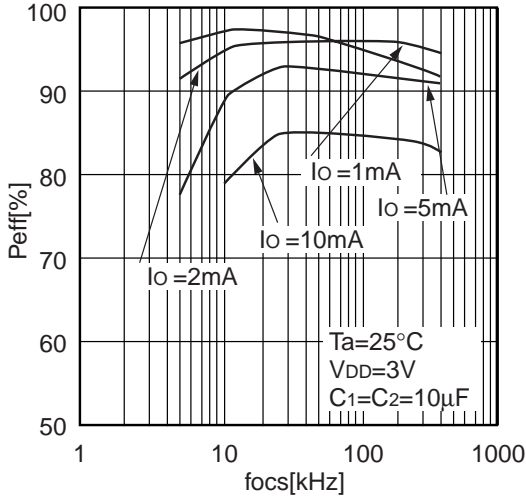


(11) Step-up power conversion efficiency vs. Output current 3
Input current vs. Output current 3

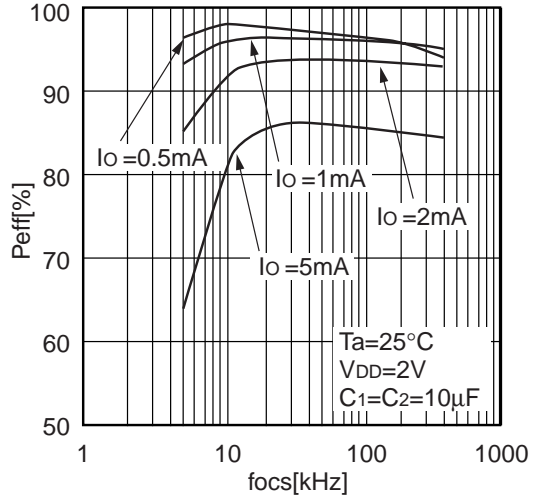


(12) Step-up power conversion efficiency vs. Oscillation frequency 1

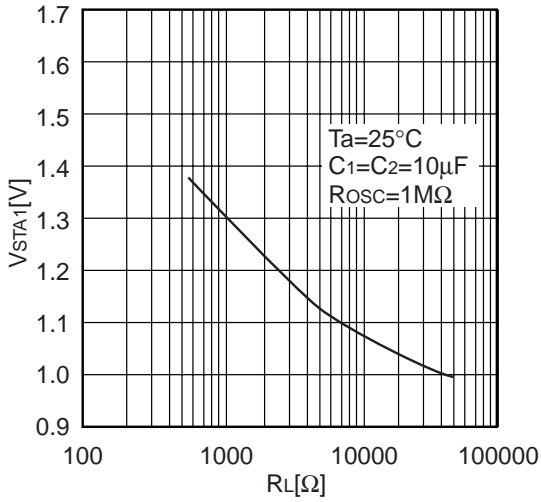
S1F76620 Series



(13) Step-up power conversion efficiency vs. Oscillation frequency 2



(14) Step-up power conversion efficiency vs. Oscillation frequency 3



(15) Step-up start voltage (1) vs. Load resistance

EXAMPLE OF REFERENCE EXTERNAL CONNECTION

2 Times Step-up

2 times step-up output of V_O ($2 \times V_{DD}$) is obtained from the circuit shown in Figure 1.

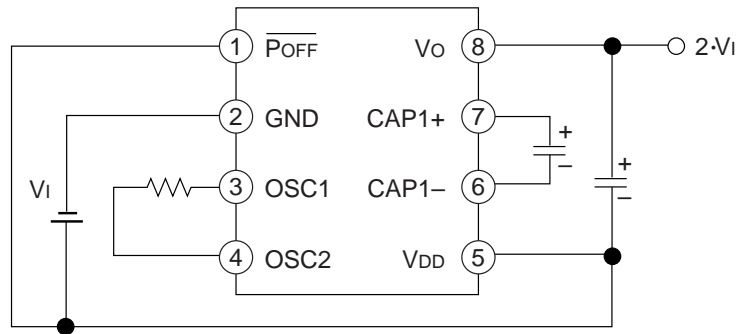


Figure 1 2 Time Step-up Operation

Parallel Connection

It is possible to make the output impedance (R_O) small when several pieces of the circuit shown in Figure 1 are connected. Parallel connection of n circuits reduces R_O to $1/n$ approximately. One piece of the smoothing capacitor C_2 can be commonly used.

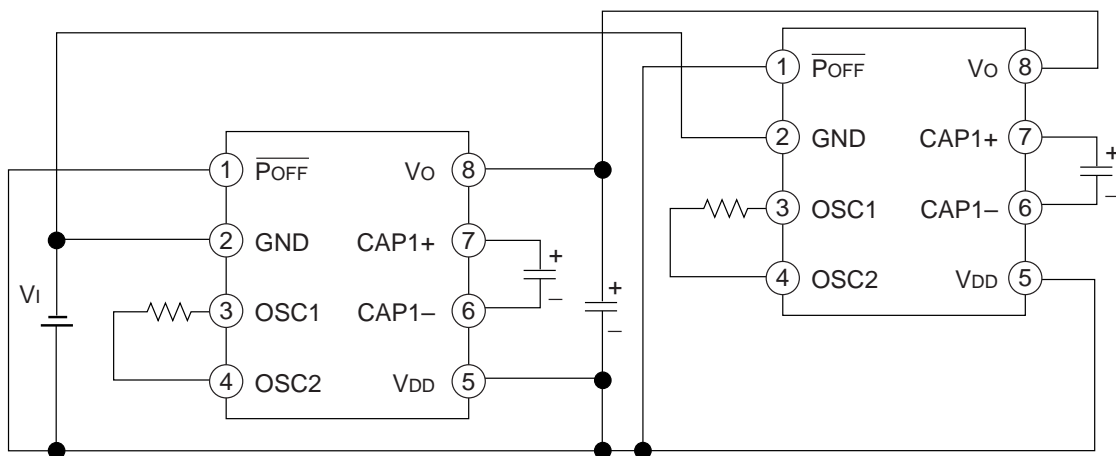


Figure 2 Parallel Connection

S1F76620 Series

S1F76620 Series

Series Connection

When S1F76620 is connected in series (V_{DD} and V_O in the previous stage are connected to GND and V_{DD} in the next stage respectively), the output voltage can be increased more. But the series connection makes the output impedance high. Figure 3 shows an example of the series connection to get $V_O = 15V$ from $V_{DD} = 5V$.

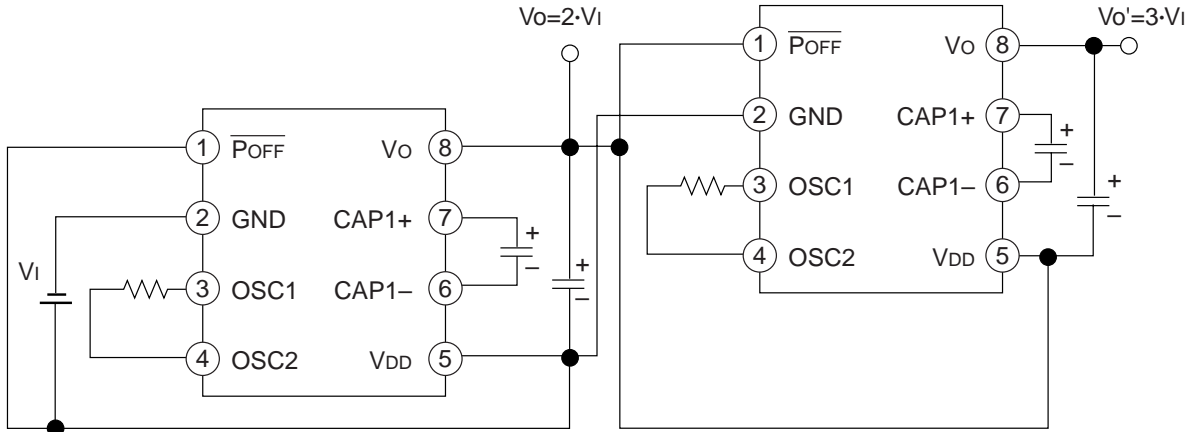


Figure 3 Series Connection

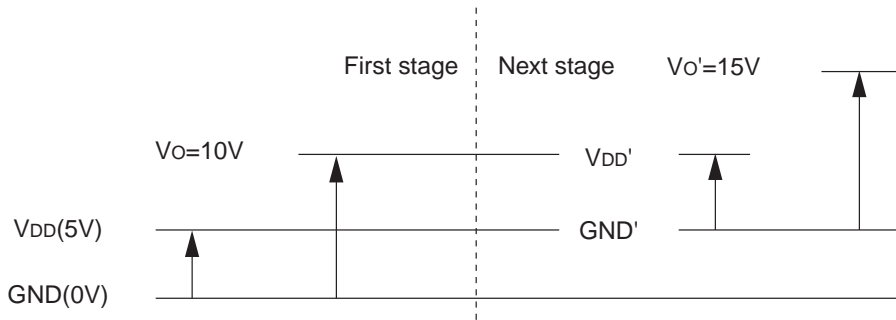


Figure 4 Power Supply Relations in Series Connection (1)

Note

When the input voltage in the next stage is as per the specification ($V_{DD}-GND \leq 8V$) in a series connection, the output in the first stage (V_O-V_{DD}) can be used as the input in the next stage ($V_{DD}-GND$). (See Figure 5.)

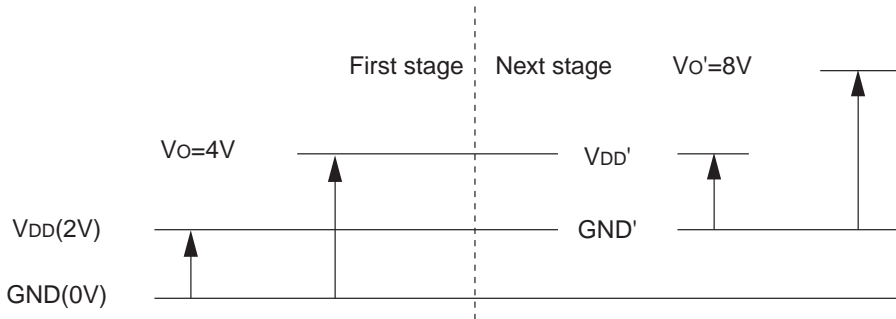


Figure 5 Power Supply Relations in Series Connection (2)

Negative Voltage Conversion

S1F76620 can boost input voltage to twice on the positive potential side by using the circuit shown in Figure 6. But the output voltage drops by the forward voltage V_F of the diode. When GND is 0V, V_{DD} is 5V and V_F is 0.6V as shown in Figure 6 for example, V_O is calculated as follows: $V_O = -5V + 2 \times 0.6V = -3.8V$.

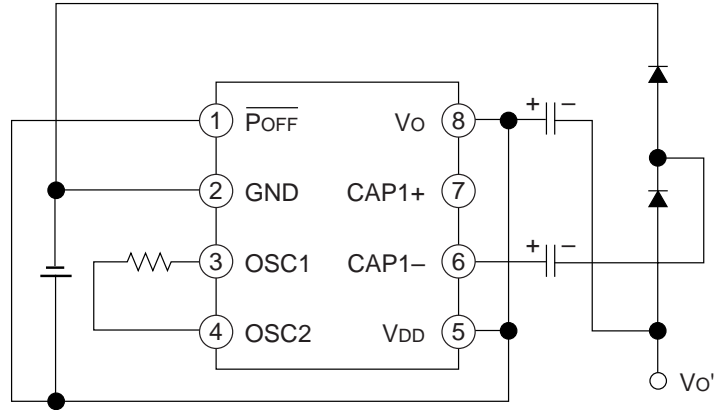


Figure 6 Negative Voltage Conversion

Negative Voltage Conversion + Positive Voltage Conversion

When the 3 times step-up operation shown in Figure 1 and the positive voltage conversion in Figure 6 are combined, the circuit shown in Figure 7 can be formed and 10V and $-3.8V$ can be obtained from the input 5V. However, the output impedance is higher than in case of connection of either one only (the negative voltage conversion or the positive voltage conversion).

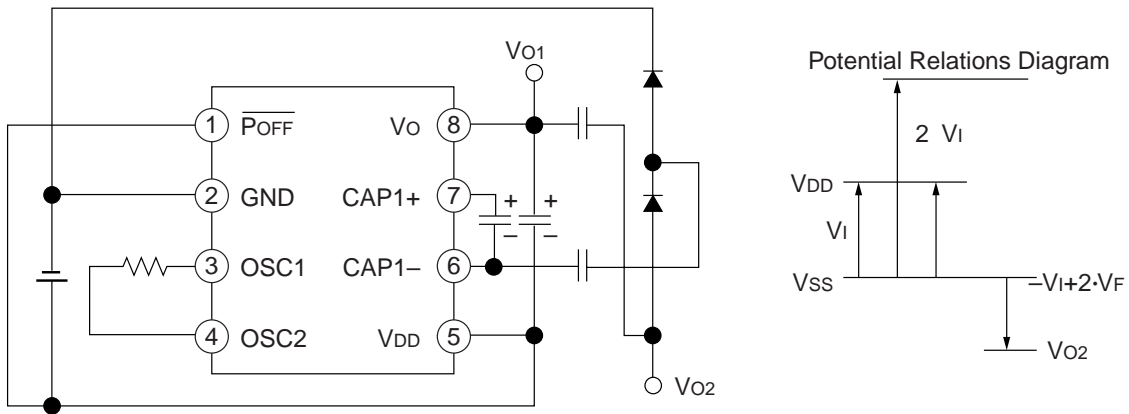
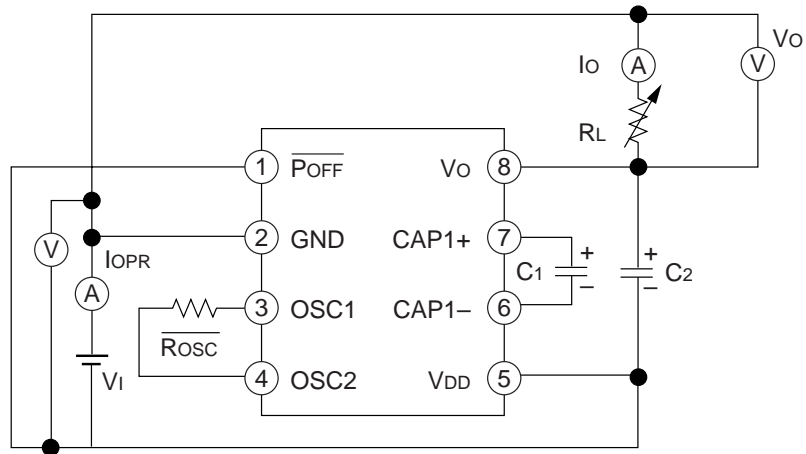


Figure 7 Negative Voltage Conversion + Positive Voltage Conversion

S1F76620 Series

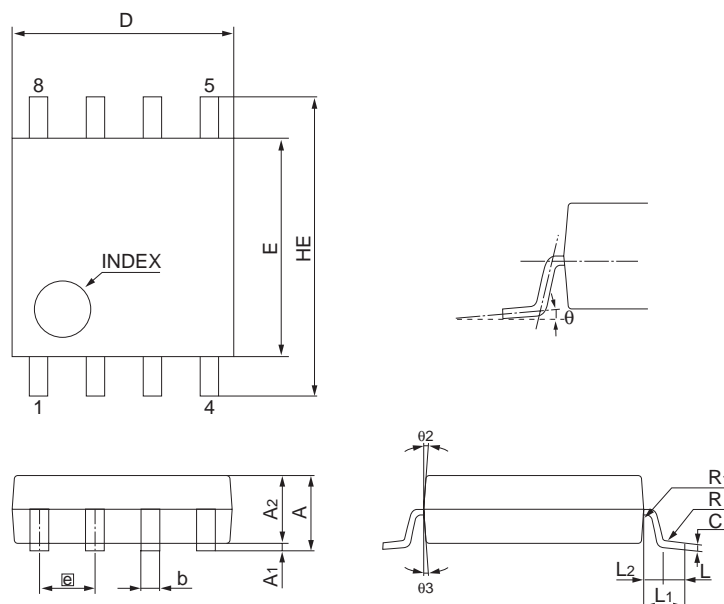
MEASUREMENT CIRCUIT



MECHANICAL DATA

S1F76620M0A0 SOP4-8pin

Reference



Symbol	Dimension in Millimeters			Dimension in Inches*		
	Min.	Nom.	Max.	Min.	Nom.	Max.
E	4.8	5	5.2	(0.189)	(0.197)	(0.204)
D1	—	—	—	—	—	—
A		1.75			(0.069)	
A1		0.15			(0.006)	
A2		1.6			(0.063)	
Ⓜ		1.27			(0.050)	
b	0.25	0.35	0.45	(0.010)	(0.014)	(0.017)
C	0.05	0.15	0.25	(0.002)	(0.006)	(0.009)
θ						
L		0.55			(0.022)	
L1						
L2						
HE	6.4	6.8	7.2	(0.252)	(0.268)	(0.283)
D	4.8	5	5.2	(0.189)	(0.197)	(0.204)
θ2						
θ3						
R						
R1						

* for reference

Note

This drawing is subject to change without notice for improvement.

2. DC/DC Converter & Voltage Regulator

S1F76610 Series CMOS DC/DC Converter (Voltage Doubler / Tripler) & Voltage Regulator

DESCRIPTION

The S1F76610 Series is a highly efficient CMOS DC/DC converter for doubling or tripling an input voltage. It incorporates an on-chip voltage regulator to ensure stable output at the specified voltage. The S1F76610 Series offers a choice of three, optional temperature gradients for applications such as LCD panel power supplies.

The S1F76610C0B0 is available in 14-pin plastic DIPs, the S1F76610M0B0, in 14-pin plastic SOPs, and the S1F76610M2B0 in 16-pin plastic SSOPs.

FEATURES

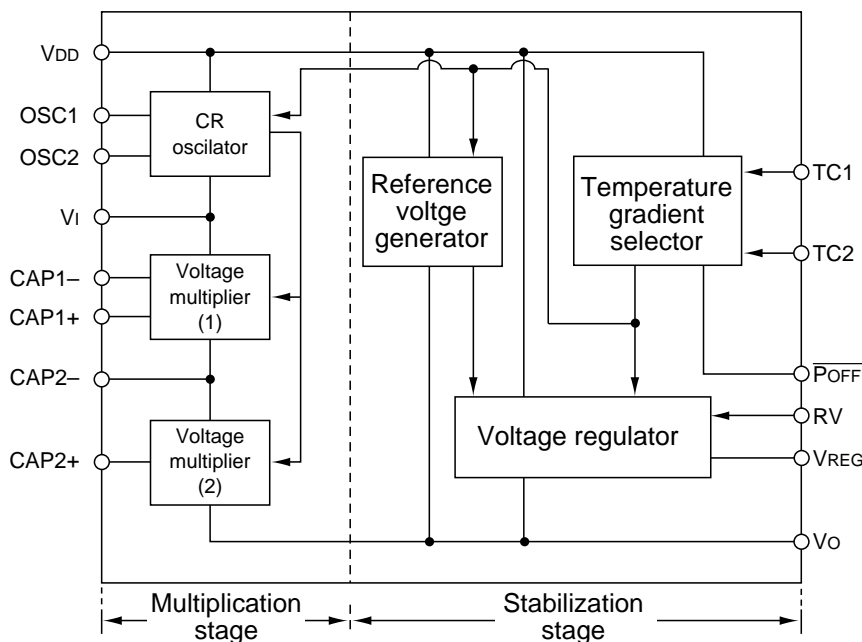
- 95% (Typ.) conversion efficiency
- Up to four output voltages, V_O , relative to the input voltage, V_I
- On-chip voltage regulator
- 20mA maximum output current at $V_I = -5V$
- Three temperature gradients : -0.1 , -0.4 and $-0.6\%/^{\circ}C$

- External shut-down control
- 2 μ A maximum output current when shut-down
- Two-in-series configuration doubles negative output voltage.
- On-chip RC oscillator
- S1F76610C0B0 Plastic DIP-14 pin
- S1F76610M0B0 Plastic SOP5-14 Pin
- S1F76610M2B0 Plastic SSOP2-16 pin

APPLICATIONS

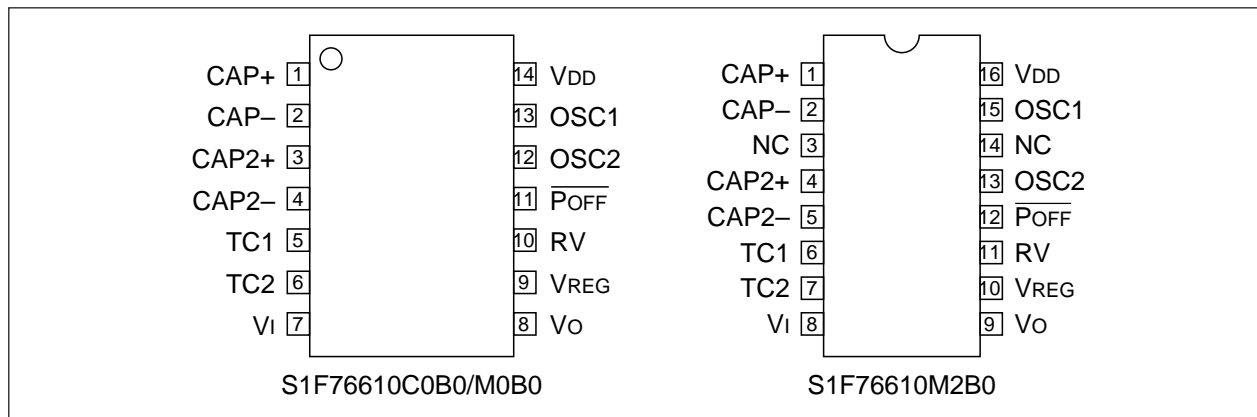
- Power supplies for LCD panels
- Fixed-voltage power supplies for battery-operated equipment
- Power supplies for pagers, memory cards, calculators and similar hand-held equipment
- Fixed-voltage power supplies for medical equipment
- Fixed-voltage power supplies for communications equipment
- Power supplies for microcomputers
- Uninterruptable power supplies

BLOCK DIAGRAM



S1F76610 Series

PIN ASSIGNMENTS



PIN DESCRIPTIONS

S1F76610C0B0/M0B0

Pin No.	Pin name	Description
1	CAP1+	Positive charge-pump connection for ×2 multiplier
2	CAP1-	Negative charge-pump connection for ×2 multiplier
3	CAP2+	Positive charge-pump connection for ×3 multiplier
4	CAP2-	Negative charge-pump connection for ×3 multiplier or ×2 multiplier output
5	TC1	Temperature gradient selects
6	TC2	
7	Vi	Negative supply (system ground)
8	Vo	×3 multiplier output
9	VREG	Voltage regulator output
10	RV	Voltage regulator output adjust
11	POFF	Voltage regulator output ON/OFF control
12	OSC2	Resistor connection. Open when using external clock
13	OSC1	Resistor connection. Clock input when using external clock
14	VDD	Positive supply (system Vcc)

SPECIFICATIONS

Absolute Maximum Ratings

Parameter	Codes	Ratings	Units	Remarks
Input supply voltage	$V_I - V_{DD}$	$-20/N$ to $V_{DD} + 0.3$	V	N = 2: Boosting to a double voltage N = 3: Boosting to a triple voltage
Input terminal voltage	$V_I - V_{DD}$	$V_I - 0.3$ to $V_{DD} + 0.3$	V	OSC1, OSC2, $\overline{P_{OFF}}$
		$V_O - 0.3$ to $V_{DD} + 0.3$	V	TC1, TC2, RV
Output voltage	$V_O - V_{DD}$	-20 to $V_{DD} + 0.3$	V	V_O (Note 3)
		V_O to $V_{DD} + 0.3$	V	V_{REG} (Note 3)
Allowable dissipation	P_D	Max. 300	mW	
Working temperature	T_{opr}	-40 to $+85$	$^{\circ}\text{C}$	Plastic package
Storage temperature	T_{stg}	-55 to $+150$	$^{\circ}\text{C}$	
Soldering temperature and time	T_{sol}	$260 \cdot 10$	$^{\circ}\text{C} \cdot \text{s}$	At leads

Notes

- Using the IC under conditions exceeding the aforementioned absolute maximum ratings may lead to permanent destruction of the IC. Also, if an IC is operated at the absolute maximum ratings for a longer period of time, its functional reliability may be substantially deteriorated.
- All the voltage ratings are based on $V_{DD} = 0\text{V}$.
- The output terminals (V_O, V_{REG}) are meant to output boosted voltage or stabilized boosted voltage. They, therefore, are not the terminals to apply an external voltage. In case the using specifications unavoidably call for application of an external voltage, keep such voltage below the voltage ratings given above.

Recommended Operating Conditions

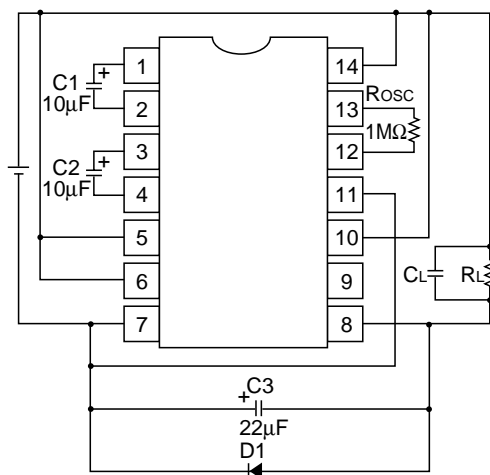
$V_{DD} = 0\text{V}$, $T_a = -40$ to $+85^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Conditions	Rating			Unit
			Min.	Typ.	Max.	
Oscillator startup voltage	V_{STA}	$R_{OSC} = 1\text{M}\Omega$ $C_3 = 10 \mu\text{F}$, $C_L/C_3 \leq 1/20$, $T_a = -20$ to $+85^{\circ}\text{C}$. See note 1.	—	—	-1.8	V
		$R_{OSC} = 1\text{M}\Omega$	—	—	-2.2	
Oscillator shutdown voltage	V_{STP}	$R_{OSC} = 1\text{M}\Omega$	-1.8	—	—	V
Load resistance	R_L		R_{Lmin} . See note 2.	—	—	Ω
Output current	I_O		—	—	20.0	mA
Clock frequency	f_{osc}		10.0	—	30.0	kHz
CR oscillator network resistance	R_{OSC}		680	—	2,000	k Ω
Capacitance	C_1, C_2, C_3		3.3	—	—	μF
Stabilization voltage sensing resistance	R_{RV}		100	—	1,000	k Ω

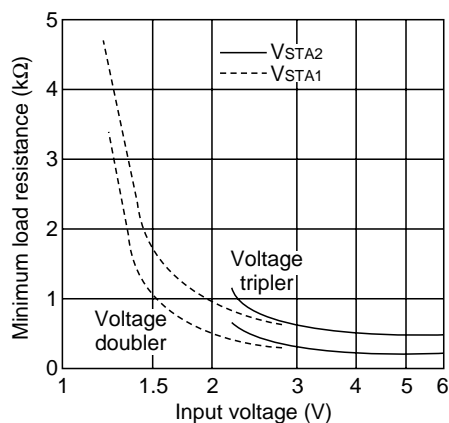
Notes

- The recommended circuit configuration for low-voltage operation (when V_I is between -1.2V and -2.2V) is shown in the following figure. Note that diode D1 should have a maximum forward voltage of 0.6V with 1.0mA forward current.
- R_L min can be varied depending on the input voltage.

S1F76610 Series



3. R_{Lmin} is a function of V_1



Electrical Characteristics

$V_{DD} = 0V$, $V_1 = -5V$, $T_a = -40$ to $+85^\circ C$ unless otherwise noted

Parameter	Symbol	Conditions	Rating			Unit
			Min.	Typ.	Max.	
Input voltage	V_1		-6.0	—	-1.8	V
Output voltage	V_O		-18.0	—	—	V
Regulator voltage	V_{REG}	$R_L = \infty$, $R_{RV} = 1M\Omega$, $V_O = -18V$	-18.0	—	-2.6	V
Stabilization circuit operating voltage	V_O		-18.0	—	-3.2	V
Multiplier current	I_{OPR1}	$R_L = \infty$, $R_{OSC} = 1M\Omega$	—	40	80	μA
Stabilization current	I_{OPR2}	$R_L = \infty$, $R_{RV} = 1M\Omega$, $V_O = -15V$	—	5.0	12.0	μA
Quiescent current	I_Q	$TC2 = TC1 = V_O$, $R_L = \infty$	—	—	2.0	μA
Clock frequency	f_{OSC}	$R_{OSC} = 1M\Omega$	16.0	20.0	24.0	kHz

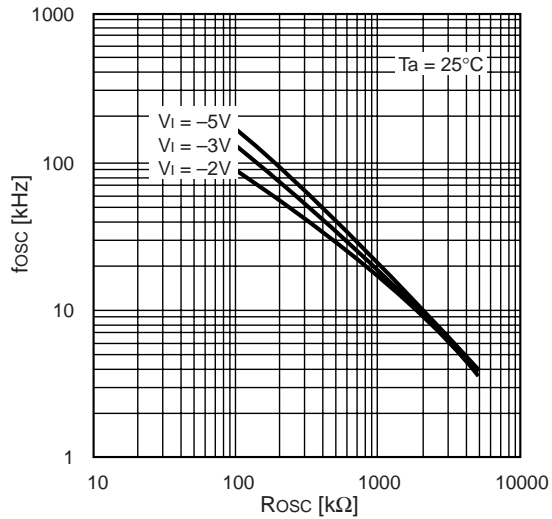
Parameter	Symbol	Conditions	Rating			Unit
			Min.	Typ.	Max.	
Output impedance	R _O	I _O = 10mA	—	150	200	Ω
Multiplication efficiency	P _{eff}	I _O = 5mA	90.0	95.0	—	%
Stabilization output voltage differential	$\frac{\Delta V_{REG}}{\Delta V_O \cdot V_{REG}}$	V _O = -18 to -8V, V _{REG} = -8V, R _L = ∞, T _a = 25°C	—	0.2	—	%/V
Stabilization output load differential	$\frac{\Delta V_{REG}}{\Delta I_O}$	V _O = -15V, V _{REG} = -8V, T _a = 25°C, I _O = 0 to 10μA, TC1 = V _{DD} , TC2 = V _O	—	5.0	—	Ω
Stabilization output saturation resistance	R _{SAT}	R _{SAT} = Δ(V _{REG} - V _O)/ΔI _O , I _O = 0 to 10μA, R _V = V _{DD} , T _a = 25°C	—	8.0	—	Ω
Reference voltage	V _{RV}	R _{C2} = V _O , TC1 = V _{DD} , T _a = 25°C	-2.3	-1.5	-1.0	V
		TC2 = TC1 = V _O , T _a = 25°C	-1.7	-1.3	-1.1	
		TC2 = V _{DD} , TC1 = V _O , T _a = 25°C	-1.1	-0.9	-0.8	
Temperature gradient	C _T	See note.	-0.25	-0.1	-0.01	%/ ^o C
			-0.5	-0.4	-0.3	
			-0.7	-0.6	-0.5	
P _{OFF} , TC1, TC2, OSC1, and RV input leakage current	I _{LKI}		—	—	2.0	μA

Note

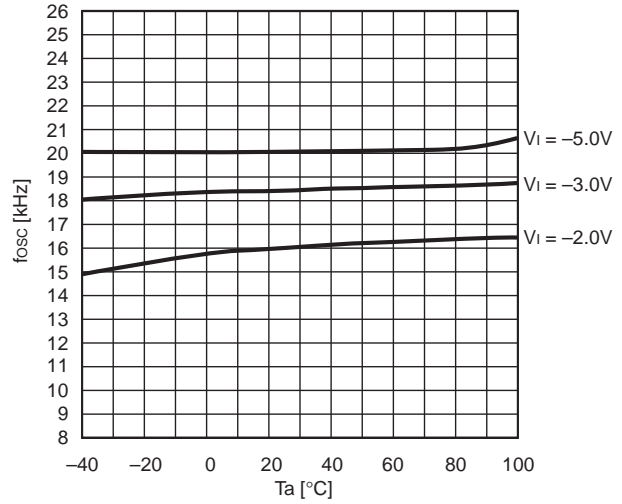
$$C_T = \frac{|V_{REG}(50^{\circ}C)| - |V_{REG}(0^{\circ}C)|}{50^{\circ}C - 0^{\circ}C} \times \frac{100}{|V_{REG}(25^{\circ}C)|}$$

S1F76610 Series

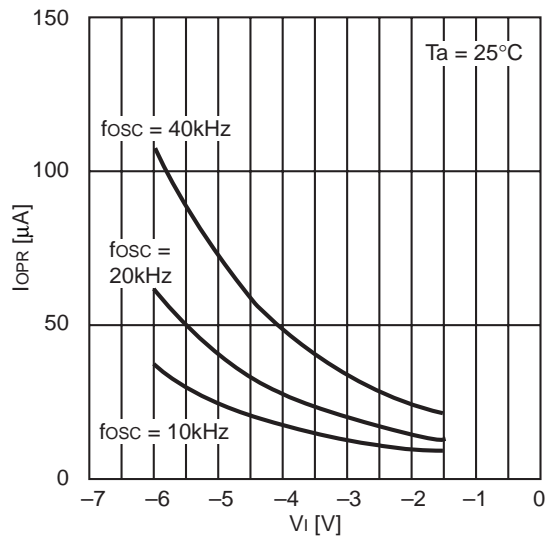
Typical Performance Characteristics



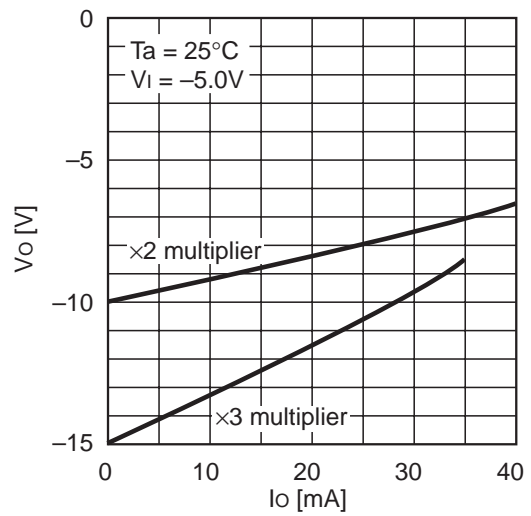
(1) Clock frequency vs. External resistance



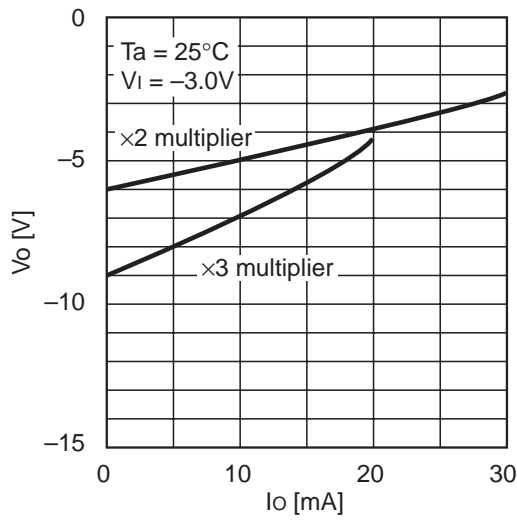
(2) Clock frequency vs. Ambient temperature



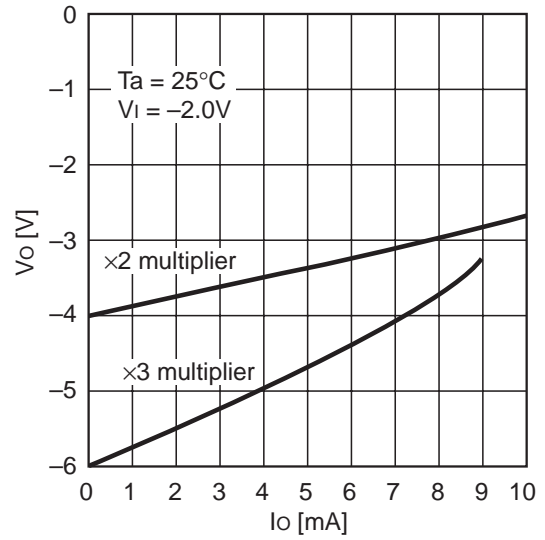
(3) Multiplier current vs. Input voltage



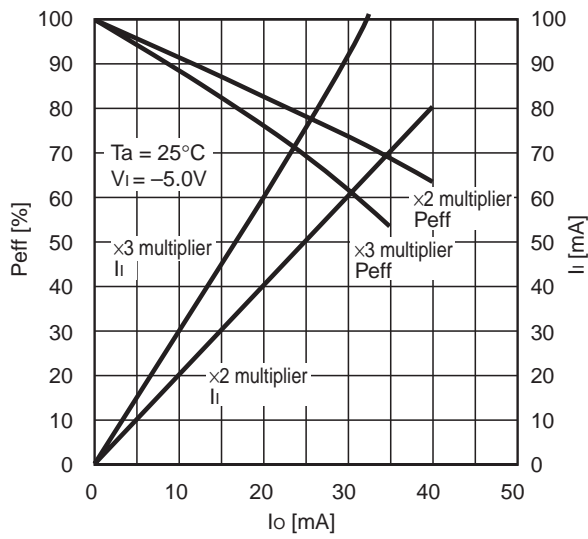
(4) Output voltage vs. Output current



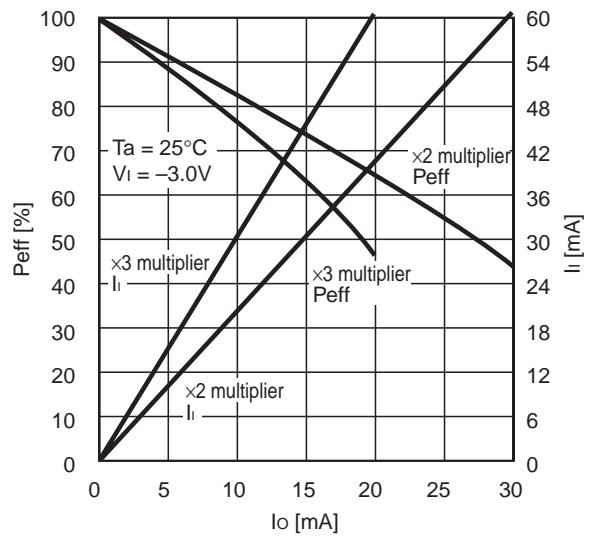
(5) Output voltage vs. Output current



(6) Output voltage vs. Output current



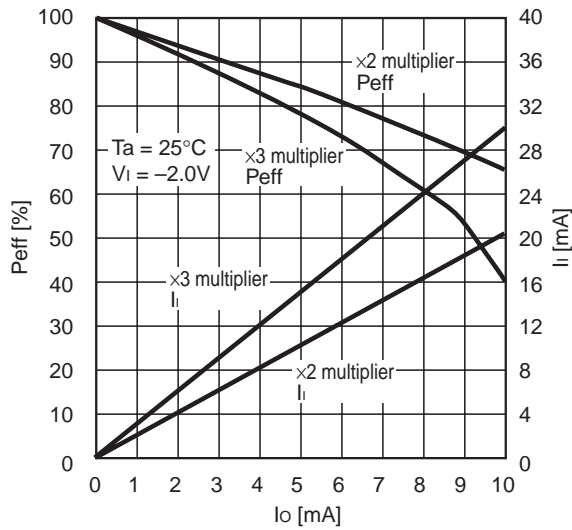
(7) Multiplication efficiency/input current vs. Output current



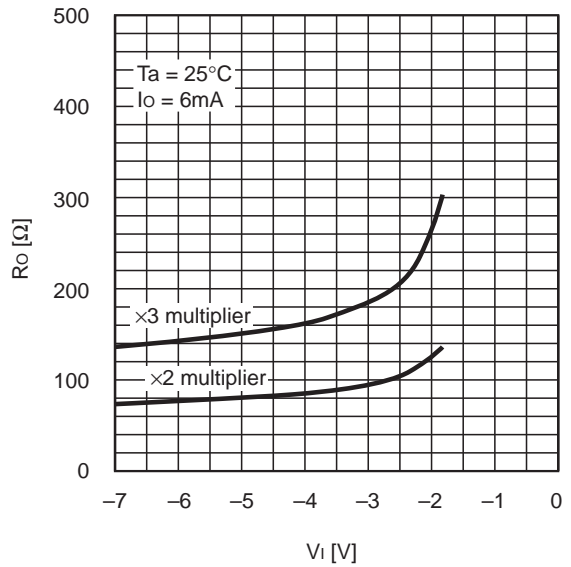
(8) Multiplication efficiency/input current vs. Output current

S1F76610 Series

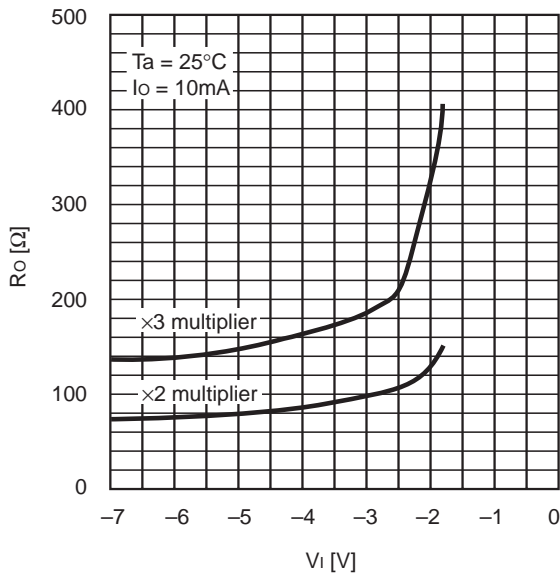
S1F76610 Series



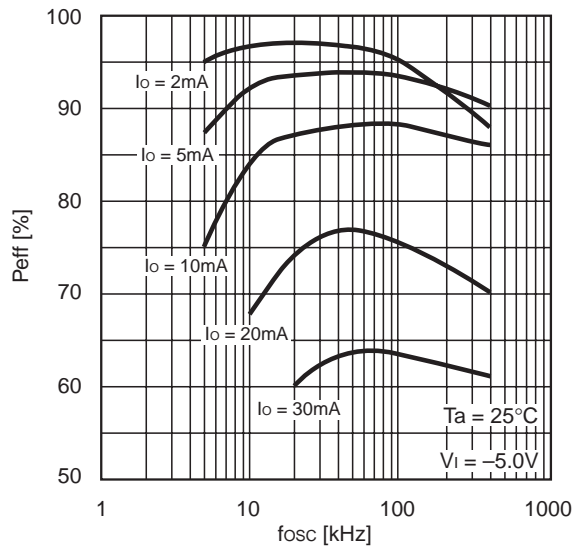
(9) Multiplication efficiency/input current vs. Output current



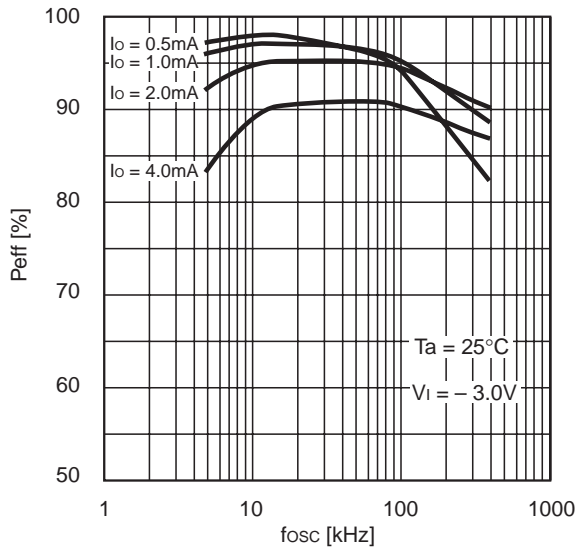
(10) Output impedance vs. Input voltage



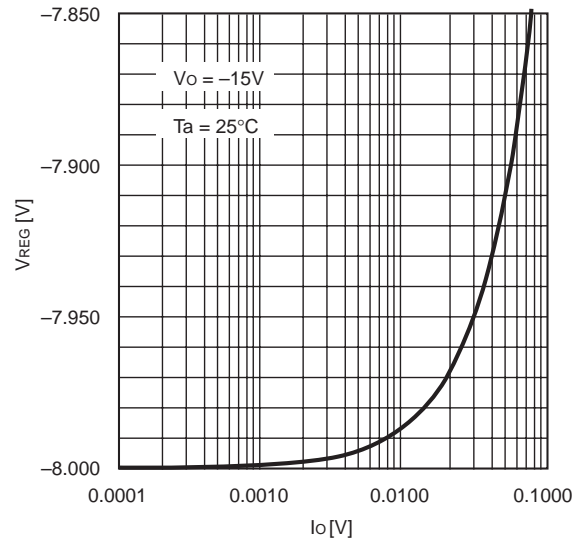
(11) Output impedance vs. Input voltage



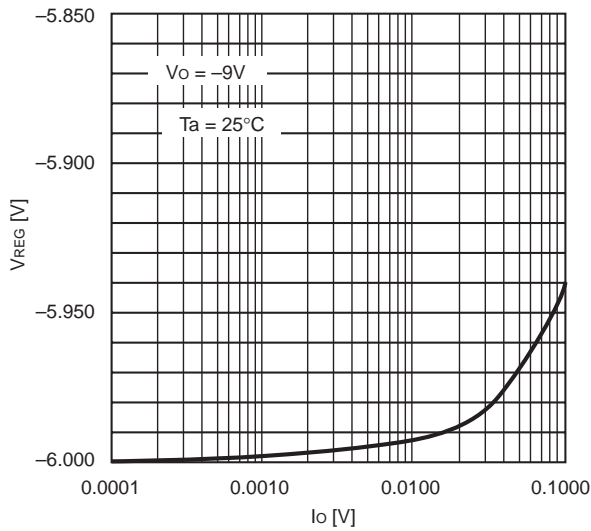
(12) Multiplication efficiency vs. Clock frequency



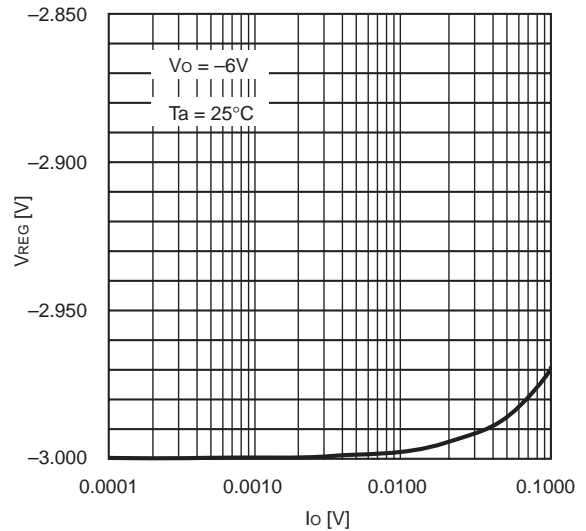
(13) Multiplication efficiency vs. Clock frequency



(14) Output voltage vs. Output current



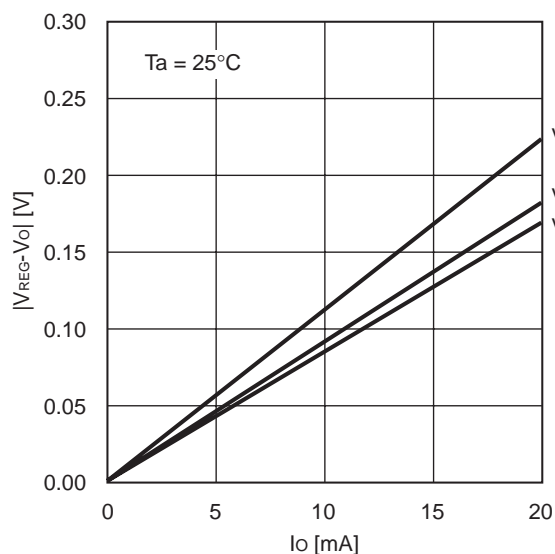
(15) Output voltage vs. Output current



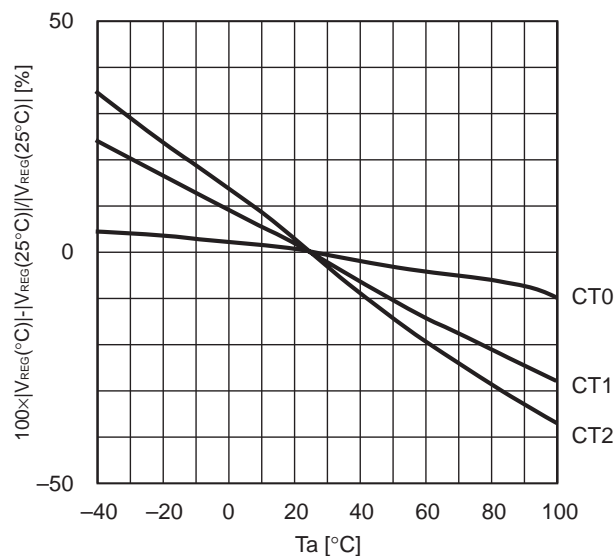
(16) Output voltage vs. Output current

S1F76610 Series

S1F76610 Series



(17) Regulator voltage vs. Output current



(18) Regulator output stability ratio vs. Ambient temperature

Temperature Gradient Control

The S1F7661C0B0 offers a choice of three temperature gradients which can be used to adjust the voltage regulator output in applications such as power supplies for driving LCDs.

$\overline{\text{POFF}}$	TC2	TC1	Temperature gradient (%/°C) See note 2.	Voltage regulator output	CR oscillator	Remarks
See note 1.						
1 (V _{DD})	Low (V _o)	Low (V _o)	-0.4	ON	ON	
1 (V _{DD})	Low (V _o)	High (V _{DD})	-0.1	ON	ON	
1 (V _{DD})	High (V _{DD})	Low (V _o)	-0.6	ON	ON	
1 (V _{DD})	High (V _{DD})	High (V _{DD})	-0.6	ON	OFF	Serial connection
0 (V _i)	Low (V _o)	Low (V _o)	—	OFF (high impedance)	OFF	
0 (V _i)	Low (V _o)	High (V _{DD})	—	OFF (high impedance)	OFF	
0 (V _i)	High (V _{DD})	Low (V _o)	—	OFF (high impedance)	OFF	
0 (V _i)	High (V _{DD})	High (V _{DD})	—	OFF (high impedance)	OFF	Multiplier operational

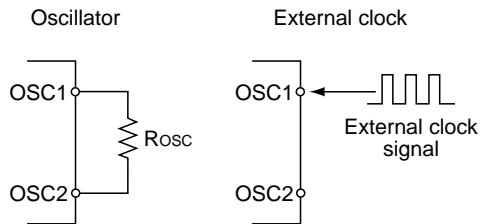
Notes

- The definition of LOW for $\overline{\text{POFF}}$ differs from that for TC1 and TC2.
- The temperature gradient affects the voltage between V_{DD} and V_{REG}.

FUNCTIONAL DESCRIPTIONS

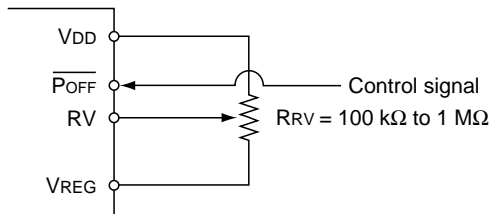
CR Oscillator

The on-chip CR oscillator network frequency is determined by the external resistor, R_{osc} , connected between OSC1 and OSC2. This oscillator can be disabled in favor of an external clock by leaving OSC2 open and applying an external clock signal to OSC1.



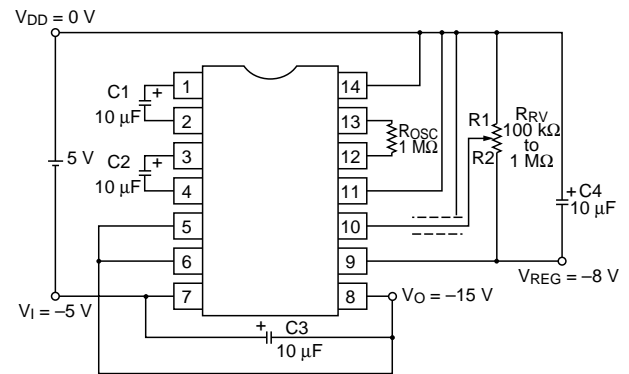
Reference Voltage Generator and Voltage Regulator

The reference voltage generator supplies a reference voltage to the voltage regulator to control the output. This voltage can be switched ON and OFF.

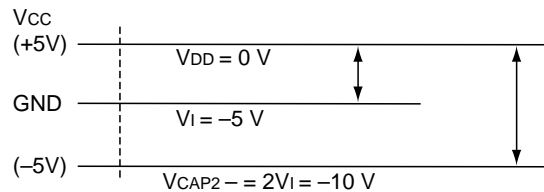


Voltage Multiplier

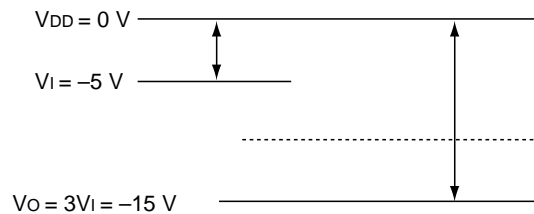
The voltage multiplier uses the clock signal from the oscillator to double or triple the input voltage. This requires three external capacitors—two charge-pump capacitors between CAP1+ and CAP1- and CAP2+ and CAP2-, respectively, and a smoothing capacitor between VI and VO.



Double voltage potential levels



Tripled voltage potential levels



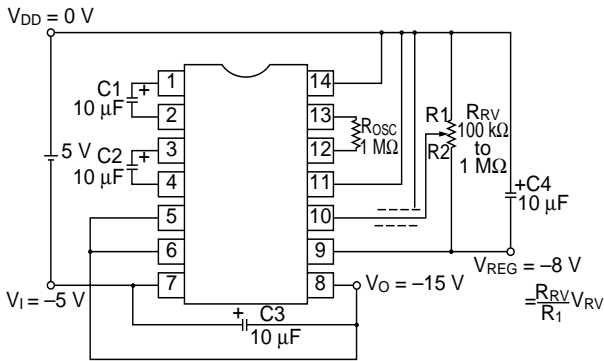
S1F76610 Series

S1F76610 Series

TYPICAL APPLICATIONS

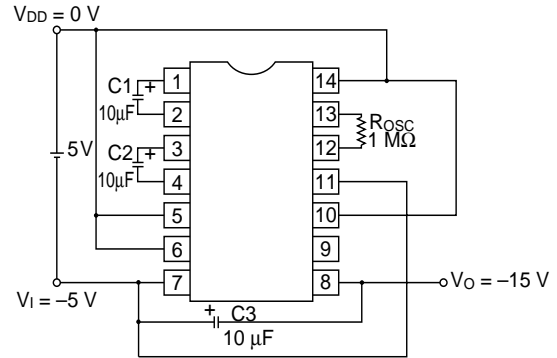
Voltage Tripler with Regulator

The following figure shows the circuit required to triple the input voltage, regulate the result and add a temperature gradient of $-0.4\%/^{\circ}\text{C}$. Note that the high input impedance of RV requires appropriate noise countermeasures.



Converting a Voltage Tripler to a Voltage Doubler

To convert this circuit to a voltage doubler, remove capacitor C2 and short circuit CAP2- to VO.

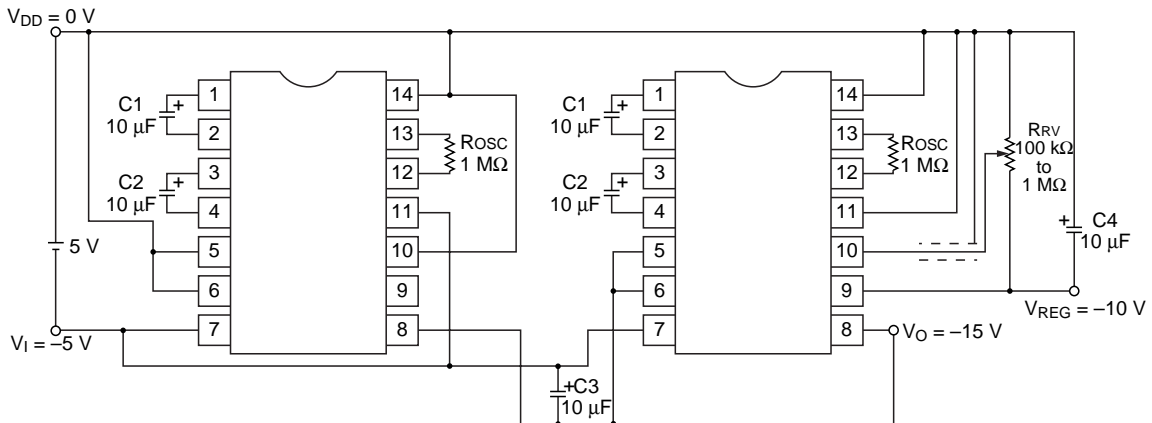


Parallel Connection

Connecting two or more chips in parallel reduces the output impedance by $1/n$, where n is the number of devices used.

Only the single output smoothing capacitor, C3, is re-

quired when any number of devices are connected in parallel. Also, the voltage regulator in one chip is sufficient to regulate the combined output.



Serial Connection

Connecting two or more chips in series obtains a higher output voltage than can be obtained using a parallel

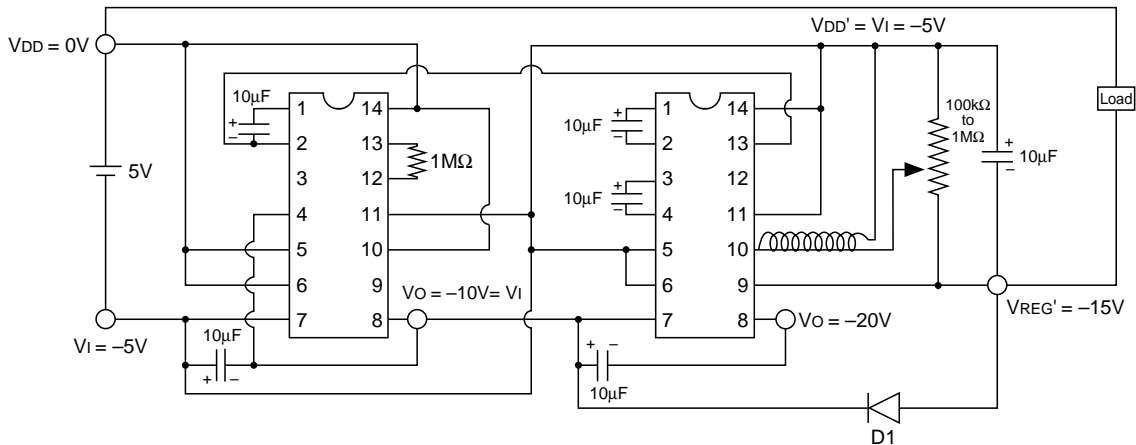
connection, however, this also raises the output impedance.

<Precautions when connecting loads>

In case of series connections, when connecting loads between the first stage VDD (or other potential of the second stage VDD or up) and the second stage VREG as shown in Fig. 2-13, be cautions about the following point.

the first stage VDD (or other potential of the second stage VDD or up) to cause a voltage exceeding the absolute maximum rating for the second stage VDD at the VREG terminal, normal operation of the IC may be hampered. Consequently, When making a series connection, insert a diode D1 between the second stage VI and VREG as shown in Fig. 2-13 so that a voltage exceeding the second stage VDD or up may not be applied to the VREG terminal.

- * When normal output is not occurring at the VREG terminal such as at times of starting up or when turning the VREG off by POF signals, if current flows into the second stage VREG terminal through the load from

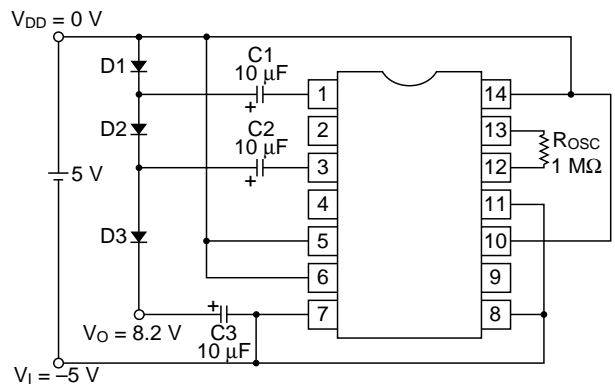


Positive Voltage Conversion

Adding diodes converts a negative voltage to a positive one.

To convert the voltage tripler shown earlier to a voltage doubler, remove C2 and D2, and short circuit D3. Small Schottky diodes are recommended for all these diodes. The resulting voltage is lowered by V_F , the voltage drop in the forward direction for each diode used. For example, if $V_{DD} = 0V$, $V_I = -5V$, and $V_F = 0.6V$, the resulting voltages would be as follows.

- For a voltage tripler,
 $V_O = 10 - (3 \times 0.6) = 8.2V$
- For a voltage doubler,
 $V_O = 5 - (2 \times 0.6) = 3.8V$

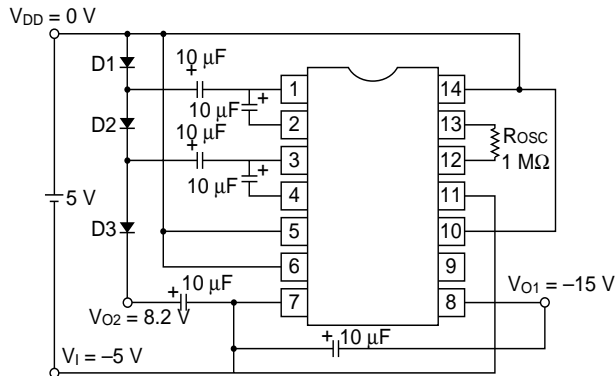


S1F76610 Series

S1F76610 Series

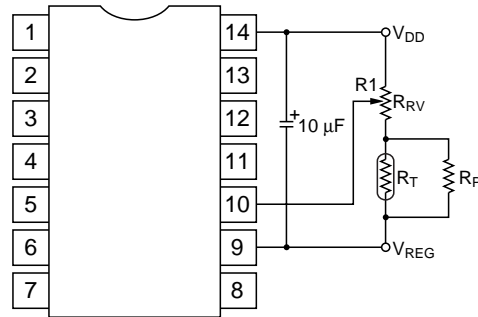
Simultaneous Voltage Conversion

Combining a standard voltage tripler circuit with one for positive voltage conversion generates both -15 and 8.2V outputs from a single input, however, it also raises the output impedance.
A voltage doubler generates -10 and 3.8V outputs.

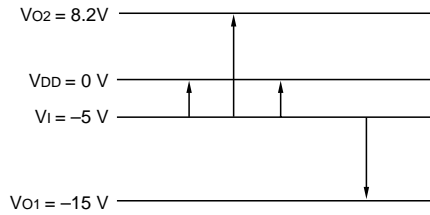


Using an External Gradient

The S1F7661C0B0/M0B0 offers three built-in temperature gradients— -0.1 , -0.4 and $-0.6\%/^{\circ}\text{C}$. To set the gradient externally, place a thermistor, R_T , in series with the variable resistor, R_{RV} , used to adjust the output voltage.



Potential levels



S1F76540 Series Charge Pumping DC/DC Converter & Voltage Regulator

DESCRIPTION

The S1F76540C0A0/M0A0 is a CMOS process, charge-pumping DC/DC converter and voltage regulator featuring the very high efficiency but low power consumption. An addition of four, three, or two external capacitors can generate four-, three- or two-time output voltage in negative direction than the input voltage. Also, the built-in voltage regulator can set any output voltage of DC/DC converter and can output the regulated voltage using two external resistances. As the regulator output can have a negative temperature gradient that is required for LCD panels, it is optimum for the LCD panel power supply.

FEATURES

- Charge-pumping, DC-to-DC converter (four-, three- or two-time negative boosting)
- Built-in voltage regulator (regulated voltage output circuit)
- High power conversion efficiency : 95%
- Low current consumption : 130 μ A ($V_I = -5.0$ V during four-time boosting, Typ.)
- High output capacity : 20 mA (Max.)

- Input voltages : -2.4 to -5.5 V (during four-time boosting)
: 2.4 to -7.3 V (during three-time boosting)
: 2.4 to -11 V (during two-time boosting)
- DC/DC converter output voltage : |Input voltage| \times 4 (Max.)
- Built-in reference voltage for high-precision regulator : 1.5 \pm 0.05 V (at C_{T0})
- Temperature gradient function of regulator output voltages : -0.04, -0.15, -0.35, -0.55 (%/ $^{\circ}$ C)
- Low standby current (during power-off) : 5.0 μ A
- Power-off by the external signal
- Full built-in oscillator circuit
- Lineup : S1F76540M0A0, 16-pin SSOP
: S1F76540C0A0, 16-pin DIP

APPLICATIONS

- Power supply of medium- and small-capacity LCD panels
- Regulated power supply of battery driven devices

S1F76540 Series

BLOCK DIAGRAM

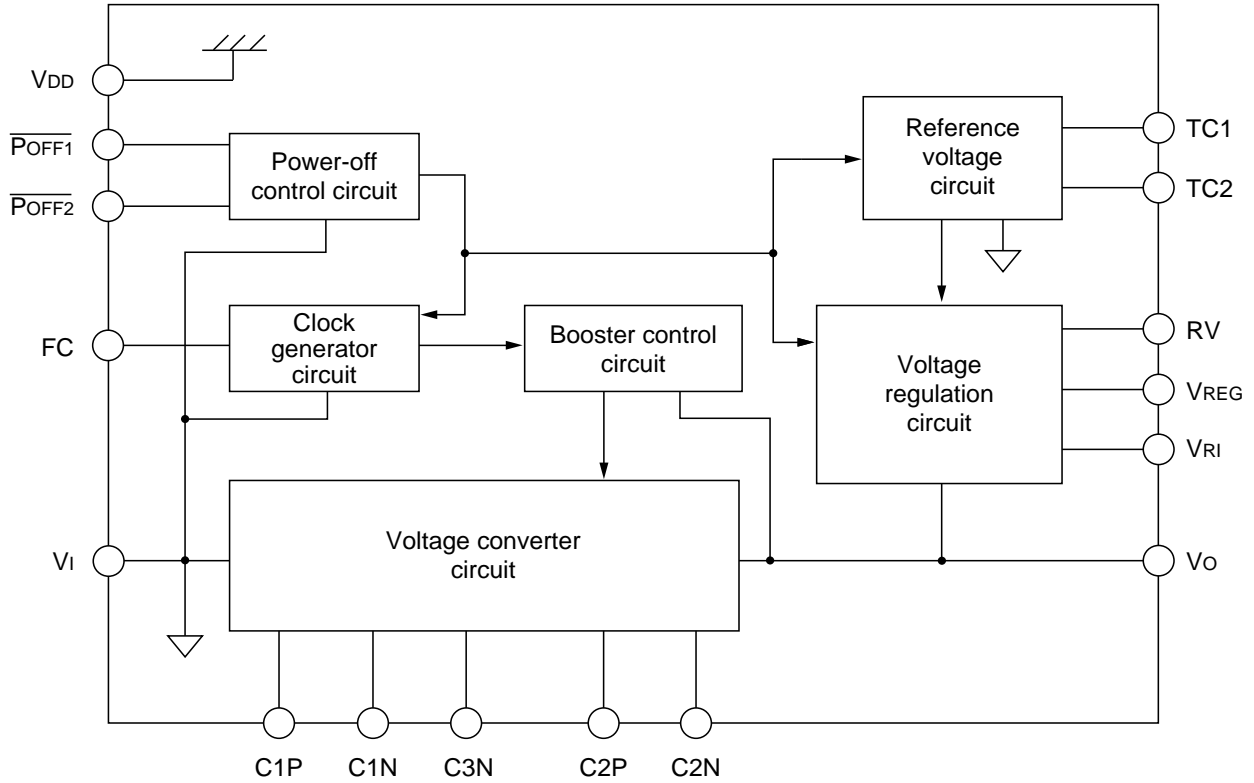


Figure 2.1 Block diagram

PIN DESCRIPTIONS

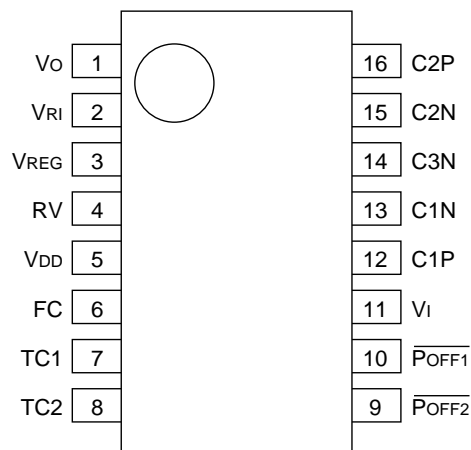


Figure 2.2 S1F76540M0A0/C0A0 pin assignments

Table 2.1 Pin descriptions

Pin name	Pin No.	Pad No.	Description
VO	1	18	Four-time booster output
VRI	2	19	Regulator input
VREG	3	20	Regulator output
RV	4	21	Regulator output voltage adjustment input
VDD	5	22, 23	Power pin (positive)
FC	6	24	Internal clock frequency input, and clock input in serial/parallel connection
TC1	7	3	Regulator output temperature gradient setup input (1)
TC2	8	4	Regulator output temperature gradient setup input (2)
$\overline{\text{POFF2}}$	9	5	Power-off control input (2)
$\overline{\text{POFF1}}$	10	6	Power-off control input (1)
VI	11	11, 12	Power voltage (negative)
C1P	12	13	Two- or four-time booster capacitor positive pin
C1N	13	14	Two-time booster capacitor negative pin
C3N	14	15	Four-time booster capacitor negative pin
C2N	15	16	Three-time booster capacitor negative pin
C2P	16	17	Three-time booster capacitor positive pin

S1F76540 Series

Table 2.2 Absolute maximum ratings
 V_{DD} reference

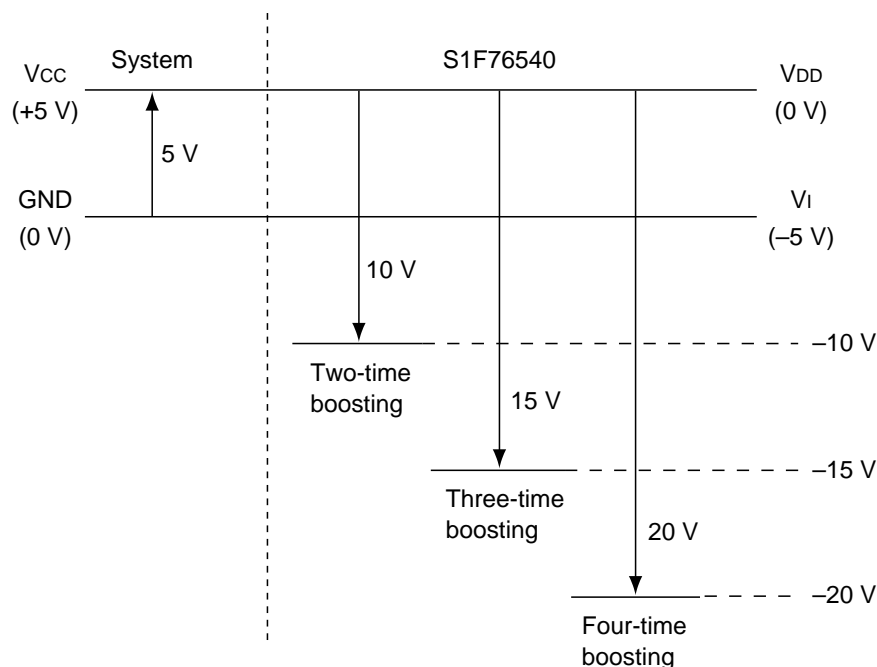
Parameter	Symbol	Rating		Unit	Remarks
		Min.	Max.		
Input power voltage	V_I	-26.0/N	$V_{DD} + 0.3$	V	N = Boost time V_I pin
Input pin voltage	V_I	$V_I - 0.3$	$V_{DD} + 0.3$	V	$\overline{POFF1}$, $\overline{POFF2}$, TC1, TC2 and FC pins
Output pin voltage 1	V_{OC1}	$V_I - 0.3$	$V_{DD} + 0.3$	V	C1P and C2P pins
Output pin voltage 2	V_{OC2}	$2 \times V_I - 0.3$	$V_I + 0.3$	V	C1N pin
Output pin voltage 3	V_{OC3}	$3 \times V_I - 0.3$	$2 \times V_I + 0.3$	V	C2N pin
Output pin voltage 4	V_{OC4}	$4 \times V_I - 0.3$	$3 \times V_I + 0.3$	V	C3N pin
Regulator input power voltage	V_{RI}	$N \times V_I - 0.3$	$V_{DD} + 0.3$	V	N = Boost time, V_{RI} pin
Regulator input pin voltage	V_{RV}	$N \times V_I - 0.3$	$V_{DD} + 0.3$	V	N = Boost time, RV pin
Output voltage	V_O	$N \times V_I - 0.3$	$V_{DD} + 0.3$	V	N = Boost time V_O and V_{REG} pins
Input current	I_I		80	mA	V_I pin
Output current	I_O		$N \leq 4: 20$ $N > 4: 80/N$	mA	N = Boost time V_O and V_{REG} pins
Allowable loss	P_D		210	mW	$T_a \leq 25^\circ\text{C}$
Operating temperature	T_{opr}	-30	85	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55	150	$^\circ\text{C}$	
Soldering temperature and time	T_{sol}		$260 \cdot 10$	$^\circ\text{C} \cdot \text{s}$	At leads

Notes: 1. An operation exceeding the above absolute maximum ratings may cause a malfunction or permanent damage of devices. The device reliability may drop excessively even if the devices temporarily operate normally.

2. Electrical potential to peripheral systems:

The S1F76540 common power supply has the highest potential (V_{DD}). The electrical potential given by this specification is based on $V_{DD} = 0$ V. Take care to avoid a potential problem during connection to a peripheral system.

Figure 2.3 Potential relationship



ELECTRICAL CHARACTERISTICS

Table 2.3 DC characteristics (1)

$T_a = -30^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_{DD} = 0\text{ V}$, $V_I = -5.0\text{ V}$
unless otherwise noted

Parameter	Symbol	Characteristics	Min.	Typ.	Max.	Unit
Input power voltage	V_I	N = Boost time if CT0 is selected	-22/N		-2.4	V
		N = Boost time if CT1 is selected	-22/N		-2.4	V
		N = Boost time if CT2 is selected	-22/N		-2.4	V
		N = Boost time if CT3 is selected	-22/N		-2.4	V
Boost start input power voltage	V_{STA}	N = Boost time, FC = V_{DD} during no loading	-22/N		-2.4	V
Boost output voltage	V_O		-22			V
Regulator input voltage	V_{RI}		-22		-2.4	V
Regulator output voltage	V_{REG}	$I_{REG} = 0$, $V_{RI} = -22\text{ V}$ $R_{RV} = 1\text{ M}\Omega$			-2.4	V

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Table 2.3 DC characteristics (2)

$T_a = -30^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_{DD} = 0\text{ V}$, $V_I = -5.0\text{ V}$
unless otherwise noted

Parameter	Symbol	Characteristics	Min.	Typ.	Max.	Unit
Boost output impedance	R _O	$I_o = 10\text{ mA}$, $V_I = -5.0\text{ V}$ during 4-time boosting C1, C2, C3, C _O = 10 μF (tantalum)		200	300	Ω
		$I_o = 10\text{ mA}$, $V_I = -3.0\text{ V}$, $T_a = 25^{\circ}\text{C}$ during 4-time boosting C1, C2, C3, C _O = 10 μF (tantalum)		250	300	Ω
Boost power conversion efficiency	P _{eff}	$I_o = 2\text{ mA}$, $V_I = -5.0\text{ V}$ during 4-time boosting C1, C2, C3, C _O = 10 μF (tantalum)		95		%
		$I_o = 2\text{ mA}$, $V_I = -3.0\text{ V}$, $T_a = 25^{\circ}\text{C}$ during 4-time boosting C1, C2, C3, C _O = 10 μF (tantalum)		94		%
Booster operation current consumption 1	I _{OPR1}	FC = V _{DD} , $\overline{\text{POFF1}} = V_I$, $\overline{\text{POFF2}} = V_{DD}$, $V_I = -5.0\text{ V}$ during no loading C1, C2, C3, C _O = 10 μF (tantalum)		130	220	μA
		FC = V _{DD} , $\overline{\text{POFF1}} = V_I$, $\overline{\text{POFF2}} = V_{DD}$, $V_I = -3.0\text{ V}$, $T_a = 25^{\circ}\text{C}$ during no loading C1, C2, C3, C _O = 10 μF (tantalum)		100	150	μA
Booster operation current consumption 2	I _{OPR2}	FC = V _I , $\overline{\text{POFF1}} = V_I$, $\overline{\text{POFF2}} = V_{DD}$, $V_I = -5.0\text{ V}$ during no loading C1, C2, C3, C _O = 10 μF (tantalum)		520	880	μA
		FC = V _I , $\overline{\text{POFF1}} = V_I$, $\overline{\text{POFF2}} = V_{DD}$, $V_I = -3.0\text{ V}$, $T_a = 25^{\circ}\text{C}$ during no loading C1, C2, C3, C _O = 10 μF (tantalum)		400	600	μA
Regulator operation current consumption	I _{OPVR}	$V_{RI} = -20\text{ V}$, $R_{RV} = 1\text{ M}\Omega$ during no loading		10	15	μA
Static current	I _Q	$\overline{\text{POFF1}} = V_I$, $\overline{\text{POFF2}} = V_I$ FC = V _{DD}			5.0	μA
Input leakage current	I _{LKI}	Pins used: $\overline{\text{POFF1}}$, $\overline{\text{POFF2}}$, FC, TC1, TC2			0.5	μA
Regulated output saturation resistance	R _{SAT} (*1)	$0 < I_{REG} < 20\text{ mA}$ $R_V = V_{DD}$ $T_a = 25^{\circ}\text{C}$		10	20	Ω
Regulated output voltage stability	ΔV_R (*2)	$-20\text{ V} < V_{RI} < -10\text{ V}$, $I_{REG} = 1\text{ mA}$ $V_{REG} = -9\text{ V}$ $T_a = 25^{\circ}\text{C}$			0.2	%/V

Table 2.3 DC characteristics (3)

Ta = -30°C to +85°C, VDD = 0 V, VI = -5.0 V
unless otherwise noted

Parameter	Symbol	Characteristics	Min.	Typ.	Max.	Unit
Regulated output load variation	ΔV_O (*3)	VRI = -20 V, VREG = -15 V, Ta = 25°C setup 0 < IREG < 20 mA		30	50	mV
Reference voltage (Ta = 25°C)	VREF0	TC1 = VDD, TC2 = VDD	-1.55	-1.50	-1.45	V
	VREF1	TC1 = VDD, TC2 = VI	-1.70	-1.50	-1.30	V
	VREF2	TC1 = VI, TC2 = VDD	-1.90	-1.50	-1.10	V
	VREF3	TC1 = VI, TC2 = VI	-2.15	-1.50	-0.85	V
Reference voltage temperature coefficient (*4, *5)	CT0	TC1 = VDD, TC2 = VDD, SSOP product	-0.07	-0.04	0	%/°C
	CT1	TC1 = VDD, TC2 = VI, SSOP product	-0.25	-0.15	-0.07	%/°C
	CT2	TC1 = VI, TC2 = VDD, SSOP product	-0.45	-0.35	-0.20	%/°C
	CT3	TC1 = VI, TC2 = VI, SSOP product	-0.75	-0.55	-0.30	%/°C
Input voltage level	VIH	VI = -2.4 to -5.5 V Pins used: P _{OFF1} , P _{OFF2} , FC, TC1, TC2	0.2 VI			V
	VIL	VI = -2.4 to -5.5 V Pins used: P _{OFF1} , P _{OFF2} , FC, TC1, TC2			0.8 VI	V
Booster capacitance	C _{MAX}	Capacitors used: C1, C2 and C3			47	μF

$$*1 \quad R_{SAT} = \frac{\Delta (V_{REG} - V_{RI})}{\Delta I_{REG}}$$

$$*2 \quad \Delta V_R = \frac{V_{REG} (V_{RI} = -20 \text{ V}) - V_{REG} (V_{RI} = -10 \text{ V})}{\Delta V_{RI} \cdot V_{REG} (V_{RI} = -10 \text{ V})}$$

$$*3 \quad \Delta V_O = \frac{V_{REG} (I_{REG} = 20 \text{ mA}) - V_{REG} (I_{REG} = 0 \text{ mA})}{\Delta I_{REG}}$$

$$*4 \quad C_T = \frac{|V_{REF} (50^\circ\text{C})| - |V_{REF} (0^\circ\text{C})|}{50^\circ\text{C} - 0^\circ\text{C}} \times \frac{100}{|V_{REF} (25^\circ\text{C})|}$$

*5 The reference voltage and temperature coefficient of the chip products may vary depending on the moldings used on each chip. Use these chips only after the temperature test.

S1F76540 Series

Table 2.4 AC characteristics

$V_{DD} = 0\text{ V}$ and $V_I = -5.0\text{ V}$
unless otherwise noted

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	
Internal clock frequency 1	f _{CL1}	$FC = V_{DD}$, $P_{OFF1} = V_I$ $P_{OFF2} = V_{DD}$ Pin used: C1P	Ta = 25°C	3.0	4.0	6.0	kHz
			Ta = -30°C to +85°C	2.0	4.0	7.0	kHz
Internal clock frequency 2	f _{CL2}	$FC = V_I$, $P_{OFF1} = V_I$ $P_{OFF2} = V_{DD}$ Pin used: C1P	Ta = 25°C	12.0	16.0	24.0	kHz
			Ta = -30°C to +85°C	8.0	16.0	28.0	kHz

FUNCTIONAL DESCRIPTIONS

Clock Generator Circuit

As the S1F76540 has a built-in clock generator circuit, no more parts are required for voltage boost control. The clock frequency changes according to the FC pin voltage level as defined on Table 2.5. Low Output mode or High Output mode is selectable. This allows frequency selection according to the used capacitance and

load current as the boost output impedance changes depending on the clock frequency and external booster capacitance. However, the High Output mode has the current consumption approximately four times larger than the Low Output mode.

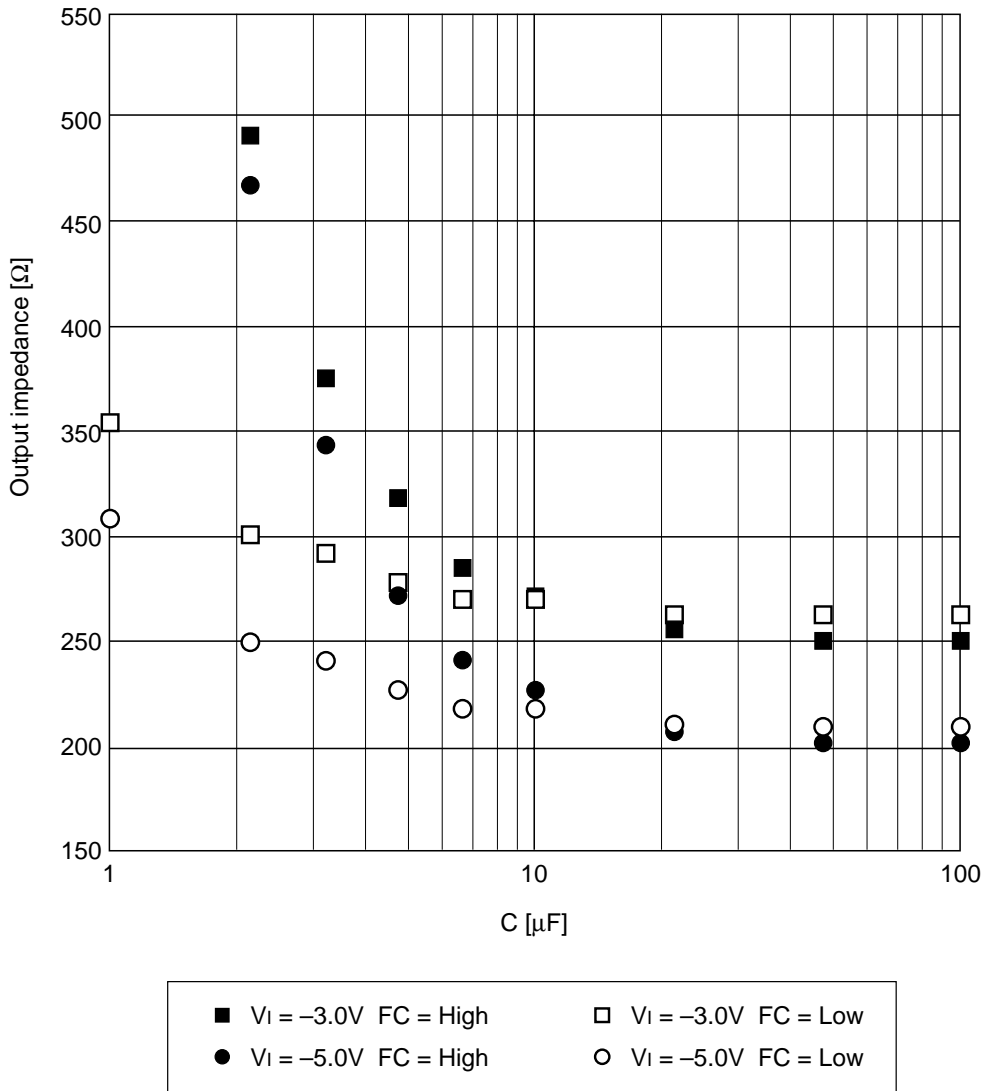
Table 2.5 FC pin setup

FC pin	Mode	Clock frequency	Characteristics			
			Current consumption	Output ripple	Output impedance	Capacitance
High (V _{DD})	Low Output	4.0 kHz (Typ.)	I _{OP} (*1)	V _{RR} (*2)	See Figure A1.	See Figure A1.
Low (V _I)	High Output	16.0 kHz (Typ.)	I _{OP} × Approx. 4	V _{RR} × Approx. 1/4	See Figure A1.	See Figure A1.

*1 See the DC characteristics table for current consumption.

*2 See Section Page 2-32 for the output ripple definition and calculation.

Capacitance vs. output impedance characteristic when 4X pressure is applied
 Load current = 10 mA, Ta = 25°C, C1 = C2 = C₀
 Capacitor used: Tantalum electrolytic capacitor



S1F76540 Series

Figure A1 Characteristic chart: Capacitance vs. output impedance when 4X pressure is applied
 NOTE: This characteristic chart simply indicates an approximate trend in the characteristics, which may vary depending on evaluation environment, parts used, and other factors.

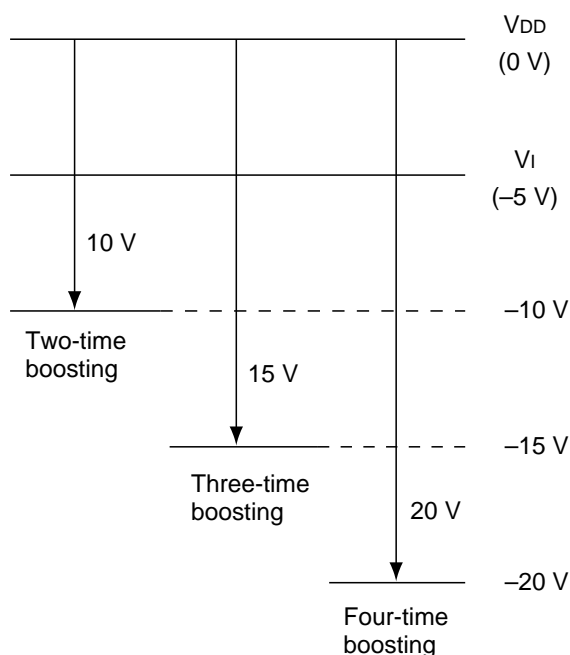
S1F76540 Series

Voltage Converter

The voltage converter, consisting of a boost control circuit and a voltage converter circuit, receives clocks from the clock generator circuit and boosts the input power voltage (V_I) four, three or two times. During four-time boosting, however, the three-time and two-

time boost outputs cannot be obtained simultaneously. Figure 2.4 gives the potential relationship during four-, three- and two-time boosting. The C2P pin is also used as the master clock output during parallel connection.

Figure 2.4 Electrical potentials during boosting (at $-5V$ input)



Caution:

- When connecting a capacitor to the C1P, C2P, C1N, C2N, C3N, or V_O pin for voltage conversion, close the capacitor to the IC package as much as possible to minimize the wiring length.

Reference Voltage Circuit

The S1F76540 has a built-in reference voltage circuit for voltage regulation. The regulated voltage (explained in the next “voltage regulator circuit” section) is set depending on the division ratio between this refer-

ence voltage and the external resistance. The reference voltage can be used to change the temperature coefficient at pins TC1 and TC2. One of four states can be selected as listed on Table 2.6.

Table 2.6 Setup of reference voltage and temperature coefficient

Mode	TC1 (High = VDD) (Low = Vi)	TC2 (High = VDD) (Low = Vi)	Reference voltage, VREF (V)			Temperature coefficient, CT (%/°C)		
			Min.	Typ.	Max.	Min.	Typ.	Max.
CT0	High	High	-1.55	-1.5	-1.45	-0.07	-0.04	0
CT1	High	Low	-1.70	-1.5	-1.30	-0.25	-0.15	-0.07
CT2	Low	High	-1.90	-1.5	-1.10	-0.45	-0.35	-0.20
CT3	Low	Low	-2.15	-1.5	-0.85	-0.75	-0.55	-0.30

Notes: 1. The reference voltage is given at Ta = 25°C.

2. The reference voltage and temperature coefficient of the chip products may vary depending on the moldings used on each chip. Use these chips only after the temperature test.

The temperature coefficient (CT) is defined by the following equation. The negative sign of the temperature coefficient (CT) means that the |VREF| value decreases when the temperature rises.

$$CT = \frac{|V_{REF}(50^{\circ}C)| - |V_{REF}(0^{\circ}C)|}{50^{\circ}C - 0^{\circ}C} \times \frac{100}{|V_{REF}(25^{\circ}C)|}$$

Notes on TC1 and TC2 pin replacement:

- When replacing the TC1 and TC2 pins after power-on, always select the power-off mode ($\overline{POFF1} = \overline{POFF2} = Vi$) and replace them by each other.

Voltage Regulator Circuit

The voltage regulator circuit regulates a voltage entered in the VRI pin and can output any voltage. It uses the series voltage regulation. As shown in Figure 2.5, the VRI and VO pins must be short-circuited by a jumper as short as possible except for larger time boosting by using external diodes.

As shown by equation (1), any output voltage can be set by the ratio of external division resistors R1 and R2. The sum of division resistance is recommended to be

small as possible to avoid an external noise interference. As the current consumed by division resistors (equation (2)) flows, the 100Ω to 1MΩ are recommended to use.

The temperature coefficient of the regulated voltage is equal to the temperature coefficient of the reference voltage that is explained in the “reference voltage circuit” section.

S1F76540 Series

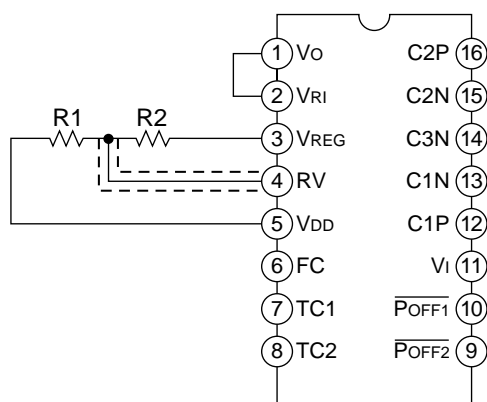


Figure 2.5 VREG setup and mounting notes

Setup:

- Relationship between VREG and reference voltage

$$V_{REG} = \frac{R1 + R2}{R1} \times (\text{Reference voltage}) \quad \bullet \bullet \bullet \text{Equation (1)}$$

- Current consumption of division resistors

$$I_{REG} = \frac{|V_{REG}|}{R1 + R2} \quad \bullet \bullet \bullet \text{Equation (2)}$$

Setup example:

- To output VREG = -18 V by four-time boosting if Vi = -5 V and Vo = -20 V

First, determine the total resistance of division resistors R1 and R2. If the current consumption is assumed to be 20 μA , the total resistance can be obtained from equation (2) as follows:

$$R1 + R2 = 12\text{V} \div 20 \mu\text{A} = 900 \text{ k}\Omega$$

If the reference voltage is -1.5 V, the division resistance ratio can be obtained from equation (1) as follows:

$$(R1 + R2) / R2 = (-18 \text{ V}) \div (-1.5 \text{ V}) = 12$$

Therefore, R1 and R2 are:

$$\begin{aligned} R1 &= 75 \text{ k}\Omega \\ R2 &= 825 \text{ k}\Omega \end{aligned}$$

Changing the temperature coefficient:

- The temperature coefficient of the regulated voltage depends on the temperature coefficient of the reference voltage (if the division ratio of setup resistors does not depend on the temperature). It is necessary to change the temperature coefficient using thermistors, resistors or others to set any other temperature coefficient of the regulated voltage. The following explains how to calculate the VREG voltage in temperature T.

$$V_{REG}(T) = \left\{ 1 + \frac{CTR2 \times R2(T_0)}{CTR1 \times R1(T_0)} \right\} \times \left[1 + (T - T_0) \times \frac{CT}{100} \right] \quad \dots \text{Equation (3)}$$

T ₀	: 25°C
CTR1	: Temperature coefficient of resistor R1 (Ratio to the value at 25°C)
CTR2	: Temperature coefficient of resistor R2 (Ratio to the value at 25°C)
CT	: Temperature coefficient of internal reference voltage (%/°C)
R1 (T ₀)	: R1 value (Ω) at 25°C
R2 (T ₀)	: R2 value (Ω) at 25°C
VREF (T ₀)	: Internal reference voltage (V) at 25°C

If the temperature coefficient of R1 and R2 is identical in equation (3), the VREG voltage depends on the temperature coefficient of internal reference voltage only.

Application notes on voltage regulator circuit:

- To satisfy the absolute maximum ratings of the S1F76540, the setup resistor(s) must be inserted between VDD and VREG pins of the S1F76540 that uses the voltage regulator. The S1F76540 IC itself may be degraded or destroyed if the R1 resistor is connected to pin VDD of S1F76540 that does not use the regulator during serial connection.
- The regulation voltage adjustment input (pin RV) has the very high input impedance, and its noise insertion can drop the regulator stability. As shown in Figure 2.5, shield the cable between the division resistor and RV pin or use a cable as short as possible between them.

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Power-off Control Function

The S1F76540 has the power-off function and turns on or off each circuit function when control signals are entered in the $\overline{\text{POFF1}}$ and $\overline{\text{POFF2}}$ pins from an external system (such as microprocessor) as defined on Table 2.7. This power-off function can also cut the reactive current

in parallel connection and other application circuits. To use the dual-state, power-off control (all ON and all OFF states) only, connect pin $\overline{\text{POFF2}}$ to pin V_I and use only pin $\overline{\text{POFF1}}$ for power-off control.

Table 2.7 Available combination of power-off control

Mode	$\overline{\text{POFF1}}$ (High = V_{DD}) (Low = V_I)	$\overline{\text{POFF2}}$ (High = V_{DD}) (Low = V_I)	Functions			Applications
			Oscillator	Booster circuit	Regulator circuit	
PS1	High	Low	ON	ON	ON	All circuits are turned on.
PS2	Low	Low	OFF	OFF (*1)	OFF (*2)	All circuits are turned off.
PS3	High	High	OFF	ON	ON	Slave unit side of parallel connection (Booster and regulator)
PS4	Low	High	ON	ON	OFF	Master unit side of parallel connection (Booster only)

*1 When the booster circuit is off, approximately $V_I + 0.6$ V voltage appears at V_O pin.

*2 When the regulator is off, the V_{REG} pin becomes high-impedance state.

Application notes on power-off function:

- When using external system signals for power-on control, start to control the power only when V_I voltage becomes stable after power-on. Unstable V_I voltage may destroy the IC permanently during on/off control.

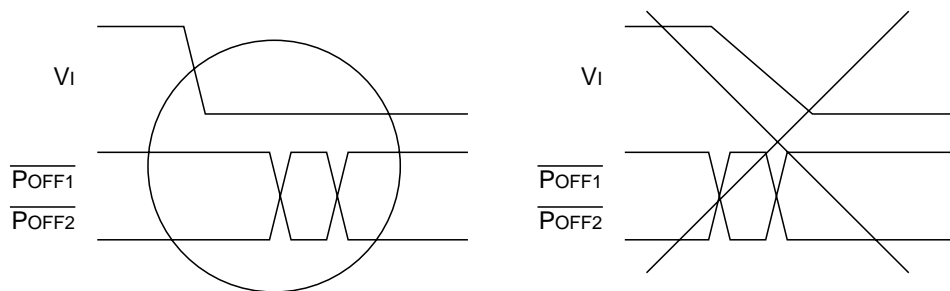
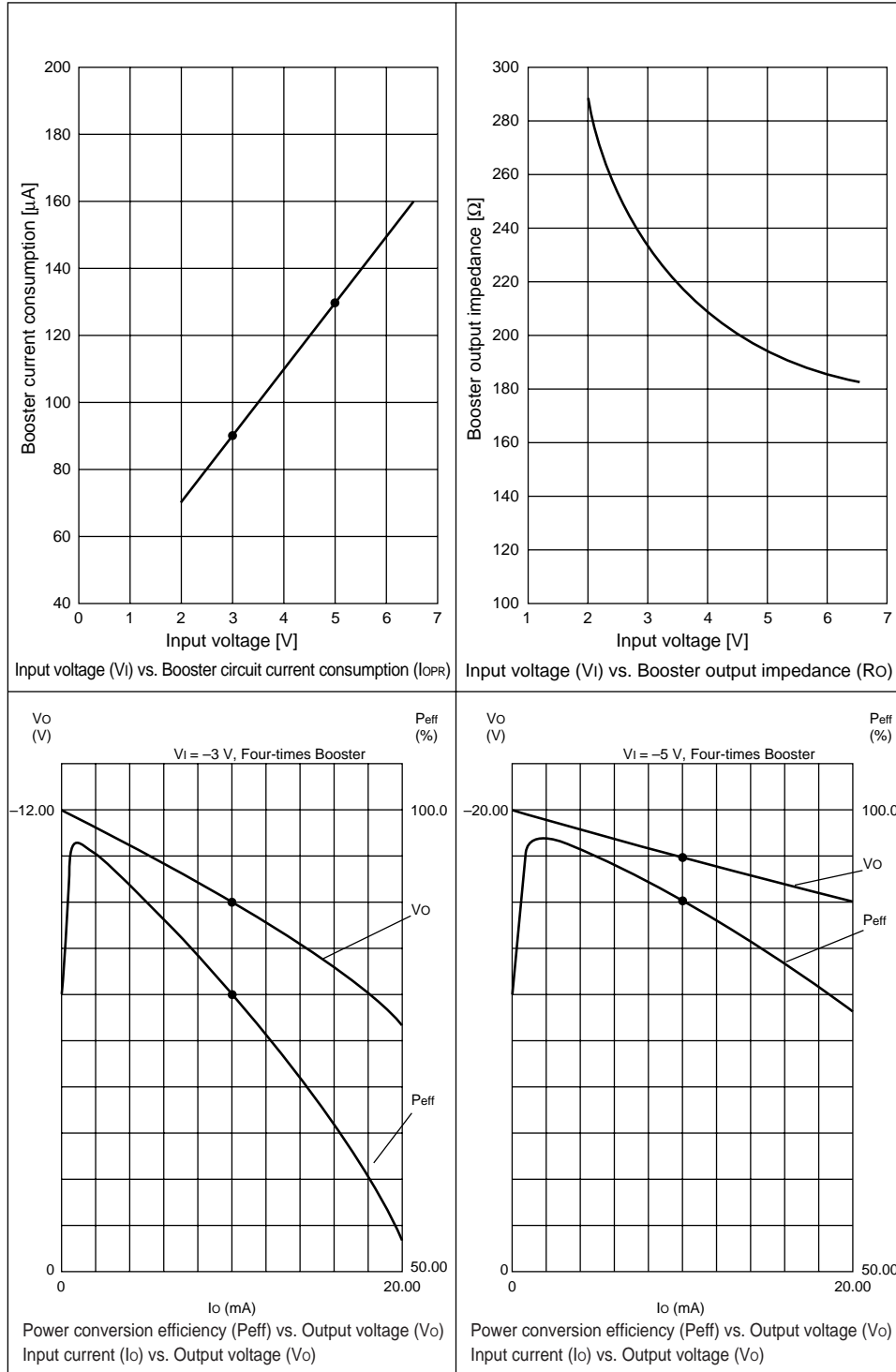


Figure 2.6 Start timing of power-off control

CHARACTERISTICS GRAPH



S1F76540 Series

Figure 2.7 Characteristics graphs

S1F76540 Series

APPLICATION CIRCUIT EXAMPLES

Four-time Booster and Regulator

Figure 2.8 gives a wiring example of four-time booster and regulator that is the typical S1F76540 application. This example boosts the input voltage (V_I) four times in

negative direction, and outputs the regulated voltage at V_{REG} pin.

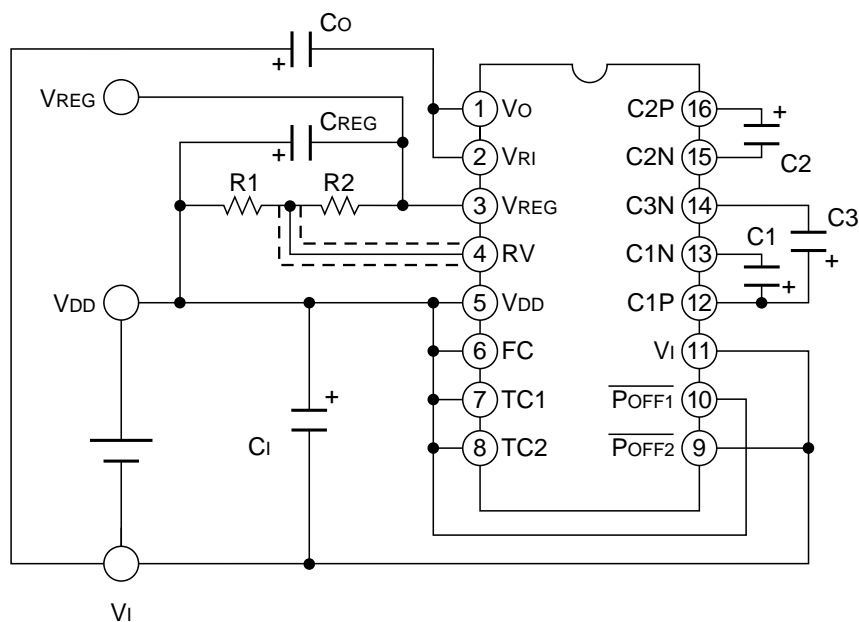


Figure 2.8 Wiring example of 4-time booster and regulator

◇ Setup conditions of Figure 2.8

- Internal clock : ON (Low Output mode)
- Booster circuit : ON
- Regulator : ON (if $C_T = -0.04\%/^{\circ}\text{C}$)

◇ Power-off procedure

- Set the $\overline{\text{POFF1}}$ pin to logical low (V_I) to turn off all circuits.

◇ Regulator

- For the regulator setup and notes, see the “voltage regulator circuit” section.

◇ Application in other setup conditions

- ① When used in the High Output mode
 - Connect the FC pin to the V_I pin.
- ② When changing the temperature coefficient (C_T)
 - Change the TC1 and TC2 pin setup by following the definition of Table 2.7.

4-time Booster

Only the booster circuit operates, and it boosts the input voltage (V_I) four times in negative direction and outputs it at the V_O pin. As the regulator is not used, the voltage

appearing at the V_O pin may contain ripple components. Figure 2.9 gives a wiring example.

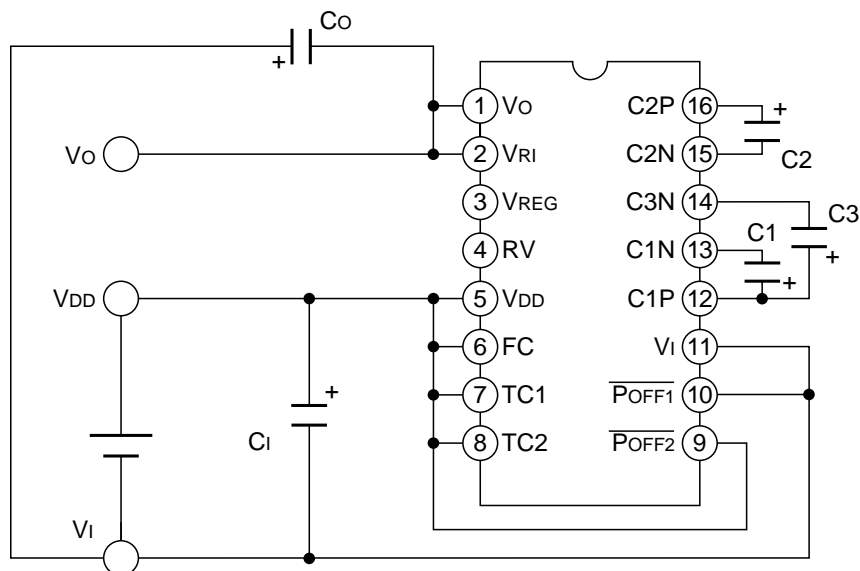


Figure 2.9 Wiring example of 4-time booster

◇ Setup conditions of Figure 2.9

- Internal clock : ON (Low Output mode)
- Booster circuit : ON
- Regulator : OFF

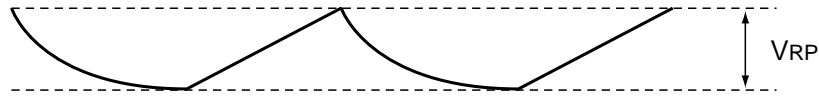
◇ Power-off procedure

- Set the $\overline{\text{POFF2}}$ pin to low (V_I) to turn off all circuits.

◇ Ripple voltage

- As the output at V_O pin is unstable, it can contain ripple components as shown in Figure 2.10. The ripple voltage (V_{RP}) increases according to the load current, and it can roughly be calculated by equation (4).

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$$V_{RP} = \frac{I_O}{2 \cdot f_{CL} \cdot C_O} + I_O \cdot R_{COUT} \quad \dots \text{Equation (4)}$$

where,

I_O : Load current (A)

f_{CL} : Clock frequency (Hz)

R_{COUT} : Serial equivalent resistance (Ω) of output capacitor C_O

Figure 2.10 Ripple waveforms

- ◇ Application in other setup conditions
 - ① When used in the High Output mode
Connect the FC pin to the V_I pin.

Parallel Connection (for Increased Boosting)

The parallel connection is useful for reduction of booster output impedance or reduction of ripple voltage. In the parallel connection of “n” lines, the booster output impedance can be reduced to approximately “1/n”. Only the smoothing capacitor (C_O) for booster output can be used commonly in the parallel connection. When using the regulator, use only one of “n”

S1F76540 chips which are in parallel connection. (If multiple regulators are operated in parallel mode, the reactive current consumption occurs.) Figure 2.11 gives a wiring example of 4-time booster and regulator where two S1F76540s are parallelly connected.

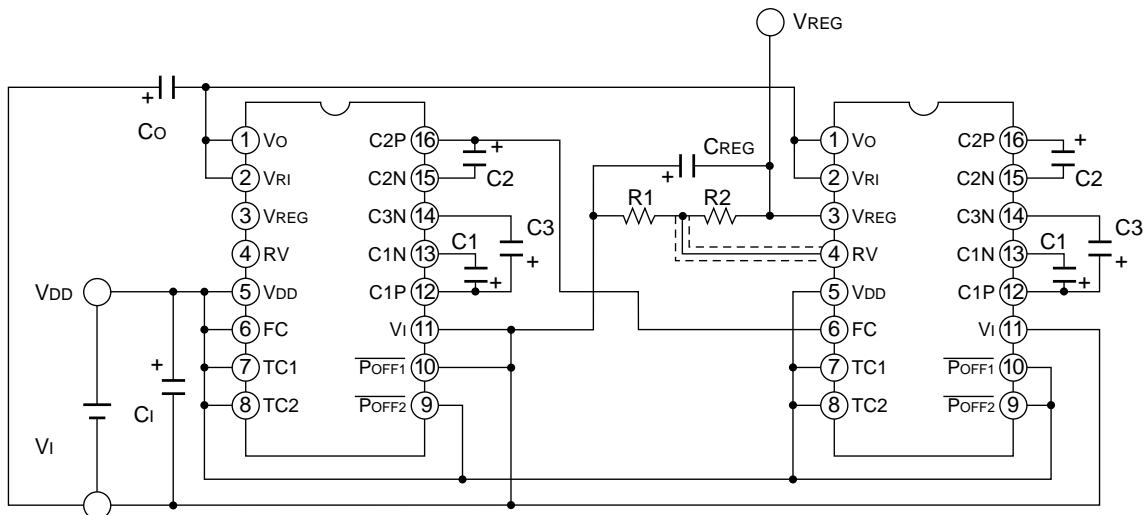


Figure 2.11 Parallel connection example

◇ Setup conditions of Figure 2.11

- | | |
|-----------------------------------------|--------------------------------------------------|
| First stage | Second stage |
| • Internal clock : ON (Low Output mode) | • Internal clock : OFF |
| • Booster circuit : ON | • Booster circuit : ON |
| • Regulator : OFF | • Regulator : ON (if $C_T = -0.04\%/^{\circ}C$) |

◇ Power-off procedure

- In Figure 2.11, when the $\overline{POFF2}$ pin of the first-stage S1F76540 is set to low (V_I), voltage boosting is stopped at the first and second stages. However, the regulator at the second stage does not stop. Therefore, the voltage that is approximately V_I appears at V_{REG} pin during $|V_{REG}| > |V_I|$ setup.
- To set the V_{REG} pin to high-impedance state, set both $\overline{POFF1}$ and $\overline{POFF2}$ pins to low at the first and second stages.

◇ Application in other setup conditions

- ① When used in the High Output mode
 - Connect the FC pin of the first-stage S1F76540 to the V_I pin.
- ② When changing the temperature coefficient (C_T)
 - Change the TC1 and TC2 pin setup by following the definition of Table 2.7.

Larger Time Boosting Using Diodes

The S1F76540 can be configured to have the five-time or larger voltage boosting and regulation by adding external diodes. As the booster output impedance increases due to the diode forward voltage drop (V_F), the diodes having a smaller V_F are recommended to use.

Figure 2.12 gives a wiring example of 6-time booster and regulator that use two diodes. The wiring between V_O and V_{RI} must be minimal. Figure 2.13 provides the potential relationship.

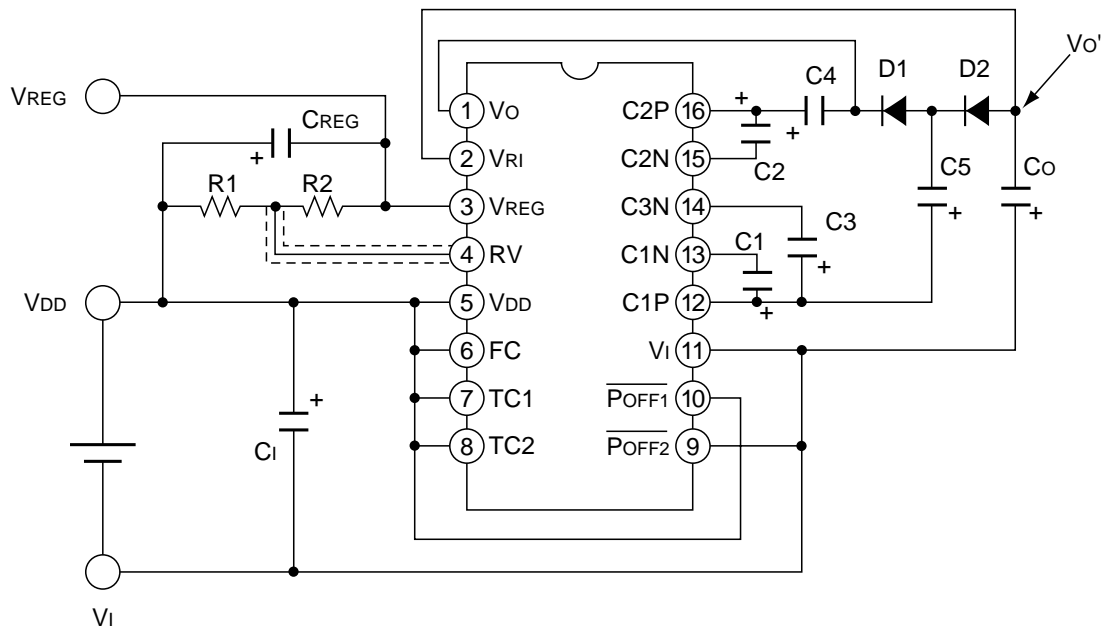


Figure 2.12 Wiring example for 6-time boosting using diodes

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- ◇ Setup conditions of Figure 2.12
 - Internal clock : ON (Low Output mode)
 - Booster circuit : ON
 - Regulator : ON (if $C_T = -0.04\%/^{\circ}\text{C}$)

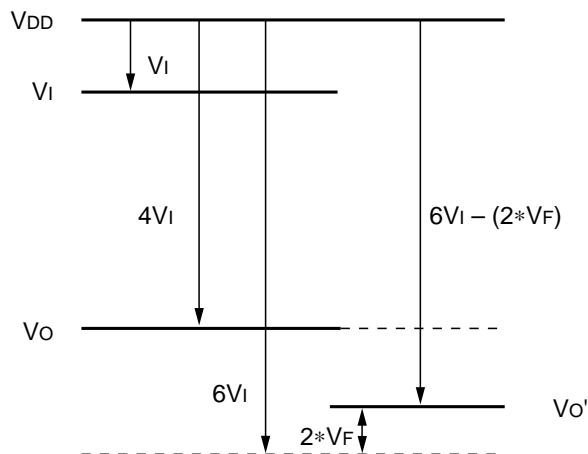


Figure 2.13 Potential relationship during 6-time boosting using diodes

- ◇ Power-off procedure
 - Set the P_{OFF1} pin to low (V_I) to turn off all circuits.
- ◇ Output voltages
 - When diodes are used for voltage boosting, the characteristics of diodes directly affect on the voltage boosting characteristics. The forward voltage drop (V_F) of diodes can reduce the booster output voltage. As the example of Figure 2.12 uses two diodes, the drop of “ V_F ” voltage multiplied by two occurs as shown in Figure 2.13. The booster output voltage is expressed by equation (5).
To increase the $|V_{O'}|$ value, use the diodes having a smaller V_F .

$$|V_{O'}| = 6 \times |V_I| - 2 \times V_F$$

•••• Equation (5)

◇ Notes

① Input and output current conditions

To satisfy the input and output current ratings, limit the total current does not exceed the rated input current. The total current means the total boost time multiplied by the output load current. The example of Figure 2.12 has the maximum load current of 13.3 mA (= 80 mA divided by 6).

② Input and output voltage conditions

To satisfy the input and output voltage ratings, take care not to violate the electric potential relationship of higher time boosting using diodes. The example of Figure 2.12 must have the “ V_I ” that can satisfy the input voltage conditions during 6-time boosting (see Table 2.3).

◇ Application in other setup conditions

① When used in the High Output mode

Connect the FC pin to the V_I pin.

② When changing the temperature coefficient (C_T)

Change the TC1 and TC2 pin setup by following the definition of Table 2.7.

Positive Voltage Conversion

The S1F76540 can also boost up a voltage to the positive potential using external diodes. In such case, however, the regulator function is unavailable. Figure 2.14

gives a wiring example for three-time positive boosting, and Figure 2.15 provides its electrical potential relationship.

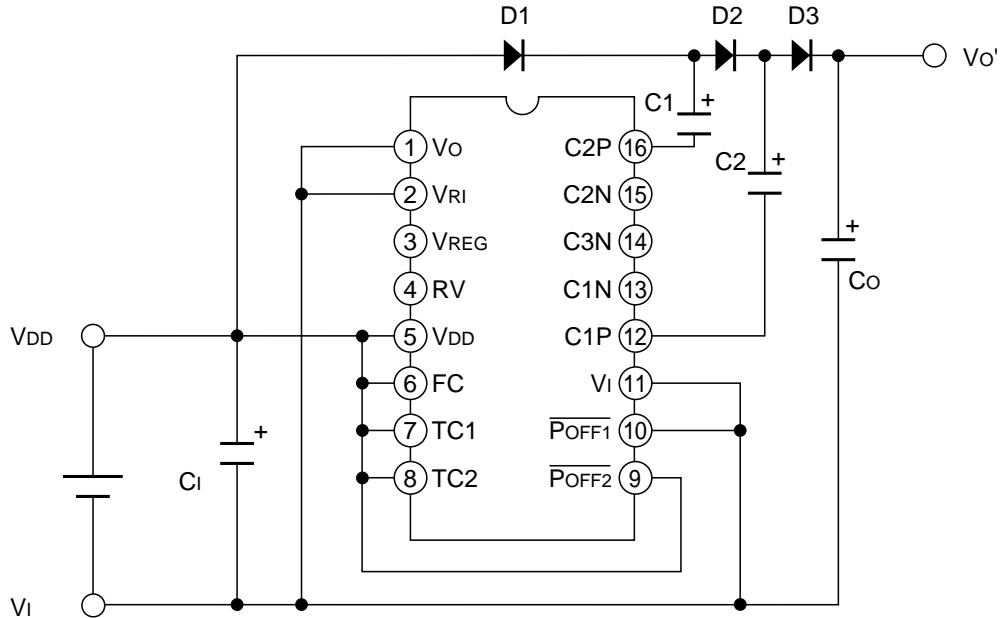


Figure 2.14 Wiring example of positive voltage conversion (3-time boosting)

- ◇ Setup conditions of Figure 2.14
 - Internal clock : ON (Low Output mode)
 - Booster circuit : ON
 - Regulator : OFF

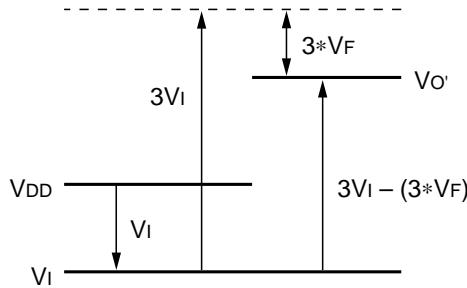


Figure 2.15 Potential relationship during positive voltage conversion (3-time boosting)

- ◇ Power-off procedure
 - Set the $\overline{\text{POFF2}}$ pin to low (V_i) to turn off all circuits.
- ◇ Two-time boosting
 - To boost up a voltage two times, remove capacitor C1 and diode D1 of Figure 2.14, and connect the anode of diode D2 to the VDD pin.

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◇ Output voltages

- When diodes are used for voltage boosting, the characteristics of diodes directly affect on the voltage boosting characteristics. The forward voltage drop (V_F) of diodes can reduce the booster output voltage. As the example of Figure 2.14 uses three diodes, the drop of “ V_F ” voltage multiplied by three occurs. The booster output voltage is expressed by equation (5).

To increase the $|V_O|$ value, use the diodes having a smaller V_F .

$$|V_O| = 3 \times |V_I| - (3 \times V_F)$$

•••• Equation (6)

◇ Notes

① Input and output current conditions

To satisfy the input and output current ratings, take care to limit the input current below the ratings.

② Input and output voltage conditions

During forward voltage conversion, the input voltage ratings are the same as two-time negative voltage boosting (see Table 2.3).

◇ Application in other setup conditions

When used in the High Output mode, connect the FC pin to the V_I pin.

Wiring Example When Changing the Regulator Temperature Coefficient

The temperature coefficient of the regulator depends on the temperature coefficient of the internal reference

voltage. To set another temperature coefficient, use a thermistor resistor or others as shown in Figure 2.16.

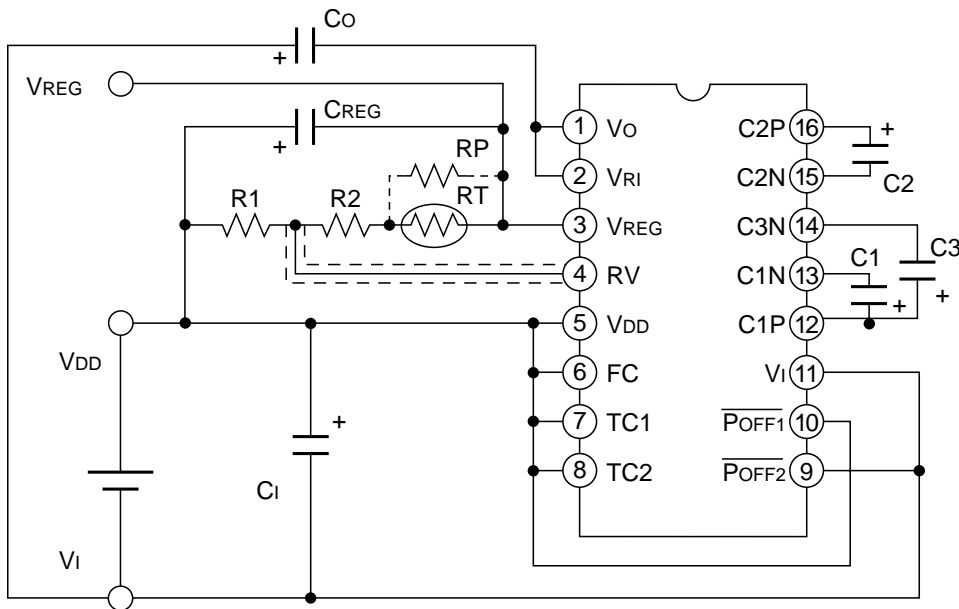


Figure 2.16 Wiring example when changing the regulator temperature coefficient

- ◇ Setup conditions of Figure 2.16
 - Internal clock : ON (Low Output mode)
 - Booster circuit : ON
 - Regulator : ON
 - Thermistor resistor : RT
- ◇ Power-off procedure
 - Set the $\overline{\text{POFF1}}$ pin to low (V_I) to turn off all circuits.
- ◇ Regulator temperature coefficient
 - For the regulator setup and notes, see the “voltage regulator circuit” section of the function.
 - The thermistor resistor (RT) has the non-linear temperature characteristics. To correct them to the linear characteristics, insert the RP as shown Figure 2.16.
- ◇ Application in other setup conditions
 - When used in the High Output mode, connect the FC pin to the V_I pin.

S1F76640 Series**S1F76640 Series CMOS DC/DC Converter & Voltage Regulator****DESCRIPTION**

S1F76640 is a high efficiency and low power consumption CMOS DC/DC converter. It is roughly divided into two portions, step-up circuit and stabilization circuit. The step-up circuit can provide 2 times step-up outputs (3.6 to 11V), 3 times step-up outputs (5.4 to 16.5V) or 4 times step-up outputs (7.2 to 22V) of input voltages (1.8 to 5.5V). If external parts (diode, capacitor) are attached to it, it can realize step-up operations of higher magnifications.

The stabilization circuit enables to set outputs to any voltages. Since the stabilization circuit can provide three kinds of minus temperature gradients to stabilized outputs, it is optimum as a power supply for liquid crystal display (LCD).

Also, S1F76640 enable to drive ICs (liquid crystal driver, analog IC, etc.), which requires another power supply in addition to logic main power supply, with a single power supply. Also, its small power consumption makes it suitable as a micro power supply for handy devices like hand-held computer.

FEATURES

- High efficiency and low power consumption CMOS DC/DC converter
- Easy three kinds voltage conversions to positive potential side from input voltage VDD (+3.3V)
 - From input voltage VDD (+3.3V) to outputs 2×VDD (+6.6V), 3×VDD (+9.9V) and 4×VDD (+13.2V).
- Attachment of external parts (diode, capacitor) makes step-up operations of higher magnifications possible.
- Built-in output voltage stabilization circuit
 - External resistor enables to set any output voltages.
- Output current : Max. 20mA (VDD=+5V)
- Power conversion efficiency : Typ. 95%
- 3 kinds of reference voltages with negative temperature gradient characteristic suitable for LCD drive power supply can be selected.
- Power off operation by external signal
 - Static current at power off time : Max. 2μA
- Possibility of high magnification step-up operation by series connection
- Low voltage operation Optimum for battery drive
- Built-in CR oscillator
- SSOP2-16pin S1F76640M0A0
Bare Chip S1F76640D0A0
- Radiation-resistant design has not been provided for this specification.

BLOCK DIAGRAM

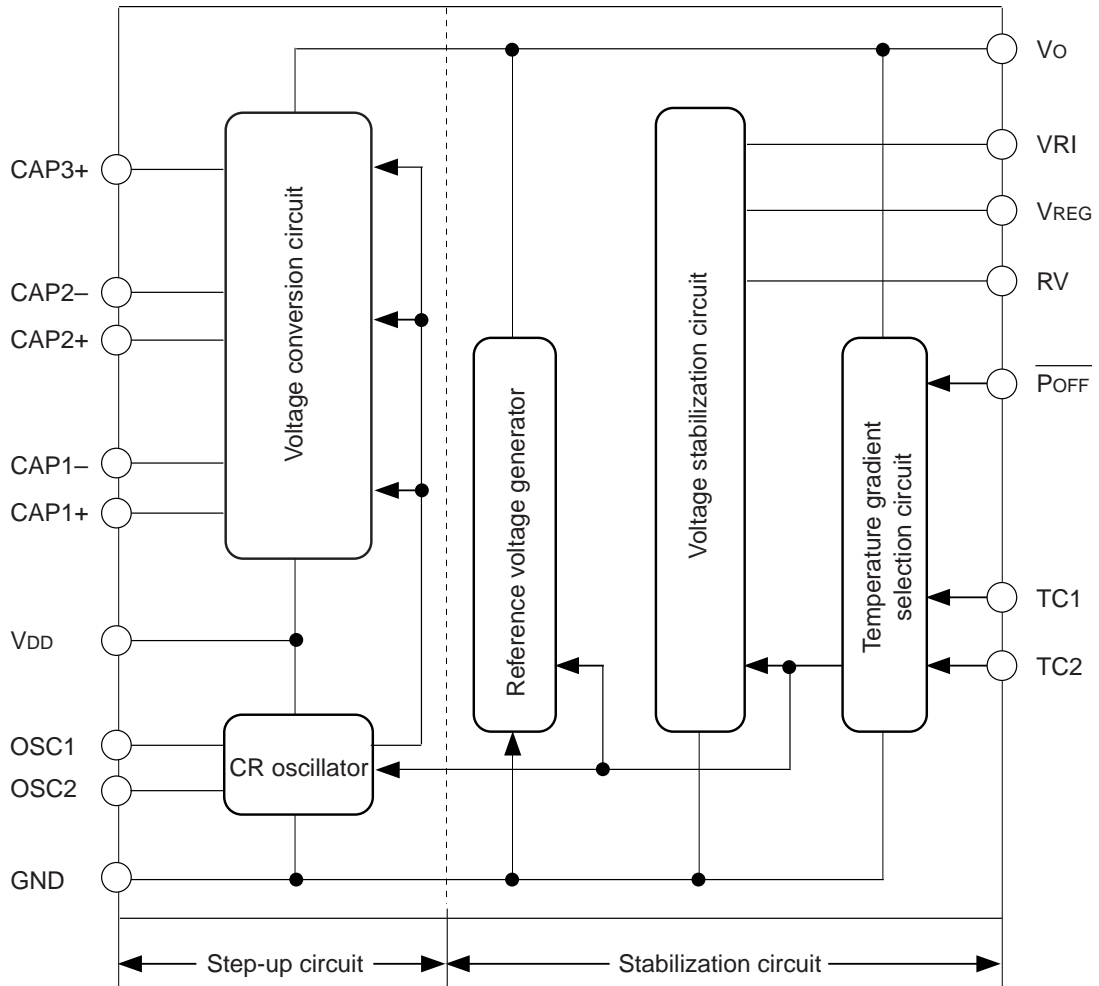


Figure 3-1 Block Diagram

S1F76640 Series

S1F76640 Series

PIN ASSIGNMENTS

SSOP2-16pin

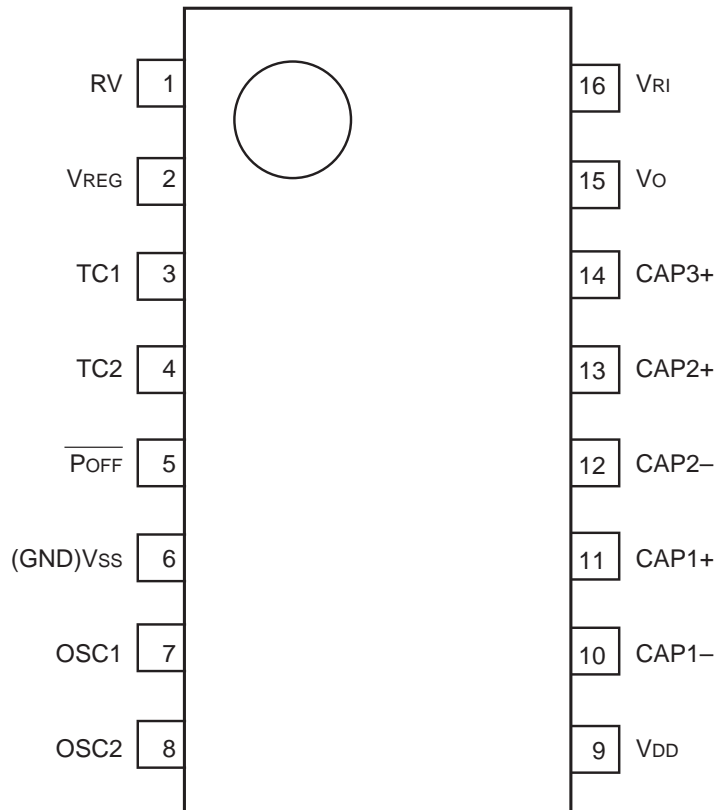


Figure 4-2 Pin Assignments of SSOP2-16pin

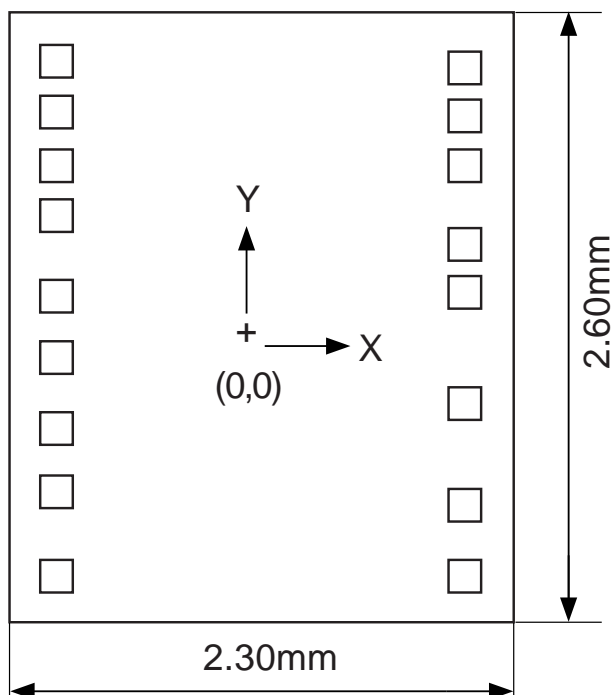
PIN DESCRIPTIONS

Pin No.	Pin name	Description
1	RV	Stabilization voltage regulation pin. When the intermediate tap of the external volume (3-pin resistor) connected between the VDD pin and the VREG pin is connected to the RV pin, VREG output voltage can be adjusted.
2	VREG	Stabilized voltage output pin
3	TC1	Temperature gradient selection pin
4	TC2	Temperature gradient selection pin
5	$\overline{\text{POFF}}$	VREG output ON/OFF control pin. When control signal from the system side is input to this pin, the power off (VREG output power off) control of S1F76640 becomes available.
6	GND	Power supply pin (minus side, system GND)
7	OSC1	Oscillation resistor connection pin. This pin becomes the clock input pin when an external clock operates.
8	OSC2	Oscillation resistor connection pin. This pin is released when an external clock operates.
9	VDD	Power supply pin (plus side, system VCC)
10	CAP1-	Pump up capacitor minus side connection pin for 2 times step-up. Next stage clock at series connection time.
11	CAP1+	Pump up capacitor plus side connection pin for 2 times step-up
12	CAP2-	Pump up capacitor minus side connection pin for 3 times step-up. Output pin at 2 time step-up time (to be short-circuited to Vo).
13	CAP2+	Pump up capacitor plus side connection pin for 3 times step-up
14	CAP3+	Pump up capacitor plus side connection pin for 4 times step-up. Output pin at 3 times step-up time (to be short-circuited to Vo).
15	Vo	Output pin at 3 times step-up time
16	VRI	Stabilization circuit input pin

S1F76640 Series

CHIP EXTERNAL SHAPE AND PAD CENTER COORDINATES

Chip External Shape



Pad Center Coordinates

S1F7664D0A0

Pad		Pad Center Coordinates	
No.	Name	X[μ m]	Y[μ m]
1	RV	-984.0	1096.0
2	VREG		788.0
3	(TESTOUT)		580.0
4	TC1		390.0
5	TC2		96.0
6	$\overline{\text{POFF}}$		-218.0
7	GND		-510.0
8	OSC1		-802.0
9	OSC2	984.0	-1094.0
10	VDD		-1134.0
11	CAP1-		-892.0
12	CAP1+		-514.0
13	CAP2-		182.0
14	CAP2+		372.0
15	CAP3+		750.0
16	VO		942.0
17	VRI		1134.0

Figure 4-4 Pad Assignments

Chip size : (x) (y) (t)
 2.30mm \times 2.60mm \times 0.30mm
 PAD aperture : 100 μ m \times 100 μ m
 DIE number : F76640D0A0

FUNCTIONAL DESCRIPTIONS

CR Oscillator

S1F76640 has a built-in CR oscillator as the internal oscillator, and an external oscillation resistor ROSC is connected between the pins OSC1 and OSC2 before operation. (Figure 5.1)

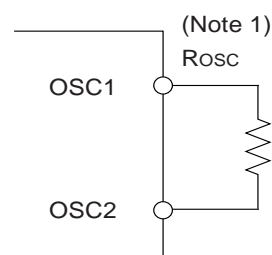


Figure 5-1 CR Oscillator

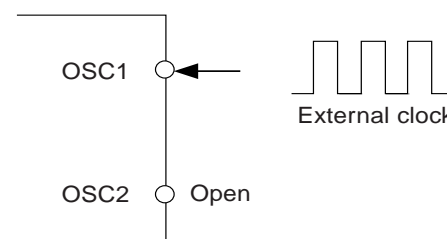


Figure 5-2 External Clock Operation

Note 1 : Since the oscillation frequency varies with wiring capacitance, make the cables between the terminals OSC1 and OSC2 and ROSC as short as possible.

When setting the external resistor ROSC, find the oscillation frequency fOSC that brings about the maximum efficiency from Figures 6.5.12 and 6.5.13 and find ROSC suitable for the fOSC from Figure 6.5.1. The relations between ROSC and fOSC in Figure 6.5.1 are expressed approximately with the following formula as far as the straight portion (500kΩ < ROSC < 2MΩ) is concerned:

$$R_{OSC} = A \cdot \frac{1}{f_{OSC}} \left[\begin{array}{l} A : \text{Constant, When GND is 0V and} \\ V_{DD} \text{ is 5V, A is } 2.0 \times 10^{10} \text{ (1/F).} \end{array} \right]$$

So, the ROSC value can be obtained from this formula.

(Recommended oscillation frequency : 10kHz to 30kHz (ROSC : 2MΩ to 680kΩ))

When the external clock operates, make the pin OSC2 open as shown in Figure 5.2 and input the 50% duty of the external clock from the pin OSC1.

Voltage Conversion Circuits (I) and (II)

The voltage conversion circuits (I) and (II) doubles and triples the input voltage VDD respectively by using clock generated in the CR oscillator.

In case of 2 times step-up, 2 times step-up output of the input voltage is obtained from the VO pin when a pump up capacitor is connected between CAP1+ and CAP1-, CAP2+ and CAP3+ are short-circuited to VO and a smoothing capacitor is connected between VDD and VO outside.

In case of 3 times step-up, 3 VDD is output from the VO pin when a pump up capacitor is connected between CAP1+ and CAP1- and between CAP2+ and CAP2- respectively and a smoothing capacitor is connected between the VDD and VO pins outside.

In case of 4 times step-up, 4 VDD is output from the VO pin when a pump up capacitor is connected between CAP1+ and CAP1-, between CAP2+ and CAP2- and between CAP1+ and CAP3- respectively and a smoothing capacitor is connected between the VDD and VO pins outside.

When GND is 0 and VDD is 5, the relations between the input voltage and the output voltage are as shown in Figures 5-3, 5-4 and 5-5.

S1F76640 Series

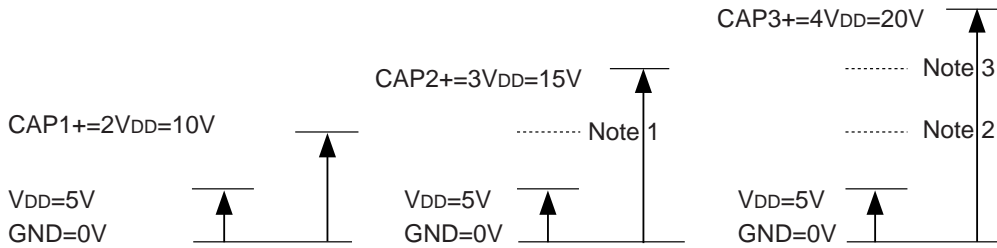


Figure 5-3 Example of 2 times step-up potential relations **Figure 5-4 Example of 3 times step-up potential relations** **Figure 5-5 Example of 4 times step-up potential relations**

- Note 1 : At the 3 times step-up time, 2 times step-up output (–10V) cannot be taken out from the CAP2– pin.
- Note 2 : At the 4 times step-up time, 2 times step-up output (–10V) cannot be taken out from the CAP2– pin.
- Note 3 : At the 4 times step-up time, 3 times step-up output (–15V) cannot be taken out from the CAP3– pin.

Reference Voltage Generator, Voltage Stabilization Circuit

The reference voltage generator generates reference voltage necessary for operation of the voltage stabilization circuit and adds temperature gradient to reference voltage. Three temperature gradients are available, and signal from the temperature gradient selection circuit select one of them.

The voltage stabilization circuit stabilizes the step-up output voltage V_O and outputs optional voltages. When an external resistor R_{RV} is connected as shown in Figure 5-5 and the potential of the intermediate tap is changed, V_{REG} output voltage can be set to optional voltages between the reference voltage V_{RV} and V_O .

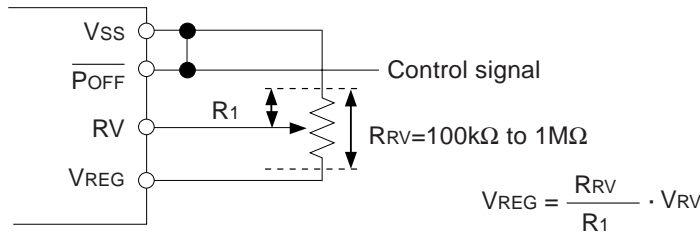


Figure 5-6 Voltage Stabilization Circuit

The voltage stabilization circuit has power off function and can control ON/OFF of V_{REG} output according to signals from the system side (microprocessor, etc.) When \overline{POFF} is high (V_{DD}), V_{REG} output is turned on, and when \overline{POFF} is Low (GND), it is turned off. When the control is not necessary, \overline{POFF} is fixed to High (V_{DD}).

Temperature Gradient Selection Circuit

S1F76640 can provide three kinds of temperature gradients suitable for driving LCD to VREG output as shown Table 5-1.

Table 5-1 Temperature Gradient Adaptation Table

$\overline{\text{POFF}}$ (Note 1)	TC2 (Note 1)	TC1 (Note 1)	Temperature Gradient C_T (Note 2)	VREG Output	CR Oscillator	Remarks
1(VDD)	Low(VSS)	Low(VSS)	-0.40%/°C	ON	ON	—
1(VDD)	Low(VSS)	High(Vo)	-0.25%/°C	ON	ON	—
1(VDD)	High(Vo)	Low(VSS)	-0.55%/°C	ON	ON	—
1(VDD)	High(Vo)	High(Vo)	-0.55%/°C	ON	OFF	Series connection (Note 4)
0(VSS)	Low(VSS)	Low(VSS)	—	OFF(Hi-Z)(Note 3)	OFF	—
0(VSS)	Low(VSS)	High(Vo)	—	OFF(Hi-Z)(Note 3)	OFF	—
0(VSS)	High(Vo)	Low(VSS)	—	OFF(Hi-Z)(Note 3)	OFF	—
0(VSS)	High(Vo)	High(Vo)	—	OFF(Hi-Z)	ON	Boosting only (Note 5)

Note 1 : Please note that potentials on the High side are different between the $\overline{\text{POFF}}$ pin and TC2/TC1 pin.

Note 2 : The formula below is used to define temperature gradient C_T :

$$C_T = \frac{V_{\text{REG}}(50^\circ\text{C}) - V_{\text{REG}}(0^\circ\text{C})}{50^\circ\text{C} - 0^\circ\text{C}} \times \frac{1}{V_{\text{REG}}(25^\circ\text{C})} \times 100 (\%/^\circ\text{C})$$

Example : When $C_T = -0.6\%/^\circ\text{C}$ is selected,

· When T_a is 25°C , the VREG output becomes -8V at 25°C .

$$\Delta V_{\text{REG}}/\Delta T = C_T \cdot |V_{\text{REG}}(25^\circ\text{C})| = -0.6 \times 10^{-2} \times 8 = -48\text{mV}/^\circ\text{C}$$

When the temperature rises 1°C , the $|V_{\text{REG}}|$ value reduces by 48mV .

· When VREG is -10V at 25°C , the formula below is formed:

$$\Delta |V_{\text{REG}}|/\Delta T = -60\text{mV}/^\circ\text{C}$$

Note 3 : At power off time (VREG output : OFF, CR oscillator : OFF), the potential of the Vo output is about $V_{\text{DD}} + 0.5\text{V}$.

Note 4 : When this mode is selected at a series connection, the first stage clock can drive the next stage IC and this mode is effective for reducing the power consumption of the next stage IC. (See Figure 8.4)

Note 5 : Select this mode for boosting only. And the current consumption can be reduced.

S1F76640 Series

ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings

Parameter	Symbol	Rating		Unit	Remarks
		Min.	Max.		
Input supply voltage	V _{DD}	GND-0.3	24/N	V	V _{DD} N = 2 : 2 times step-up N = 3 : 3 times step-up N = 4 : 4 times step-up
Input pin voltage	V _I	GND-0.3	V _{DD} -0.3	V	OSC1, $\overline{\text{POFF}}$
		GND-0.3	V _O -0.3	V	TC1, TC2, RV
Output voltage	V _O	GND-0.3	22	V	V _O Note 3
		GND-0.3	V _O	V	V _{REG} Note 3
Output pin voltage 1	V _{OC1}	GND-0.3	V _{DD} -0.3	V	CAP1+, CAP2+ OSC2
Output pin voltage 2	V _{OC2}	GND-0.3	2 × V _{DD} -0.3	V	CAP1-
Output pin voltage 3	V _{OC3}	GND-0.3	3 × V _{DD} -0.3	V	CAP2-
Output pin voltage 4	V _{OC4}	GND-0.3	4 × V _{DD} -0.3	V	CAP3-
Allowable loss	P _D	—	210	mW	SSOP-16PIN
Operating temperature	T _{opr}	-40	85	°C	—
Storage temperature	T _{stg}	-55	150	°C	—
Soldering temperature and time	T _{sol}	—	260 · 10	°C · s	At leads

Note 1 : Under the conditions exceeding the above absolute maximum ratings, the IC may result in a permanent destruction. An operation for a long period under the conditions of the above absolute maximum ratings may deteriorate the reliability remarkably.

Note 2 : All voltage values are based on GND.

Note 3 : The output pins (V_O and V_{REG}) are for stabilizing and outputting boosted voltages. So, they are not used to apply voltage from outside. When voltage is applied from outside for unavoidable reasons, limit the voltage to the rated voltage mentioned above or less.

Recommended Operating Conditions

Parameter	Symbol	Rating		Unit	Remarks
		Min.	Max.		
Step-up start voltage	VSTA1	1.8	—	V	ROSC=1M Ω , C4 \geq 10 μ F CL/C4 \leq 1/20 Note 2
	VSTA2	2.2	—	V	ROSC=1M Ω
Step-up stop voltage	VSTP	—	1.8	V	ROSC=1M Ω
Output load resistance	RL	RLmin Note 3)	—	Ω	—
Output load current	Io	—	20	mA	—
Oscillation frequency	fOSC	10	30	kHz	—
External resistor for oscillation	ROSC	680	2000	k Ω	—
Step-up capacitor	C1,C2,C3,C4	3.3	—	μ F	—
Stabilization output regulation resistance	RRV	100	1000	k Ω	—

Note 1 : All voltages are based on the GND being 0V.

Note 2 : The figure below shows the recommended circuit for operation with low voltages (VDD=1.8 to 2.2V):

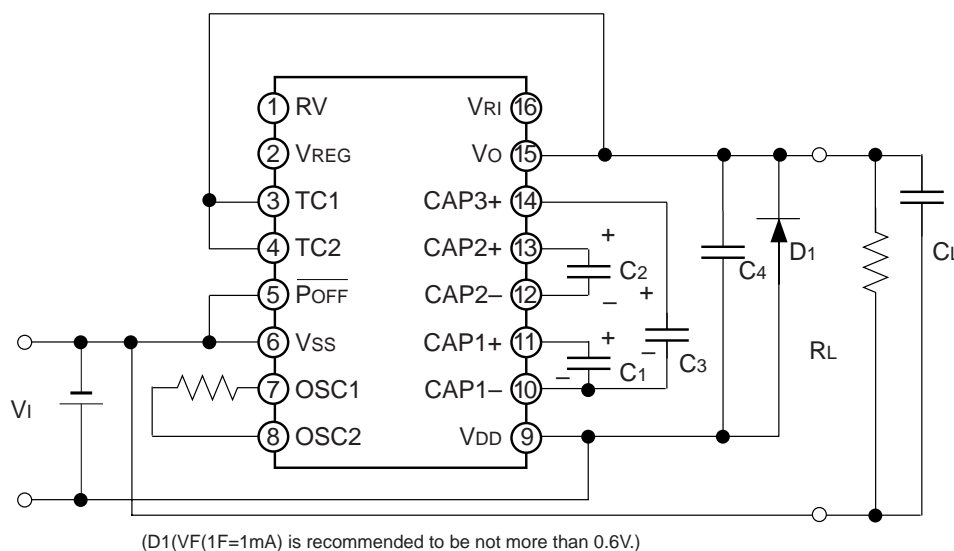


Figure 6-2-1 Recommended Circuit Diagram for Low Voltage Operation (Example of 4 times step-up circuit)

Note 3 : RLmin varies with input voltage. See Characteristics Graph (15).

S1F76640 Series

Electrical Characteristics

Unless otherwise specified, Ta=−40°C to +85°C
GND=0V, VDD=5V

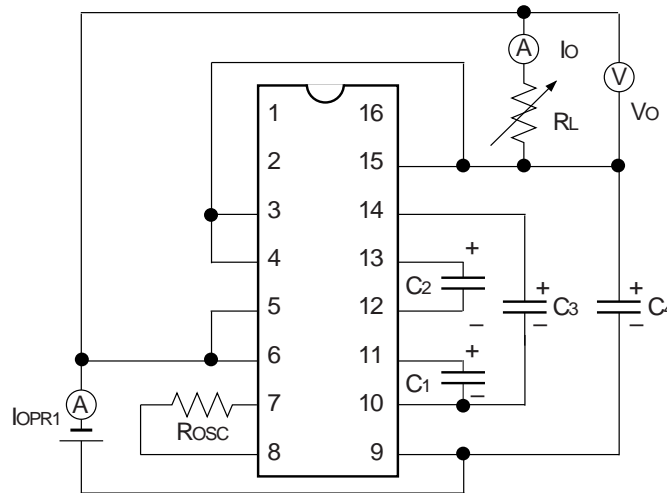
Parameter	Symbol	Specification Value			Unit	Conditions	Measurement Circuit
		Min.	Typ.	Max.			
Input supply voltage	VDD	1.8	—	5.5	V	—	—
Output voltage	VO	—	—	22	V	—	—
	VREG	VRV	—	22	V	R=∞, RRV=1MΩ, VO=22V	②
Stabilization circuit operating voltage	VO	VRV+2.1	—	22	V	—	—
Step-up circuit current consumption (VDD system)	IOPR1	—	60	100	μA	RL=∞, ROSC=1MΩ	①
Step-up circuit current consumption (VRI system)	IOPR2	—	12	25	μA	RL=∞, ROSC=1MΩ, VO=20V	②
Static current	IQ	—	—	2	μA	TC2=TC1=VO, RI=∞	①
Oscillation frequency	fOSC	16	20	24	kHz	ROSC=1MΩ	①
Output impedance	RO	—	250	350	Ω	IO=10mA	①
Step-up power conversion efficiency (Note 2)	Peff	90	95	—	%	IO=5mA	①
Stabilized output voltage fluctuation	$\frac{\Delta V_{REG}}{\Delta V_O \cdot V_{REG}}$	—	0.2	—	%/V	10V < VO < 20V, VREG=10V RL=∞, Ta=25°C	②
Stabilized output load fluctuation (Note 3)	$\frac{\Delta V_{REG}}{\Delta I_O}$	—	5.0	—	Ω	VO=20V, VREG=15V Ta=25°C, 0 < IO < 10mA TC1=VO, TC2=GND	②
Stabilized output saturation resistance (Note 4)	RSAT	—	12	—	Ω	RSAT=Δ(VO-VREG)/ΔIO 0 < IO < 10mA, RV=VO Ta=25°C	②
Reference voltage	VRV0	2.20	3.00	3.80	V	TC2=GND, TC1=VO, Ta=25°C	②
	VRV1	2.30	2.80	3.30	V	TC2=TC1=GND, Ta=25°C	
	VRV2	1.70	2.00	2.30	V	TC2=VO, TC1=GND, Ta=25°C	
Temperature gradient	CT0	−0.45	−0.27	−0.10	%/°C	VDD=5V, VO=20V	②
	CT1	−0.60	−0.42	−0.25	%/°C	(Note 5)	
	CT2	−0.70	−0.55	−0.40	%/°C		
Input leak current	ILKI	—	—	2	μA	POFF, TC1, TC2, OSC1, RV pins	③

- Note 1 : All voltage values are based on GND being 0V.
- Note 2 : The value shown here is the step-up circuit conversion efficiency, and $(V_O - V_{REG})I_{OUT}$ is lost when the stabilization circuit operates. So, it is recommended to operate this so that $(V_O - V_{REG})$ becomes as small as possible. When $(V_O - V_{REG}) \times I_O$ is large, the IC temperature rises and the characteristics of the stabilization circuit change.
- Note 3 : See Figures 6-5-14, 6-5-15 and 6-5-16.
- Note 4 : RSAT means inclination in Fig. 6-5-17, and $V_O - \Delta$ ($V_O - V_{REG}$) indicates the lower limit voltage of the VREG output.
- Note 5 : The calculation formula of C_T is as follows:

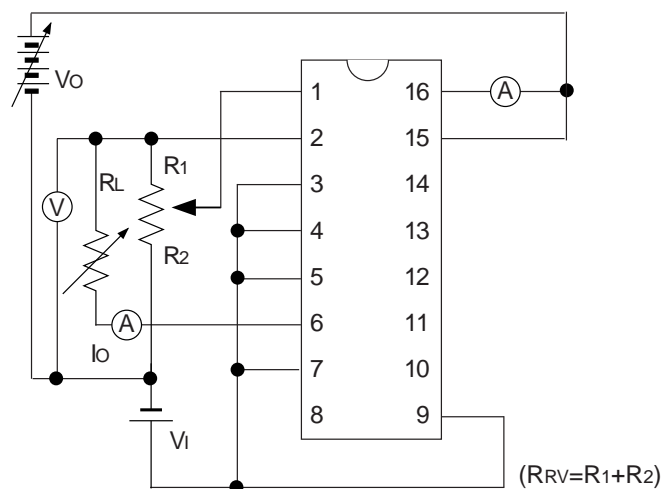
$$C_T = \frac{V_{REG}(50^\circ\text{C}) - V_{REG}(0^\circ\text{C})}{50^\circ\text{C} - 0^\circ\text{C}} \times \frac{1}{V_{REG}(25^\circ\text{C})} \times 100(\%/^\circ\text{C})$$

Measurement Circuit (Described on S1F76640M0A0)

Step-up circuit characteristic measurement circuit

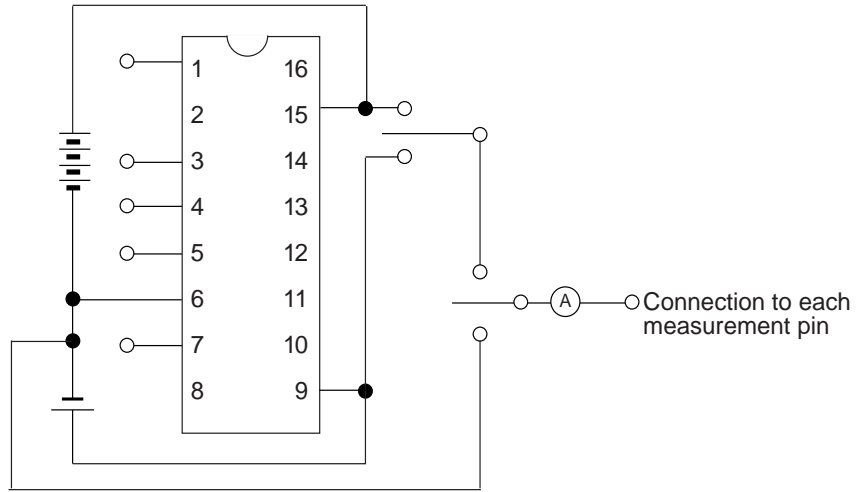


Stabilization circuit characteristic measurement circuit

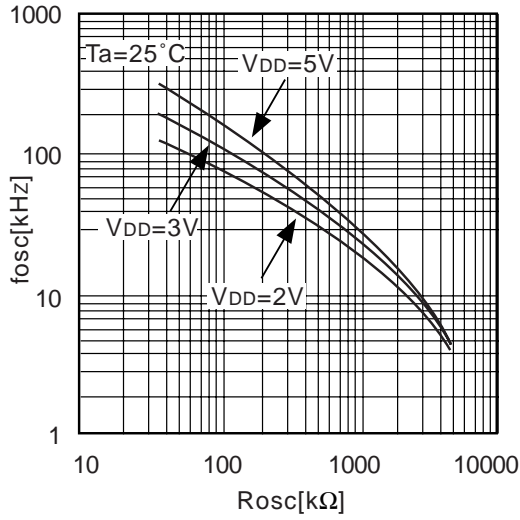


S1F76640 Series

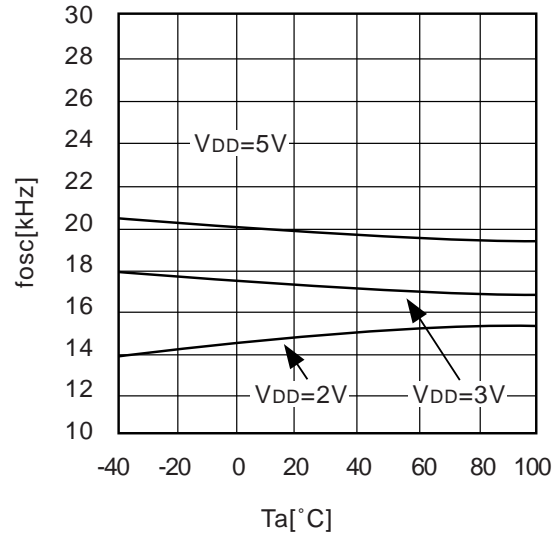
Input leak current measurement circuit



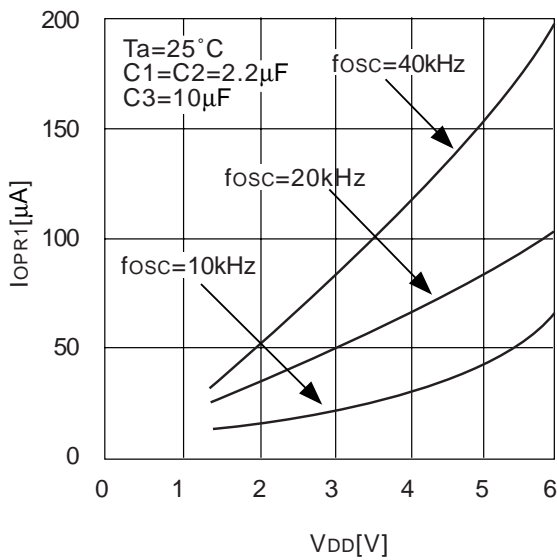
CHARACTERISTICS GRAPH



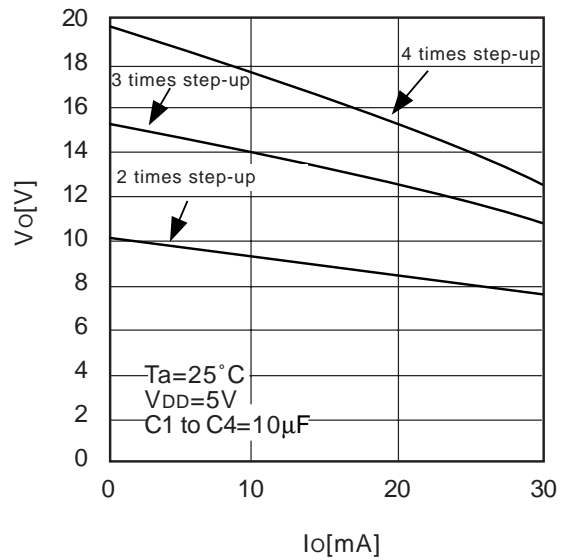
(1) Oscillation frequency vs. External resistance for oscillation



(2) Oscillation frequency vs. Temperature



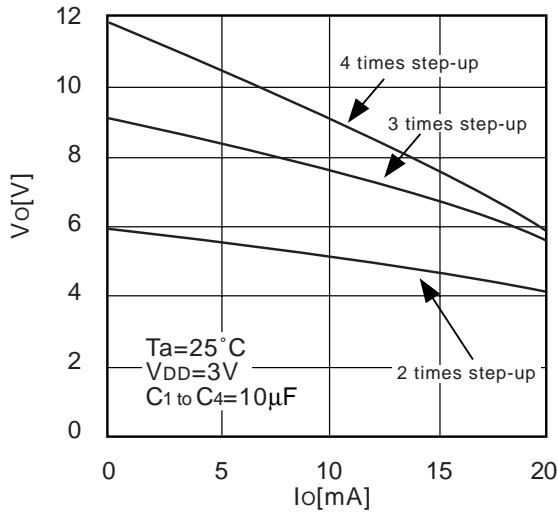
(3) Step-up circuit current consumption vs. Input voltage



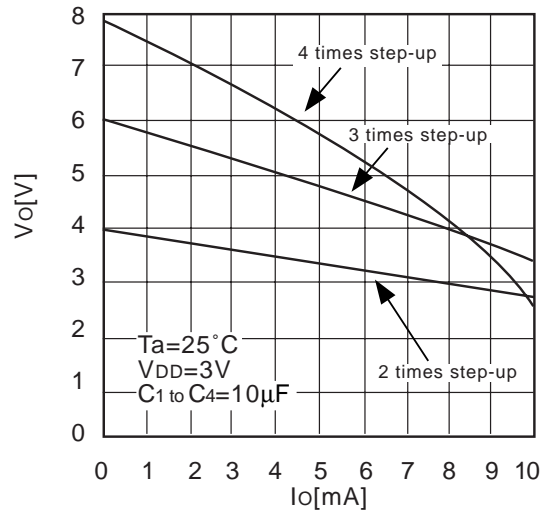
(4) Output voltage (Vo) vs. Output current 1

S1F76640 Series

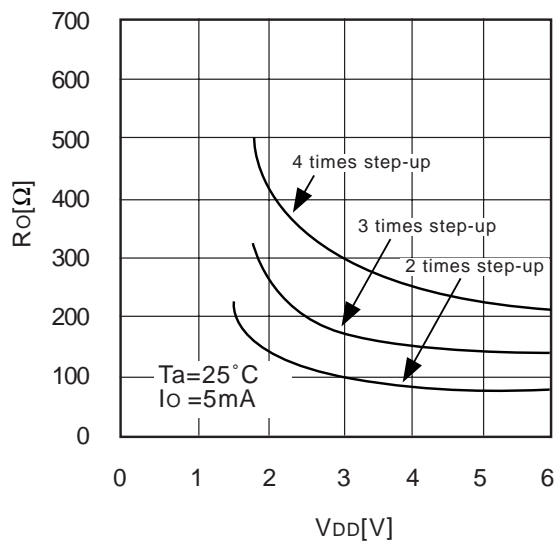
S1F76640 Series



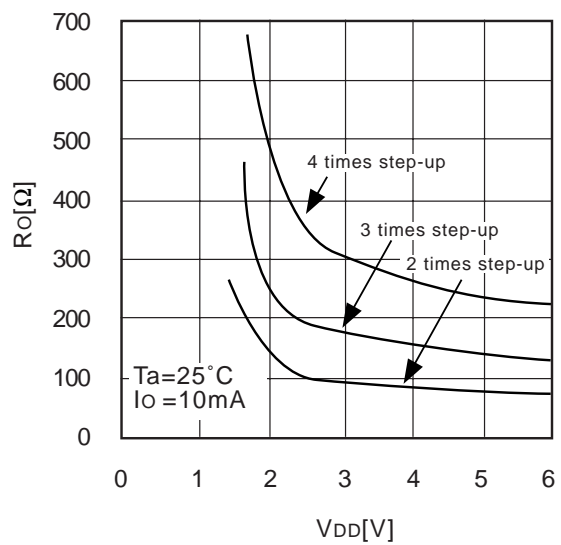
(5) Output voltage (V_o) vs. Output current 2



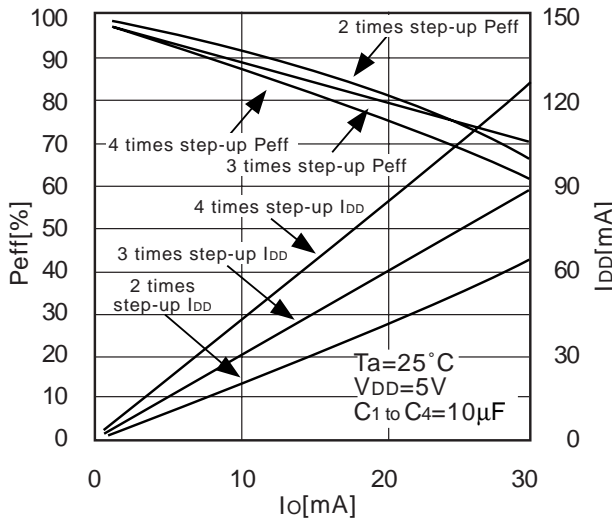
(6) Output voltage (V_o) vs. Output current 3



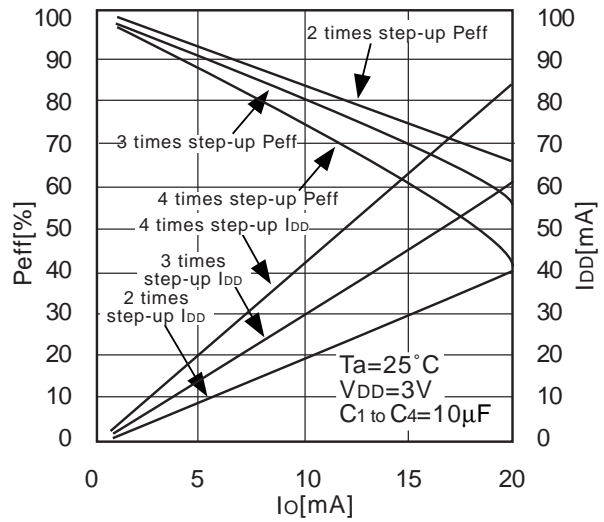
(7) Output impedance vs. Input voltage 1



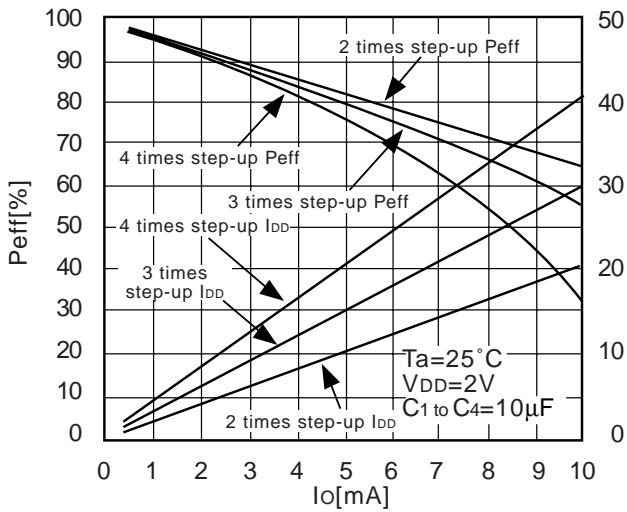
(8) Output impedance vs. Input voltage 2



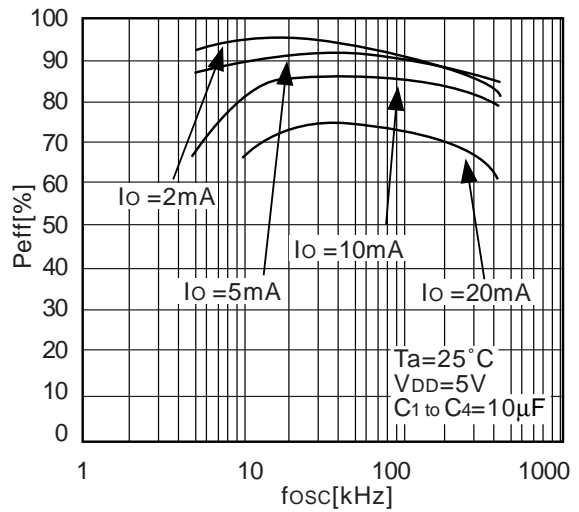
(9) Step-up power conversion efficiency vs. Output current 1
Input current vs. Output current 1



(10) Step-up power conversion efficiency vs. Output current 2
Input current vs. Output current 2

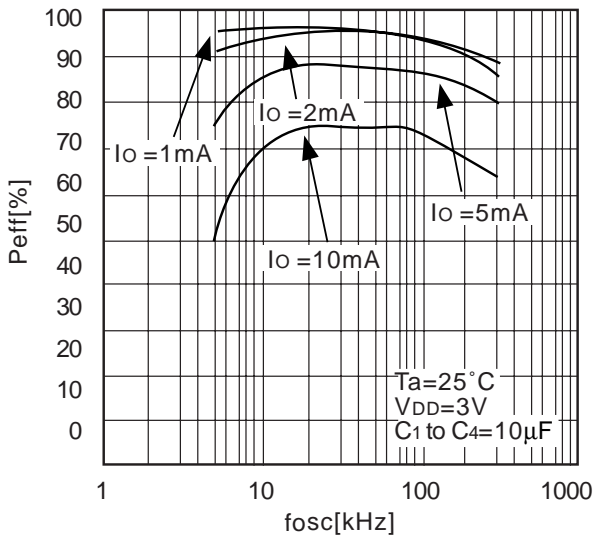


(11) Step-up power conversion efficiency vs. Output current 3
Input current vs. Output current 3

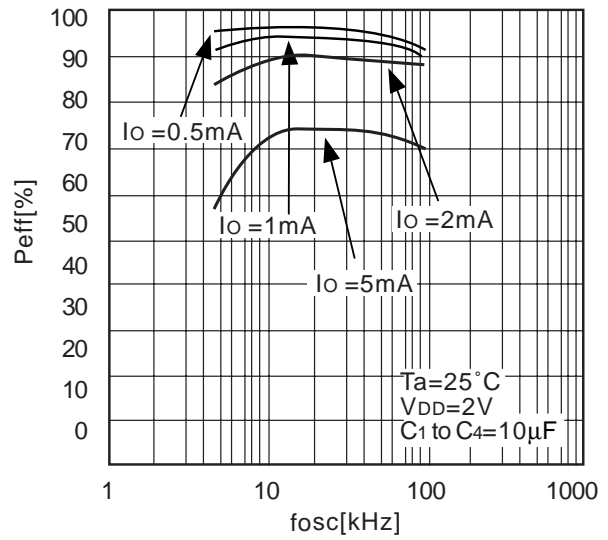


(12) Step-up power conversion efficiency - Os vs.illation frequency 1

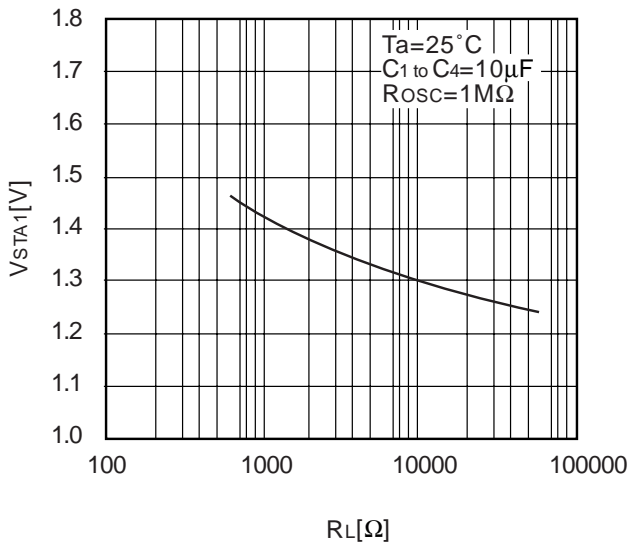
S1F76640 Series



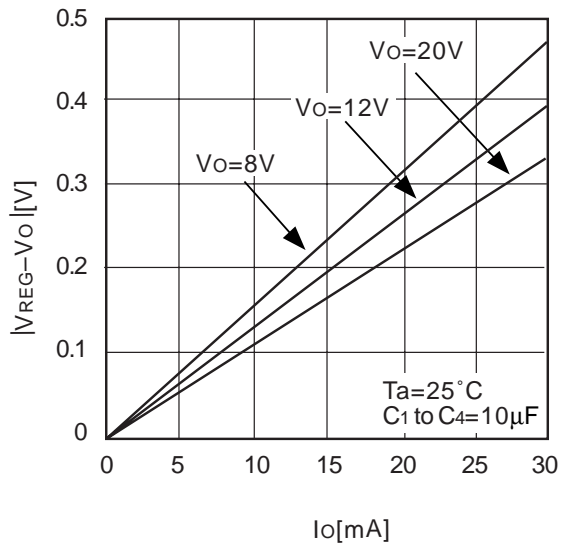
(13) Step-up power conversion efficiency vs. Oscillation frequency 2



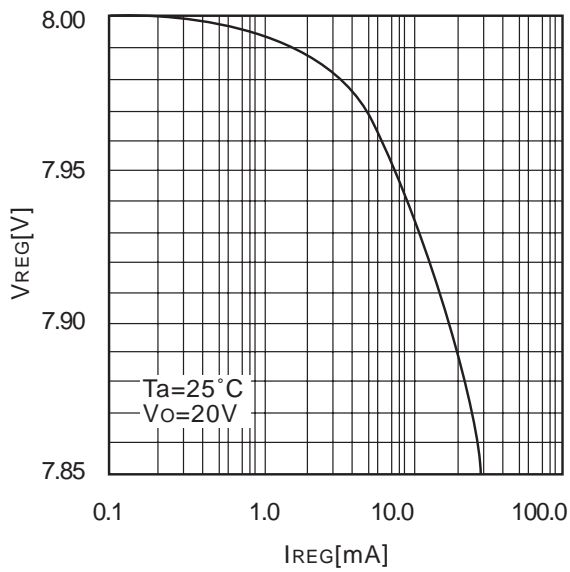
(14) Step-up power conversion efficiency vs. Oscillation frequency 3



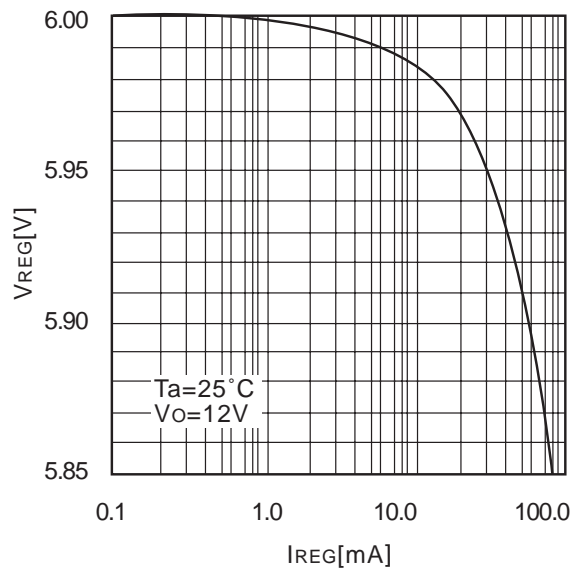
(15) Step-up start voltage (1) vs. Load resistance



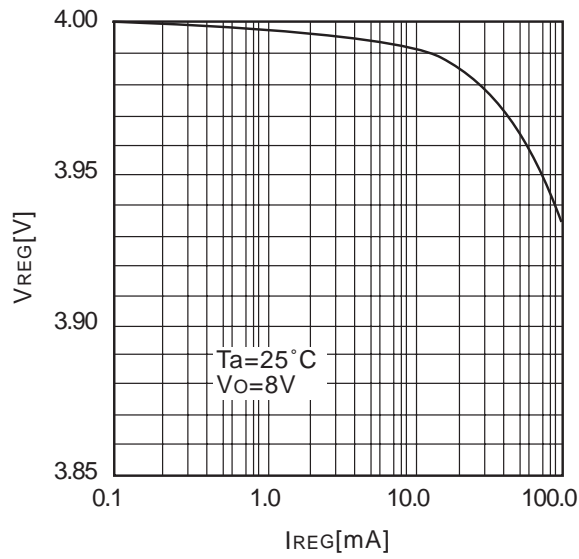
(16) Stabilization output saturation resistance vs. Load current



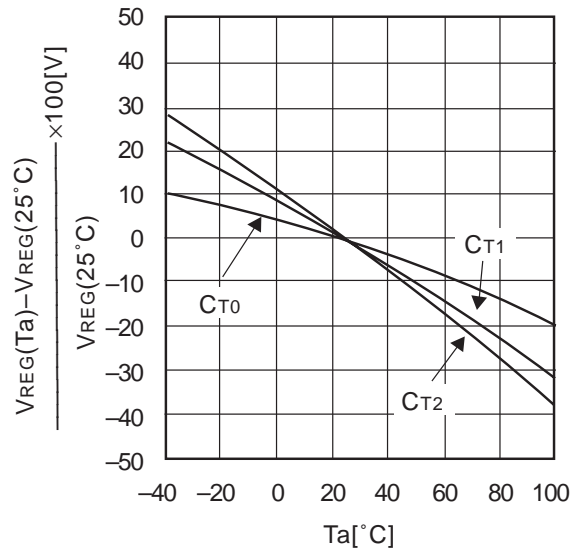
(17) Output voltage (V_{REG}) vs. Output current 1



(18) Output voltage (V_{REG}) vs. Output current 2



(19) Output voltage (V_{REG}) vs. Output current 3



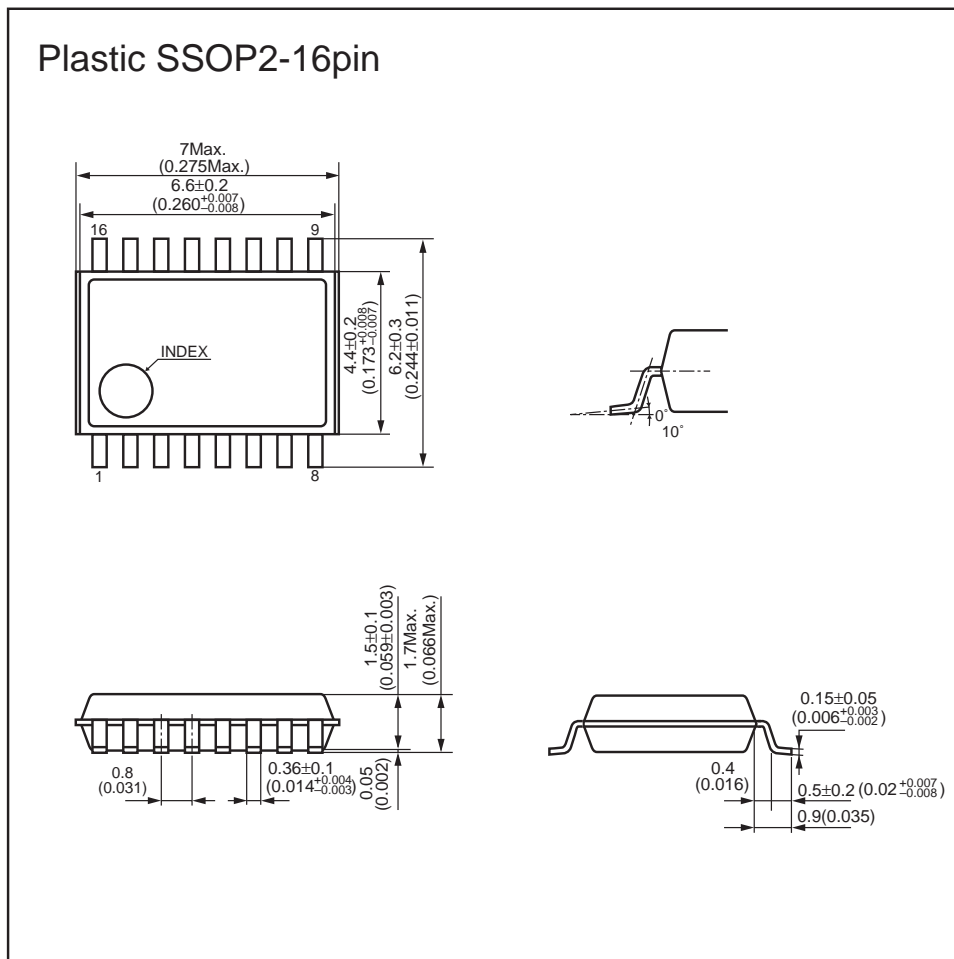
(20) Reference voltage vs. Temperature

S1F76640 Series

MECHANICAL DATA

Reference

Unit : mm



Note : This dimensional drawing is subject to change without notice for improvement.

APPLICATION EXAMPLE

2 Times Step-up, 3 Times Step-up and 4 Times Step-up

Figure 8.1 shows the connection for getting 4 times step-up output of an input voltage by operating the step-up circuit only. In case of 3 times step-up, the capacitor C3 is removed and CAP3+ (Pin No. 14) is short-circuited to V_O (Pin No. 15), and 3 times step-up voltage is obtained from V_O(CAP3+). In case of 2 times step-up, the capacitor C2 is also removed and CAP2+ (Pin No. 13) is short-circuited to V_O (Pin No. 15), and 2 times step-up voltage (10V) is obtained from V_O (CAP2+).

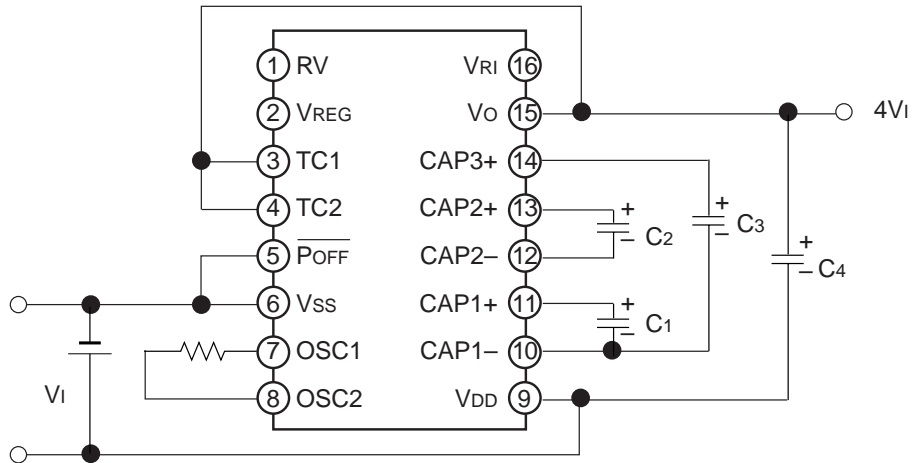


Figure 8-1 4 times step-up circuit

4 Times Step-up + Stabilization Circuit

Figure 8-2 shows an application example for stabilizing step-up outputs obtained in 8-(1) through the stabilization circuit and for providing temperature gradient to V_{REG} output by means of the temperature gradient selection circuit. In this application example, both outputs from V_O and V_{REG} can be indicated at the same time. Also, operation of 3 times step-up + stabilization circuit is possible by using the 3 times step-up operation mentioned in 8-(1), and operation of 2 times step-up + stabilization circuit is possible by using the 2 times step-up operation.

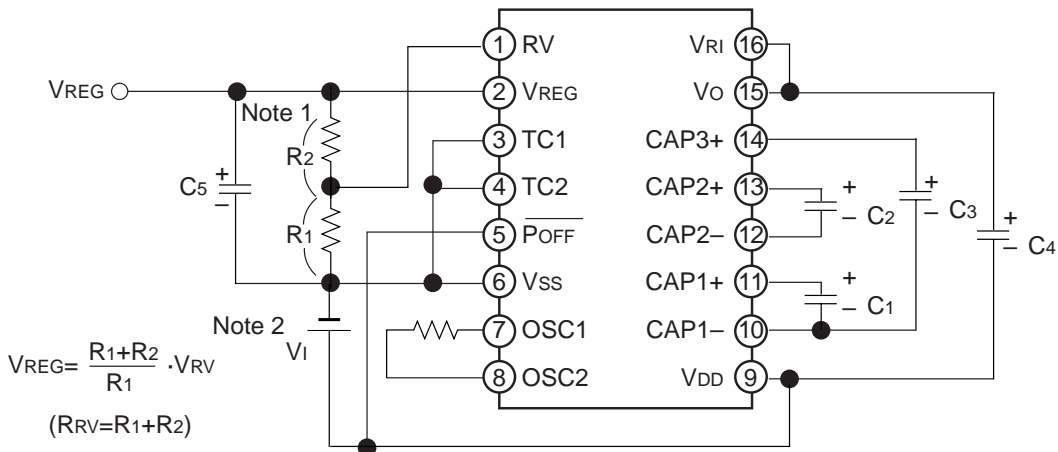


Figure 8-2 Operation of 4 Times Step-up + Stabilization Circuit (Temperature Gradient CT1 is selected.)

Note 1 : Since input impedance at the RV pin (No. 1) is high, it is necessary to use a shielded wire as a measure against noise in case of a long connection. It is also effective to make the R_{RV} value small for reducing noise influence. (In this case, however, more current comes to be consumed at R_{RV}.)

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Parallel Connection

It is possible to make the output impedance R_O small when several pieces of the circuit shown in Figure 8.1 are connected. Parallel connection of n circuits reduces R_O to $1/n$ approximately. One piece of the smoothing capacitor C_4 can be commonly used in the same way. To get stabilized outputs after parallel connection, include 1 pieces of the circuit shown in Figure 8.2 in the parallel connection of n circuits as shown in Figure 8.3.

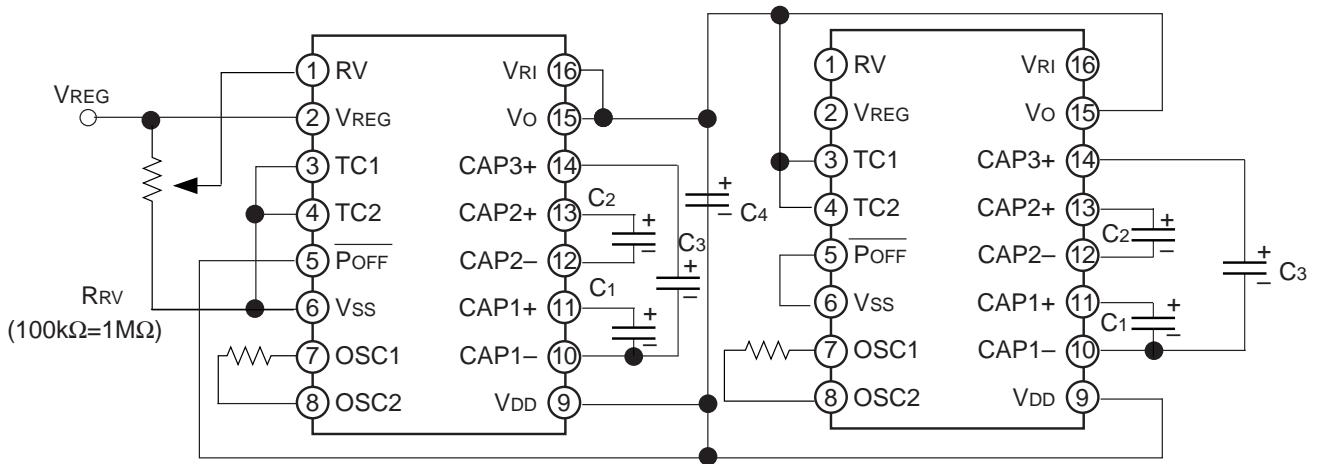


Figure 8.3 Parallel Connection

Series Connection

When S1F76640 is connected in series (V_{DD} and V_O in the previous stage are connected to GND and V_{DD} in the next stage respectively), the output voltage can be increased more. But the series connection makes the output impedance high. Figure 8.4 shows an example of the series connection to get $V_O=25V$ from $V_{DD}=5V$ and to stabilize it.

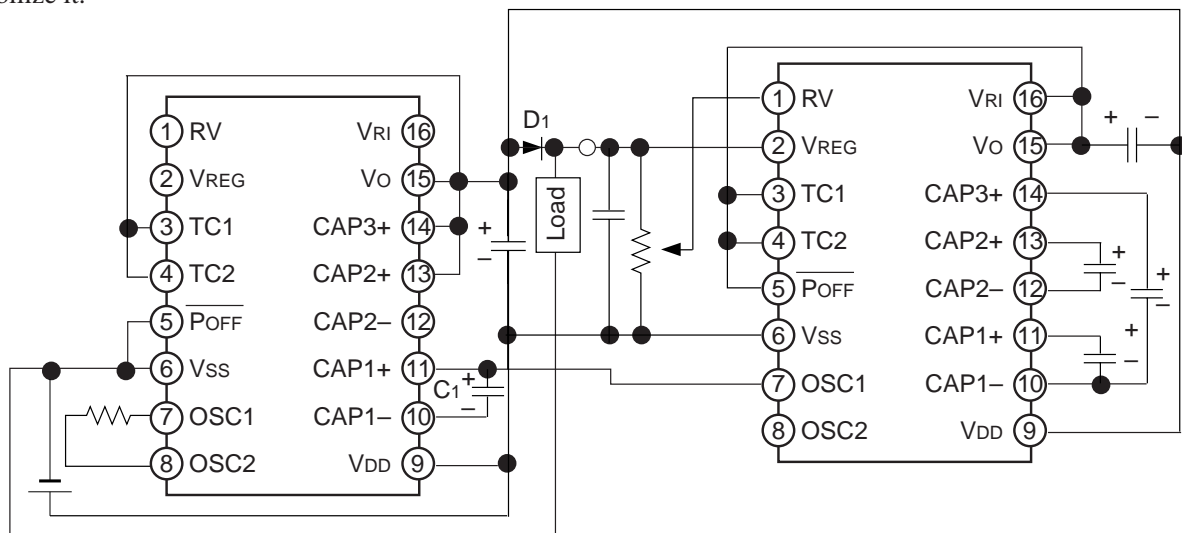


Figure 8.4 Series Connection

Note 1 : Precautions on Load Connection

When a load is connected between GND in the first stage (or potential below GND in the second stage other than that) and VREG in the second stage as shown in Figure 8.4, pay attention to the following. When a normal output is not available at the VREG pin at the starting time or when the \overline{POFF} signal turns off VREG, current may flows from GND in the first stage (or potential below GND in the second stage other than that) to the VREG pin in the second stage through the load and a voltage higher than the absolute maximum rating below GND in the second stage may be generated at the VREG pin. As a result, the IC may not work normally. For series connection, connect the diode D1 between VDD and VREG in the second stage as shown in Figure 8.4, so that no potential below GND in the second stage is added to the VREG pin.

Note 2 : Figure 8.4 shows 3 times step-up in the first stage and 4 times step-up in the next stage, but 4 times step-up is possible both in the first stage and in the next stage unless the input voltage $V_{DD}'-GND'$ exceeds the specification value (6.0V). This means that each IC in this series connection is requested to satisfy the specification values ($V_{DD}-GND \leq 6, 0V, V_o-GND \leq 24V$). (See Figure 8.5.)

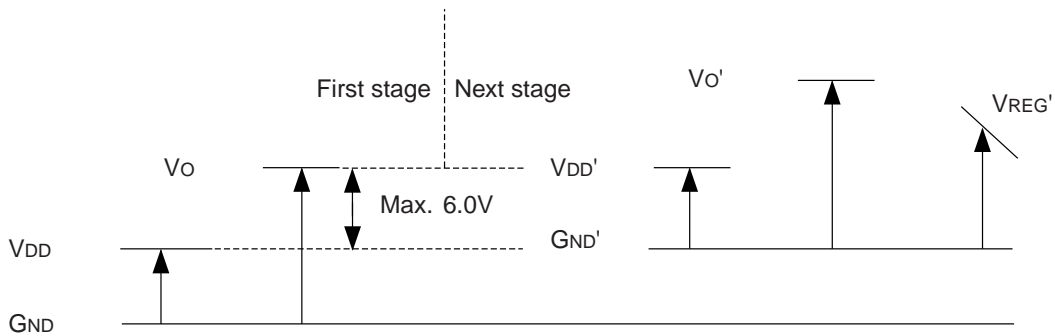


Figure 8.5 Power Supply System in Series Connection

Note 3 : 2 times step-up in the first stage allows using the CAP- output in the first stage as the next stage clock, but 3 times step-up does not. Attach an external ROSC as the next stage clock for internal oscillation. Also, since the next stage external clock can operate according the CAP- output in the previous stage as shown in Table 4.1 only when the temperature gradient C_T is $-0.6\%/^{\circ}C$, use the internal oscillator in the same way when other temperature gradients are necessary.

Note 4 : In case of series connection, the voltage $V_{DD}-V_{REG}$ ($V_{REG}'-V_{DD}'$ in Figure 8.5) of the IC, for which the stabilization circuit operates, has temperature gradient. This means that VREG changes at the following rate as temperature changes:

$$\frac{\Delta |V_{REG}|}{\Delta T} = C_T (V_{REG}' (25^{\circ}C) - GND')$$

S1F76640 Series

Negative Voltage Conversion

S1F76640 can boost input voltage to negative power on the negative potential side by using the circuit shown in Figure 8.6. (In case of 3 times step-up, remove the capacitor C3 and the diode D4 and short-circuit the both ends of D4. In case of 2 times step-up, remove the capacitor C2 and the diode D3 and short-circuit the both ends of D3.) But the output voltage drops by the forward voltage V_F of the diode. When GND is 0V, V_{DD} is 5V and V_F is 0.6V as shown in Figure 8.6 for example, V_O is calculated as follows: $V_O = -15V - 4 \times 0.6V = -12.6V$ (In case of 3 times step-up, V_O is calculated to $-10V - 3 \times 0.6V = -8.2V$, and in case of 2 times step-up, V_O is calculated to $-5V - 2 \times 0.6V = -3.8V$.)

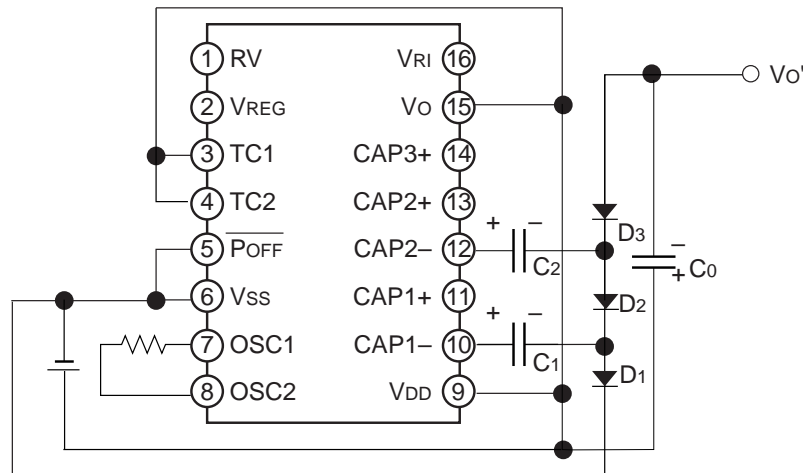


Figure 8.6 Negative Voltage Conversion (Example of 3 times step-up circuit)

Negative Voltage Conversion + Positive Voltage Conversion

When the 3 times step-up operation shown in Figure 8.1 and the positive voltage conversion in Figure 8.6 are combined, the circuit shown in Figure 8.7 can be formed and 20V and $-12.6V$ can be obtained from the input 5V. However, the output impedance is higher than in case of connection of either one only (the negative voltage conversion or the positive voltage conversion).

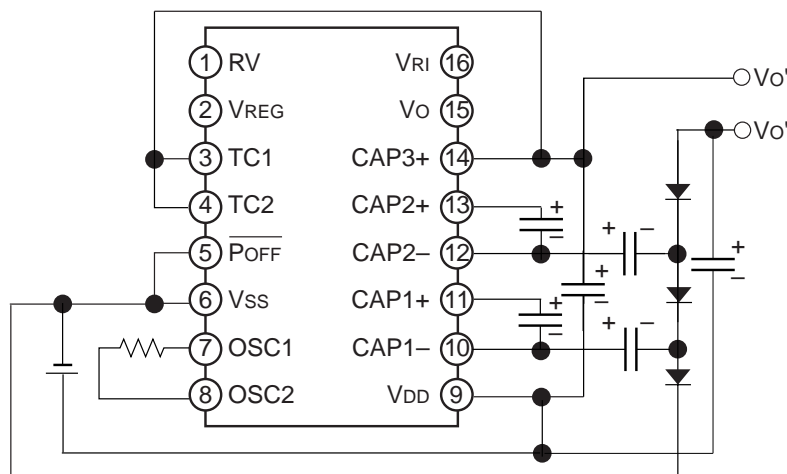


Figure 8.7 Negative Voltage Conversion + Positive Voltage Conversion

Example of Temperature Gradient Change by External Temperature Sensor (Thermistor)

S1F76640 has a temperature gradient selection circuit inside the stabilization circuit, and three kinds of temperature gradients, $-0.20\%/^{\circ}\text{C}$, $-0.40\%/^{\circ}\text{C}$ and $-0.60\%/^{\circ}\text{C}$, can be selected as the VREG output. When other temperature gradients are necessary, a thermistor is connected in series to the resistor RRV for output voltage regulation as shown in Figure 8.8, and temperature gradients can be changed to any values.

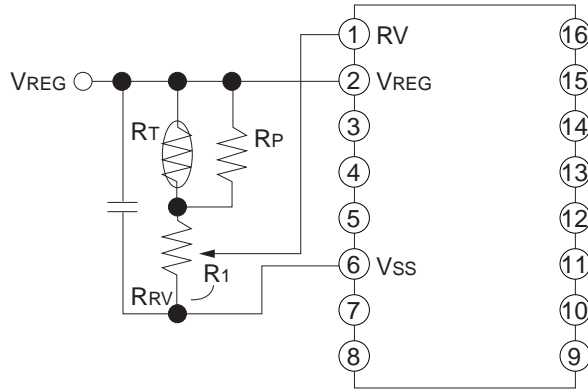


Figure 8.8 Example of Temperature Gradient Change

(Pins other than the above Pins 1, 2 and 6 are connected as per Figure 5.2. For Pins 3 and 4, smaller temperature gradients than those to be changed are selected from Table 4.1 and are set.)

Note 1 : Relations among the thermistor, RT and VREG are expressed as follows:

$$V_{REG} = \frac{R_{RV} + R_T}{R_1} \cdot V_{RV}$$

When a thermistor is used for RT, it can make the temperature gradient of VREG larger..

Note 2 : The thermistor temperature characteristics are non-linear but can be corrected to linear ones when the resistor RP is connected to the thermistor in parallel.

S1F76640 Series

Configuration Example of High Magnification Step-up Circuit with Diode

S1F76640, if an external diode is attached, can realize 5 times or more step-up operation and voltage stabilized output. Since the forward voltage drop V_F of the diode makes the output impedance of the step-up output higher, it is recommended to use a diode of small V_F . Figure 8.10 shows a configuration example of a circuit with 2 diodes, which realizes 6 times step-up operation and voltage stabilized output. Make the wire between V_O and V_{RI} as short as possible. Figure 8.11 shows the potential relations diagram

By the way, use the voltage applied to the V_{RI} pin below the absolute maximum rated voltage.

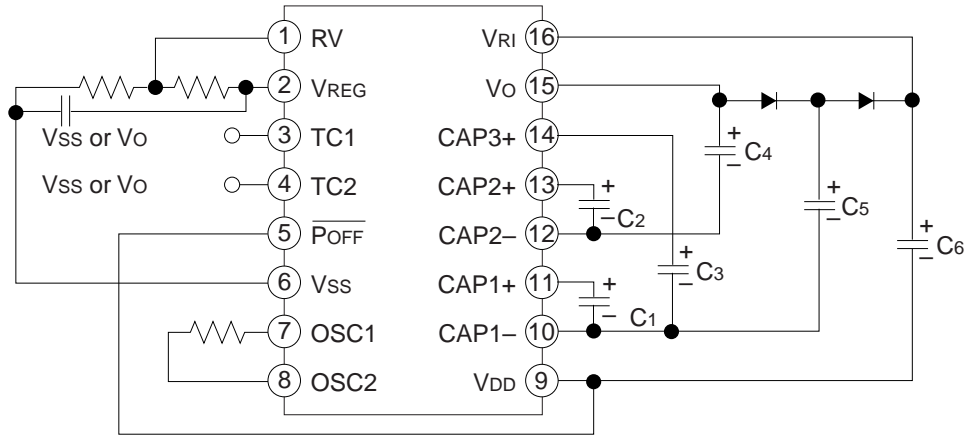


Figure 8.10 Configuration Example of 6 times step-up Circuit with Diode

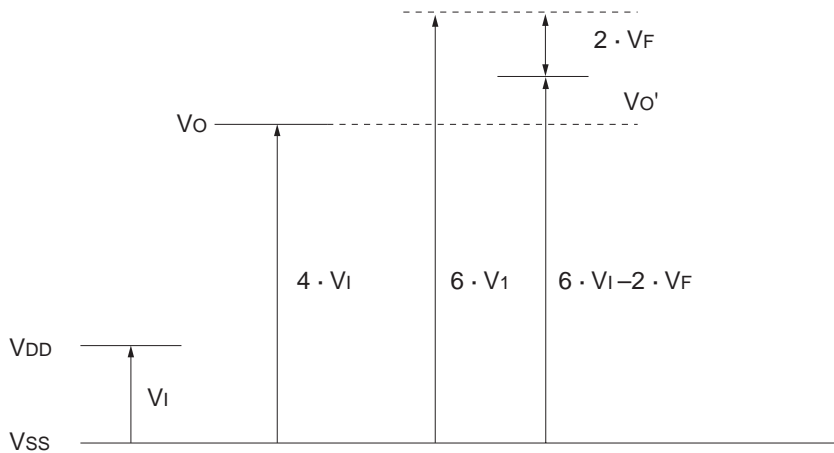


Figure 8.11 Potential Relations Diagram of 6 times Step-up Circuit with Diode

S1F76640 Series

3. Voltage Regulator

S1F78100Y Series CMOS Positive Voltage Regulators

DESCRIPTION

SCI78100Y Series is a fixed type positive voltage regulator developed by using the CMOS silicon gate process and is composed of a low current consumption reference voltage circuit, a differential amplifier, an output control transistor and a voltage setting resistor.

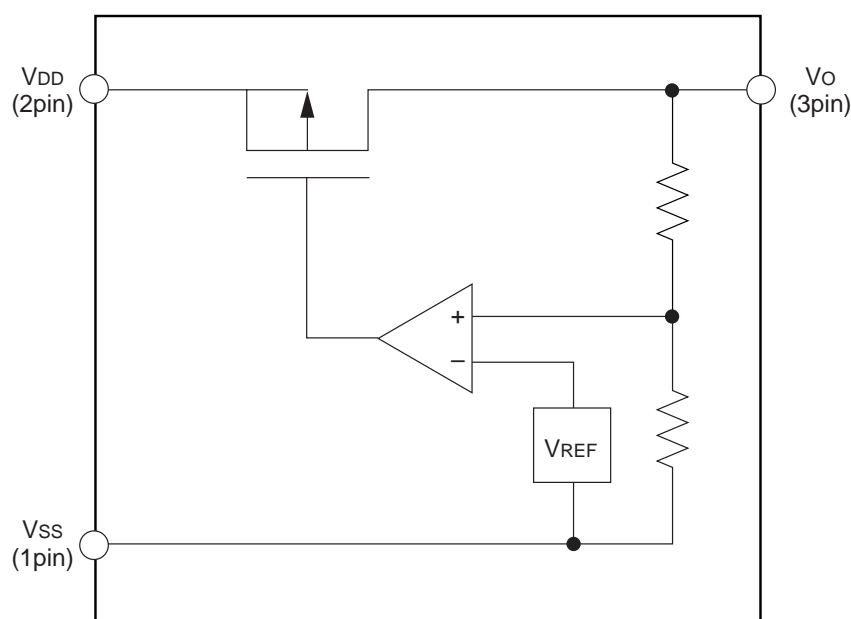
The output voltage is fixed inside the IC, and various standard voltage parts are available.

The package is a SOT89-3pin plastic package.

FEATURES

- Ample lineup : 12 kinds are available in the range from 2V to 6V.
- Low current consumption : Typ. $3.0\mu\text{A}$ ($V_{\text{DD}}=5.0\text{V}$)
- Small difference between input and output voltages : Typ. 0.25V ($I_{\text{O}}=-10\text{mA}$, $V_{\text{O}}=5.0\text{V}$)
- Built-in highly stable reference voltage source : Typ. 1.0V
- Small output voltage temperature coefficient : Typ. $+100\text{ppm}/^{\circ}\text{C}$
- Wide operating voltage range : 15V Max.

BLOCK DIAGRAM



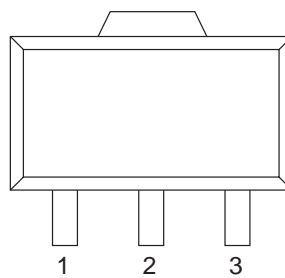
S1F78100Y Series

PIN DESCRIPTIONS

Pin No.	Pin name	Description
1	VSS	Input voltage pin (minus side)
2	VDD	Input voltage pin (plus side)
3	Vo	Output voltage pin

PIN ASSIGNMENTS

SOT89-3pin

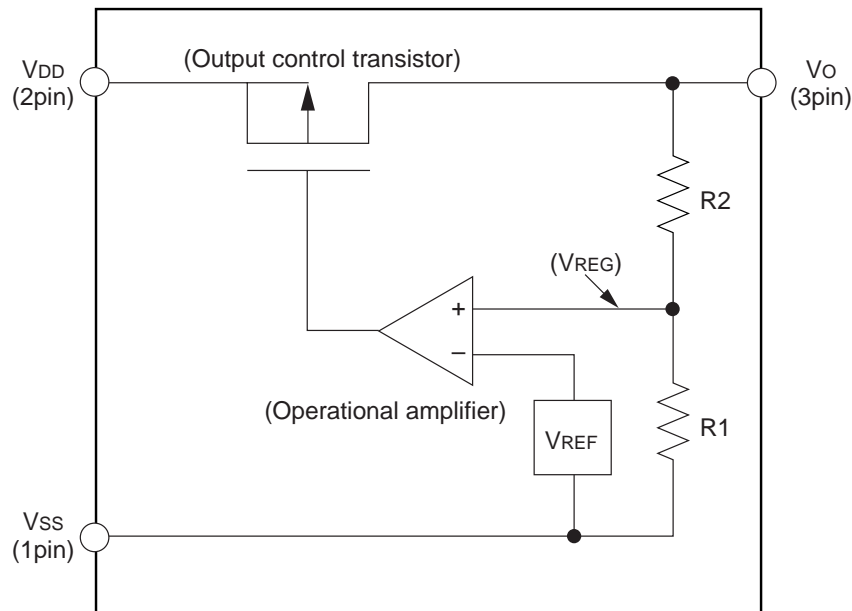


FUNCTIONAL DESCRIPTIONS

S1F78100Y Series is a fixed positive output type voltage regulator of series regulator system and is fitted with an output control MOS transistor between the input and output pins as shown in the figure below. The voltage regulator feeds back voltages (V_{REG}) divided with the built-in resistors R_1 and R_2 connected between

the output pin (V_O pin) and the V_{SS} pin to compare them with the reference voltage (V_{REF}) and outputs the stable output voltage (V_O) not depending on input voltage by controlling the gate voltage of the output control transistor. The output voltage is fixed inside and is decided with the following formula:

$$V_O = \frac{R_1 + R_2}{R_1} \cdot V_{REF}$$



S1F78100Y Series

LINEUP

Product	Output Voltage		
	Min.	Typ.	Max.
S1F78100Y2A0	5.75	6.00	6.25
S1F78100Y2B0	4.90	5.00	5.10
S1F78100Y2M0	4.40	4.50	4.60
S1F78100Y2P0	3.90	4.00	4.10
S1F78100Y2K0	3.80	3.90	4.00
S1F78100Y2N0	3.43	3.50	3.57
S1F78100Y2T0	3.23	3.30	3.37
S1F78100Y2C0	3.13	3.20	3.27
S1F78100Y2D0	2.93	3.00	3.07
S1F78100Y2R0	2.73	2.80	2.87
S1F78100Y2L0	2.53	2.60	2.67
S1F78100Y2F0	2.15	2.20	2.25
S1F78100Y2G0	1.75	1.80	1.85
S1F78100Y2H0	1.45	1.50	1.55

Note :

Other output voltages than those listed in the above table are also applicable.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rating	Unit
Input voltage	$V_{DD}-V_{SS}$	21	V
Output voltage	V_O	$V_{DD}+0.3$ to $V_{SS}-0.3$	
Output current	I_O	100	mA
Allowable loss	P_D	200	mW
Operating temperature	T_{opr}	-40 to +85	°C
Storage ambient temperature	T_{stg}	-65 to +150	
Soldering temperature and time	T_{sol}	260 • 10 (at leads)	°C • s

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min.	Typ.	Max.	Unit
Input voltage	$V_{DD}-V_{SS}$	-	-	15	V
Output current	I_O	0.01	-	-	mA

S1F78100Y Series**ELECTRICAL CHARACTERISTICS****S1F78100Y2A0**

(Unless otherwise specified, Ta ranges from -40°C to +85°C.)

Parameter	Symbol	Conditions (V _{SS} =0.0V)	Min.	Typ.	Max.	Unit
Input voltage	V _I	—	—	—	15	V
Output voltage	V _O	V _{DD} =8.0V, I _O =-10mA T _a =25°C	5.75	6.00	6.25	V
Current consumption	I _{OPR}	V _{DD} =6.0V to 15.0V, No load	—	3.0	8.0	μA
Difference between input and output voltages	V _I -V _O	V _O =6.0V, I _O =-10mA	—	0.24	0.38	V
Output voltage temperature characteristic	$\frac{\Delta V_O}{V_O}$	—	0	+100	+200	ppm/°C
Input stability	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	T _a =-30°C to +85°C (Same temperature condition) V _{DD} =7.0V to 15.0V I _O =-10mA	—	0.1	—	%/V
Load stability	ΔV _O	T _a =-30°C to +85°C (Same temperature condition) V _{DD} =8.0V I _O =-1mA to -50mA	—	50	—	mV
Supply voltage rejection ratio	P _{SR}	V _{DD} =8.0V, f _{in} =40kHz C _L =10μF, I _O =-5mA	—	-40	—	dB

S1F78100Y2B0

(Unless otherwise specified, Ta ranges from -40°C to +85°C.)

Parameter	Symbol	Conditions (V _{SS} =0.0V)	Min.	Typ.	Max.	Unit
Input voltage	V _I	—	—	—	15	V
Output voltage	V _O	V _{DD} =7.0V, I _O =-10mA T _a =25°C	4.90	5.00	5.10	V
Current consumption	I _{OPR}	V _{DD} =5.0V to 15.0V, No load	—	3.0	8.0	μA
Difference between input and output voltages	V _I -V _O	V _O =5.0V, I _O =-10mA	—	0.25	0.40	V
Output voltage temperature characteristic	$\frac{\Delta V_O}{V_O}$	—	0	+100	+200	ppm/°C
Input stability	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	T _a =-30°C to +85°C (Same temperature condition) V _{DD} =6.0V to 15.0V I _O =-10mA	—	0.1	—	%/V
Load stability	ΔV _O	T _a =-30°C to +85°C (Same temperature condition) V _{DD} =7.0V I _O =-1mA to -50mA	—	50	—	mV
Supply voltage rejection ratio	P _{SR}	V _{DD} =7.0V, f _{in} =40kHz C _L =10μF, I _O =-5mA	—	-40	—	dB

S1F78100Y2M0

(Unless otherwise specified, Ta ranges from -40°C to +85°C.)

Parameter	Symbol	Conditions (Vss=0.0V)	Min.	Typ.	Max.	Unit
Input voltage	V_I	—	—	—	15	V
Output voltage	V_O	$V_{DD}=6.0V$, $I_O=-10mA$ $T_a=25^\circ C$	4.40	4.50	4.60	V
Current consumption	I_{OPR}	$V_{DD}=4.5V$ to $15.0V$, No load	—	3.0	8.0	μA
Difference between input and output voltages	V_I-V_O	$V_O=4.5V$, $I_O=-10mA$	—	0.26	0.42	V
Output voltage temperature characteristic	$\frac{\Delta V_O}{V_O}$	—	0	+100	+200	ppm/ $^\circ C$
Input stability	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	$T_a=-30^\circ C$ to $+85^\circ C$ (Same temperature condition) $V_{DD}=6.0V$ to $15.0V$ $I_O=-10mA$	—	0.1	—	%/V
Load stability	ΔV_O	$T_a=-30^\circ C$ to $+85^\circ C$ (Same temperature condition) $V_{DD}=6.0V$ $I_O=-1mA$ to $-40mA$	—	40	—	mV
Supply voltage rejection ratio	$PSRR$	$V_{DD}=6.0V$, $f_{in}=40kHz$ $C_L=10\mu F$, $I_O=-5mA$	—	-40	—	dB

S1F78100Y2P0

(Unless otherwise specified, Ta ranges from -40°C to +85°C.)

Parameter	Symbol	Conditions (Vss=0.0V)	Min.	Typ.	Max.	Unit
Input voltage	V_I	—	—	—	15	V
Output voltage	V_O	$V_{DD}=6.0V$, $I_O=-10mA$ $T_a=25^\circ C$	3.90	4.00	4.10	V
Current consumption	I_{OPR}	$V_{DD}=4.0V$ to $15.0V$, No load	—	3.0	8.0	μA
Difference between input and output voltages	V_I-V_O	$V_O=4.0V$, $I_O=-10mA$	—	0.27	0.44	V
Output voltage temperature characteristic	$\frac{\Delta V_O}{V_O}$	—	0	+100	+200	ppm/ $^\circ C$
Input stability	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	$T_a=-30^\circ C$ to $+85^\circ C$ (Same temperature condition) $V_{DD}=5.0V$ to $15.0V$ $I_O=-10mA$	—	0.1	—	%/V
Load stability	ΔV_O	$T_a=-30^\circ C$ to $+85^\circ C$ (Same temperature condition) $V_{DD}=6.0V$ $I_O=-1mA$ to $-40mA$	—	40	—	mV
Supply voltage rejection ratio	$PSRR$	$V_{DD}=6.0V$, $f_{in}=40kHz$ $C_L=10\mu F$, $I_O=-5mA$	—	-40	—	dB

S1F78100Y Series

S1F78100Y2K0

(Unless otherwise specified, Ta ranges from -40°C to +85°C.)

Parameter	Symbol	Conditions (V _{SS} =0.0V)	Min.	Typ.	Max.	Unit
Input voltage	V _I	—	—	—	15	V
Output voltage	V _O	V _{DD} =6.0V, I _O =-10mA T _a =25°C	3.80	3.90	4.00	V
Current consumption	I _{OPR}	V _{DD} =3.9V to 15.0V, No load	—	3.0	8.0	μA
Difference between input and output voltages	V _I -V _O	V _O =3.9V, I _O =-10mA	—	0.27	0.44	V
Output voltage temperature characteristic	$\frac{\Delta V_O}{V_O}$	—	0	+100	+200	ppm/°C
Input stability	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	T _a =-30°C to +85°C (Same temperature condition) V _{DD} =5.0V to 15.0V I _O =-10mA	—	0.1	—	%/V
Load stability	ΔV _O	T _a =-30°C to +85°C (Same temperature condition) V _{DD} =6.0V I _O =-1mA to -40mA	—	40	—	mV
Supply voltage rejection ratio	P _{SR}	V _{DD} =6.0V, f _{in} =40kHz C _L =10μF, I _O =-5mA	—	-40	—	dB

S1F78100Y2N0

(Unless otherwise specified, Ta ranges from -40°C to +85°C.)

Parameter	Symbol	Conditions (V _{SS} =0.0V)	Min.	Typ.	Max.	Unit
Input voltage	V _I	—	—	—	15	V
Output voltage	V _O	V _{DD} =5.0V, I _O =-10mA T _a =25°C	3.43	3.50	3.57	V
Current consumption	I _{OPR}	V _{DD} =3.5V to 15.0V, No load	—	3.0	8.0	μA
Difference between input and output voltages	V _I -V _O	V _O =3.5V, I _O =-10mA	—	0.29	0.48	V
Output voltage temperature characteristic	$\frac{\Delta V_O}{V_O}$	—	0	+100	+200	ppm/°C
Input stability	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	T _a =-30°C to +85°C (Same temperature condition) V _{DD} =5.0V to 15.0V I _O =-10mA	—	0.1	—	%/V
Load stability	ΔV _O	T _a =-30°C to +85°C (Same temperature condition) V _{DD} =5.0V I _O =-1mA to -30mA	—	30	—	mV
Supply voltage rejection ratio	P _{SR}	V _{DD} =5.0V, f _{in} =40kHz C _L =10μF, I _O =-5mA	—	-40	—	dB

S1F78100Y2T0

(Unless otherwise specified, Ta ranges from -40°C to +85°C.)

Parameter	Symbol	Conditions (V _{SS} =0.0V)	Min.	Typ.	Max.	Unit
Input voltage	V _I	—	—	—	15	V
Output voltage	V _O	V _{DD} =5.0V, I _O =-10mA Ta=25°C	3.23	3.30	3.37	V
Current consumption	I _{OPR}	V _{DD} =3.3V to 15.0V, No load	—	3.0	8.0	μA
Difference between input and output voltages	V _I -V _O	V _O =3.3V, I _O =-10mA	—	0.30	0.50	V
Output voltage temperature characteristic	$\frac{\Delta V_O}{V_O}$	—	0	+100	+200	ppm/°C
Input stability	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	Ta=-30°C to +85°C (Same temperature condition) V _{DD} =4.0V to 15.0V I _O =-10mA	—	0.1	—	%/V
Load stability	ΔV _O	Ta=-30°C to +85°C (Same temperature condition) V _{DD} =5.0V I _O =-1mA to -30mA	—	30	—	mV
Supply voltage rejection ratio	PSRR	V _{DD} =5.0V, f _{in} =40kHz C _L =10μF, I _O =-5mA	—	-40	—	dB

S1F78100Y2C0

(Unless otherwise specified, Ta ranges from -40°C to +85°C.)

Parameter	Symbol	Conditions (V _{SS} =0.0V)	Min.	Typ.	Max.	Unit
Input voltage	V _I	—	—	—	15	V
Output voltage	V _O	V _{DD} =5.0V, I _O =-10mA Ta=25°C	3.13	3.20	3.27	V
Current consumption	I _{OPR}	V _{DD} =3.2V to 15.0V, No load	—	3.0	8.0	μA
Difference between input and output voltages	V _I -V _O	V _O =3.2V, I _O =-10mA	—	0.30	0.50	V
Output voltage temperature characteristic	$\frac{\Delta V_O}{V_O}$	—	0	+100	+200	ppm/°C
Input stability	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	Ta=-30°C to +85°C (Same temperature condition) V _{DD} =4.0V to 15.0V I _O =-10mA	—	0.1	—	%/V
Load stability	ΔV _O	Ta=-30°C to +85°C (Same temperature condition) V _{DD} =5.0V I _O =-1mA to -30mA	—	30	—	mV
Supply voltage rejection ratio	PSRR	V _{DD} =5.0V, f _{in} =40kHz C _L =10μF, I _O =-5mA	—	-40	—	dB

S1F78100Y Series

S1F78100Y2D0

(Unless otherwise specified, Ta ranges from -40°C to +85°C.)

Parameter	Symbol	Conditions (Vss=0.0V)	Min.	Typ.	Max.	Unit
Input voltage	V_I	—	—	—	15	V
Output voltage	V_O	$V_{DD}=5.0V$, $I_O=-10mA$ $T_a=25^\circ C$	2.93	3.00	3.07	V
Current consumption	I_{OPR}	$V_{DD}=3.0V$ to $15.0V$, No load	—	3.0	8.0	μA
Difference between input and output voltages	V_I-V_O	$V_O=3.0V$, $I_O=-10mA$	—	0.31	0.52	V
Output voltage temperature characteristic	$\frac{\Delta V_O}{V_O}$	—	0	+100	+200	ppm/ $^\circ C$
Input stability	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	$T_a=-30^\circ C$ to $+85^\circ C$ (Same temperature condition) $V_{DD}=4.0V$ to $15.0V$ $I_O=-10mA$	—	0.1	—	%/V
Load stability	ΔV_O	$T_a=-30^\circ C$ to $+85^\circ C$ (Same temperature condition) $V_{DD}=5.0V$ $I_O=-1mA$ to $-30mA$	—	30	—	mV
Supply voltage rejection ratio	$PSRR$	$V_{DD}=5.0V$, $f_{in}=40kHz$ $C_L=10\mu F$, $I_O=-5mA$	—	-40	—	dB

S1F78100Y2R0

(Unless otherwise specified, Ta ranges from -40°C to +85°C.)

Parameter	Symbol	Conditions (Vss=0.0V)	Min.	Typ.	Max.	Unit
Input voltage	V_I	—	—	—	15	V
Output voltage	V_O	$V_{DD}=5.0V$, $I_O=-10mA$ $T_a=25^\circ C$	2.73	2.80	2.87	V
Current consumption	I_{OPR}	$V_{DD}=2.8V$ to $15.0V$, No load	—	3.0	8.0	μA
Difference between input and output voltages	V_I-V_O	$V_O=2.8V$, $I_O=-10mA$	—	0.32	0.54	V
Output voltage temperature characteristic	$\frac{\Delta V_O}{V_O}$	—	0	+100	+200	ppm/ $^\circ C$
Input stability	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	$T_a=-30^\circ C$ to $+85^\circ C$ (Same temperature condition) $V_{DD}=4.0V$ to $15.0V$ $I_O=-10mA$	—	0.1	—	%/V
Load stability	ΔV_O	$T_a=-30^\circ C$ to $+85^\circ C$ (Same temperature condition) $V_{DD}=5.0V$ $I_O=-1mA$ to $-30mA$	—	30	—	mV
Supply voltage rejection ratio	$PSRR$	$V_{DD}=5.0V$, $f_{in}=40kHz$ $C_L=10\mu F$, $I_O=-5mA$	—	-40	—	dB

S1F78100Y2L0

(Unless otherwise specified, Ta ranges from -40°C to +85°C.)

Parameter	Symbol	Conditions (V _{SS} =0.0V)	Min.	Typ.	Max.	Unit
Input voltage	V _I	—	—	—	15	V
Output voltage	V _O	V _{DD} =5.0V, I _O =-10mA Ta=25°C	2.53	2.60	2.67	V
Current consumption	I _{OPR}	V _{DD} =2.6V to 15.0V, No load	—	3.0	8.0	μA
Difference between input and output voltages	V _I -V _O	V _O =2.6V, I _O =-10mA	—	0.33	0.56	V
Output voltage temperature characteristic	$\frac{\Delta V_O}{V_O}$	—	0	+100	+200	ppm/°C
Input stability	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	Ta=-30°C to +85°C (Same temperature condition) V _{DD} =4.0V to 15.0V I _O =-10mA	—	0.1	—	%/V
Load stability	ΔV _O	Ta=-30°C to +85°C (Same temperature condition) V _{DD} =5.0V I _O =-1mA to -40mA	—	30	—	mV
Supply voltage rejection ratio	PSRR	V _{DD} =5.0V, f _{in} =40kHz C _L =10μF, I _O =-5mA	—	-40	—	dB

S1F78100Y2F0

(Unless otherwise specified, Ta ranges from -40°C to +85°C.)

Parameter	Symbol	Conditions (V _{SS} =0.0V)	Min.	Typ.	Max.	Unit
Input voltage	V _I	—	—	—	15	V
Output voltage	V _O	V _{DD} =3.0V, I _O =-10mA Ta=25°C	2.15	2.20	2.25	V
Current consumption	I _{OPR}	V _{DD} =2.2V to 15.0V, No load	—	3.0	8.0	μA
Difference between input and output voltages	V _I -V _O	V _O =2.2V, I _O =-5mA	—	0.36	0.62	V
Output voltage temperature characteristic	$\frac{\Delta V_O}{V_O}$	—	0	+100	+200	ppm/°C
Input stability	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	Ta=-30°C to +85°C (Same temperature condition) V _{DD} =3.0V to 15.0V I _O =-10mA	—	0.1	—	%/V
Load stability	ΔV _O	Ta=-30°C to +85°C (Same temperature condition) V _{DD} =3.0V I _O =-1mA to -10mA	—	20	—	mV
Supply voltage rejection ratio	PSRR	V _{DD} =3.0V, f _{in} =40kHz C _L =10μF, I _O =-5mA	—	-40	—	dB

S1F78100Y Series

S1F78100Y2G0

(Unless otherwise specified, Ta ranges from -40°C to +85°C.)

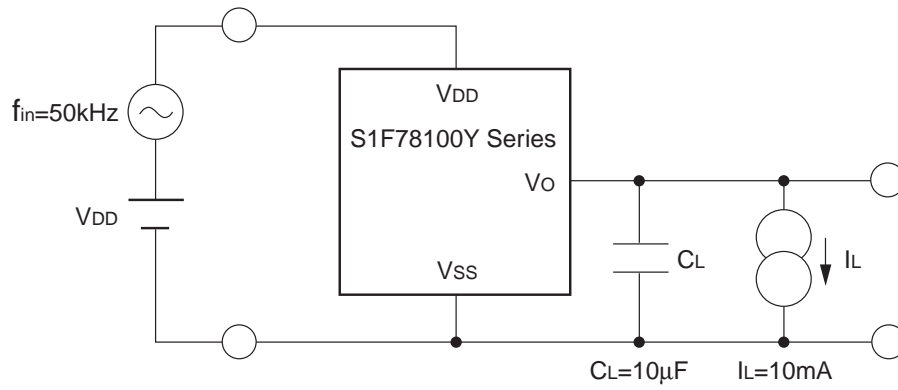
Parameter	Symbol	Conditions (V _{SS} =0.0V)	Min.	Typ.	Max.	Unit
Input voltage	V _I	—	—	—	15	V
Output voltage	V _O	V _{DD} =3.0V, I _O =-1mA T _a =25°C	1.75	1.80	1.85	V
Current consumption	I _{OPR}	V _{DD} =2.2V to 15.0V, No load	—	3.0	8.0	μA
Difference between input and output voltages	V _I -V _O	V _O =1.8V, I _O =-1mA	—	0.075	0.18	V
Output voltage temperature characteristic	$\frac{\Delta V_O}{V_O}$	—	0	+100	+200	ppm/°C
Input stability	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	T _a =-30°C to +85°C (Same temperature condition) V _{DD} =3.0V to 15.0V I _O =-10mA	—	0.1	—	%/V
Load stability	ΔV _O	T _a =-30°C to +85°C (Same temperature condition) V _{DD} =3.0V I _O =-1mA to -10mA	—	20	—	mV
Supply voltage rejection ratio	P _{SR}	V _{DD} =3.0V, f _{in} =40kHz C _L =10μF, I _O =-5mA	—	-40	—	dB

S1F78100Y2H0

(Unless otherwise specified, Ta ranges from -40°C to +85°C.)

Parameter	Symbol	Conditions (V _{SS} =0.0V)	Min.	Typ.	Max.	Unit
Input voltage	V _I	—	—	—	15	V
Output voltage	V _O	V _{DD} =3.0V, I _O =-1mA T _a =25°C	1.45	1.50	1.55	V
Current consumption	I _{OPR}	V _{DD} =2.2V to 15.0V, No load	—	3.0	8.0	μA
Difference between input and output voltages	V _I -V _O	V _O =1.5V, I _O =-1mA	—	0.18	0.5	V
Output voltage temperature characteristic	$\frac{\Delta V_O}{V_O}$	—	0	+100	+200	ppm/°C
Input stability	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	T _a =-30°C to +85°C (Same temperature condition) V _{DD} =3.0V to 15.0V I _O =-10mA	—	0.1	—	%/V
Load stability	ΔV _O	T _a =-30°C to +85°C (Same temperature condition) V _{DD} =3.0V I _O =-1mA to -10mA	—	20	—	mV
Supply voltage rejection ratio	P _{SR}	V _{DD} =3.0V, f _{in} =40kHz C _L =10μF, I _O =-5mA	—	-40	—	dB

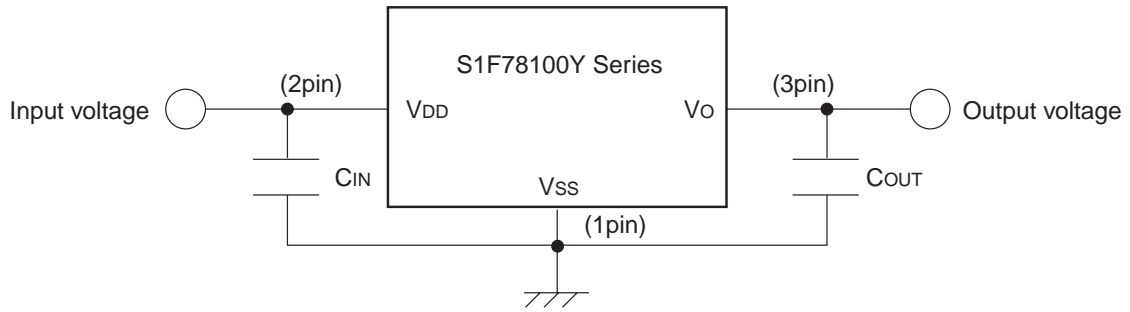
Note : Circuit Diagram for Measuring Supply Voltage Rejection Ratio Characteristic



S1F78100Y Series

S1F78100Y Series

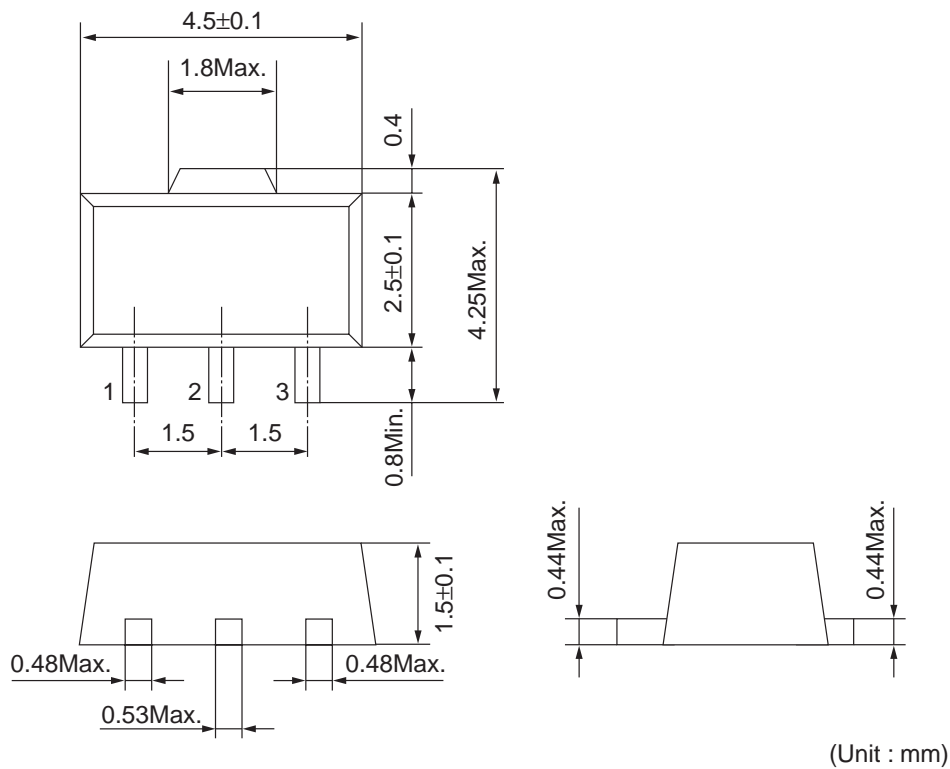
EXAMPLE OF REFERENCE EXTERNAL CONNECTION



MECHANICAL DATA

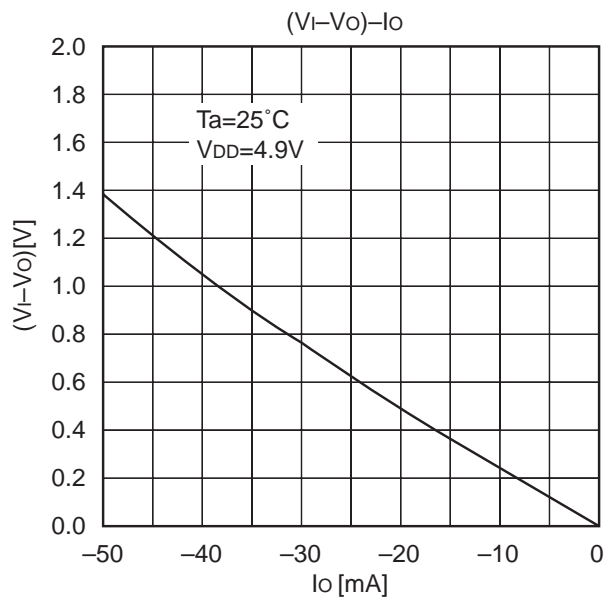
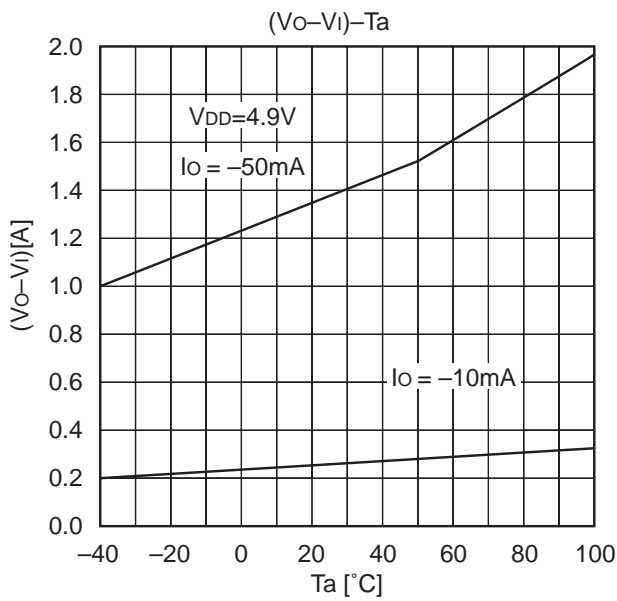
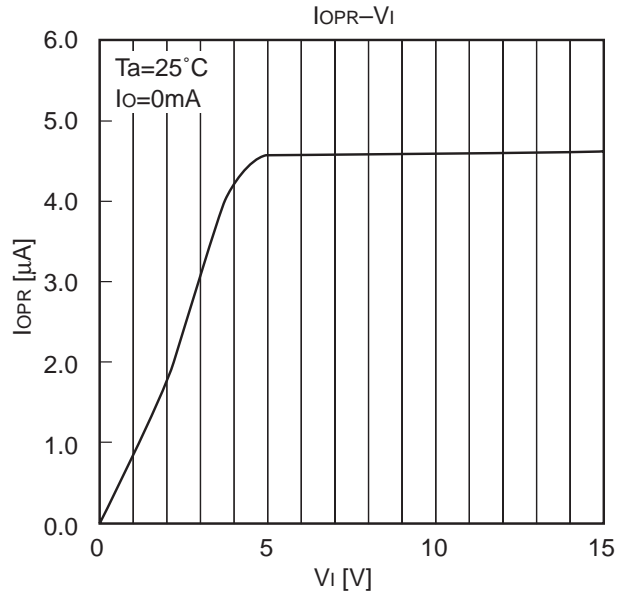
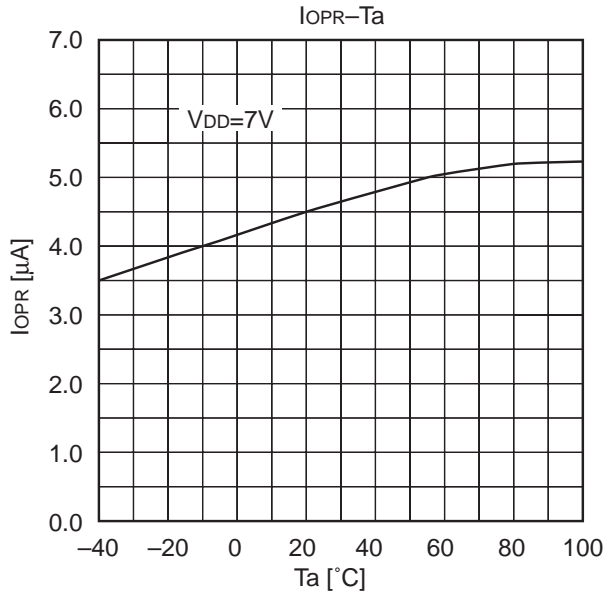
S1F78100Y SOT89-3pin

Reference



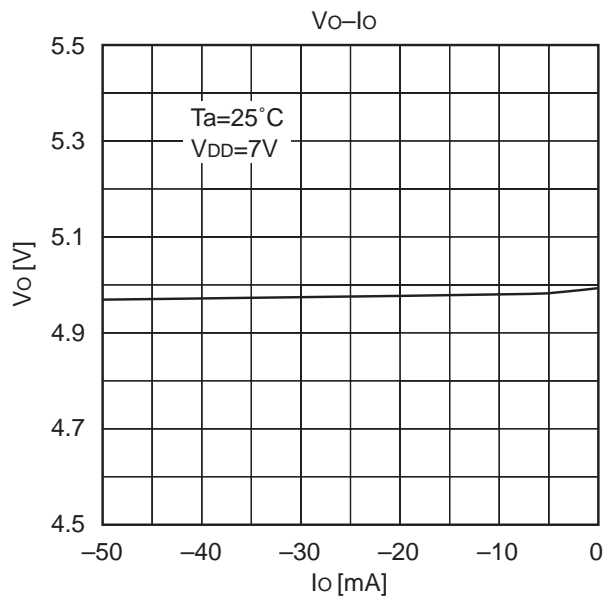
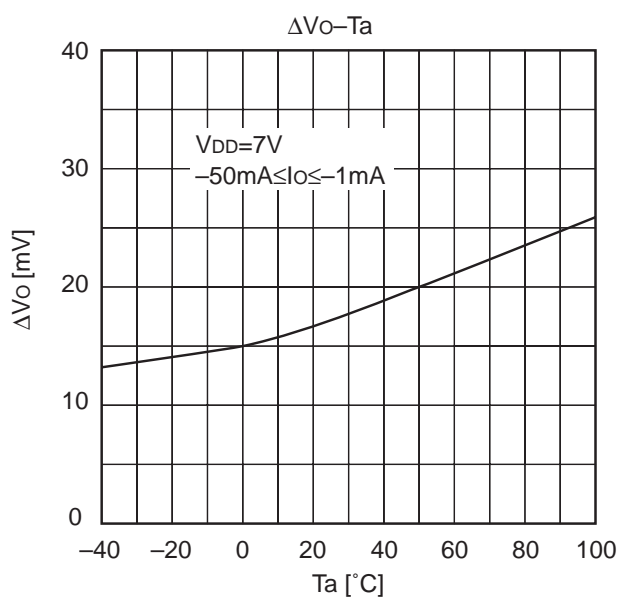
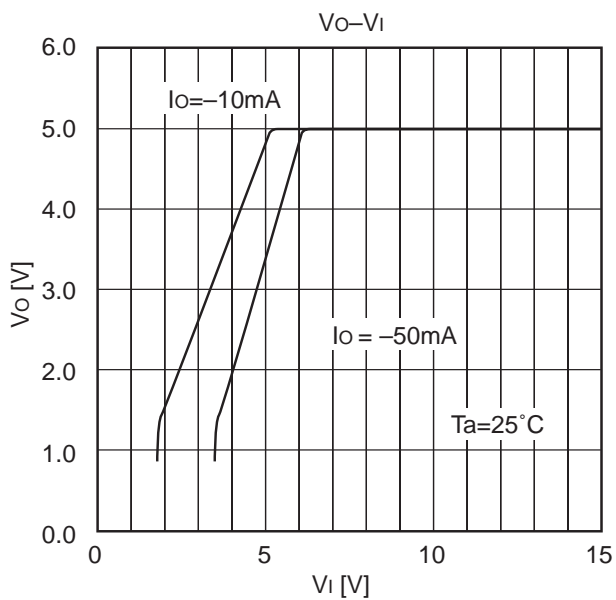
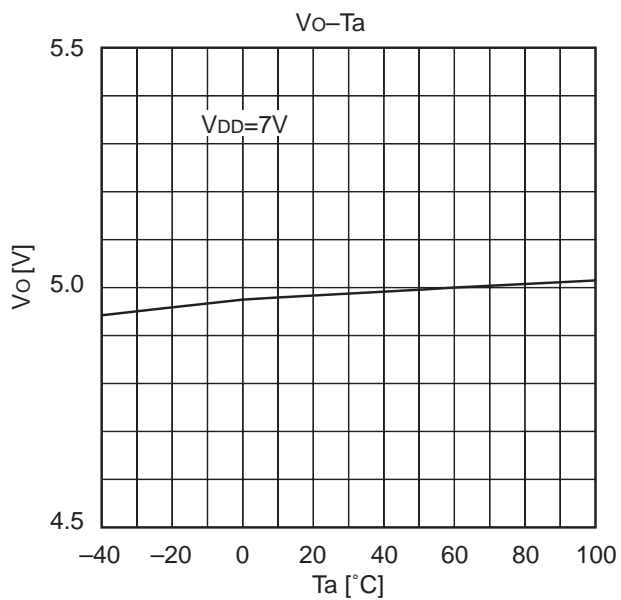
CHARACTERISTICS GRAPH

S1F78100Y2B0

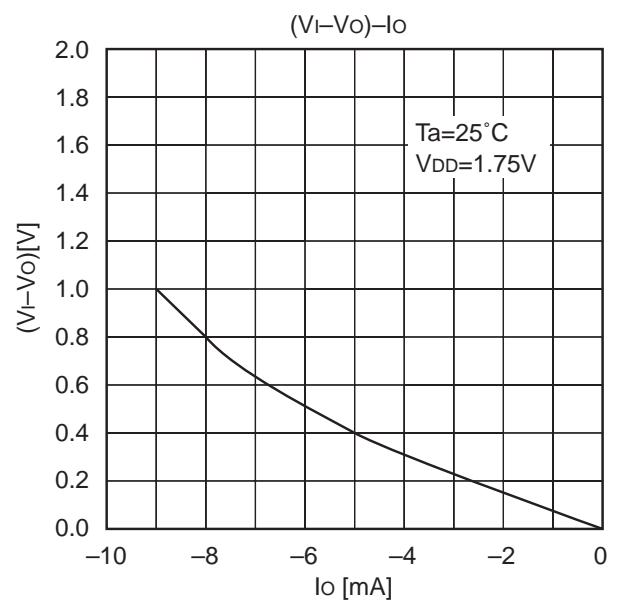
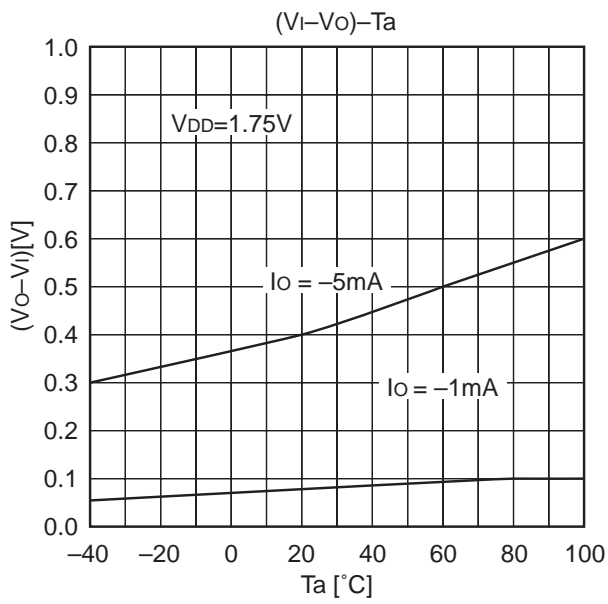
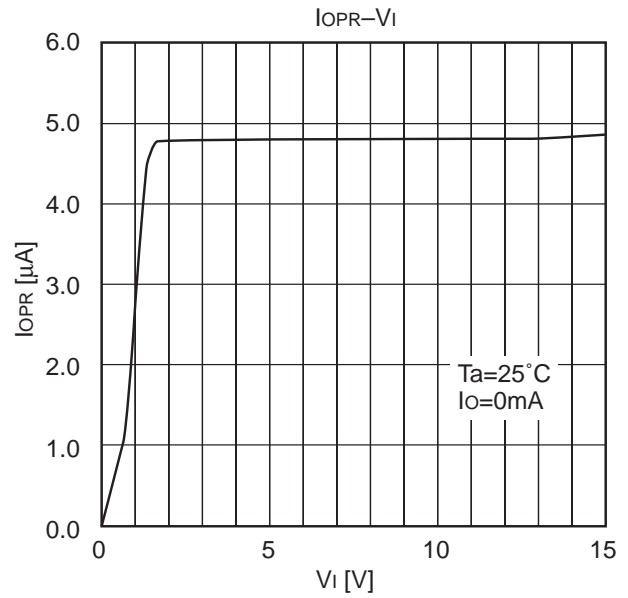
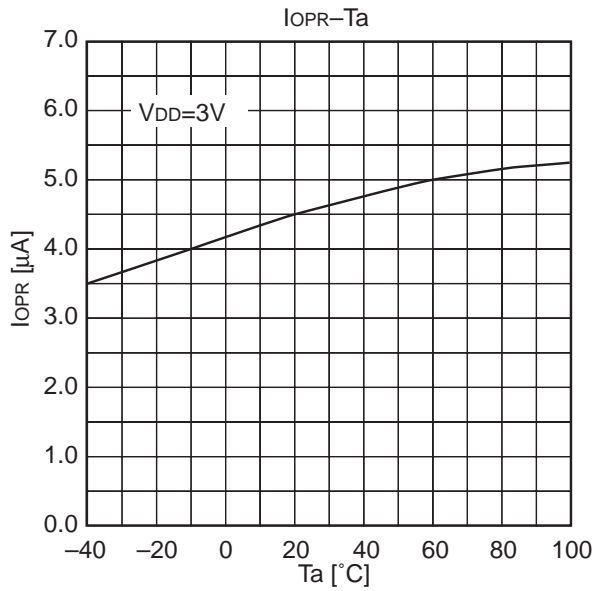


S1F78100Y Series

S1F78100Y Series

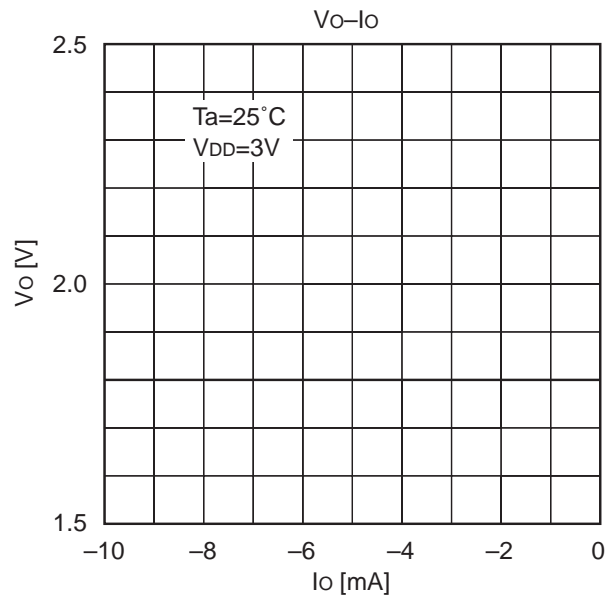
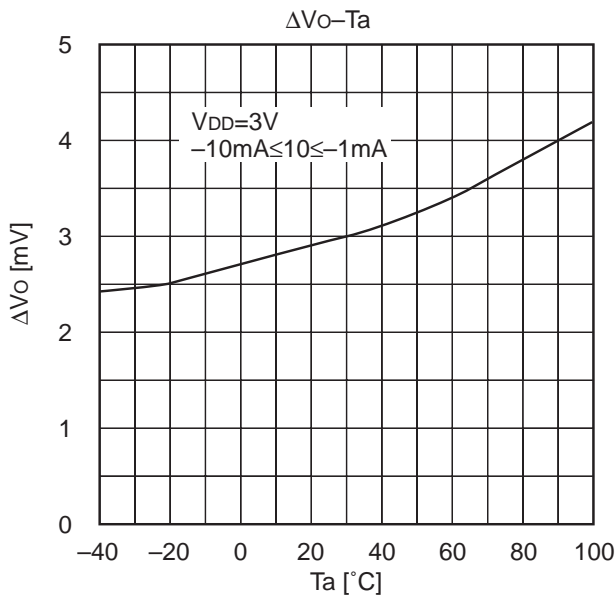
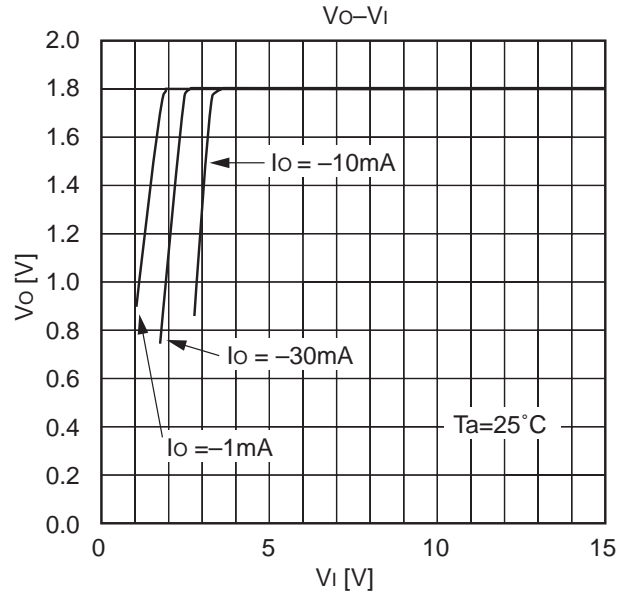
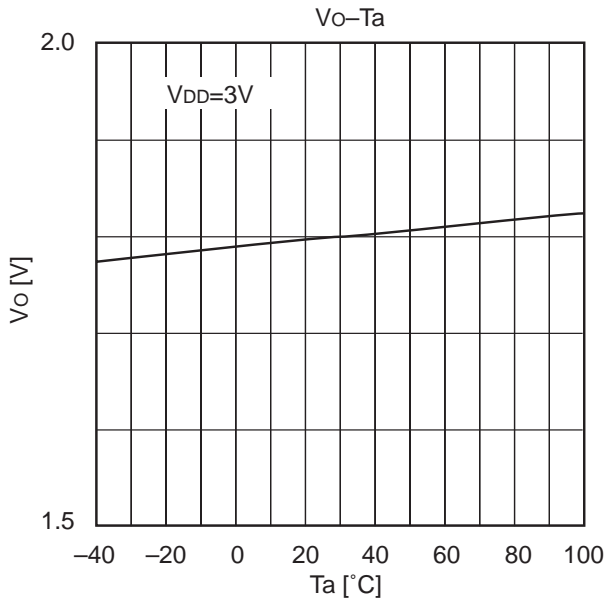


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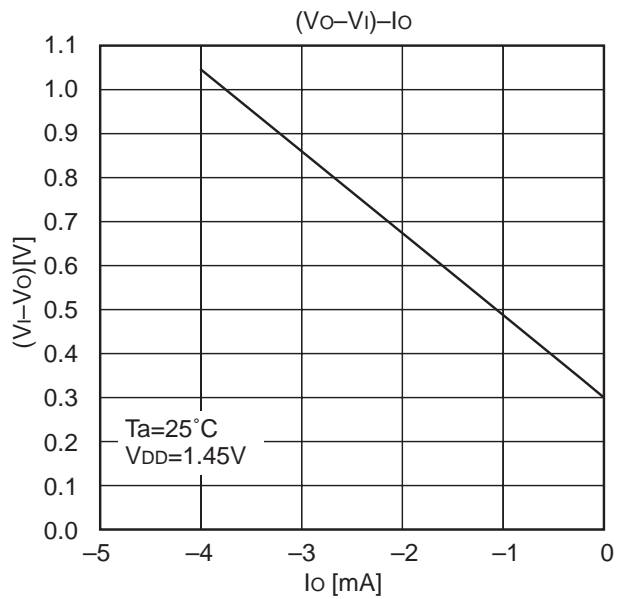
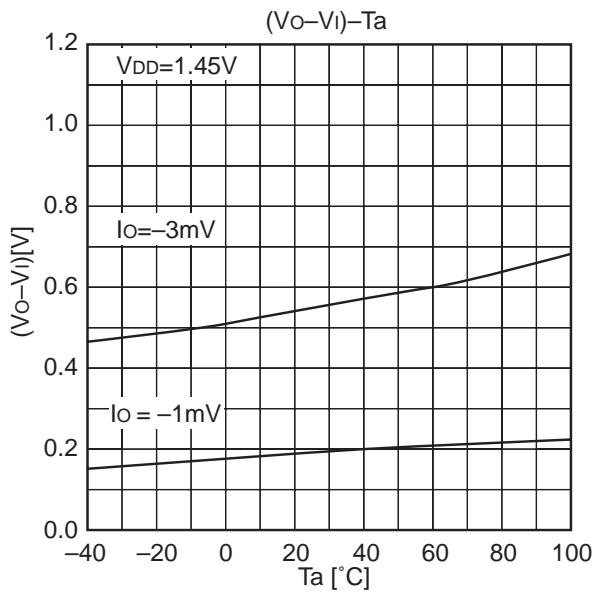
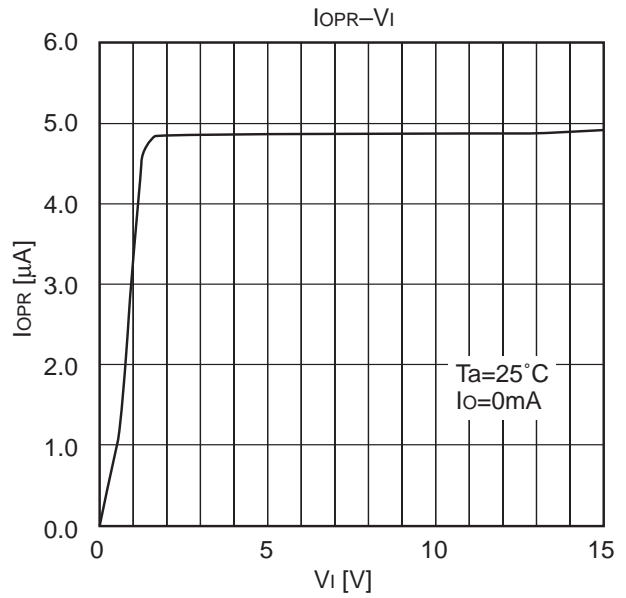
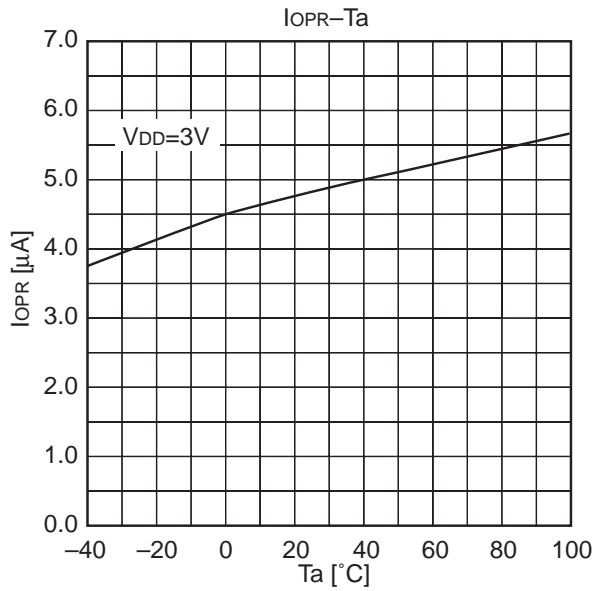


S1F78100Y Series

S1F78100Y Series

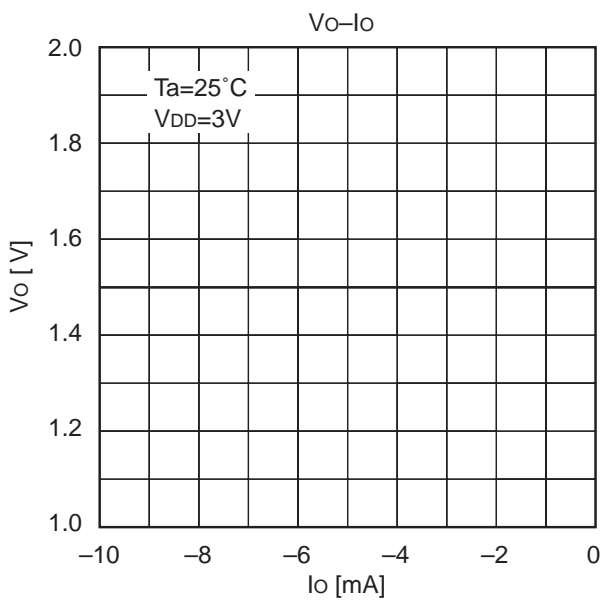
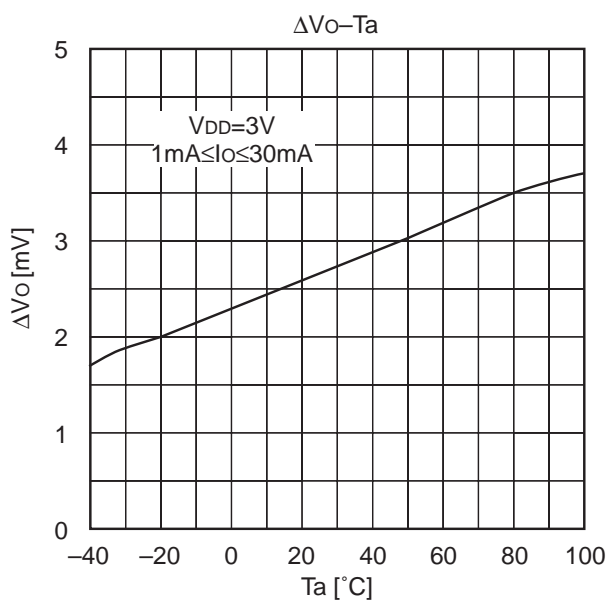
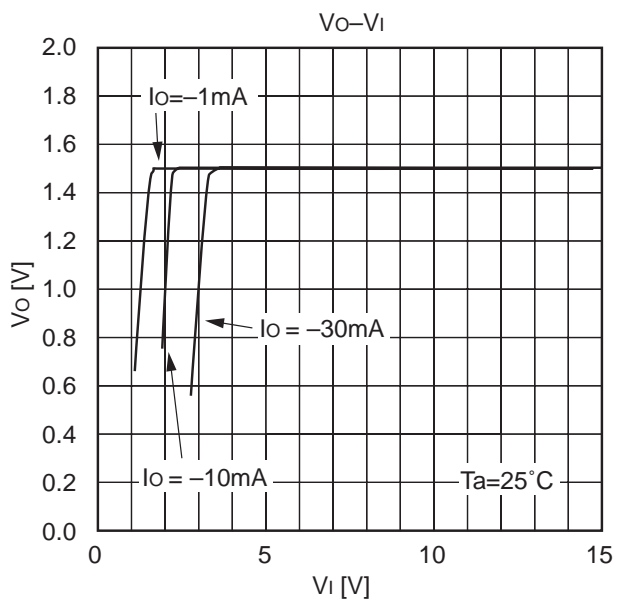
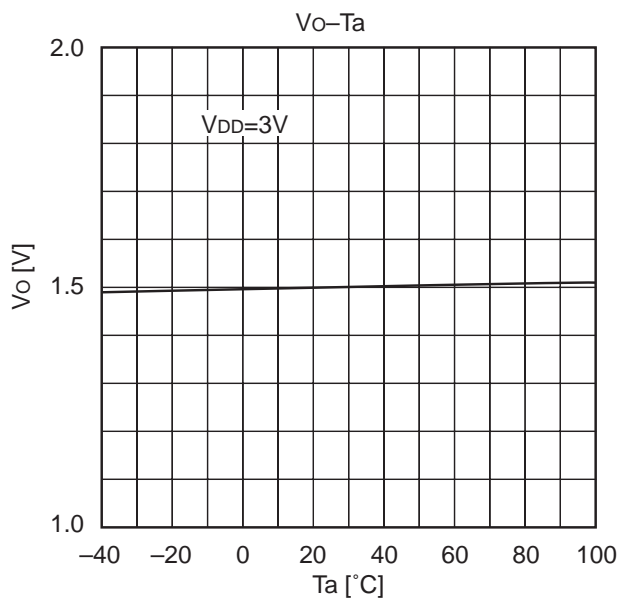


S1F78100Y2H0



S1F78100Y Series

S1F78100Y Series



S1F79100Y Series CMOS Negative Voltage Regulators

DESCRIPTION

S1F79100Y series voltage regulators provide step-down and stabilization for an input voltage to a specified fixed voltage. The four devices in the series incorporate a precision, power-saving reference voltage generator, a transistorized differential amplifier and resistors for determining the output voltage.

The S1F79100Y series is available in 3-pin plastic SOT89s.

FEATURES

- Ample lineup : 5 kinds are available in the range from -1.5V to -5V .
- Small difference between input and output voltage : Typ. 0.17V ($I_o=10\text{mA}$, $V_o=-5.0\text{V}$)

- Built-in highly stable reference voltage source : Typ. -1.0V
- Small output voltage temperature coefficient : Typ. $-100\text{ppm}/^\circ\text{C}$
- Wide operating voltage range : 15V Max.

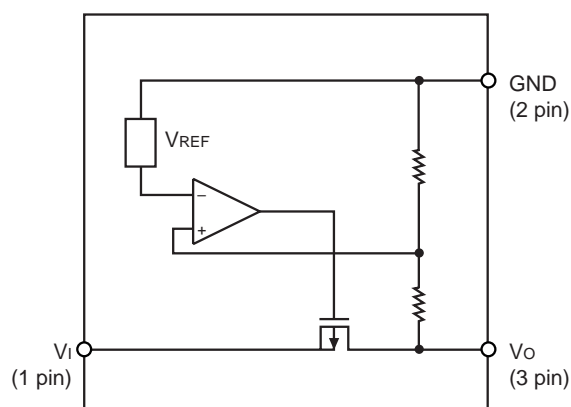
APPLICATIONS

- Fixed-voltage power supplies for battery-operated equipment such as portable video cassette recorders, video cameras and radios
- Fixed-voltage power supplies for communications equipment
- High-stability reference voltage generators

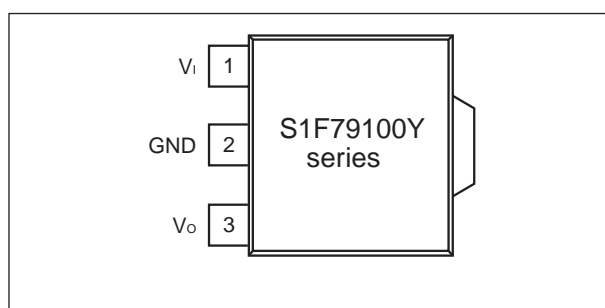
LINEUP

Product	Voltage (V)		Current consumption (μA)	Operating temperature ($^\circ\text{C}$)
	Input	Output		
S1F79100Y1H0	-15	-1.5	4.0	-40 to +85
S1F79100Y1G0		-1.8	4.0	
S1F79100Y1D0		-3.0	4.0	
S1F79100Y1P0		-4.0	4.0	
S1F79100Y1B0		-5.0	4.0	

BLOCK DIAGRAM



PIN ASSIGNMENTS



S1F79100Y Series

PIN DESCRIPTIONS

Pin No.	Pin name	Description
1	V _I	Input voltage
2	GND	Ground
3	V _O	Output voltage

SPECIFICATIONS

Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Input voltage	V _I -GND	-21	V
Output voltage	V _O	GND + 0.3 to V _I - 0.3	V
Output current	I _O	100	mA
Power dissipation	P _D	200	mW
Operating temperature range	T _{opr}	-40 to +85	°C
Storage temperature range	T _{stg}	-65 to +150	°C
Soldering temperature (for 10 s). See note.	T _{sol}	260	°C

Note

Temperatures during reflow soldering must remain within the limits set out in LSI Device Precautions. Never use solder dip to mount S1F70000 series power supply devices.

Electrical Characteristics

S1F79100Y1H0

(T_a = -40°C to +85°C)

Parameter	Symbol	Conditions (GND = 0.0V)	Rating			Unit
			Min.	Typ.	Max.	
Input voltage	V _I	—	-15.0	—	—	V
Output voltage	V _O	V _I = -3.0V, I _O = 10mA T _a = 25°C	-1.57	-1.50	-1.43	V
Operating current	I _{OPR}	V _I = -1.5V to -15V	—	4.0	18.0	μA
Input/output voltage differential	V _I - V _O	V _I = -1.5V, I _O = 5mA	—	0.25	0.60	V
Input voltage stabilization ratio	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	V _I = -3.0V to -15.0V, I _O = 5mA	—	0.10	—	%/V
Output voltage drift	ΔV _O	V _I = -3.0V, I _O = 1mA to 5mA	—	20.0	—	mV

S1F79100Y Series

S1F79100Y1G0

(V_{DD} = 0V, T_a = -40°C to +85°C unless otherwise noted)

Parameter	Symbol	Conditions	Rating			Unit
			Min.	Typ.	Max.	
Input voltage	V _I	—	-15.0	—	—	V
Output voltage	V _O	V _I = -3.0V, I _O = 10mA T _a = 25°C	-1.87	-1.80	-1.73	V
Operating current	I _{OPR}	V _I = -1.8V to -15.0V	—	4.0	18.0	μA
Input/output voltage differential	V _I - V _O	V _I = -1.8V, I _O = 10mA	—	0.35	0.70	V
Input voltage stabilization ratio	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	V _I = -3.0V to -15.0V, I _O = 10mA, Isothermal	—	0.10	—	%/V
Output voltage drift	ΔV _O	V _I = -3.0V, I _O = 1mA to 10mA, Isothermal	—	20.0	—	mV

S1F79100Y1D0

(V_{DD} = 0V, T_a = -40°C to +85°C unless otherwise noted)

Parameter	Symbol	Conditions	Rating			Unit
			Min.	Typ.	Max.	
Input voltage	V _I	—	-15.0	—	—	V
Output voltage	V _O	V _I = -5.0V, I _O = 10mA T _a = 25°C	-3.07	-3.00	-2.93	V
Operating current	I _{OPR}	V _I = -3.0V to -15.0V	—	4.0	18.0	μA
Input/output voltage differential	V _I - V _O	V _I = -3.0V, I _O = 10mA	—	0.23	0.46	V
Input voltage stabilization ratio	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	V _I = -4.0V to -15.0V, I _O = 10mA, Isothermal	—	0.10	—	%/V
Output voltage drift	ΔV _O	V _I = -5.0V, I _O = 1mA to 30mA	—	30.0	—	mV

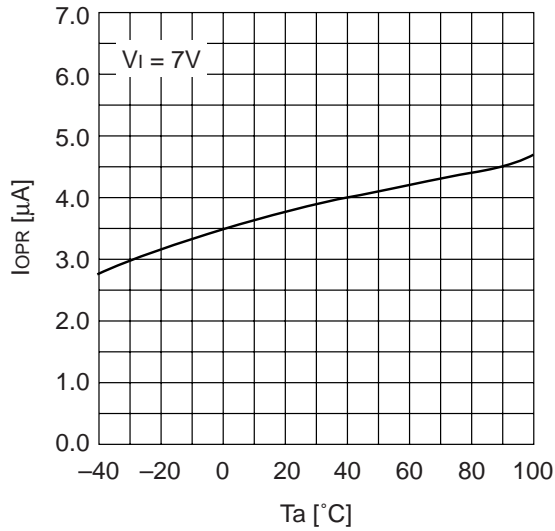
S1F79100Y Series**S1F79100Y1P0**(V_{DD} = 0V, T_a = -40°C to +85°C unless otherwise noted)

Parameter	Symbol	Conditions	Rating			Unit
			Min.	Typ.	Max.	
Input voltage	V _I	—	-15.0	—	—	V
Output voltage	V _O	V _I = -6.0V, I _o = 10mA T _a = 25°C	-4.10	-4.00	-3.90	V
Operating current	I _{OPR}	V _I = -4.0V to -15.0V	—	4.0	18.0	μA
Input/output voltage differential	V _I - V _O	V _I = -4.0V, I _o = 10mA	—	0.19	0.38	V
Input voltage stabilization ratio	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	V _I = -5.0V to -15V, I _o = 10mA, Isothermal	—	0.10	—	%/V
Output voltage drift	ΔV _O	V _I = -7V, I _o = 1mA to 30mA	—	40.0	—	mV

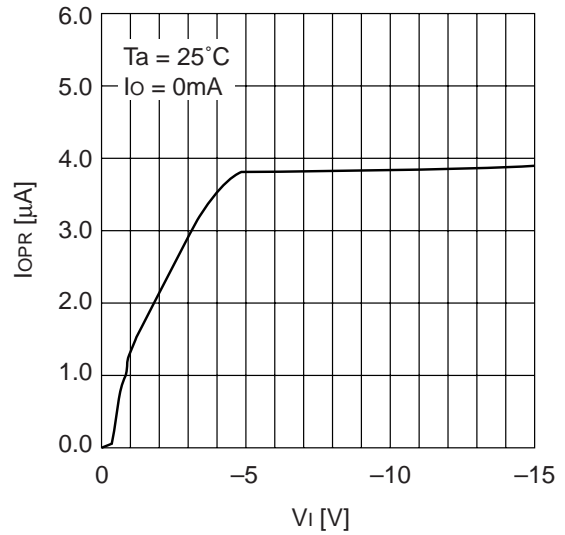
S1F79100Y1B0(V_{DD} = 0V, T_a = -40°C to +85°C unless otherwise noted)

Parameter	Symbol	Conditions	Rating			Unit
			Min.	Typ.	Max.	
Input voltage	V _I	—	-15.0	—	—	V
Output voltage	V _O	V _I = -7.0V, I _o = 10mA T _a = 25°C	-5.10	-5.00	-4.90	V
Operating current	I _{OPR}	V _I = -5.0V to -15.0V	—	4.0	18.0	μA
Input/output voltage differential	V _I - V _O	V _I = -5.0V, I _o = 10mA	—	0.17	0.34	V
Input voltage stabilization ratio	$\frac{\Delta V_O}{\Delta V_I \cdot V_O}$	V _I = -6.0V to -15.0V, I _o = 10mA, Isothermal	—	0.10	—	%/V
Output voltage drift	ΔV _O	V _I = -7.0V, I _o = 1mA to 50mA	—	50.0	—	mV

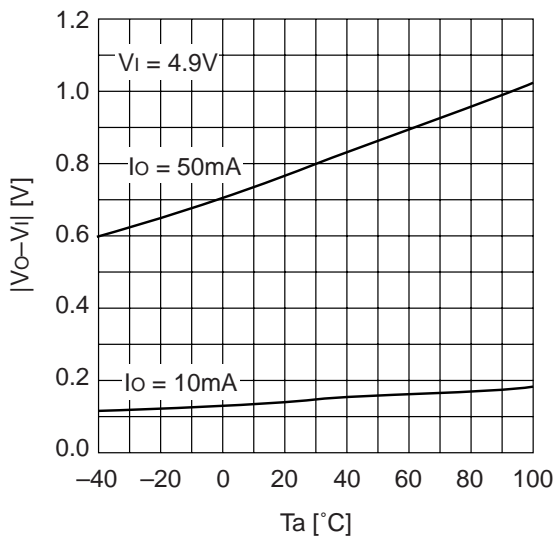
**Typical Performance Characteristics
S1F79100Y1B0**



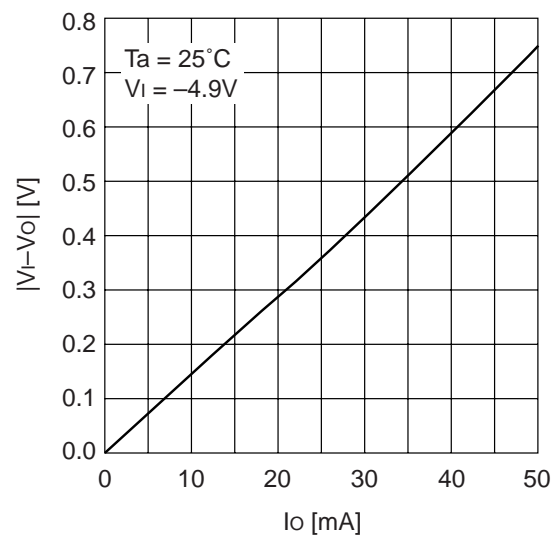
I_{OPR} vs. T_a



I_{OPR} vs. V_i



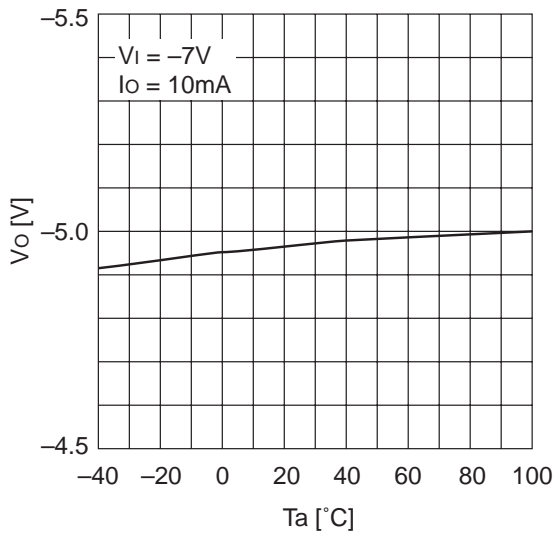
$|V_o - V_i|$ vs. T_a



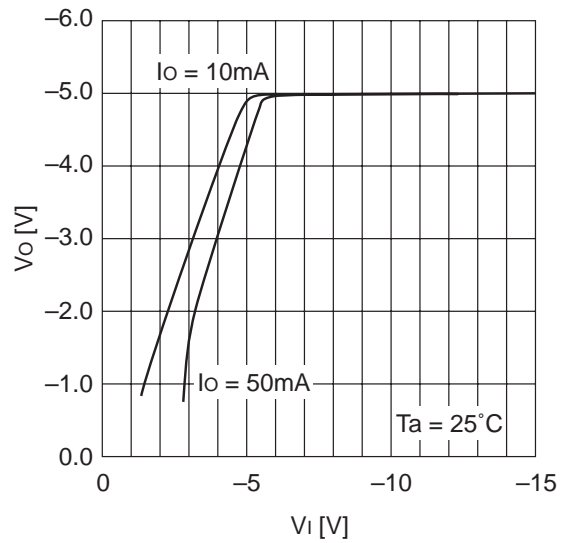
$|V_i - V_o|$ vs. I_o

S1F79100Y Series

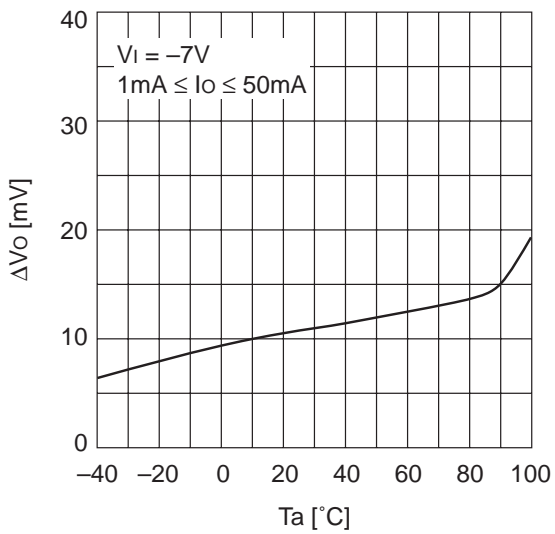
S1F79100Y Series



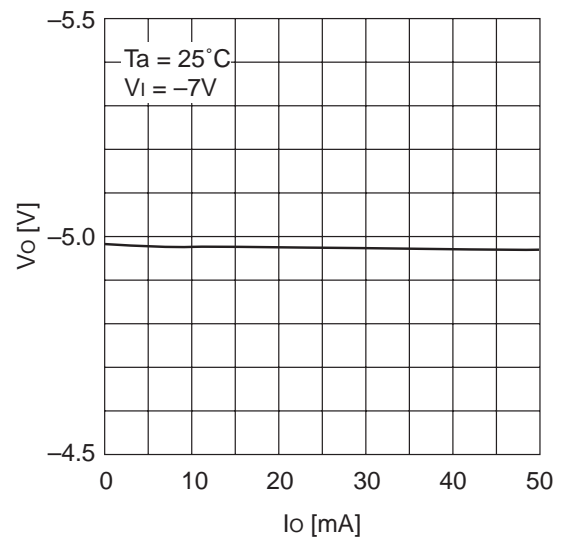
Vo vs. Ta



Vo vs. Vi

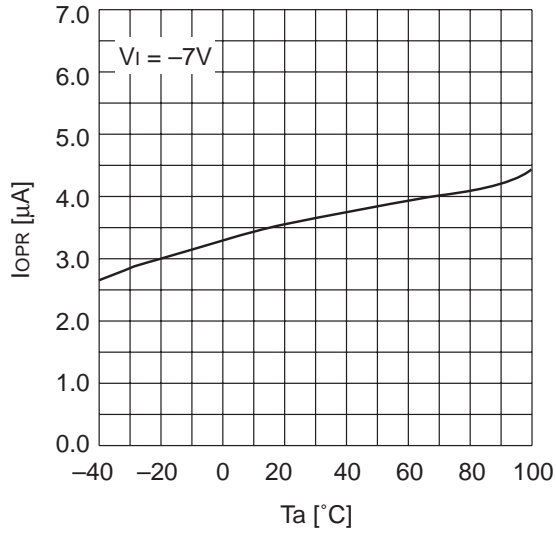


ΔVo vs. Ta

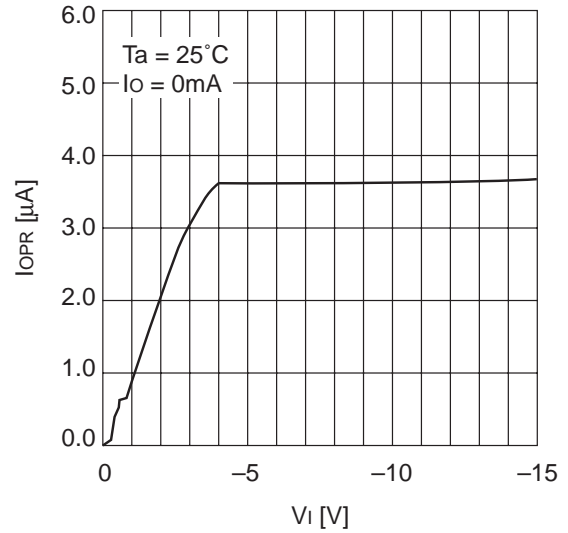


Vo vs. Io

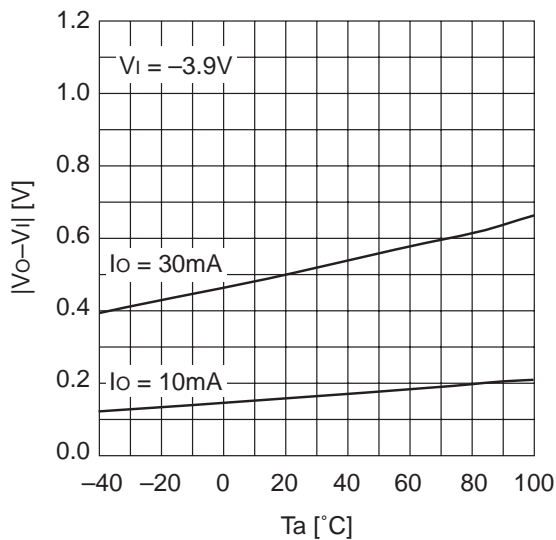
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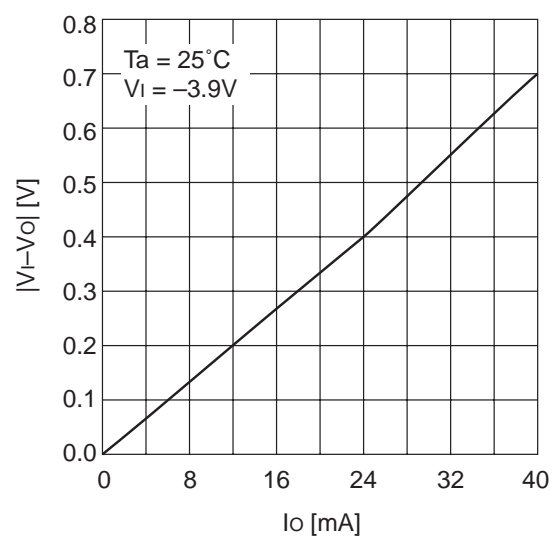
IOPR vs. Ta



IOPR vs. Vi



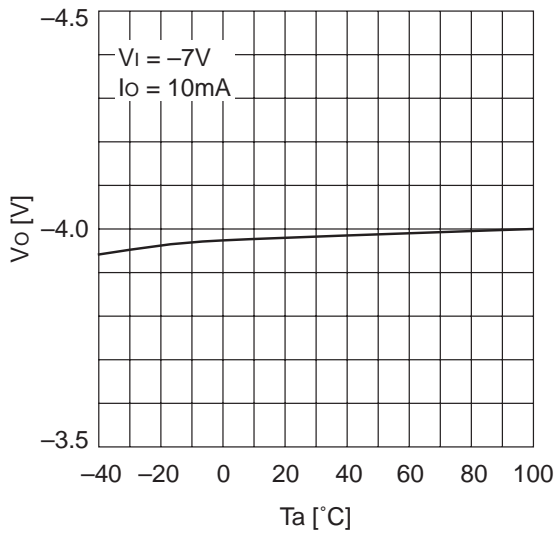
|Vo - Vi| vs. Ta



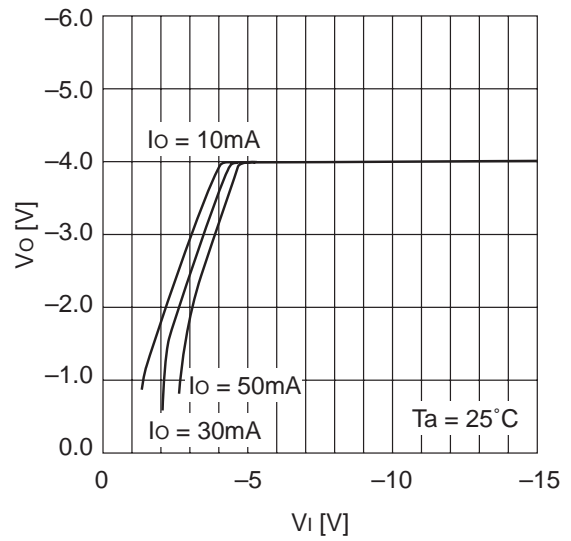
|Vi - Vo| vs. Io

S1F79100Y Series

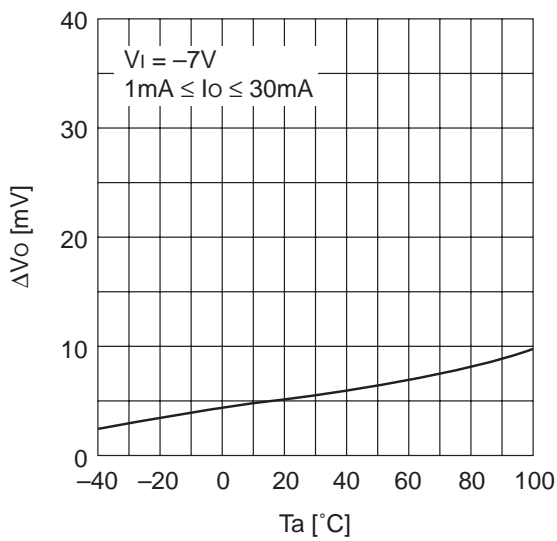
S1F79100Y Series



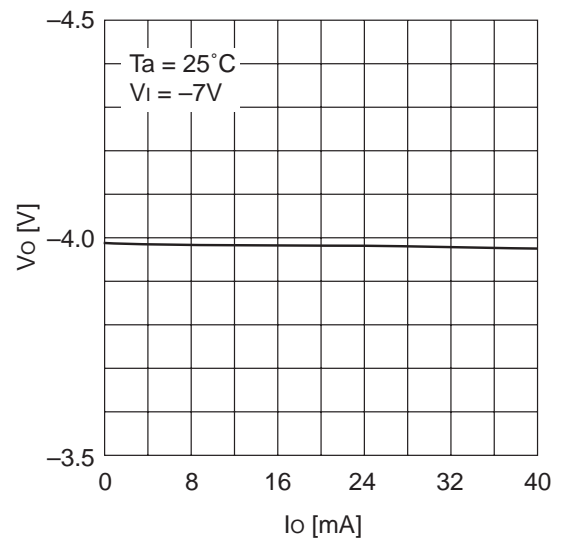
Vo vs. Ta



Vo vs. Vi

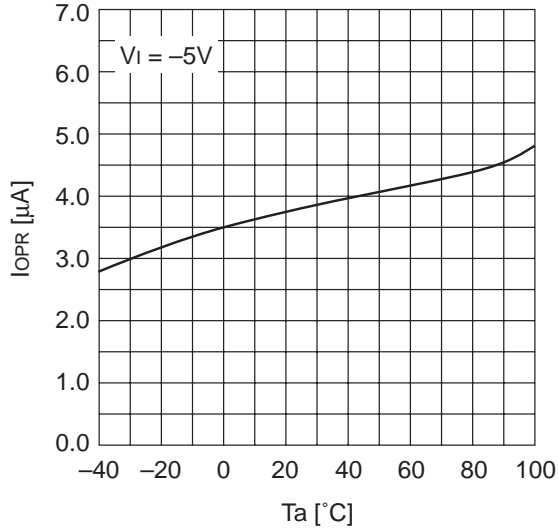


ΔVo vs. Ta

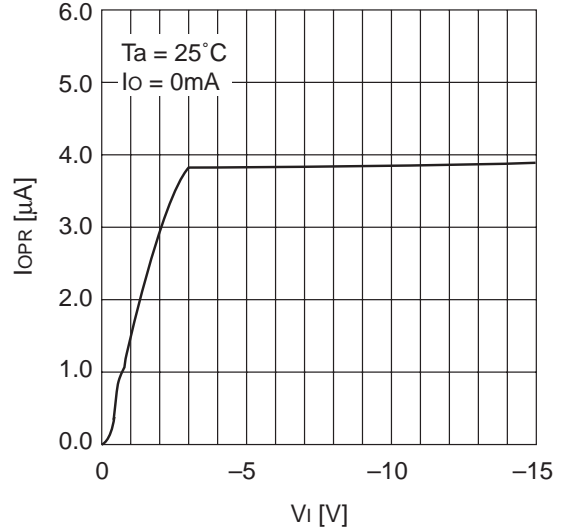


Vo vs. Io

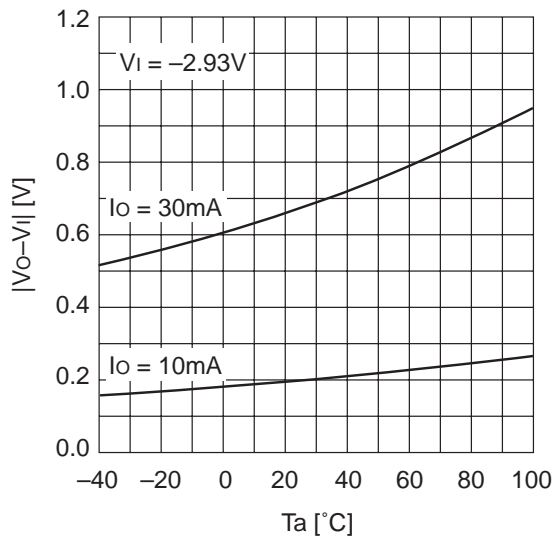
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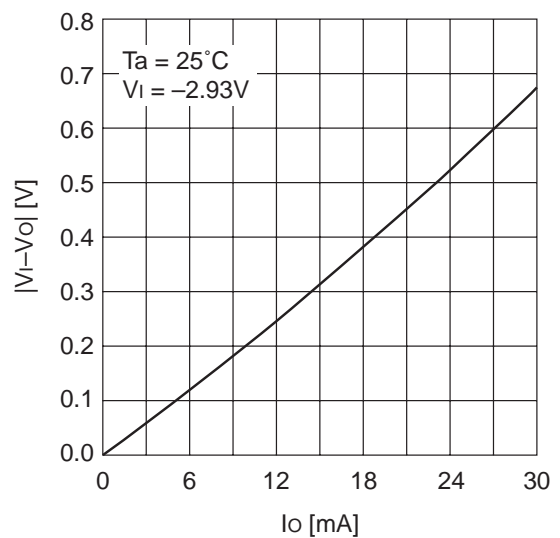
IOPR vs. Ta



IOPR vs. Vi



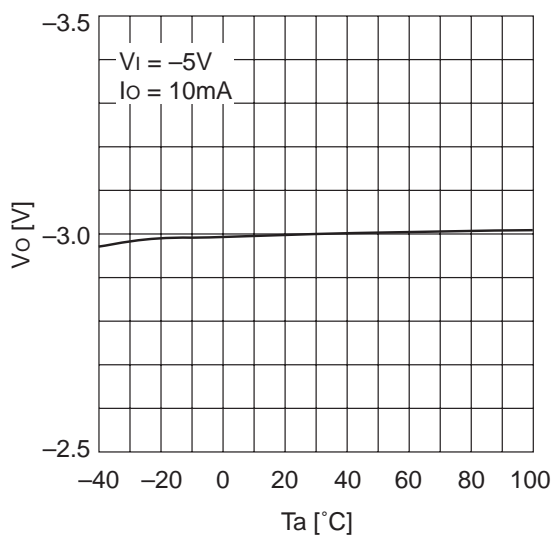
|Vo - Vi| vs. Ta



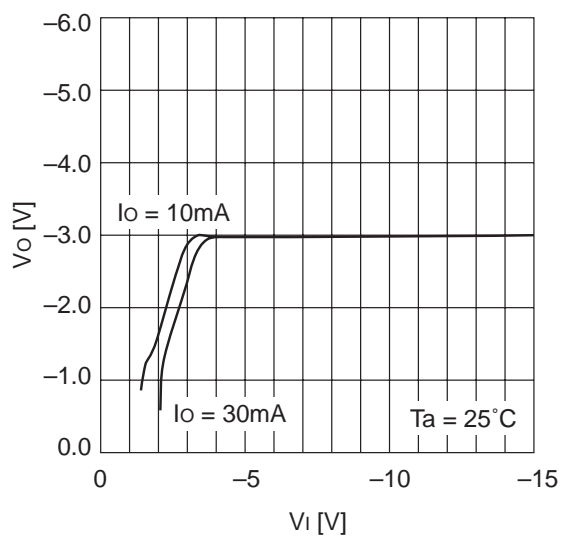
|Vi - Vo| vs. Io

S1F79100Y Series

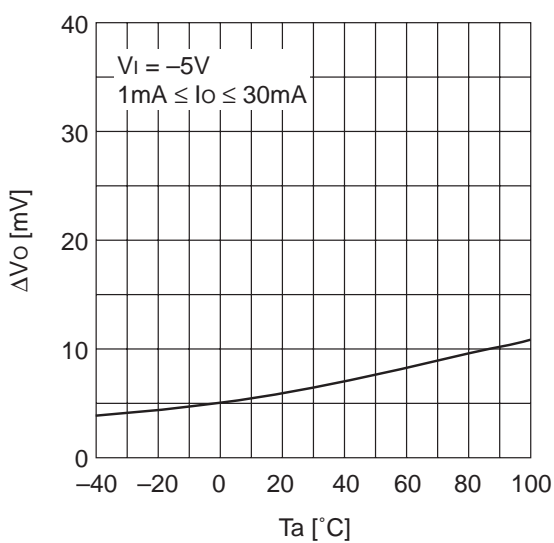
S1F79100Y Series



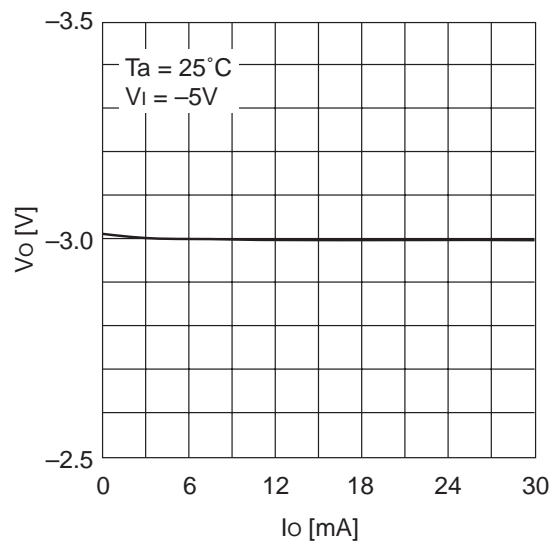
Vo vs. Ta



Vo vs. Vi

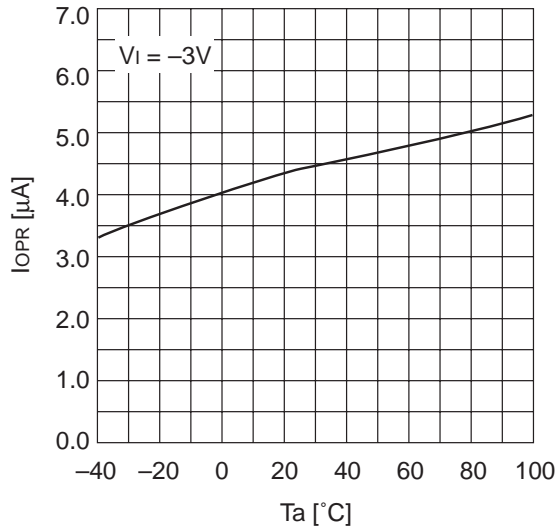


ΔVo vs. Ta

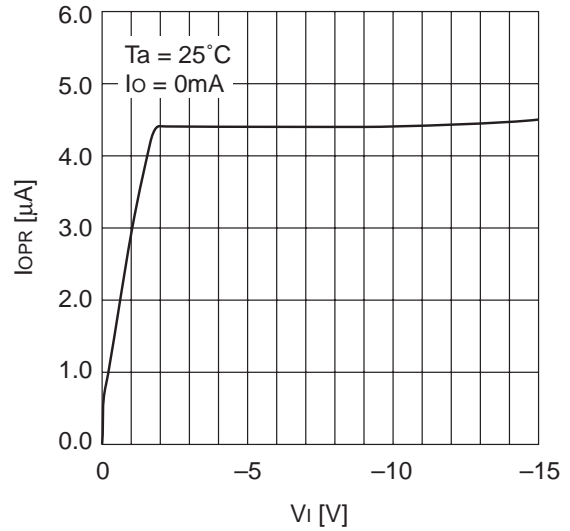


Vo vs. Io

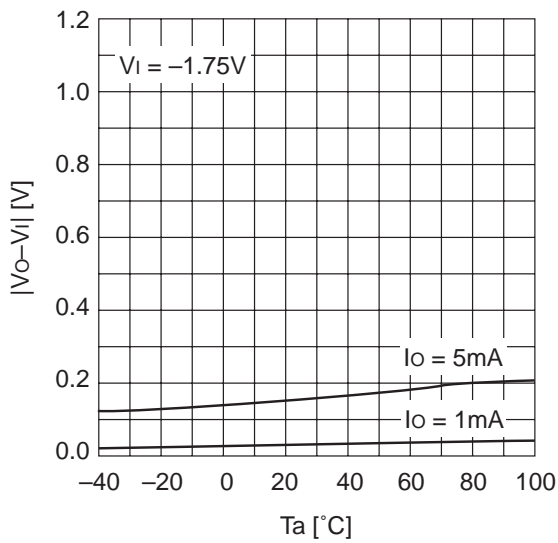
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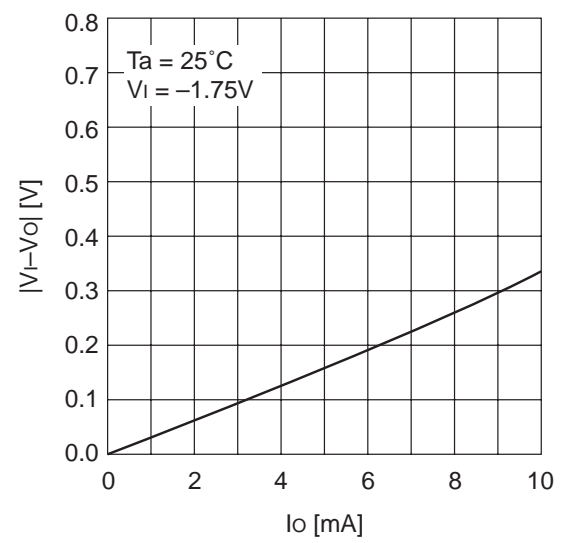
IOPR vs. Ta



IOPR vs. VI



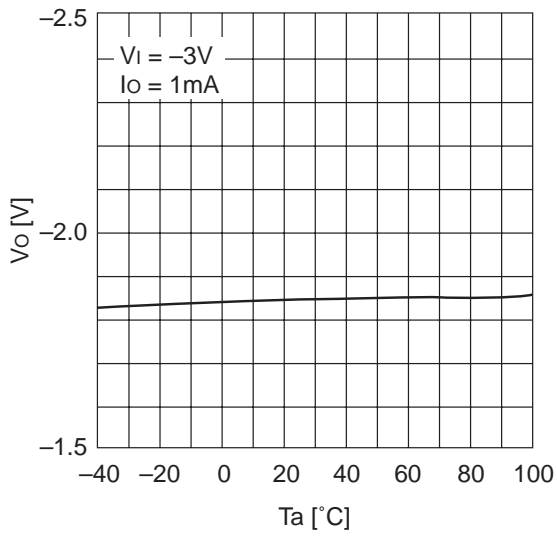
|Vo - VI| vs. Ta



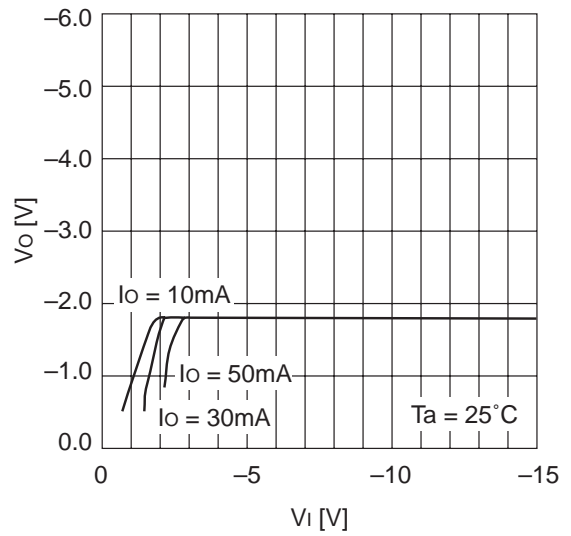
|VI - Vo| vs. Io

S1F79100Y Series

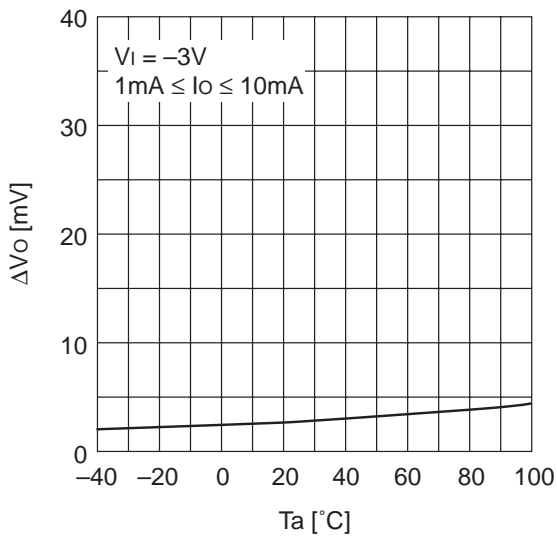
S1F79100Y Series



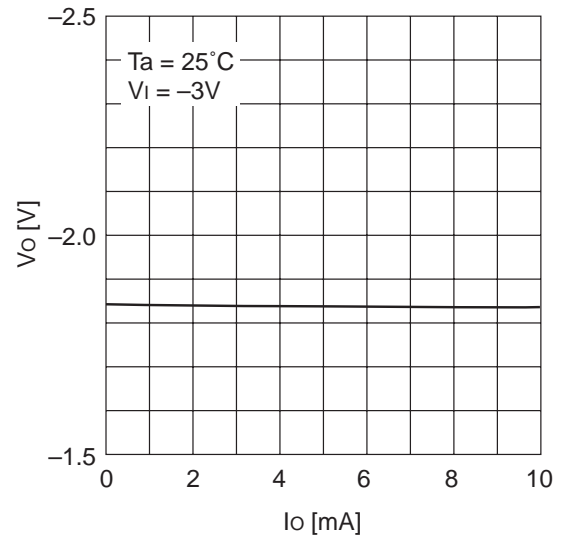
Vo vs. Ta



Vo vs. Vi

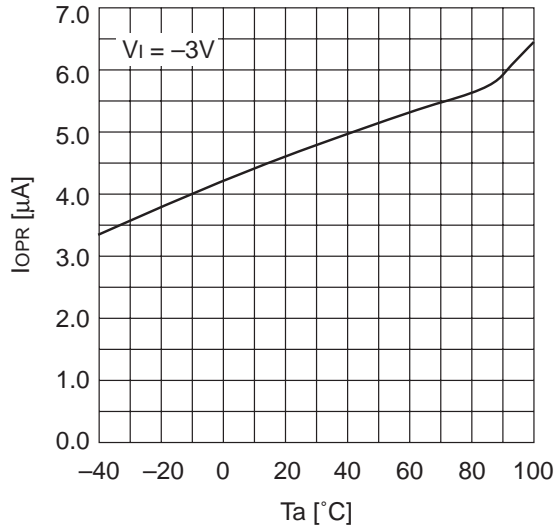


ΔVo vs. Ta

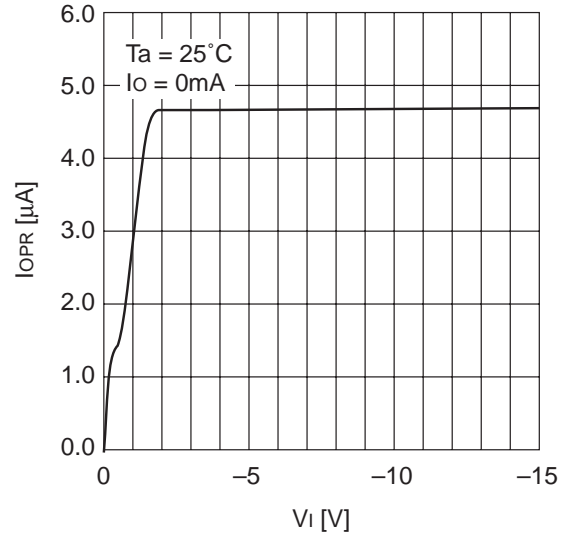


Vo vs. Io

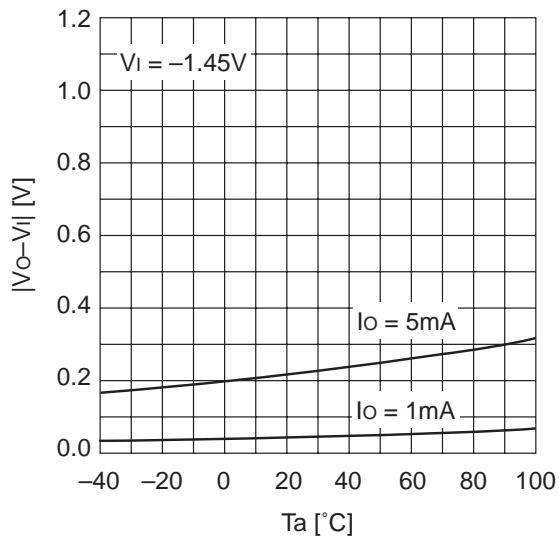
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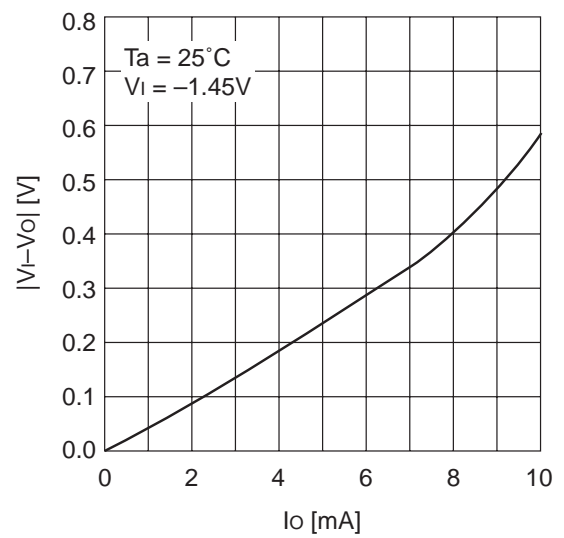
I_{OPR} vs. T_a



I_{OPR} vs. V_I



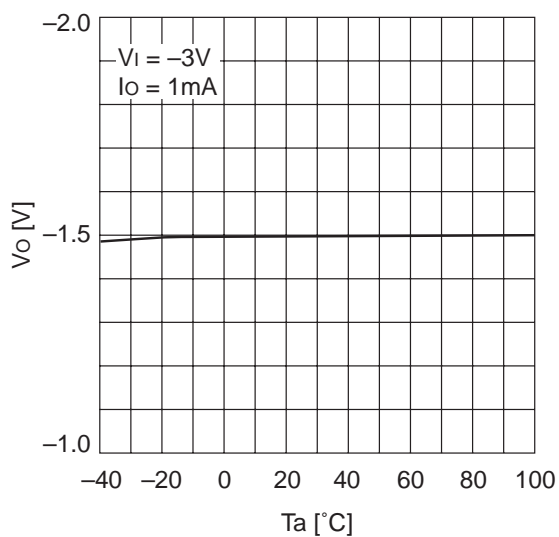
$|V_o - V_i|$ vs. T_a



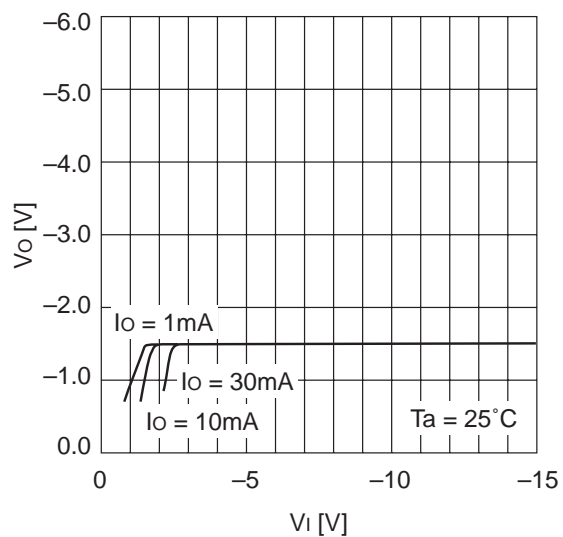
$|V_i - V_o|$ vs. I_o

S1F79100Y Series

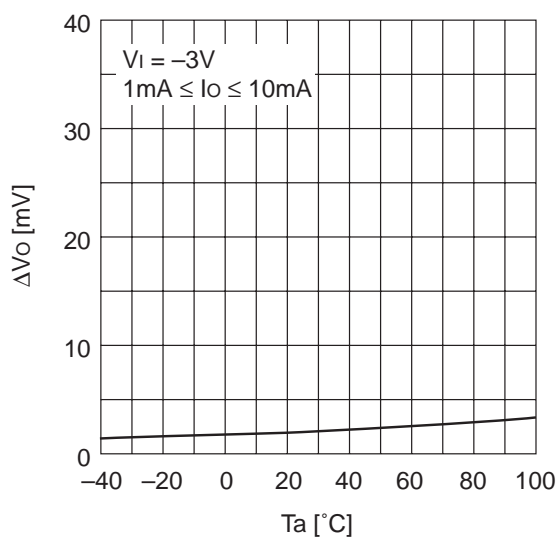
S1F79100Y Series



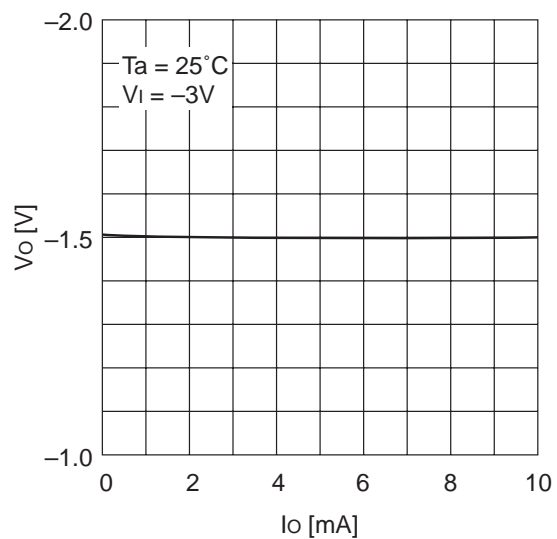
Vo vs. Ta



Vo vs. Vi



ΔVo vs. Ta



Vo vs. Io

PACKAGE MARKINGS

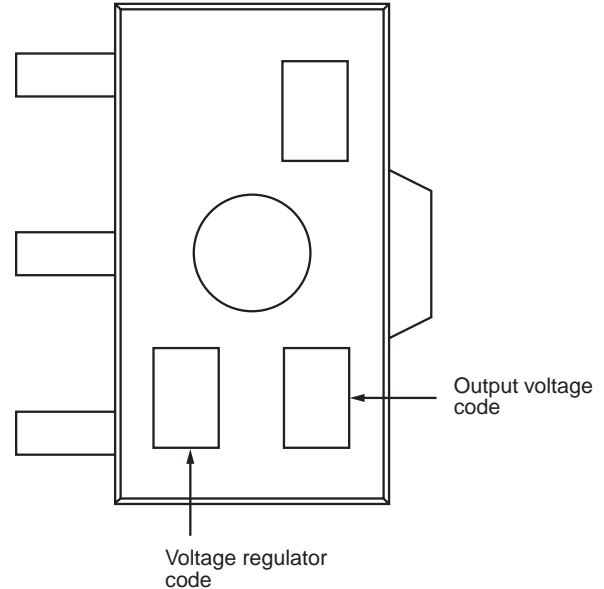
The markings on S1F79100Y series device packages use the following abbreviations.

Parameter	Code	Description
Output voltage code	B	5 V
	D	3 V
Voltage regulator code	P	Positive
	N	Negative

Note

The reflow furnace temperature profile requirements must be satisfied during package reflow. Avoid soldering on surface mount package (including SOT89) as it causes a quick temperature change of package and a device damage.

Marking locations

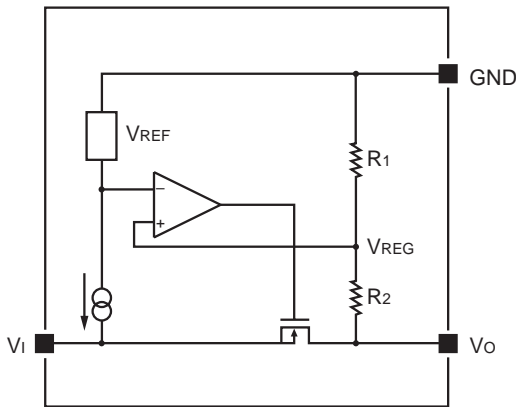


S1F79100Y Series

FUNCTIONAL DESCRIPTIONS

Basic Operation

The S1F79100Y series uses a 3-pin series regulator feedback loop. An operational amplifier compares VREG from the voltage divider formed by R1 and R2, with VREF. The amplifier output adjusts the output transistor gate bias to equalize the voltages and compensate for fluctuations in VI.



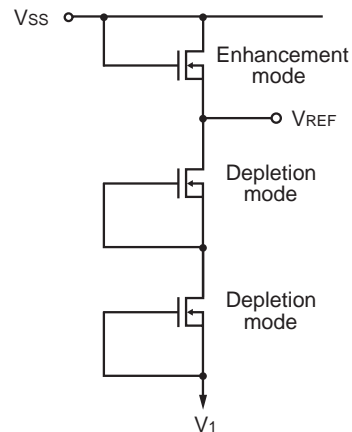
The following equation shows the relationship between VO and VREF.

$$V_O = \frac{R_1 + R_2}{R_1} V_{REF}$$

Internal Circuits

Reference voltage generator

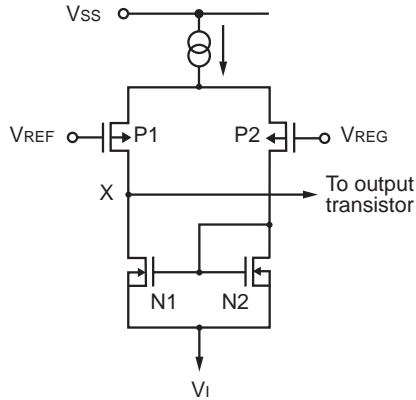
The offset structure used in all three transistors results in a high breakdown voltage that ensures a stable reference voltage output over a wide range of input voltages.



S1F79100Y Series

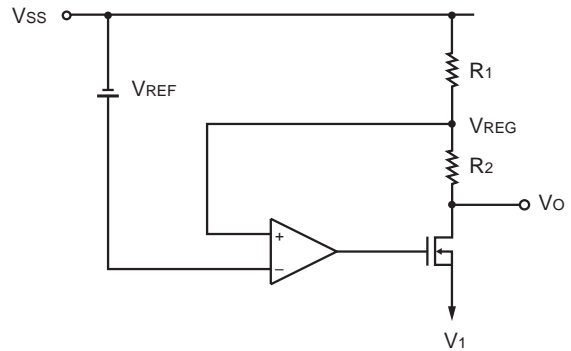
Differential amplifier

The built-in differential amplifier generates a potential at point X that adjusts the gate bias of the output transistor if there is any difference between VREF and VREG.



Output transistor

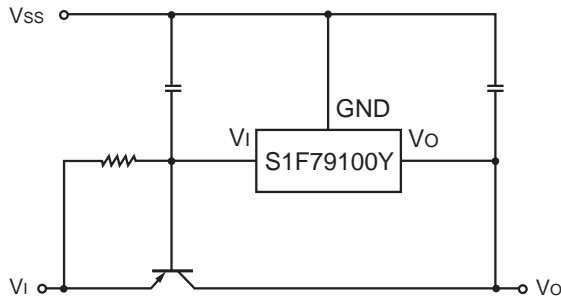
The output side of the p-channel MOS transistors in the output transistor circuit is connected to the voltage divider resistors in the feedback loop.



TYPICAL APPLICATIONS

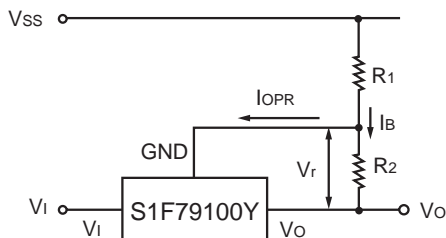
Current Booster

At the cost of a small increase in current consumption, the voltage is regulated while maintaining high current output.



External Voltage Converter

The following circuit raises the output voltage of a S1F79100Y series IC.

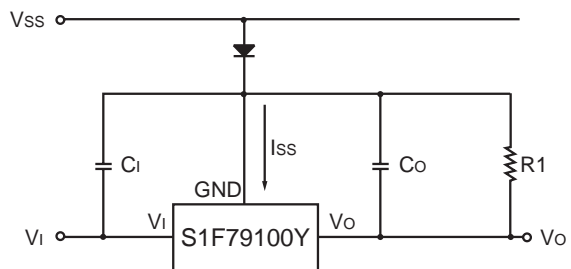


The following equation shows the relationship between the old and new voltages.

$$V_O = \frac{R_1 + R_2}{R_2} V_R$$

Note that the application must supply a bias current, I_B , high enough to offset the increase in voltage across R_1 due to I_{OPR} .

An alternative circuit for raising the output voltage is shown in the following figure.



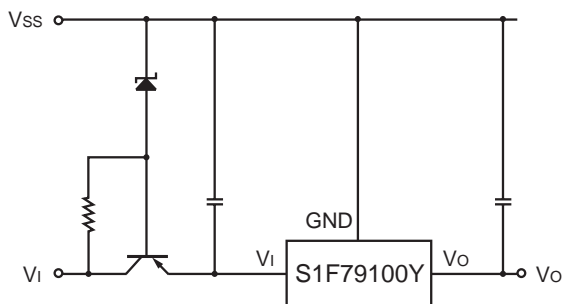
This configuration, however, introduces two design problems.

1. It reduces the output voltage by V_F , the forward voltage drop across the diode.
2. It is sensitive to fluctuations in V_F due to differences in diodes, operating temperatures and I_{SS} .

R_1 helps reduce the affect of I_{SS} on V_F . It is also required when I_{SS} is lower than the diode bias current. For certain input voltages, a Zener diode with the reverse polarity can be used.

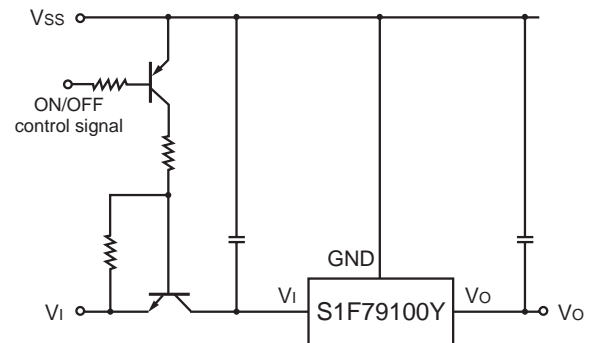
High Input Voltages

A preliminary regulator circuit is required to bring the input voltage within the S1F79100Y series rated range.



Switching Output

S1F79100Y series devices are designed for continuous operation. An external switching circuit allows the regulated output to be switched ON and OFF.



Note) Temperatures during reflow soldering must remain within the limits set out under LSI Device Precautions in this catalog. Do not immerse QFP and SOT89 packages during soldering, as the rapid temperature gradient during dipping can cause damage.

4. DC/DC Switching Regulators

The S1F76300 series of CMOS switching regulators comprises nine series—the S1F76310, S1F76380 series featuring built-in RC oscillators, the S1F76330 series requiring external crystal oscillators.

S1F76310, S1F76380 Series Built-in CR Oscillator Type CMOS Switching Regulators

DESCRIPTION

The S1F76310, S1F76380 series of CMOS switching regulators provide input voltage step-up and regulation to a specified fixed voltage using an external coil. The devices in these series incorporate precision, low-power reference voltage generators and transistors for driving an internal comparator. They feature low power consumption, low operating voltages, voltage detection and standby operation.

The devices offer a range of fixed output voltages, from 2.0 to 5.0V. The S1F76310 series features battery backup and power-on clear, the S1F76380 series features power-on clear and response compensation, the S1F76380 series offer an output voltage temperature characteristic for driving an LCD. They are available in SOP3-8pin.

FEATURES

- 0.9V (Min.) operating voltage
- 10 μ A (Typ.) maximum current consumption
- Standby operation
- 3 μ A (Typ.) standby current consumption
- 1.05 \pm 0.05V high-accuracy voltage detection
- Battery backup (available on S1F76310 series)
- On-chip CR oscillator
- Power-on clear (available on S1F76310 and S1F76380 series)
- Output voltage temperature characteristic for driving an LCD (available on S1F76380 series)
- SOP3-8pin

APPLICATIONS

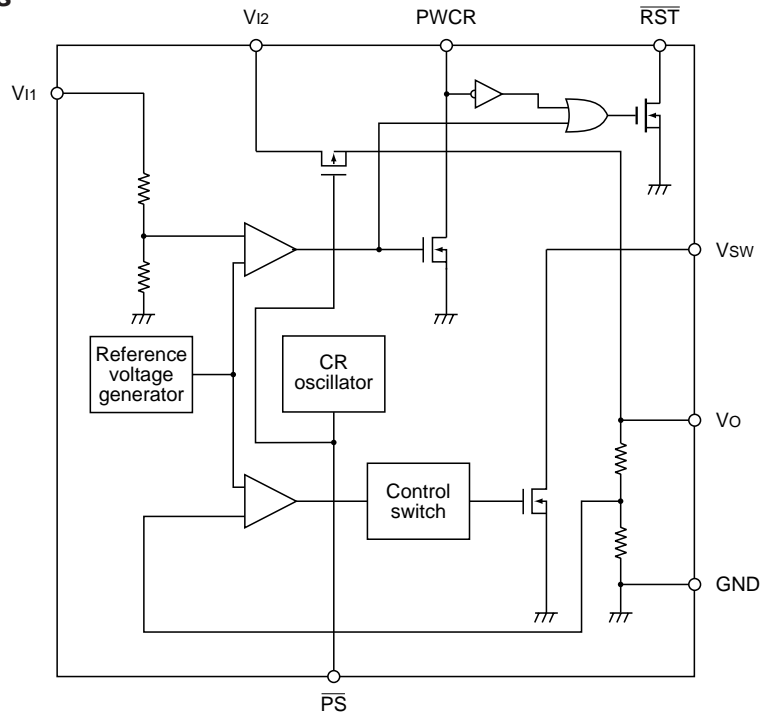
- Fixed-voltage power supplies for battery-operated equipment such as portable video cassette recorders, video cameras and radios
- Power supplies for pagers, memory cards, calculators and similar hand-held equipment
- Fixed-voltage power supplies for medical equipment
- Fixed-voltage power supplies for communications equipment
- Power supplies for microcomputers
- Uninterruptable power supplies
- Power supplies for LCD panel

LINEUP

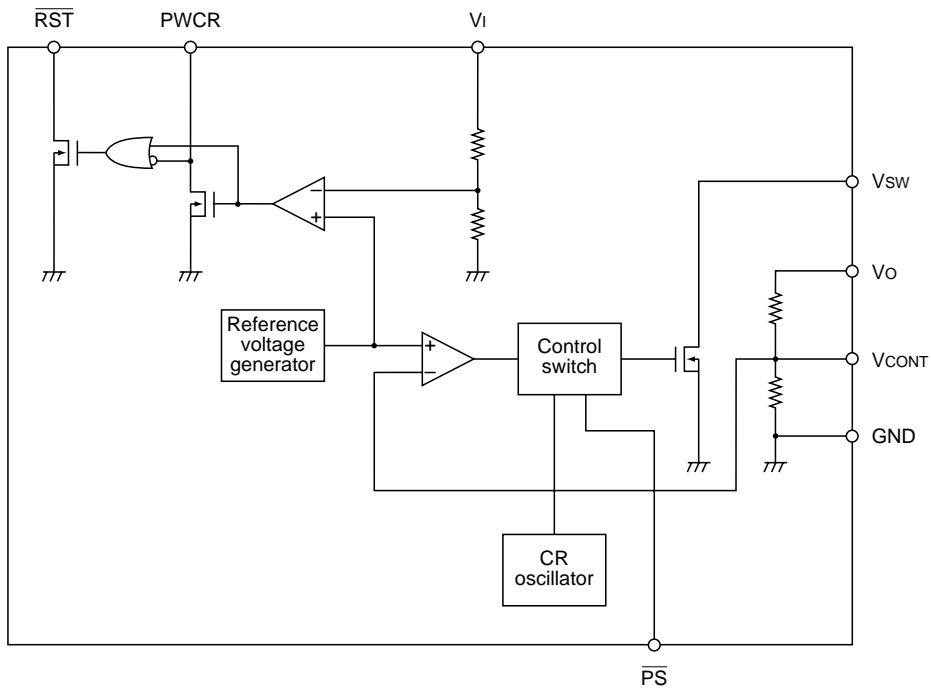
Product	Voltage (V)		Multiplication frequency source	Voltage detection	Power-on clear	Battery backup	Response compensation	Output voltage temperature characteristic	Package
	Input	Output							
S1F76310M1A0	1.5 (0.9 Min.)	5.0	On-chip CR oscillator	Yes	Yes	Yes	No	No	SOP3-8pin
S1F76310M1K0		3.5							SOP3-8pin
S1F76310M1B0		3.0							SOP3-8pin
S1F76310M1L0		2.4							SOP3-8pin
S1F76380M1L0	1.5 (0.9 Min.)	2.4	On-chip CR oscillator			No	Yes	- 4.0 mV/ $^{\circ}$ C	SOP3-8pin
S1F76380M1H0		2.2						- 4.5 mV/ $^{\circ}$ C	SOP3-8pin

S1F76300 Series

BLOCK DIAGRAMS
S1F76310 Series

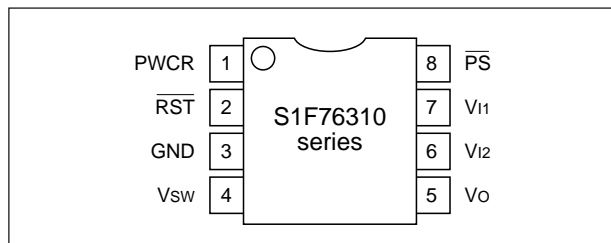


S1F76380 Series

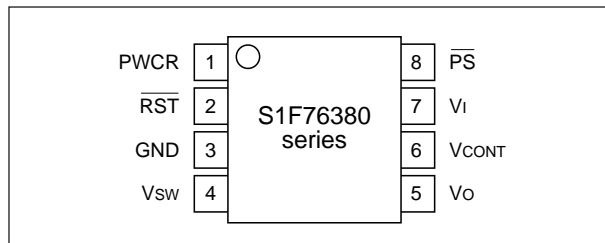


PIN ASSIGNMENTS

S1F76310 Series



S1F76380 Series



PIN DESCRIPTIONS

S1F76310 Series

Pin No.	Pin name	Description
1	PWCR	Power-on clear. See note 1.
2	RST	Reset signal output. See note 1.
3	GND	Ground
4	Vsw	External inductor drive
5	Vo	Output voltage
6	Vi2	Backup input voltage
7	Vi1	Step-up input voltage
8	PS	Power save. See note 2.

Notes

1. See voltage detection and power-on clear in the functional description.
2. See standby mode and battery backup in the functional description.

S1F76380 Series

Pin No.	Pin name	Description
1	PWCR	Power-on clear. See note 1.
2	RST	Reset signal output. See note 1.
3	GND	Ground
4	Vsw	External inductor drive
5	Vo	Output voltage
6	VCONT	Comparator input
7	Vi1	Step-up input voltage
8	PS	Power save. See note 2.

Notes

1. See voltage detection and power-on clear in the functional description.
2. See standby mode and battery backup in the functional description.

S1F76300 Series

SPECIFICATIONS

Absolute Maximum Ratings

S1F76310 series

 $V_{SS} = 0V, T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Rating	Unit
Input voltage	V_{I1}	7	V
Output current	I_o	100	mA
Output voltage	V_o	7	V
Power dissipation	P_D	200 (SOP3) 300 (DIP)	mW
Operating temperature range	T_{opr}	-30 to +85	$^{\circ}\text{C}$
Storage temperature range	T_{stg}	-65 to +150	$^{\circ}\text{C}$
Soldering temperature (for 10 s). See note.	T_{sol}	260	$^{\circ}\text{C}$

Notes

Temperatures during reflow soldering must remain within the limits set out in LSI Device Precautions. Never use solder dip to mount S1F70000 series power supply devices.

S1F76380 series

 $V_{SS} = 0V, T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Rating	Unit
Input voltage	V_{I1}	7	V
Output current	I_o	100	mA
Output voltage	V_o	7	V
Power dissipation	P_D	200 (SOP3) 300 (DIP)	mW
Operating temperature range	T_{opr}	-30 to +85	$^{\circ}\text{C}$
Storage temperature range	T_{stg}	-65 to +150	$^{\circ}\text{C}$
Soldering temperature (for 10 s). See note.	T_{sol}	260	$^{\circ}\text{C}$

Notes

Temperatures during reflow soldering must remain within the limits set out in LSI Device Precautions. Never use solder dip to mount S1F70000 series power supply devices.

Electrical Characteristics

S1F76310M1L0

V_{SS} = 0V, Ta = 25 °C unless otherwise noted

Parameter	Symbol	Condition	Rating			Unit
			Min.	Typ.	Max.	
Input voltage	V _{I1}	V _O > V _{I2}	0.9	—	1.8	V
	V _{I2}		0.9	—	1.8	V
Output voltage	V _O	V _{I1} = 1.5V	2.32	2.40	2.48	V
Detection voltage	V _{DET}		1.00	1.05	1.10	V
Detection voltage hysteresis ratio	ΔV _{DET}		—	5	—	%
Operating current	I _{DDO}	V _{I1} = 1.5V, I _O = 1.0mA	—	7	35	μA
Standby current	I _{DDS}	V _{I1} = 1.5V	—	3	10	μA
Switching transistor ON resistance	R _{SWON}	V _{I1} = 1.5V, V _O = 2.4V, V _{SW} = 0.2V	—	7	14	Ω
Switching transistor leakage current	I _{SWQ}	V _{I1} = 1.5V, V _O = 1.5V, V _{SW} = 7.0V	—	—	0.5	μA
Backup switch ON resistance	R _{BSON}	V _{I1} = 1.0V, V _{I2} = 1.5V, I _O = 1.0mA	—	100	250	Ω
Backup switching leakage current	I _{BSQ}	V _{I1} = 1.0V, V _O = 2.4V, V _{I2} = 2.0V	—	—	0.1	μA
$\overline{\text{RST}}$ Low-level output current	I _{OL}	V _{I1} = 0.9V, V _{DS} = 0.2V	0.05	0.15	—	mA
PS pull-up current	I _{IH}	V _{I1} = 1.5V	—	—	0.5	μA
Multiplication clock frequency	f _{CLK}	V _{I1} = 1.5V	25	35	45	kHz

S1F76310M1B0

V_{SS} = 0V, Ta = 25 °C unless otherwise noted

Parameter	Symbol	Condition	Rating			Unit
			Min.	Typ.	Max.	
Input voltage	V _{I1}	V _O > V _{I2}	0.9	—	2.0	V
	V _{I2}		0.9	—	2.0	V
Output voltage	V _O	V _{I1} = 1.5V	2.90	3.00	3.10	V
Detection voltage	V _{DET}		1.00	1.05	1.10	V
Detection voltage hysteresis ratio	ΔV _{DET}		—	5	—	%
Operating current	I _{DDO}	V _{I1} = 1.5V, I _O = 1.0mA	—	8	40	μA
Standby current	I _{DDS}	V _{I1} = 1.5V	—	3	10	μA
Switching transistor ON resistance	R _{SWON}	V _{I1} = 1.5V, V _O = 3.0V, V _{SW} = 0.2V	—	6	12	Ω
Switching transistor leakage current	I _{SWQ}	V _{I1} = 1.5V, V _O = 1.5V, V _{SW} = 7.0V	—	—	0.5	μA
Backup switch ON resistance	R _{BSON}	V _{I1} = 1.0V, V _{I2} = 2.0V, I _O = 1.0mA	—	70	160	Ω
Backup switching leakage current	I _{BSQ}	V _{I1} = 1.0V, V _O = 3.0V, V _{I2} = 2.0V	—	—	0.1	μA
$\overline{\text{RST}}$ Low-level output current	I _{OL}	V _{I1} = 0.9V, V _{DS} = 0.2V	0.05	0.15	—	mA
PS pull-up current	I _{IH}	V _{I1} = 1.5V	—	—	0.5	μA
Multiplication clock frequency	f _{CLK}	V _{I1} = 1.5V	30	40	50	kHz

S1F76300 Series

S1F76310M1K0

V_{SS} = 0V, T_a = 25 °C unless otherwise noted

Parameter	Symbol	Condition	Rating			Unit
			Min.	Typ.	Max.	
Input voltage	V _{I1}	V _O > V _{I2}	0.9	—	2.0	V
	V _{I2}		0.9	—	2.0	V
Output voltage	V _O	V _{I1} = 1.5V	3.40	3.50	3.60	V
Detection voltage	V _{DET}		1.00	1.05	1.10	V
Detection voltage hysteresis ratio	ΔV _{DET}		—	5	—	%
Operating current	I _{DDO}	V _{I1} = 1.5V, I _O = 1.0mA	—	8	40	μA
Standby current	I _{DDS}	V _{I1} = 1.5V	—	3	10	μA
Switching transistor ON resistance	R _{SWON}	V _{I1} = 1.5V, V _O = 3.5V, V _{SW} = 0.2V	—	6	12	Ω
Switching transistor leakage current	I _{SWQ}	V _{I1} = 1.5V, V _O = 1.5V, V _{SW} = 7.0V	—	—	0.5	μA
Backup switch ON resistance	R _{BSON}	V _{I1} = 1.0V, V _{I2} = 2.0V, I _O = 1.0mA	—	70	160	Ω
Backup switching leakage current	I _{BSQ}	V _{I1} = 1.0V, V _O = 3.5V, V _{I2} = 2.0V	—	—	0.1	μA
R _{ST} Low-level output current	I _{OL}	V _{I1} = 0.9V, V _{DS} = 0.2V	0.05	0.15	—	mA
PS pullup current	I _{IH}	V _{I1} = 1.5V	—	—	0.5	μA
Multiplication clock frequency	f _{CLK}	V _{I1} = 1.5V	30	40	50	kHz

S1F76310M1A0

V_{SS} = 0V, T_a = 25 °C unless otherwise noted

Parameter	Symbol	Condition	Rating			Unit
			Min.	Typ.	Max.	
Input voltage	V _{I1}	V _O > V _{I2}	0.9	—	2.0	V
	V _{I2}		0.9	—	2.0	V
Output voltage	V _O	V _{I1} = 1.5V	4.80	5.00	5.20	V
Detection voltage	V _{DET}		1.00	1.05	1.10	V
Detection voltage hysteresis ratio	ΔV _{DET}		—	5	—	%
Operating current	I _{DDO}	V _{I1} = 1.5V, I _O = 1.0mA	—	10	50	μA
Standby current	I _{DDS}	V _{I1} = 1.5V	—	3	10	μA
Switching transistor ON resistance	R _{SWON}	V _{I1} = 1.5V, V _O = 5.0V, V _{SW} = 0.2V	—	5	10	Ω
Switching transistor leakage current	I _{SWQ}	V _{I1} = 1.5V, V _O = 1.5V, V _{SW} = 7.0V	—	—	0.5	μA
Backup switch ON resistance	R _{BSON}	V _{I1} = 1.0V, V _{I2} = 3.0V, I _O = 1.0mA	—	50	100	Ω
Backup switching leakage current	I _{BSQ}	V _{I1} = 1.0V, V _O = 5.0V, V _{I2} = 3.0V	—	—	0.1	μA
R _{ST} Low-level output current	I _{OL}	V _{I1} = 0.9V, V _{DS} = 0.2V	0.05	0.15	—	mA
PS pullup current	I _{IH}	V _{I1} = 1.5V	—	—	0.5	μA
Multiplication clock frequency	f _{CLK}	V _{I1} = 1.5V	35	45	55	kHz

S1F76380M1H0

V_{SS} = 0V, T_a = 25 °C unless otherwise noted

Parameter	Symbol	Condition	Rating			Unit
			Min.	Typ.	Max.	
Input voltage	V _{I1}		0.9	—	2.0	V
Output voltage	V _O	V _{I1} = 1.5V	2.10	2.20	2.30	V
Output voltage temperature gradient	K _t		-5.5	-4.5	-3.5	mV/°C
Detection voltage	V _{DET}		1.00	1.05	1.10	V
Detection voltage hysteresis ratio	ΔV _{DET}		—	5	—	%
Operating current	I _{DDO}	V _{I1} = 1.5V, I _O = 1.0mA	—	7	35	μA
Standby current	I _{DDS}	V _{I1} = 1.5V	—	3	10	μA
Switching transistor ON resistance	R _{SWON}	V _{I1} = 1.5V, V _O = 2.2V, V _{SW} = 0.2V	—	7	14	Ω
Switching transistor leakage current	I _{SWQ}	V _{I1} = 1.5V, V _O = 1.5V, V _{SW} = 7.0V	—	—	0.5	μA
R _{ST} Low-level output current	I _{OL}	V _{I1} = 0.9V, V _{OL} = 0.2V	0.05	0.15	—	mA
$\overline{\text{PS}}$ pullup current	I _{IH}	V _{I1} = 1.5V	—	—	0.5	μA
Multiplication clock frequency	f _{CLK}	V _{I1} = 1.5V	25	35	45	kHz

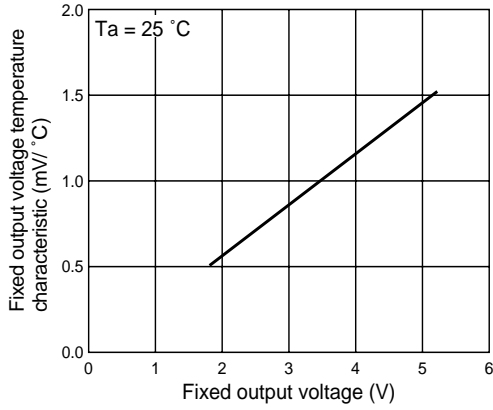
S1F76380M1L0

V_{SS} = 0V, T_a = 25 °C unless otherwise noted

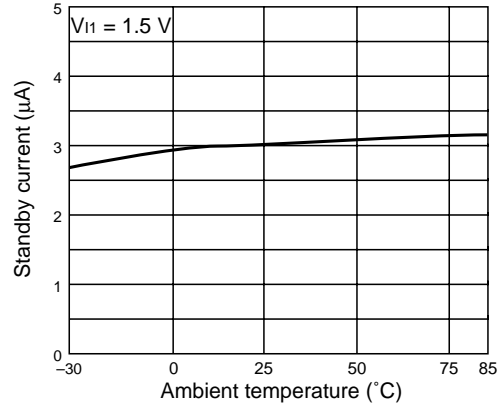
Parameter	Symbol	Condition	Rating			Unit
			Min.	Typ.	Max.	
Input voltage	V _{I1}		0.9	—	2.0	V
Output voltage	V _O	V _{I1} = 1.5V	2.30	2.40	2.50	V
Output voltage temperature gradient	K _t		-5.5	-4.0	-3.5	mV/°C
Detection voltage	V _{DET}		1.00	1.05	1.10	V
Detection voltage hysteresis ratio	ΔV _{DET}		—	5	—	%
Operating current	I _{DDO}	V _{I1} = 1.5V, I _O = 1.0mA	—	7	35	μA
Standby current	I _{DDS}	V _{I1} = 1.5V	—	3	10	μA
Switching transistor ON resistance	R _{SWON}	V _{I1} = 1.5V, V _O = 2.4V, V _{SW} = 0.2V	—	7	14	Ω
Switching transistor leakage current	I _{SWQ}	V _{I1} = 1.5V, V _O = 1.5V, V _{SW} = 7.0V	—	—	0.5	μA
R _{ST} Low-level output current	I _{OL}	V _{I1} = 0.9V, V _{OL} = 0.2V	0.05	0.15	—	mA
$\overline{\text{PS}}$ pullup current	I _{IH}	V _{I1} = 1.5V	—	—	0.5	μA
Multiplication clock frequency	f _{CLK}	V _{I1} = 1.5V	25	35	45	kHz

S1F76300 Series

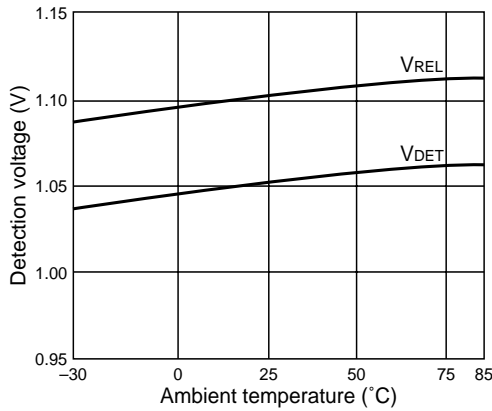
Typical Performance Characteristics



Fixed-output voltage temperature characteristic

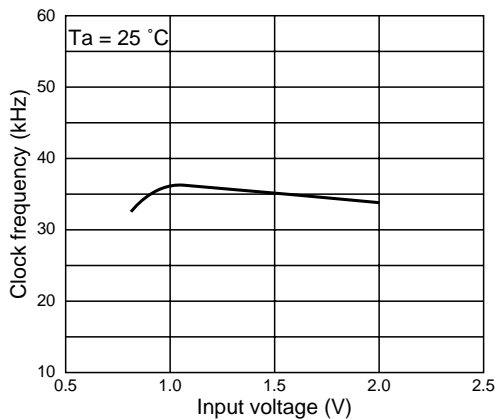


Standby current vs. ambient temperature

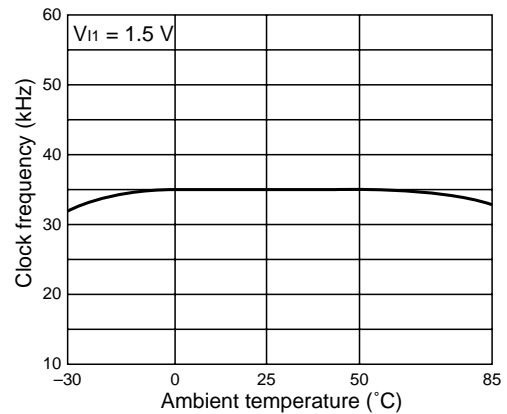


Detection voltage vs. ambient temperature

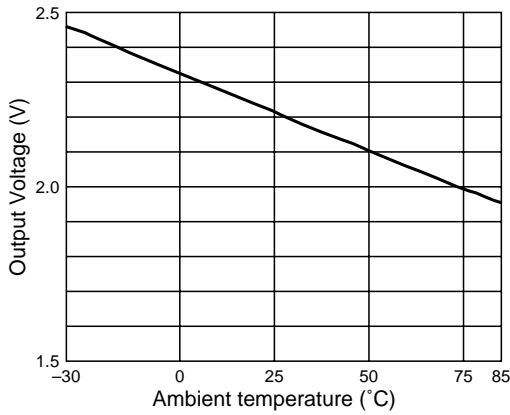
S1F76380M1H0 and S1F76380M1L0



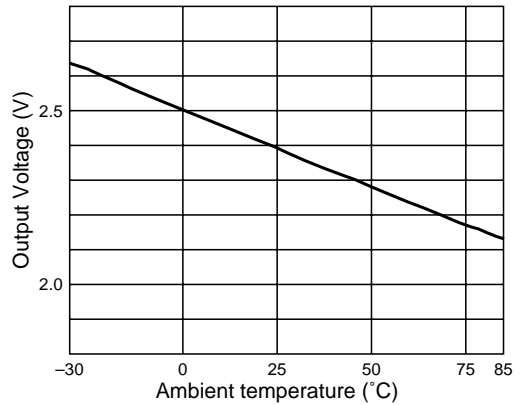
Clock frequency vs. Input voltage



Clock frequency vs. ambient temperature

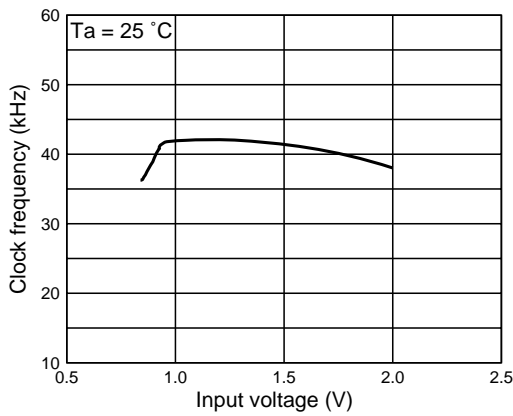


Output voltage vs. ambient temperature (S1F76380M1H0)

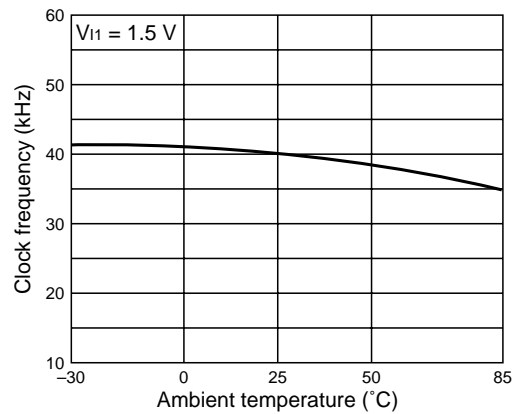


Output voltage vs. ambient temperature (S1F76380M1L0)

S1F76310M1B0, S1F76310M1K0

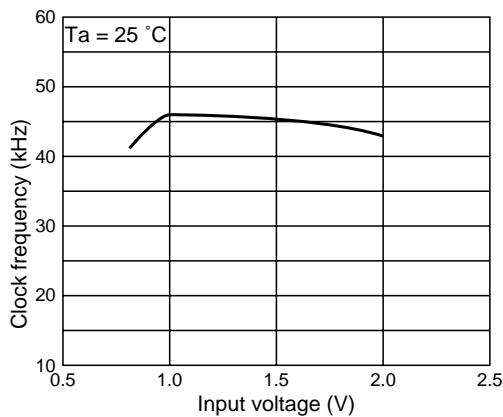


Clock frequency vs. input voltage

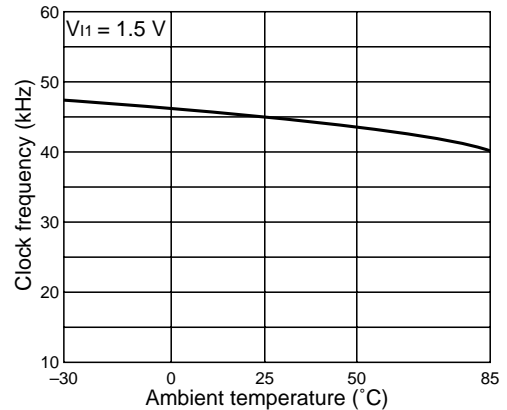


Clock frequency vs. ambient temperature

S1F76310M1A0



Clock frequency vs. input voltage

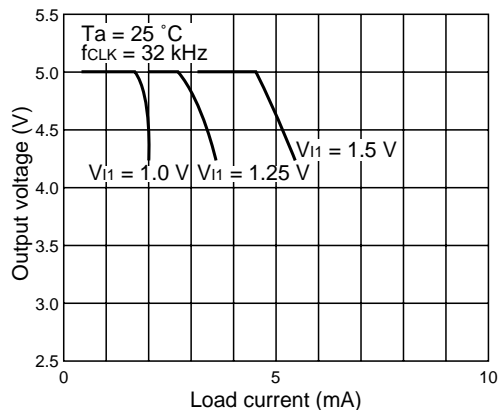


Clock frequency vs. ambient temperature

S1F76300 Series

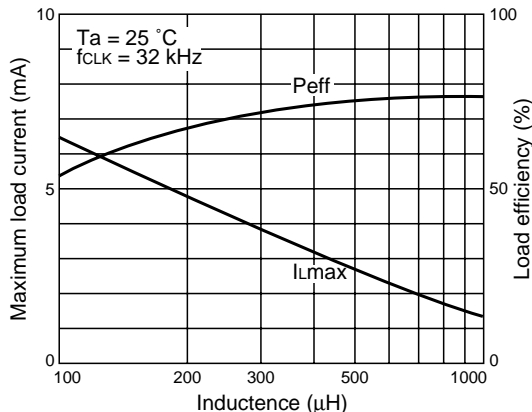
S1F76300 Series

Load Characteristics S1F76310M1A0



Notes

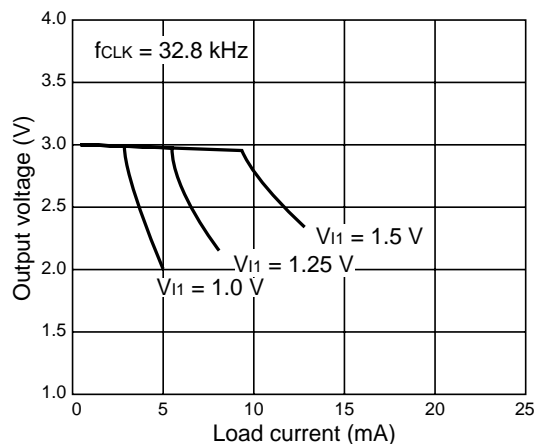
Inductor: TDK NLF453232-221k (220 μH)
 Diode: Shindengen DINS4 Schottky barrier diode
 Capacitor: NEC MSUB20J106M (10 μF)



Notes

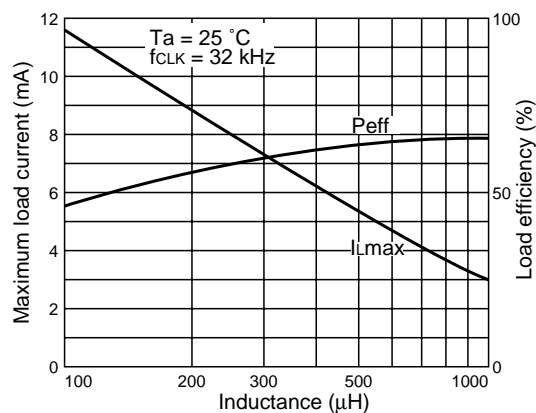
- $V_{I1} = 1.5\text{ V}$
- Inductor: TDK NLF453232 series
 Diode: Shindengen DINS4 Schottky barrier diode
 Capacitor: NEC MSUB20J106M (10 μF)

S1F76310M1B0



Notes

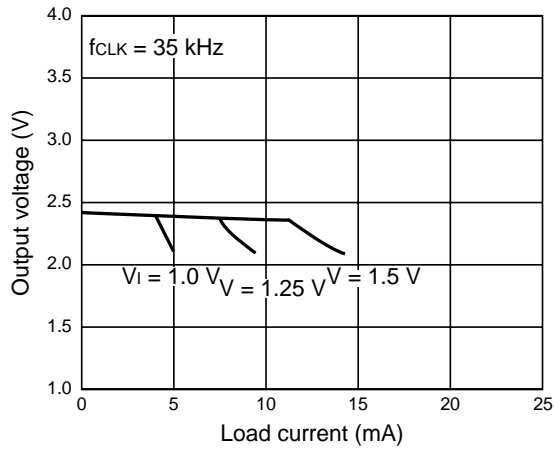
Inductor: TDK NLF453232-221k (220 μH)
 Diode: Shindengen DINS4 Schottky barrier diode
 Capacitor: NEC MSUB20J106M (10 μF)



Notes

- $V_{I1} = 1.5\text{ V}$
- Inductor: TDK NLF453232 series
 Diode: Shindengen DINS4 Schottky barrier diode
 Capacitor: NEC MSUB20J106M (10 μF)

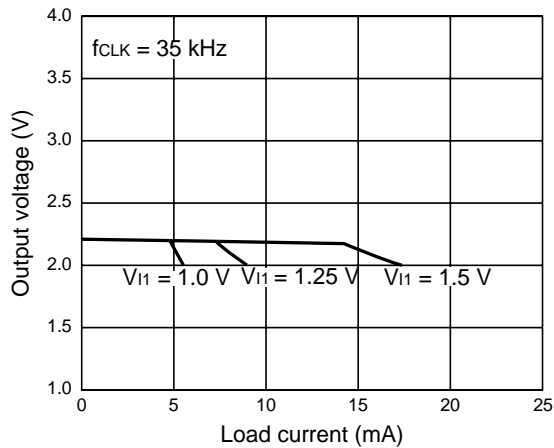
S1F76380M1L0



Notes

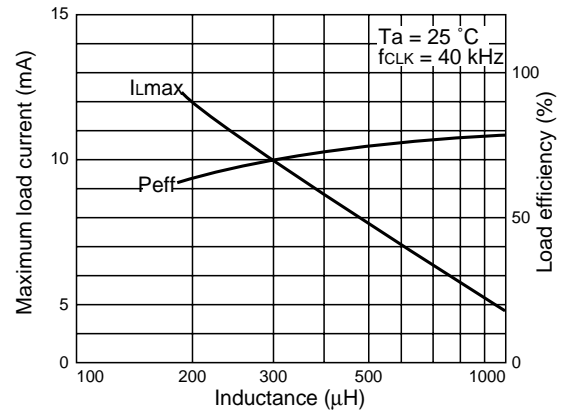
Inductor: TDK NLF453232-221k (220μH)
 Diode: Shindengen DINS4 Schottky barrier diode
 Capacitor: NEC MSUB20J106M (10μF)

S1F76380M1H0



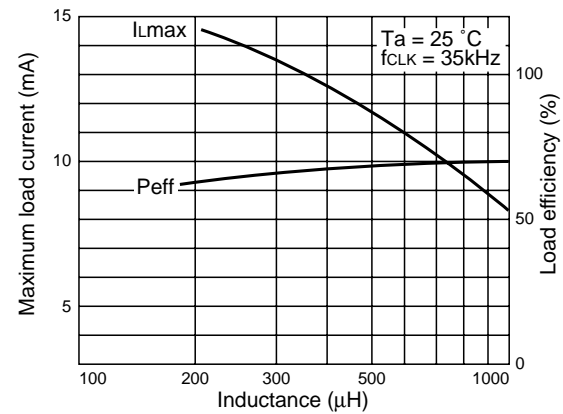
Notes

Inductor: TDK NLF453232-221k (220μH)
 Diode: Shindengen DINS4 Schottky barrier diode
 Capacitor: NEC MSUB20J106M (10μF)



Notes

1. $V_{I1} = 1.5V$
2. Inductor: TDK NLF453232 series
 Diode: Shindengen DINS4 Schottky barrier diode
 Capacitor: NEC MSUB20J106M (10μF)



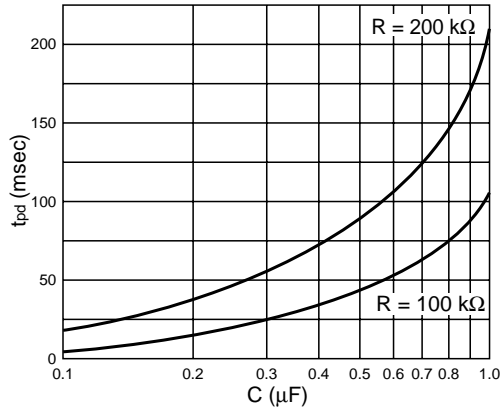
Notes

1. $V_{I1} = 1.5V$
2. Inductor: TDK NLF453232 series
 Diode: Shindengen DINS4 Schottky barrier diode
 Capacitor: NEC MSUB20J106M (10μF)

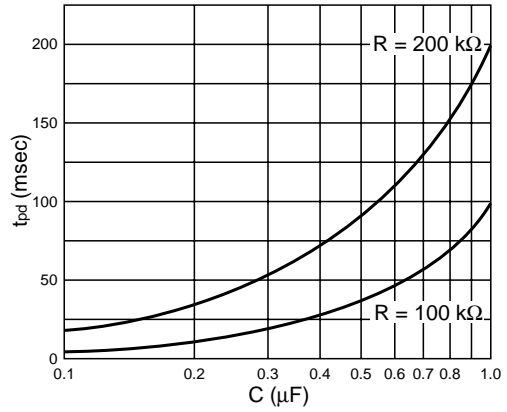
S1F76300 Series

S1F76300 Series

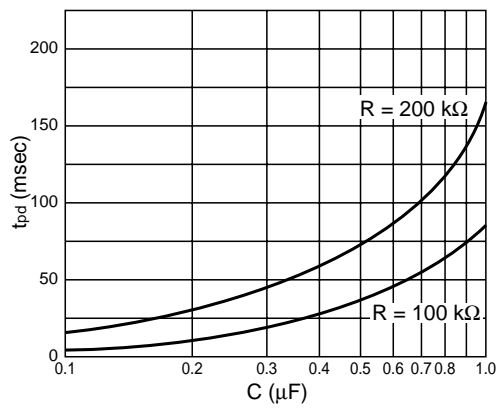
Reset delays S1F76310M1A0



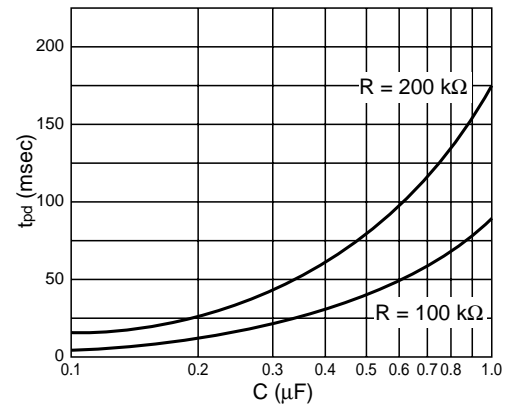
S1F76310M1K0



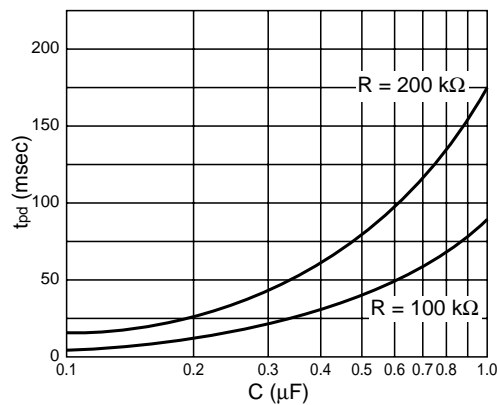
S1F76310M1B0



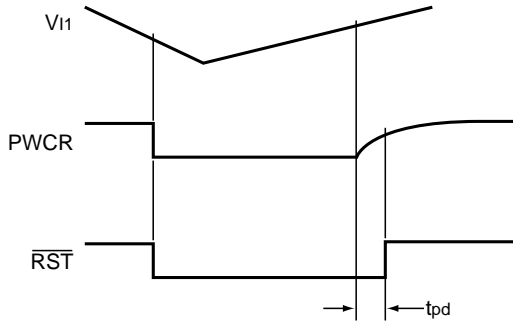
S1F76310M1L0 and S1F76380M1L0



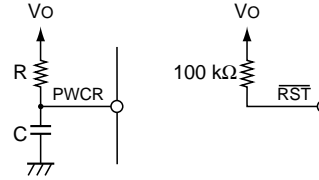
S1F76380M1H0



Timing diagram

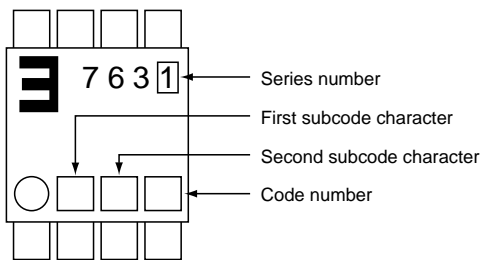


Measurement circuit



PACKAGE MARKINGS

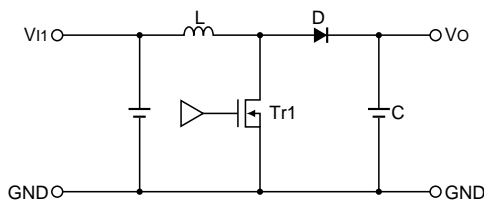
S1F76310, S1F76380 series device packages use the following markings.



FUNCTIONAL DESCRIPTIONS

Basic Voltage Booster Operation

Tr1 switches ON and OFF at half the frequency of the clock pulses from the built-in RC oscillator. When the transistor is ON, the circuit stores energy in L. When it is off, this energy flows through D to charge C.

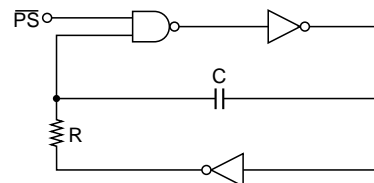


Internal Circuits

CR oscillator

The S1F76310, S1F76380 series use a built-in CR oscillator to drive the voltage booster circuit. The circuit is supplied by V11. All circuit components are on-chip and thus the drive frequency is set internally. To ensure 50% duty, this frequency is twice that used by the voltage booster circuit.

When PS is Low, the oscillator is disabled and the chip is in standby mode.

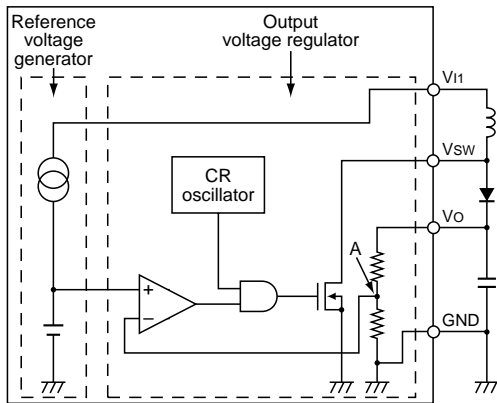


S1F76300 Series

Reference voltage generator and output voltage regulator

The reference voltage generator regulates V_{I1} to generate a voltage for the voltage regulator and voltage detection circuits.

The voltage regulator regulates the boosted output voltage. This is determined by the level at point A between the two resistors connecting V_O and GND. These series use an on-chip resistor to set the output at a specified voltage.



Note

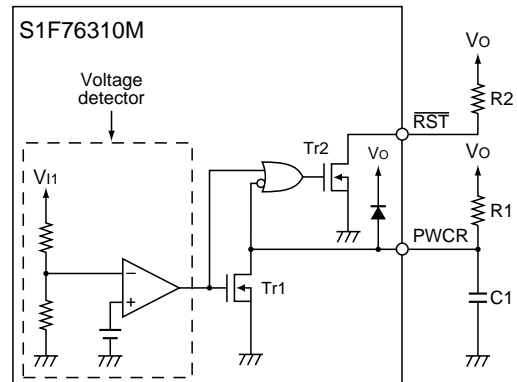
In step-up voltage operation, the ripple voltage created by the switching operation is large relative to the output voltage described above. This ripple voltage is affected by external components and load conditions. The user is advised to check this voltage carefully.

Voltage detection

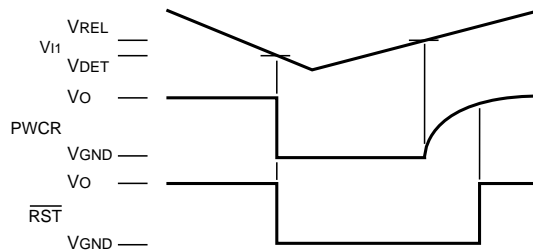
The S1F76310, S1F76380 series are equipped with a built-in voltage detection function. The detection voltage, V_{DET} , is fixed internally at $1.05 \pm 0.05V$.

Power-on clear function

The S1F76310 series and S1F76380 series are equipped with a built-in power-on clear function. As shown in the following figure, R1 and C1 are connected to PWCR, and R2 is connected to \overline{RST} to operate the function. If V_{I1} drops below V_{DET} , Tr1 and Tr2 conduct and PWCR and \overline{RST} are grounded. If V_{I1} recovers and rises higher than V_{REL} , Tr1 turns OFF. The detection voltage hysteresis is 5% (Typ.) and V_{REL} is $V_{DET} \times 1.05$ (Typ.).

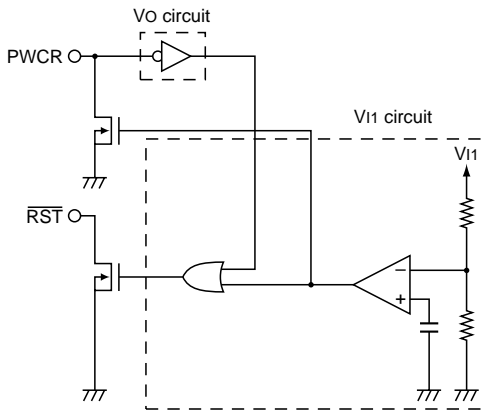


V_O returns to its normal value when the voltage of PWCR increases and Tr2 turns OFF, so that \overline{RST} returns to V_O after a delay specified by the time coefficient of R1 and C1. Thus, after normal output has been obtained, a reset pulse of adjustable width can be obtained which can reset a system connected to \overline{RST} . The output from \overline{RST} is an N-channel, open-drain. When V_{I1} exceeds V_{DET} , the drain is opened and, when V_{I1} drops below V_{DET} again, the output transistor conducts and the output is grounded. The characteristic response is shown in the following figure.



Disabling power-on clear

Always connect PWCR to either V_O or GND. If voltage detection only is required, remove the resistor between PWCR and V_O and monitor the level at \overline{RST} . If neither function is required, connect PWCR to GND. Leaving PWCR unconnected results in an undefined inverter gate voltage in the V_O circuit, causing transient currents to flow between V_O and GND.



Output voltage response compensation

The S1F76380 series are provided with a response compensation input. A response compensation capacitor is connected between VCONT and VO, allowing the ripple voltage generated by the boosted output voltage to be suppressed to a minimum.

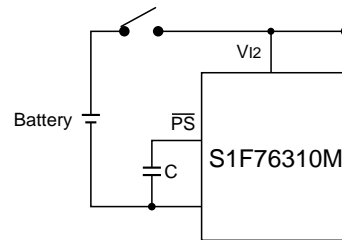
Standby mode and battery backup

The S1F76310 series are equipped with a standby mode, initiated by connecting PS to GND.

In standby mode, the booster, including the crystal oscillator, is disabled (the switching transistor used to drive the inductor is turned OFF) and the built-in backup switch is turned ON, so that the input voltage at V12 is output at VO. This enables the battery backup function. PS is pulled-up internally, so when standby mode is not required, the pin should be left open.

Powering up

Ensure that VO is at least the minimum operating voltage (0.9V) before switching on the booster circuit. One way to do this is to attach a battery so that VO never drops below the minimum required for backup mode. If no such external power supply is available, connect V12 to V11 and hold PS Low when applying power for the first time.



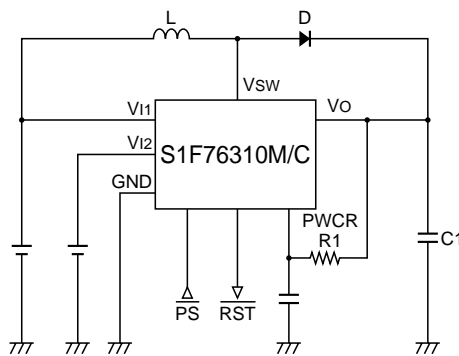
TYPICAL APPLICATIONS

Example Circuits

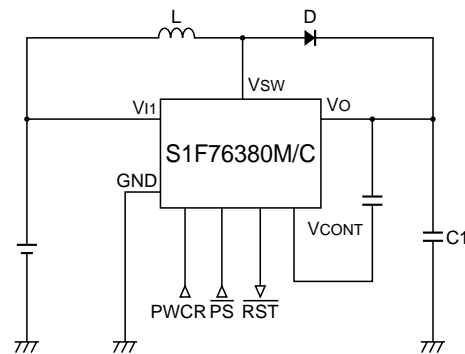
The output current, IO, and power conversion efficiency, Peff of a particular device in a series depends on

factors such as the switching frequency, type of coil, and the size and type of other external components.

S1F76310 series



S1F76380 series



S1F76300 Series

S1F76300 Series

Notes

■ $100\mu\text{H} \leq L \leq 1\text{mH}$, $C \leq 10\mu\text{F}$, D = Schottky diode

■ S1F76310M1A0

- $P_{\text{eff}} = 70\%$ when $L = 220\mu\text{H}$ (leadless inductor),
 $V_{\text{II}} = 1.5\text{V}$, $f_{\text{CLK}} = 32\text{kHz}$, $I_{\text{O}} = 4\text{mA}$
- $P_{\text{eff}} = 75\%$ when $L = 220\mu\text{H}$ (drum coil),
 $V_{\text{II}} = 1.5\text{V}$, $f_{\text{CLK}} = 32\text{kHz}$, $I_{\text{O}} = 6\text{mA}$
- $P_{\text{eff}} = 80\%$ when $L = 300\mu\text{H}$ (toroidal coil),
 $V_{\text{II}} = 1.5\text{V}$, $f_{\text{CLK}} = 32\text{kHz}$, $I_{\text{O}} = 7\text{mA}$

■ S1F76310M1B0

- $P_{\text{eff}} = 70\%$ when $L = 220\mu\text{H}$ (leadless inductor),
 $V_{\text{II}} = 1.5\text{V}$, $f_{\text{CLK}} = 32\text{kHz}$, $I_{\text{O}} = 8\text{mA}$
- $P_{\text{eff}} = 75\%$ when $L = 220\mu\text{H}$ (drum coil),
 $V_{\text{II}} = 1.5\text{V}$, $f_{\text{CLK}} = 32\text{kHz}$, $I_{\text{O}} = 9\text{mA}$
- $P_{\text{eff}} = 80\%$ when $L = 300\mu\text{H}$ (toroidal coil),
 $V_{\text{II}} = 1.5\text{V}$, $f_{\text{CLK}} = 32\text{kHz}$, $I_{\text{O}} = 10\text{mA}$

External components

The performance characteristics of switching regulators depend greatly on the choice of external components. Observing the following guidelines will ensure high performance and maximum efficiency.

Inductor

Use an inductor with low direct-current resistance and low losses.

Leadless

Pre-wound, leadless inductors using surface-mount technology are the most suitable for portable equipment and other space-critical applications.

Drum coil

Avoid using drum coils because their magnetic field can induce noise.

Toroidal coil

Use a toroidal coil to virtually eliminate magnetic field leakage, reduce losses and improve performance.

Diode

Use a Schottky barrier diode with a high switching speed and low forward voltage drop, V_{F} .

Capacitor

To minimize ripple voltages, use a capacitor with a small equivalent direct-current resistance for smoothing.

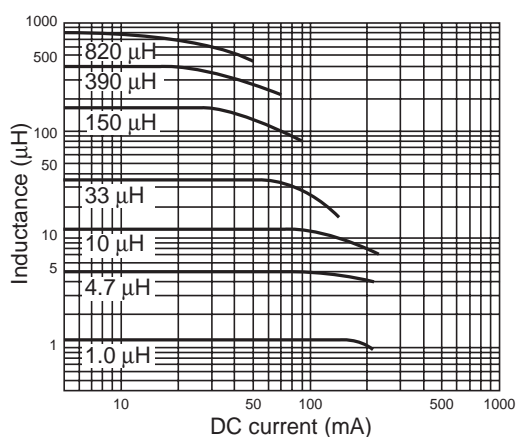
Sample External Components

Leadless Inductors

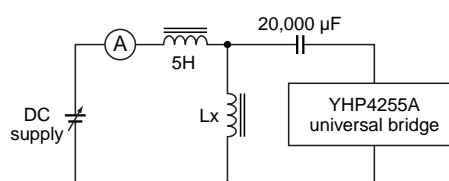
TDK NKF453232 series magnetically shielded leadless inductors

Device	Inductance (μH)	Qmin	LQ frequency (MHz)	Device frequency (MHz-Min.)	DC resistance (Ω -Max.)	Rated current (mA-Max.)
NLF453232-390K	39.0 \pm 10%	50	2.52	13	1.89	44
NLF453232-470K	47.0 \pm 10%	50	2.52	12	2.10	41
NLF453232-560K	56.0 \pm 10%	50	2.52	11	2.34	39
NLF453232-680K	68.0 \pm 10%	50	2.52	10	2.60	36
NLF453232-820K	82.0 \pm 10%	50	2.52	10	2.86	34
NLF453232-101K	100.0 \pm 10%	50	0.796	9	3.25	32
NLF453232-121K	120.0 \pm 10%	50	0.796	8	3.64	30
NLF453232-151K	150.0 \pm 10%	50	0.796	7	4.16	28
NLF453232-181K	180.0 \pm 10%	40	0.796	6	5.72	26
NLF453232-221K	220.0 \pm 10%	40	0.796	5.5	6.30	24
NLF453232-271K	270.0 \pm 10%	40	0.796	5	6.90	23
NLF453232-331K	330.0 \pm 10%	40	0.796	4.5	7.54	23
NLF453232-391K	390.0 \pm 10%	40	0.796	4	8.20	21
NLF453232-471K	470.0 \pm 10%	40	0.796	3.8	9.20	19
NLF453232-561K	560.0 \pm 10%	40	0.796	3.6	10.50	18
NLF453232-681K	680.0 \pm 10%	40	0.796	3.4	12.00	17
NLF453232-821K	820.0 \pm 10%	40	0.796	3	13.50	16
NLF453232-102K	1000.0 \pm 10%	40	0.252	2.5	16.00	15

Characteristic response



Measurement circuit



S1F76300 Series

Drum coil inductors

Taiyo Yuuden FL series micro-inductors

Device	Inductance	Direct current (mA)
FL3H	0.22 μ H to 10 μ H	280 to 670
FL4H	0.47 μ H to 12 μ H	300 to 680
FL5H	10 μ H to 1mH	50 to 320
FL7H	680 μ H to 8.2mH	50 to 170
FL9H	330 μ H to 33mH	50 to 500
FL11H	10mH to 150mH	35 to 110

Toroidal coil inductors

Tohoku Metal Industries HP series toroidal coil inductors

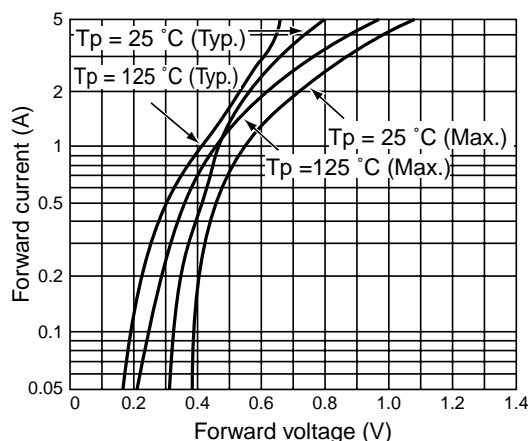
Device	Rated current I _{DC} (A)	Inductance (μ H) at 20kHz, 5V		Diameter \times height (mm-Max.)	Wire gauge (mm ϕ)
		I _{DC} = 0	I _{DC} = rating		
HP011	1	200	160	ϕ 20 \times 12	0.5
HP021	2	65	55		0.7
HP031	3	30	23		0.8
HP012	1	600	450	ϕ 22 \times 13	0.5
HP022	2	180	135		0.7
HP032	3	120	80		0.8
HP052	5	45	30		1.0
HP013	1	1000	800	ϕ 26 \times 14	0.5
HP023	2	500	330		0.7
HP033	3	130	100		0.8
HP055	5	90	55		1.0
HP034S	3	400	250	ϕ 36 \times 18	0.8
HP054S	5	350	160		1.0
HP104S	10	50	30		1.6
HP024	2	1500	950	ϕ 36 \times 21	0.7
HP034	3	300	230		0.8
HP054	3	210	140		1.0
HP104	10	45	30		1.6
HP035	3	700	500	ϕ 43 \times 23	0.5
HP055	5	600	330		1.0
HP105	10	180	95		1.6
HP205	20	20	14		1.8 \times 2 P

Diodes

Shindengen DINS4 Schottky barrier diodes

Parameter	Symbol	Condition	Rating			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 1.1A$, pulse measurement	—	—	0.55	V
Reverse current	I_R	$V_R = V_{RM}$, pulse measurement	—	—	1	mA
Junction-to-lead thermal resistance	θ_{jl}		—	—	23	$^{\circ}C/W$
Junction-to-ambient thermal resistance	θ_{ja}		—	—	157	$^{\circ}C/W$

Characteristics



Smoothing capacitors

NEC MSV series capacitors

Device	Package type	Rated voltage (V)	Static capacitance (μF)	Tan δ			Leakage current (μA)
				+25, +85 $^{\circ}C$	+125 $^{\circ}C$	-55 $^{\circ}C$	
MSVAOJ475M	A	6.3	4.7	0.08	0.1	0.12	0.5
MSVB2OJ106M	B2	6.3	10	0.08	0.1	0.12	0.6
MSVB2OJ156M	B2	6.3	15	0.08	0.1	0.12	0.9
MSVBOJ156M	B	6.3	15	0.08	0.1	0.12	0.9
MSVCOJ336M	C	6.3	33	0.08	0.1	0.12	2.0
MSVD2OJ686M	D2	6.3	68	0.08	0.1	0.12	4.2
MSVDOJ686M	D	6.3	68	0.08	0.1	0.12	4.2

Note

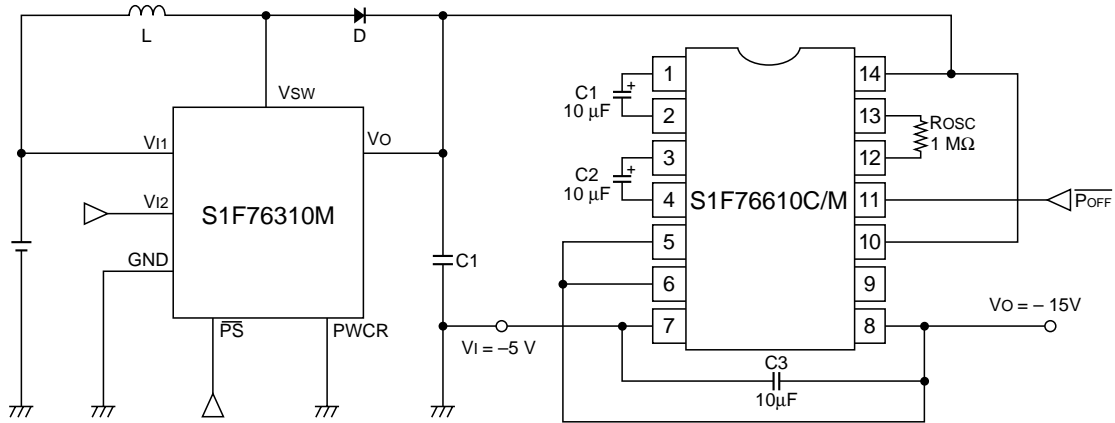
The figures on the previous pages show data from the documents of various manufactures. For further details, please contact the relevant manufacture.

S1F76300 Series

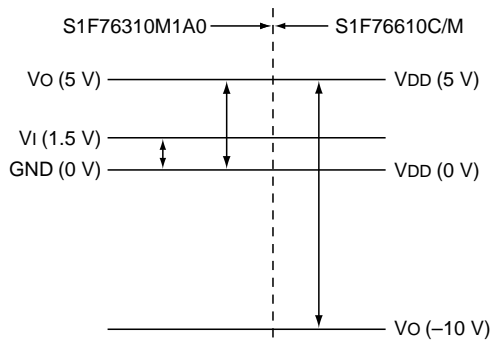
Other Applications Voltage booster

Combining an S1F76310 switching regulator with an S1F76610C/M DC/DC converter and voltage regulator

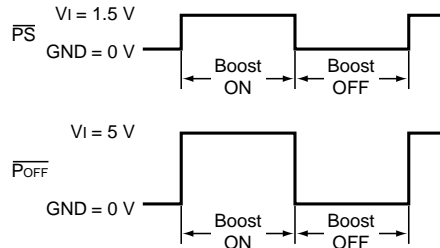
creates the voltage booster circuit shown in the following figure.



Potential levels are shown in the following figure.



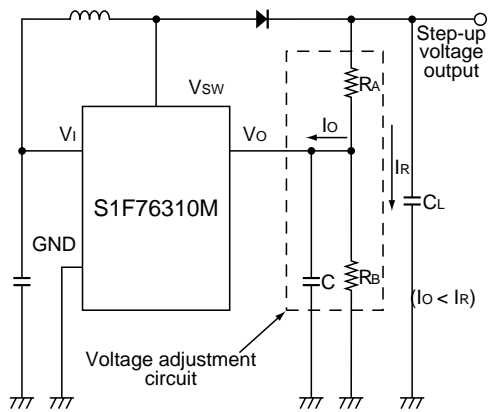
S1F76310M1A0. The input voltage still reaches the S1F76610C/M through L and D.



Although the circuit appears to have two ON/OFF control points, PS on the S1F76310M1A0 and Poff on the S1F76610C/M, PS only shuts down the

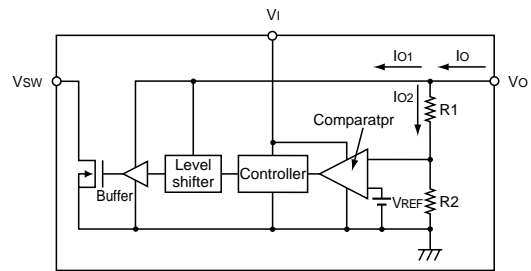
Output voltage adjustment

To ensure stable output, any circuit that adjusts the output voltage must contain C1, RA and RB. To stop switching current from affecting VO, the circuit must also satisfy the condition $I_O < I_R$.



The following figure summarizes the relevant circuits inside an S1F76300 series chip.

VO is connected to the level shift and buffer circuit, which provide the gate bias for the switching transistor driving the inductor. The current drain, IO1, varies with the load and is typically 10µA. The current, IO2, through the internal resistors R1 and R2, is typically 1µA.



S1F76300 Series**S1F76330 Series Built-in Crystal Oscillator Type CMOS Switching Regulators****DESCRIPTION**

The S1F76330 series of CMOS switching regulators provide input voltage step-up and regulation to a specified voltage using an external coil. The devices in these series incorporate precision, low-power reference voltage generators and transistors for driving an internal comparator. They feature low power consumption, low operating voltages and standby operation.

The devices offer a range of fixed output voltages, from 2.35 to 5.00V.

They are available in 8-pin SOP3s.

APPLICATIONS

- Fixed-voltage power supplies for battery-operated equipment such as portable video cassette recorders, video cameras and radios
- Power supplies for pages, memory cards, calculators and similar hand-held equipment
- Fixed-voltage power supplies for medical equipment
- Fixed-voltage power for communications equipment
- Power supplies for microcomputers
- Uninterruptable power supplies

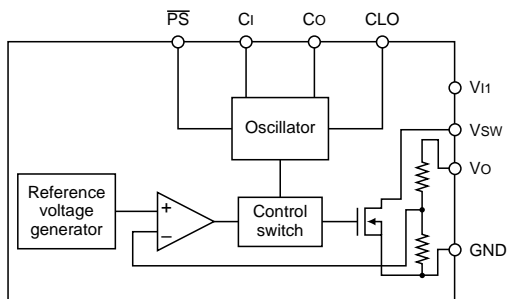
FEATURES

- 0.9V (Min.) operating voltage
- 8 μ A (Typ.) maximum current consumption
- Standby operation
- 3 μ A (Typ.) standby current consumption
- Built-in oscillator circuit for use with external crystal oscillator
- SOP3-8pin

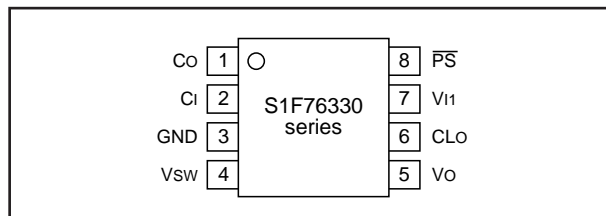
LINEUP

Product	Voltage (V)		Multiplication frequency source	Voltage detection	Power-on clear	Battery backup	Response compensation	Output voltage temperature characteristic	Crystal Oscillator Output	Package
	Input	Output								
S1F76330M1B0	1.5 (0.9 Min.)	3.00	Crystal oscillator	No	No	No	No	No	Yes	SOP3-8pin

BLOCK DIAGRAMS
S1F76330 series



PIN ASSIGNMENTS
S1F76330 series



PIN DESCRIPTIONS
S1F76330 series

Number	Name	Description
1	Co	Crystal drain
2	Ci	Crystal gate
3	GND	Ground
4	Vsw	External inductor drive
5	Vo	Output voltage
6	CLO	Oscillator output
7	Vi	Step-up input voltage
8	PS	Power save. See note.

Note

See standby mode in the functional description.

S1F76300 Series

S1F76300 Series

SPECIFICATIONS

Absolute Maximum Ratings S1F76330 series

Parameter	Symbol	Rating	Unit
Input voltage	V _{I1}	7	V
Output current	I _O	100	mA
Output voltage	V _O	7	V
Power dissipation	P _D	200 (SOP) 300 (DIP)	mW
Operating temperature range	T _{opr}	-30 to +85	°C
Storage temperature range	T _{stg}	-65 to +150	°C
Soldering temperature (for 10 s). See note.	T _{sol}	260	°C

Note

Temperatures during reflow soldering must remain within the limits set out in LSI Device Precautions. Never use solder dip to mount S1F70000 series power supply devices.

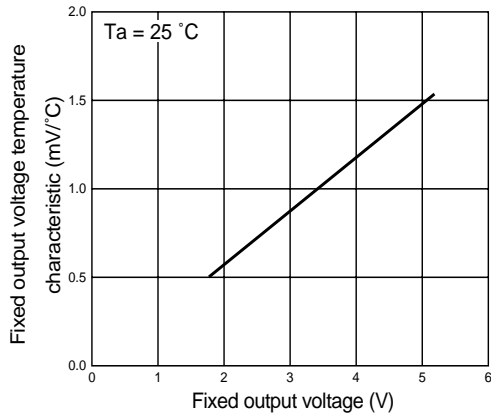
Electrical Characteristics

S1F76330M1B0

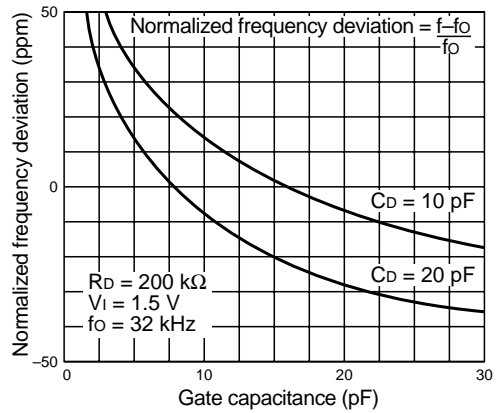
V_{SS} = 0V, T_a = 25 °C unless otherwise noted

Parameter	Symbol	Conditions	Rating			Unit
			Min.	Typ.	Max.	
Input voltage	V _{I1}	V _O > V _{I2}	0.9	—	2.0	V
Output voltage	V _O	V _{I1} = 1.5V	2.90	3.00	3.10	V
Operating current	I _{DDO}	V _{I1} = 1.5V, f _{CLK} = 32kHz, I _O = 1.0mA	—	5	30	μA
Standby current	I _{DDS}	V _{I1} = 1.5V	—	3	10	μA
Switching transistor ON resistance	R _{SWON}	V _{I1} = 1.5V, V _O = 3.0V, V _{SW} = 0.2V	—	6	12	Ω
Switching transistor leakage current	I _{SWQ}	V _{I1} = 1.5V, V _O = 1.5V, V _{SW} = 7.0V	—	—	0.5	μA
C _{Lo} Low-level output current	I _{OL}	V _{I1} = 1.5V, V _O = 3.0V, V _{OL} = 0.2V	0.5	1.0	—	μA
C _{Lo} High-level output current	I _{OH}	V _{I1} = 1.5V, V _O = 3.0V, V _{OH} = 0.2V	0.55	1.1	—	μA
PS pull-up current	I _{IH}	V _{IH} = 1.5V	—	—	0.5	μA
Oscillator start-up voltage	V _{STA}	C _G = 10pF, C _D = 10pF, R _D = 300kΩ,	0.9	—	—	V
Oscillator shut-down voltage	V _{STP}	f _{osc} = 32kHz	—	—	0.9	V

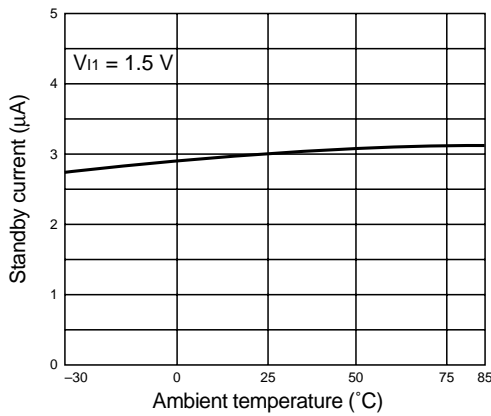
Typical Performance Characteristics



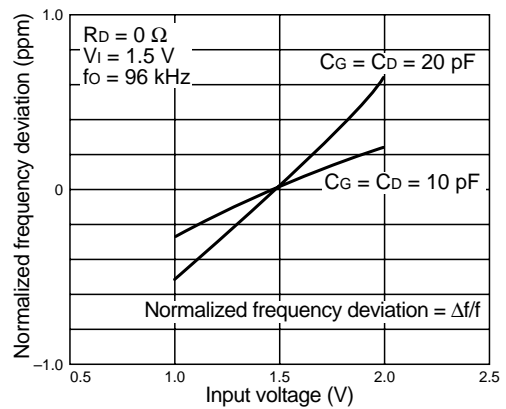
Fixed output voltage temperature characteristic



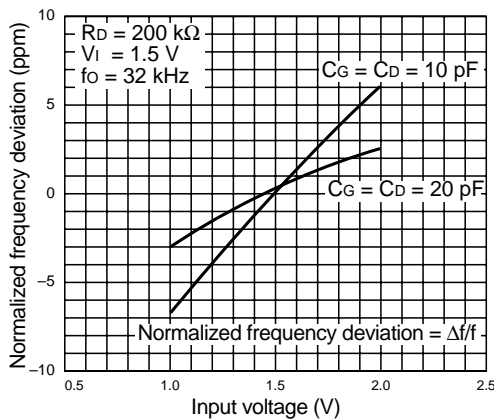
Normalized frequency deviation vs. gate capacitance 1



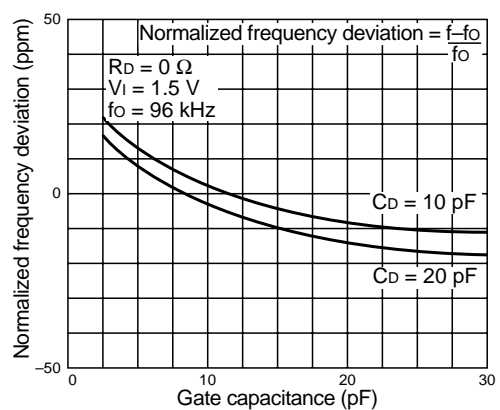
Standby current vs. ambient temperature



Normalized frequency deviation vs. input voltage 2



Normalized frequency deviation vs. input voltage 1

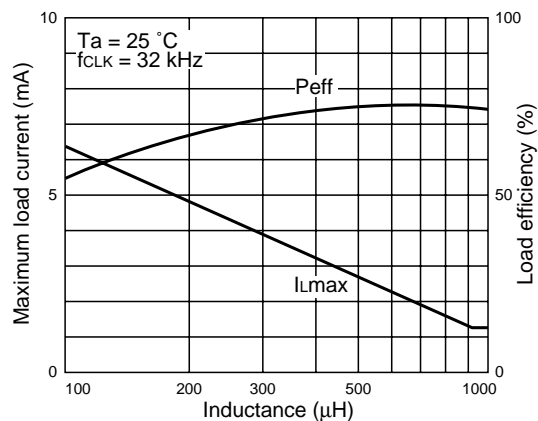
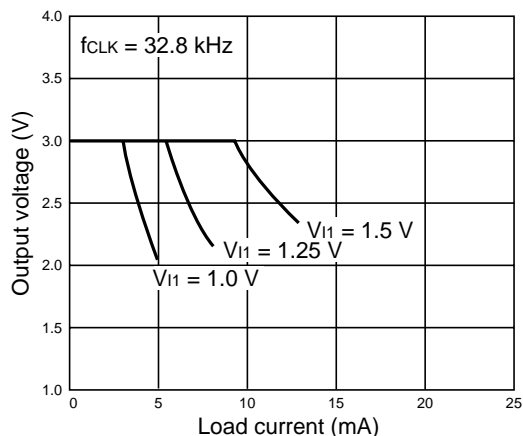


Normalized frequency deviation vs. gate capacitance 2

S1F76300 Series

S1F76300 Series

Load characteristics S1F76330M1B0



Notes

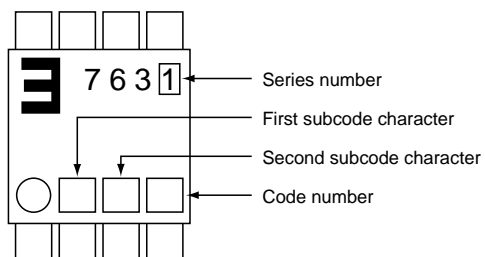
Inductor: TDK NLF453232-221k (220 μH)
 Diode: Shindengen DINS4 Schottky barrier diode
 Capacitor: NEC MSVB20J106M (10 μF)

Notes

- $V_{I1} = 1.5\text{ V}$
- Inductor: TDK NLF453232 series
 Diode: Shindengen DINS4 Schottky barrier diode
 Capacitor: NEC MSVB20J106M (10 μF)

PACKAGE MARKINGS

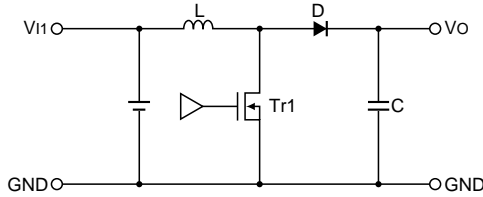
S1F76330 device packages use the following marking.



FUNCTIONAL DESCRIPTIONS

Basic Voltage Booster Operation

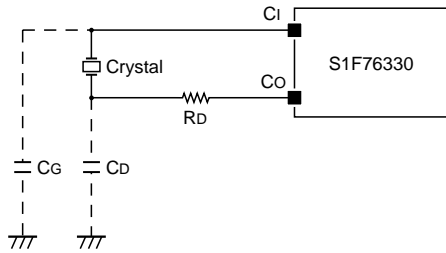
Tr1 switches ON and OFF at the frequency of the clock pulses from the crystal oscillator. When the transistor is ON, the circuit stores energy in L. When it is OFF, this energy flows through D to charge C.



Internal Circuits

Crystal oscillator

The S1F76330 series incorporate a crystal oscillator circuit. An external crystal and drain resistor are used to generate the booster circuit clock. The crystal oscillator is connected to C1 and C0 as shown in the following figure.

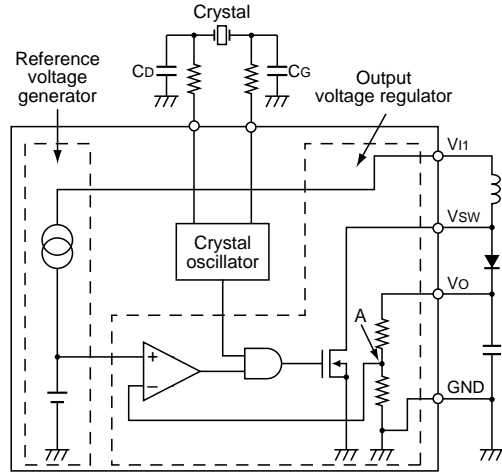


In the S1F76330 series, the crystal oscillator output is sent to CLO as the VO system signal. The crystal oscillator circuit is activated by VI but, because the output level is shifted and the output is connected to CLO, the oscillator output cannot be obtained without a voltage at VO. Since the crystal oscillator is activated when an input voltage is applied, oscillation continues even in standby mode.

Reference voltage generator and output voltage regulator

The reference voltage generator regulates V11 to generate a voltage for the voltage regulator circuit.

The output voltage regulator regulates the boosted output voltage. This voltage is determined by the level at point A between the two resistors connecting VO and GND. These series use an on-chip resistor to set the output at a specified voltage.



Note

In step-up voltage operation, the ripple voltage created by the switching operation is large relative to the output voltage described above. This ripple voltage is affected by external components and load conditions. The user is advised to check this voltage carefully.

Standby mode

Connecting \overline{PS} to GND places the chip in standby mode. In this mode, the crystal oscillator is disabled, switching off the inductor drive transistor and the voltage booster circuit. Typically, \overline{PS} is connected to \overline{RST} . If standby mode is not required, leave \overline{PS} open as it has a pull-up resistor.

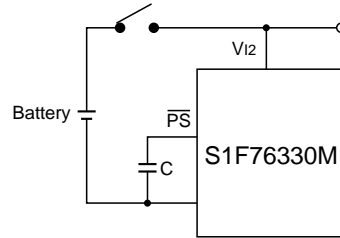
Output voltage response compensation

The S1F76340 series incorporates a response compensation input. A response compensation capacitor is connected between VCONT and VO, allowing the ripple voltage generated by the boosted output voltage to be suppressed to a minimum.

S1F76300 Series

Powering up

Ensure that V_O is at least the minimum operating voltage (0.9V) before switching on the booster circuit. One way to do this is to connect a capacitor between \overline{PS} and GND so that the chip connects V_O to V_I when the power is applied for the first time.



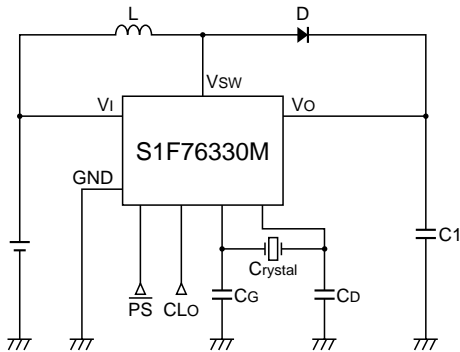
TYPICAL APPLICATIONS

Example Circuits

The output current, I_O , and power conversion efficiency P_{eff} , of a particular device in the series depends on fac-

tors such as the switching frequency, type of coil, and the size and type of other external components.

S1F76330 series



Notes

■ $100\mu\text{H} \leq L \leq 1\text{mH}$, $C \leq 10\mu\text{F}$, D: Schottky diode

■ S1F76330M1B0

- $P_{eff} = 70\%$ when $L = 220\mu\text{H}$ (leadless inductor), $V_{II} = 1.5\text{V}$, $f_{CLK} = 32\text{kHz}$, $I_O = 8\text{mA}$
- $P_{eff} = 75\%$ when $L = 220\mu\text{H}$ (drum coil), $V_{II} = 1.5\text{V}$, $f_{CLK} = 32\text{kHz}$, $I_O = 9\text{mA}$
- $P_{eff} = 80\%$ when $L = 300\mu\text{H}$ (toroidal coil), $V_{II} = 1.5\text{V}$, $f_{CLK} = 32\text{kHz}$, $I_O = 10\text{mA}$

External Components

The performance characteristics of switching regulators depend greatly on the choice of external components. Observing the following guidelines will ensure high performance and maximum efficiency.

Inductor

Use an inductor with low direct-current resistance and low losses.

Leadless

Pre-wound, leadless inductors using surface-mount technology are the most suitable for portable equipment and other space-critical applications.

Drum coil

Avoid drum coils because their magnetic field can induce noise.

Toroidal coil

Use a toroidal coil to virtually eliminate magnetic field leakage, reduce losses and improve performance.

Diode

Use a Schottky barrier diode with a high switching speed and low forward voltage drop, V_F .

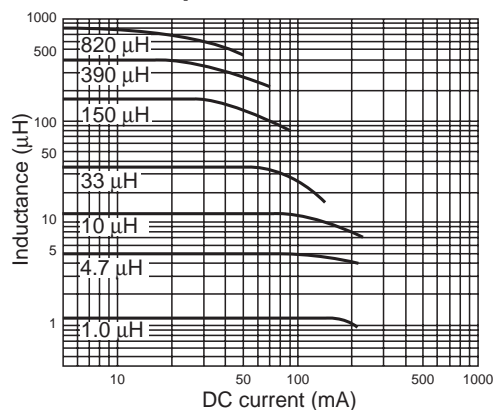
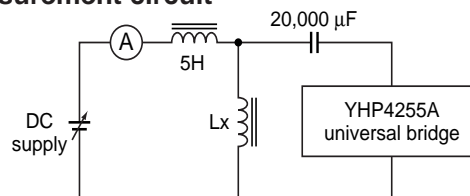
Capacitor

To minimize ripple voltages, use capacitors with a small equivalent direct-current resistance for smoothing.

Sample External Components**Leadless inductors**

TDK NLF453232 series magnetically-shielded leadless inductors

Device	Inductance (μH)	Qmin	LQ frequency (MHz)	Device frequency (MHz-Min.)	DC resistance (Ω -Max.)	Rated current (mA-Max.)
NLF453232-390K	39.0 \pm 10%	50	2.52	13	1.89	44
NLF453232-470K	47.0 \pm 10%	50	2.52	12	2.10	41
NLF453232-560K	56.0 \pm 10%	50	2.52	11	2.34	39
NLF453232-680K	68.0 \pm 10%	50	2.52	10	2.60	36
NLF453232-820K	82.0 \pm 10%	50	2.52	10	2.86	34
NLF453232-101K	100.0 \pm 10%	50	0.796	9	3.25	32
NLF453232-121K	120.0 \pm 10%	50	0.796	8	3.64	30
NLF453232-151K	150.0 \pm 10%	50	0.796	7	4.16	28
NLF453232-181K	180.0 \pm 10%	40	0.796	6	5.72	26
NLF453232-221K	220.0 \pm 10%	40	0.796	5.5	6.30	24
NLF453232-271K	270.0 \pm 10%	40	0.796	5	6.90	23
NLF453232-331K	330.0 \pm 10%	40	0.796	4.5	7.54	23
NLF453232-391K	390.0 \pm 10%	40	0.796	4	8.20	21
NLF453232-471K	470.0 \pm 10%	40	0.796	3.8	9.20	19
NLF453232-561K	560.0 \pm 10%	40	0.796	3.6	10.50	18
NLF453232-681K	680.0 \pm 10%	40	0.796	3.4	12.00	17
NLF453232-821K	820.0 \pm 10%	40	0.796	3	13.50	16
NLF453232-102K	1000.0 \pm 10%	40	0.252	2.5	16.00	15

Characteristic response**Measurement circuit**

S1F76300 Series

Drum coil inductors

Taiyo Yuuden FL series micro inductors

Device	Inductance (μH)	Direct current (mA)
FL3H	0.22 to 10	280 to 670
FL4H	0.47 to 12	300 to 680
FL5H	10 to 1000	50 to 320
FL7H	680 to 8200	50 to 170
FL9H	330 to 33000	50 to 500
FL11H	10000 to 150000	35 to 110

Toroidal coil inductors

Tohoku Metal Industries HP series toroidal coil inductors

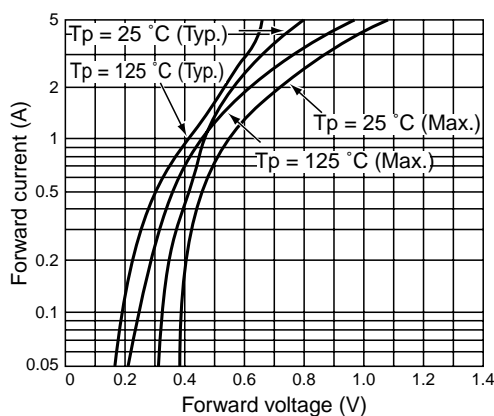
Device	Rated current IDC (A)	Inductance (μH) at 20kHz, 5V		Diameter \times height (mm-Max.)	Wire gauge (mm ϕ)
		IDC = 0	IDC = rating		
HP011	1	200	160	20 \times 12	0.5
HP021	2	65	55		0.7
HP031	3	30	23		0.8
HP012	1	600	450	22 \times 13	0.5
HP022	2	180	135		0.7
HP032	3	120	80		0.8
HP052	5	45	30		1.0
HP013	1	1000	800	26 \times 14	0.5
HP023	2	500	330		0.7
HP033	3	130	100		0.8
HP055	5	90	55		1.0
HP034S	3	400	250	36 \times 14	0.8
HP054S	5	350	160		1.0
HP104S	10	50	30		1.6
HP024	2	1500	950	36 \times 21	0.7
HP034	3	300	230		0.8
HP054	5	210	140		1.0
HP104	10	45	30		1.6
HP035	3	700	500	43 \times 23	0.8
HP055	5	600	330		1.0
HP105	10	180	95		1.6
HP205	20	20	14		1.8 \times 2 P

Diodes

Shindengen DINS4 Schottky barrier diodes

Parameter	Symbol	Conditions	Rating			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 1.1A$, pulse measurement	—	—	0.55	V
Reverse current	I_R	$V_R = V_{RM}$, pulse measurement	—	—	1	mA
Junction-to-lead thermal resistance	θ_{jl}		—	—	23	°C/W
Junction-to-ambient thermal resistance	θ_{ja}		—	—	157	°C/W

Characteristics



Smoothing capacitors

NEC MSV series capacitors

Device	Package type	Voltage (V)	Static capacitance (μF)	Tan δ			Leakage current (μA)
				+25, +85 °C	+125 °C	-55 °C	
MSVA0J475M	A	6.3	4.7	0.08	0.1	0.12	0.5
MSVB20J106M	B2	6.3	10	0.08	0.1	0.12	0.6
MSVB20J156M	B2	6.3	15	0.08	0.1	0.12	0.9
MSVB0J156M	B	6.3	15	0.08	0.1	0.12	0.9
MSVC0J336M	C	6.3	33	0.08	0.1	0.12	2.0
MSVD20J686M	D2	6.3	68	0.08	0.1	0.12	4.2
MSVD0J686M	D	6.3	68	0.08	0.1	0.12	4.2

Note

The figures on the previous pages show data from the documents of various manufacturers. For further details, please contact the relevant manufacturer.

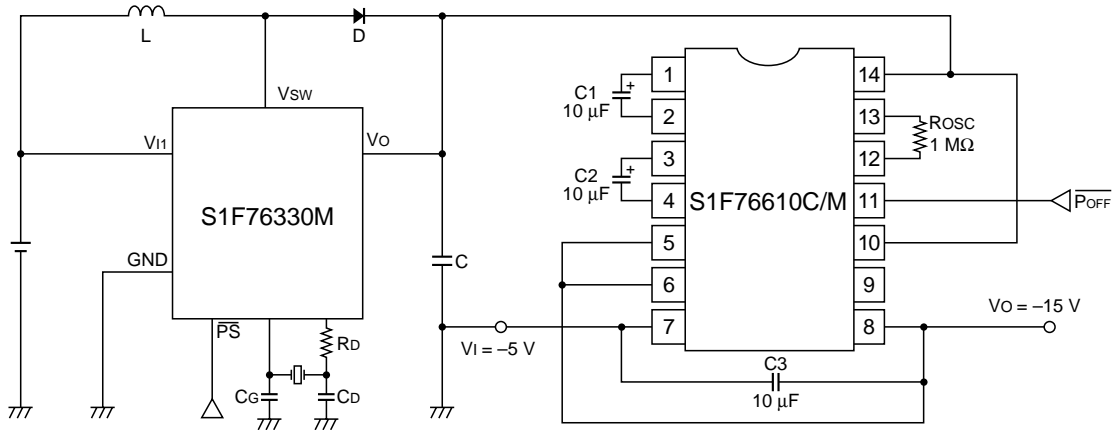
S1F76300 Series

Other Applications

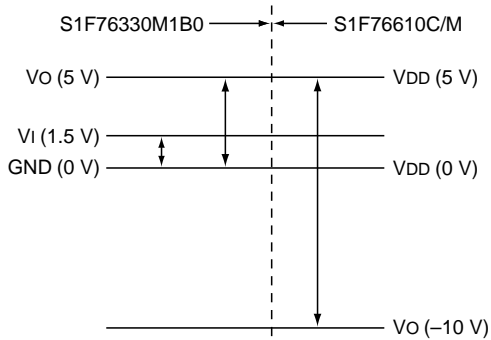
Voltage booster

Combining an S1F76330M1B0 switching regulator with an S1F76610C/M DC/DC converter and voltage

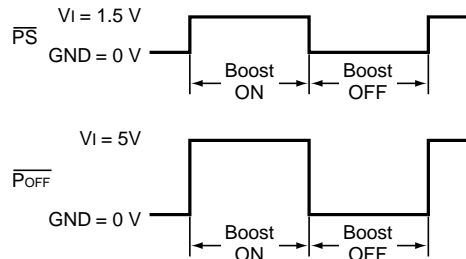
regulator creates the voltage booster circuit shown in the following figure.



Potential levels are shown in the following figure.

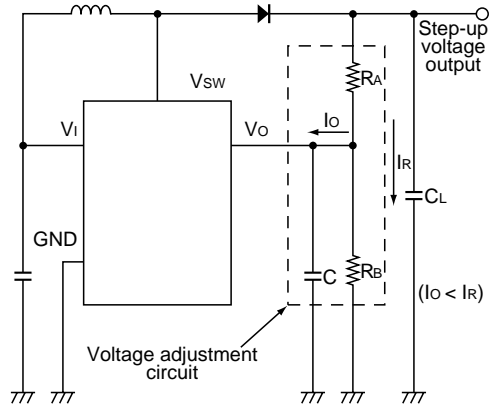


Although the circuit appears to have two ON/OFF control points, \overline{PS} on the S1F76330M1B0 and \overline{POFF} on the S1F76610C/M, \overline{PS} only shuts down the S1F76330M1B0. The input voltage still reaches the S1F76610C/M through L and D.



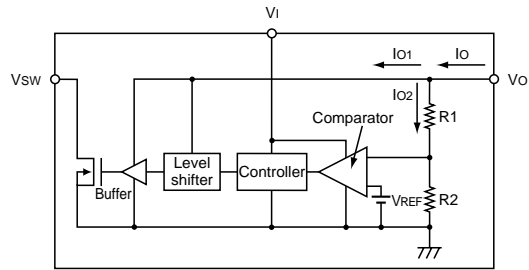
Output voltage adjustment

To ensure stable output, any circuit that adjusts the output voltage must contain C1, RA and RB. To stop switching current from affecting VO, the circuit must also satisfy the condition $I_O < I_R$.



The following figure summarizes the relevant circuits inside an S1F70000 series chip.

VO is connected to the level shift and buffer circuit, which provide the gate bias for the switching transistor driving the inductor. The current drain IO1, varies with the load and is typically 10µA. The current, IO2, through the internal resistors R1 and R2 is typically 1µA.



S1F71100 Series

S1F71100 Series PWM Type Step-down DC/DC Switching Regulator

DESCRIPTION

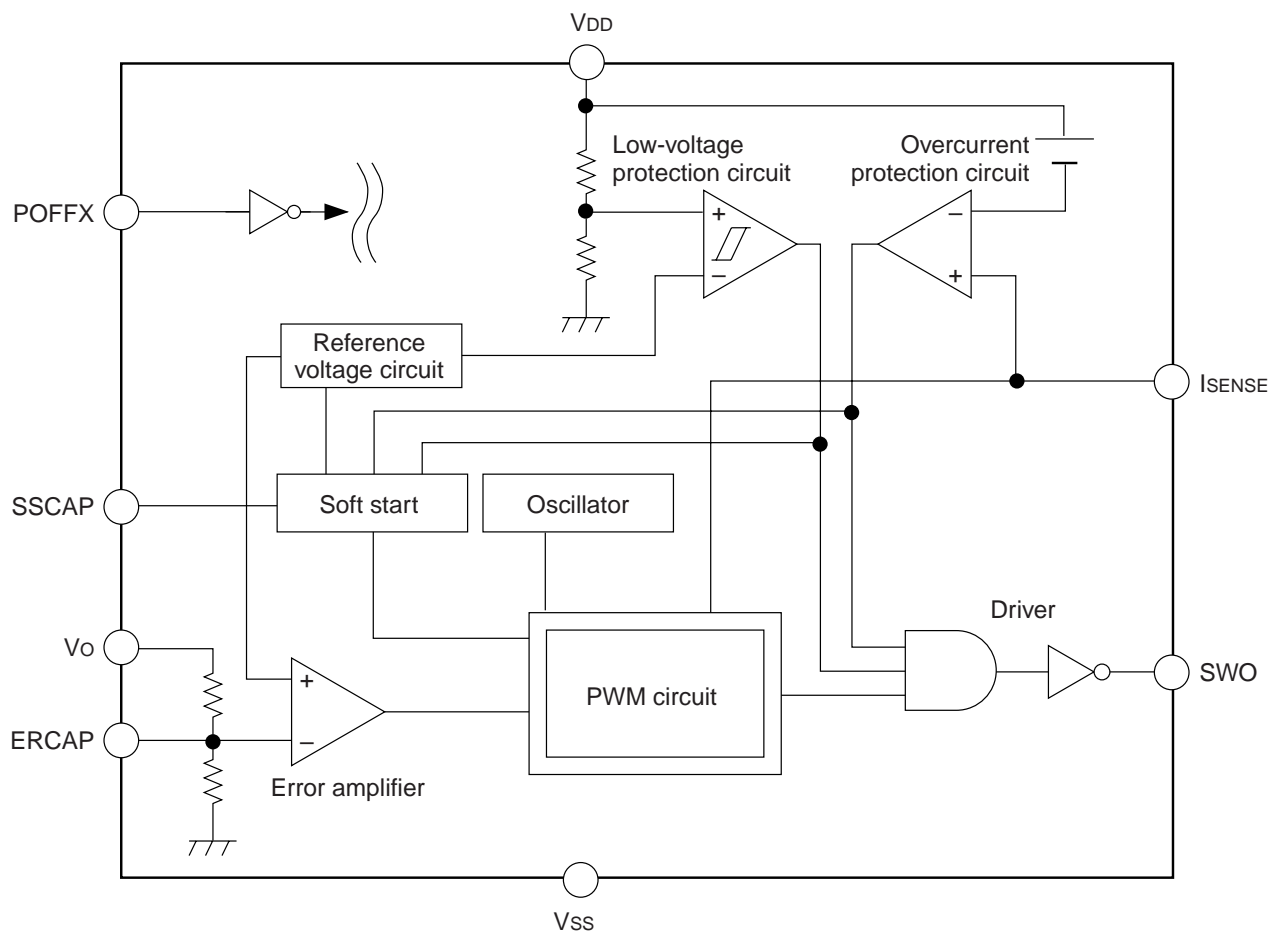
S1F71100 is a pulse width modulation (PWM) type step-down DC/DC converter control IC for which the CMOS process is used and to which a power transistor is connected outside. S1F71100 is composed of an oscillator, a reference voltage circuit, an error amplifier, a PWM circuit, a soft start circuit, a driver, etc. When this IC drives an external P ch power MOS transistor, S1F71100 can constitute a step-down DC/DC converter that converts input voltages up to 12V into the output voltage of 3.3V.

S1F71100 is also provided with a low-voltage protection circuit, an overcurrent protection circuit and a soft start protection circuit. When receiving external signals, S1F71100 can stop the oscillator and the switching circuit and turn off the power, so that it can reduce wasteful current consumption at the time of system halt.

FEATURES

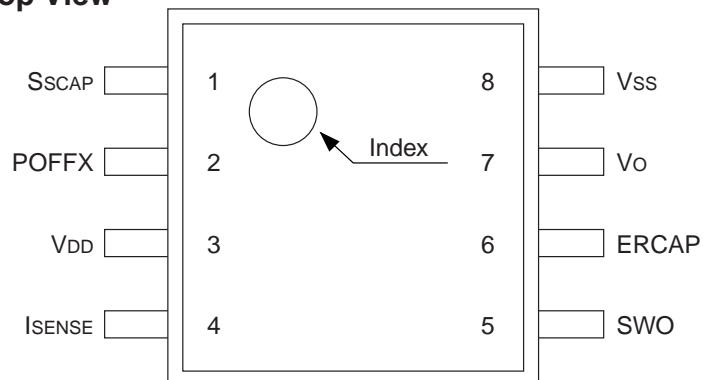
- Input voltage : 3.3V ~ 12V
- Output voltage : 3.3V (S1F71100M0A0)
- Power off current : 1 μ A
- Self current consumption : 800 μ A
- Frequency fixing (200kHz) PWM
- Power off function (IC shutdown)
- Soft start function
- Overcurrent protection function
- Low-voltage protection function
- Shipping pattern : plastic package SOP4-8pin
- * Radiation-resistant design has not been provided for this specification.

BLOCK DIAGRAM



PIN ASSIGNMENTS

Top View



SOP4-8pin

PIN DESCRIPTIONS

Pin No.	Pin name	Pin Type	Description
1	SSCAP	—	The soft start function is obtained when a capacitor is connected between the capacitor connection pin for setting soft start and the Vss pin.
2	POFFX	—	Power off control pin During normal operation : VDD level At power off time : Vss level
3	VDD	Power supply	Power supply pin (+)
4	ISENSE	—	Load current feedback pin Load current detection resistor connection pin (Connect a resistor of 100mΩ)
5	SWO	Output	Switching Pch power MOS transistor drive pin
6	ERCAP	—	Capacitor connection pin for external phase compensation
7	Vo	Input	Output voltage feedback pin
8	Vss	Power supply	Power supply pin (-)

S1F71100 Series

FUNCTIONAL DESCRIPTIONS

Description of Operation

S1F71100 is a step-down switching regulator control IC of load current detection type pulse width modulation (PWM) system and is composed of an oscillator, a reference voltage circuit, an error amplifier, a PWM circuit, various protection circuits, etc.

S1F71100 can constitute a switching regulator, which converts input voltages up to 12V into output voltages of 3.3V, when external parts such as a power MOSFET, a diode, an inductor and a capacitor are connected to it. S1F71100 controls PWM by means of the two systems of output voltage feedback and load current feedback. The output voltage feedback system converts output voltage values of the switching regulator into voltage feedback signals through the error amplifier. And the load current feedback system detects currents flown to the external load current detection resistor as voltage values at the load current detection pin and converts them into current feedback signal in the internal circuit. These two feedback signals control the switching duty so that outputs from the switching regulator become optimum all the time. When the output voltage reduces, the output level of the error amplifier changes, and the switching duty is controlled so that the switching on duty of the output transistor increases.

Oscillator

Since S1F71100 has a built-in oscillator, and no external part is necessary. The oscillation frequency is fixed to 200kHz (Typ.). The oscillator stops its operation when the power is turned off. When the low-voltage protection circuit detects a low voltage, the output transistor is turned off, but the oscillation continues inside the IC.

Soft Start

When a capacitor is connected to the SSCAP pin, S1F71100 can set a soft start operation to prevent inrush current at the time when the power is turned on. (Figure 6-1) The SSCAP pin is at the VSS level when the power is turned off. When the soft start operation begins, the soft start capacitor starts being charged and the voltage at the SSCAP pin rises slowly. The output voltage rises gradually as the voltage at the SSCAP pin rises. This operation controls the switching pulse width at the time when the power is turned on and restrains surge current and output overshoot. The soft start time can be set according to the capacitance value of a capacitor to be

connected.

The voltage at the SSCAP pin drops to the VSS level when an overcurrent is detected, when a low voltage is detected or when the power is turned off, and the soft start operation begins.

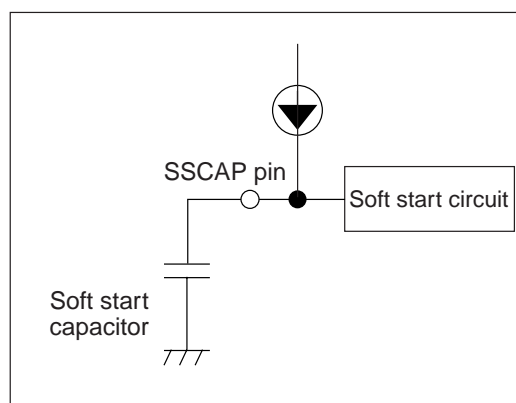


Figure 6.1 Connection Diagram of SSCAP Pin

Low-voltage Protection Circuit

The low-voltage protection circuit monitors the supply voltage (voltage at the VDD pin). When the supply voltage drops below a detected voltage value, the low-voltage protection circuit works and stops the switching operation of the output transistor. This low-voltage protection circuit links to the soft start circuit and drops the voltage at the SSCAP pin to the VSS level during detection of low voltage.

The low-voltage protection circuit has hysteresis. When the supply voltage returns to more than the release voltage, the voltage at the SSCAP pin rises slowly and the soft start circuit starts its operation, then the low-voltage protection circuit resumes the switching operation.

Overcurrent Protection Circuit

When the current flowing through the current detection resistor increases more than the set current value and the voltage at the ISENSE pin drops below a detected voltage value, the overcurrent protection circuit operates. When the overcurrent protection circuit operates, it maintains the SWO pin at the VDD level and turns off the output transistor. It links to the soft start circuit, and the soft start circuit controls output voltage rise after detection of overcurrent.

Power Off Function

S1F71100 can control circuit operations according to external signal control. When the POFFX pin is connected to the VSS level, all circuits stop their operations and their powers are turned off. The current consumption at the power off state is less than 1 μ A. When the power is off, the SWO pin is at the VDD level and turns off the voltage transistor. The voltage at the SSCAP pin

comes to the VSS level, and the output voltage is controlled with the soft start circuit after the power off state is released. In the operating state, set the POFFX pin to the VDD level to operate it. The POFFX pin cannot be operated in an open state. When the power off function is not used, connect the POFFX pin to the VDD pin.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Applicable Pin	Rated Value	Unit
Input voltage	V _{DD}	V _{DD}	15.0	V
Voltage at Vo pin	V _O	V _O	V _{SS} -0.3 to V _{DD} +0.3	V
Voltage at POFFX pin	POFFX	POFFX	V _{SS} -0.3 to V _{DD} +0.3	V
Voltage at ERCAP pin	ERCAP	ERCAP	V _{SS} -0.3 to V _{DD} +0.3	V
Voltage at SSCAP pin	SSCAP	SSCAP	V _{SS} -0.3 to V _{DD} +0.3	V
Voltage at SWO pin	SWO	SWO	V _{SS} -0.3 to V _{DD} +0.3	V
Voltage at ISENSE pin	ISENSE	ISENSE	V _{SS} -0.3 to V _{DD} +0.3	V
Package allowable loss	P _D	P _D	300 T _a ≤25°C	MW
Operating temperature	T _{opr}	—	-30 to +85	°C
Storage temperature	T _{stg}	—	-55 to +150	°C
Soldering temperature and time	T _{sol}	—	260 · 10	°C-S

Note :Any operation under conditions exceeding the above absolute maximum ratings may result in a malfunction or a permanent destruction. When even an item is more than the rating, a temporary normal operation is possible but with remarkably low reliability. So, be sure to keep all items below the ratings.

S1F71100 Series

ELECTRICAL CHARACTERISTICS

DC Characteristics (S1F71100M0A0)

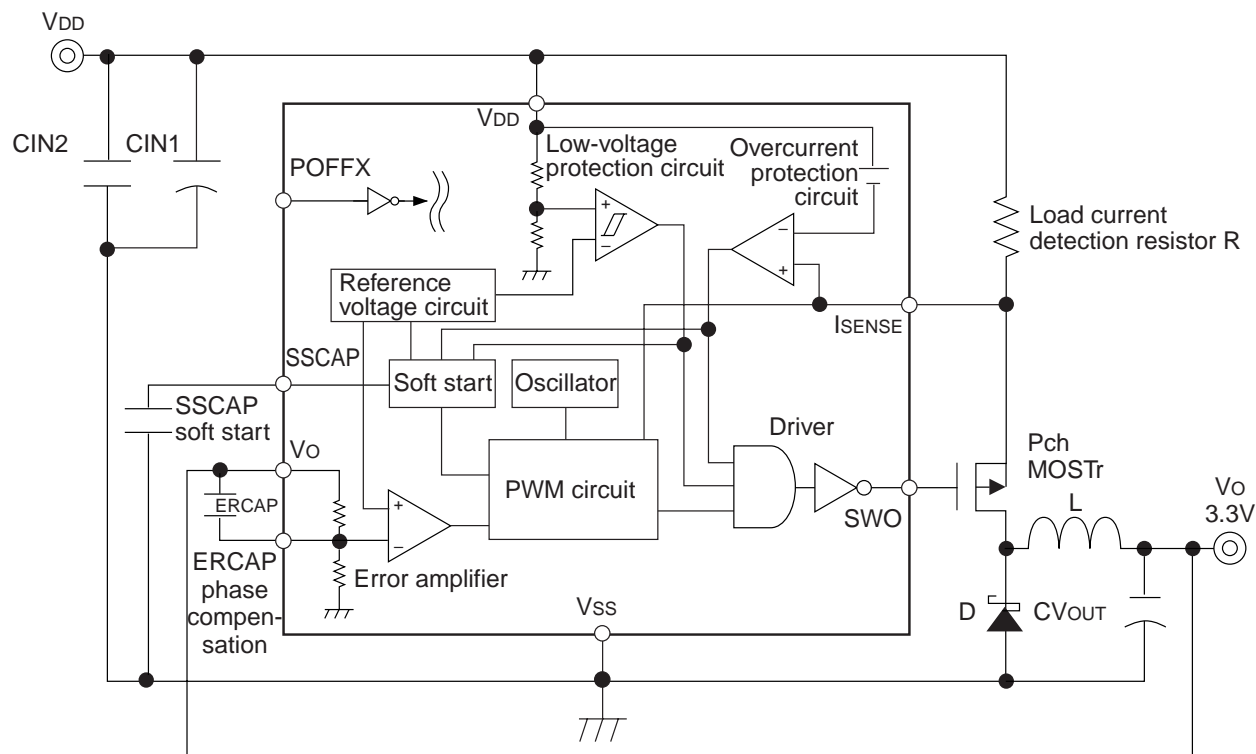
Unless otherwise specified, Ta = 25°C.

Parameter	Symbol	Conditions	Specification			Unit
			Min.	Typ.	Max.	
Input supply voltage	V _{DD}	—	3.3	—	12.0	V
Output voltage	V _O	V _{DD} =5.0V Ta=-30 to +85°C	3.150	3.3	3.450	V
Current consumption during operation	I _{VDD}	V _{DD} =5.0V V _O =V _{DD}		0.8	1.4	mA
Current consumption at power off time	I _{OPR1}	V _{DD} =5.0V POFFX=V _{SS}	—	—	1.0	μA
Output current at SWO pin	I _{OHSWO}	V _{DD} =5.0V, V _O H=50mV	-1.0	—	—	mA
	I _{OLSWO}	V _{DD} =5.0V, V _O L=50mV	1.0	—	—	mA
Input stability	ΔV _O	V _{DD} =5.0 to 10V	—	30	—	mV *
Load stability	ΔV _O	I _O =10mA to 300mA	—	30	—	mV *
Soft start time	T _{SS}	Capacitance for SS =0.1μF V _{DD} =5.0V I _O =300mA	—	40	—	ms *
Input voltage at POFFX pin	V _{IH}	—	0.8V _{DD}	—	—	V
	V _{IL}	—	—	—	0.2V _{DD}	V
Leak current at POFFX pin	I _{LINH}	V _I =V _{DD}	—	—	0.1	μA
	I _{LINL}	V _I =V _{SS}	—	—	-0.1	μA
Conversion efficiency	EFFI	V _{DD} =5.0V I _O =200mA	—	90	—	% *
Oscillation frequency	f _{OSC}	V _{DD} =5.0V V _O =V _{SS} SWO pin	150	200	250	kHz
Overcurrent detection voltage (V _{DD} -V _I SENSE)	I _{DET}	V _{DD} =5.0V	0.08	0.12	0.16	V
Low-voltage detection voltage value	V _{DET1}	Object pin : V _{DD}	2.5	2.6	2.7	V
Low-voltage detection hysteresis	V _{HYS}	Object pin : V _{DD}	—	0.15	—	V
Output voltage temperature coefficient	$\frac{\Delta V_O}{\Delta T_a}$	V _{DD} =5.0V Ta=-30 to +85°C	—	0.02	—	%/°C

* Characteristics vary with applicable conditions and parts. Select proper parts after sufficient evaluation.

EXAMPLE OF EXTERNAL CONNECTION OF REFERENCE CIRCUIT

Example of Standard Circuit



Parts examples

CIN1	100 μ F	(Sanyo 16SA100M)
CIN2	1 μ F	
SSCAP	0.1 μ F	
ERCAP	330pF	
R	100m Ω	
PchTr		(Hitachi 2SJ484)
L	47 μ H	(Sumida CD105)
CVo	47 μ F	(Sanyo 16SA47M)
D	Schottkey	(Rohm RB161L-40)

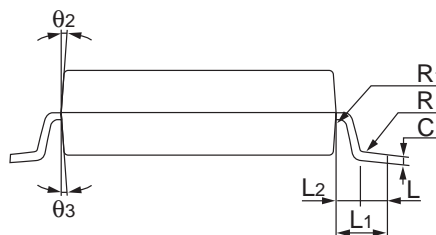
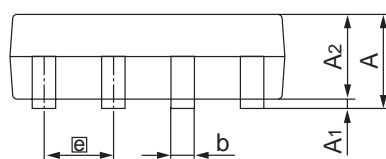
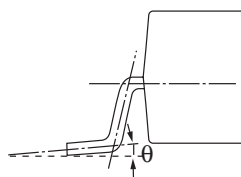
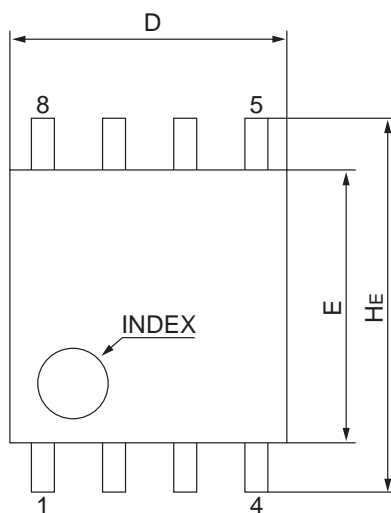
* Characteristics vary with applicable conditions and parts. Select proper parts after sufficient evaluation.

S1F71100 Series

MECHANICAL DATA

Plastic SOP4-8pin

Reference



Lead type STD (SOP4-8pin STD)

Symbol	Dimension in Millimeters			Dimension in Inches*		
	Min.	Nom.	Max.	Min.	Nom.	Max.
E	4.8	5	5.2	(0.189)	(0.197)	(0.204)
D ₁						
A		1.75			(0.069)	
A ₁		0.15			(0.006)	
A ₂		1.6			(0.063)	
e		1.27			(0.05)	
b	0.25	0.35	0.45	(0.010)	(0.014)	(0.017)
C	0.05	0.15	0.25	(0.002)	(0.006)	(0.009)
theta						
L		0.55			(0.022)	
L ₁						
L ₂						
HE	6.4	6.8	7.2	(0.252)	(0.268)	(0.283)
D	4.8	5	5.2	(0.189)	(0.197)	(0.204)
theta ₂						
theta ₃						
R						
R ₁						

* for reference

S1F71200 Series PWM Type Step-up/down DC/DC Switching Regulator

DESCRIPTION

S1F71200 is a step-up/step-down DC/DC converter control IC for which the CMOS process is used and to which a power transistor is connected outside. S1F71200 is composed of an oscillator, a reference voltage circuit, an error amplifier, a PWM circuit, a series regulator, a driver, etc. When this IC drives an external power transistor, S1F71200 can constitute a step-up/step-down DC/DC converter that operates as a [step-down] series regulator when the input voltage is High and that operates as a [step-up] switching regulator of pulse width modulation system (PWM) when the input voltage is Low.

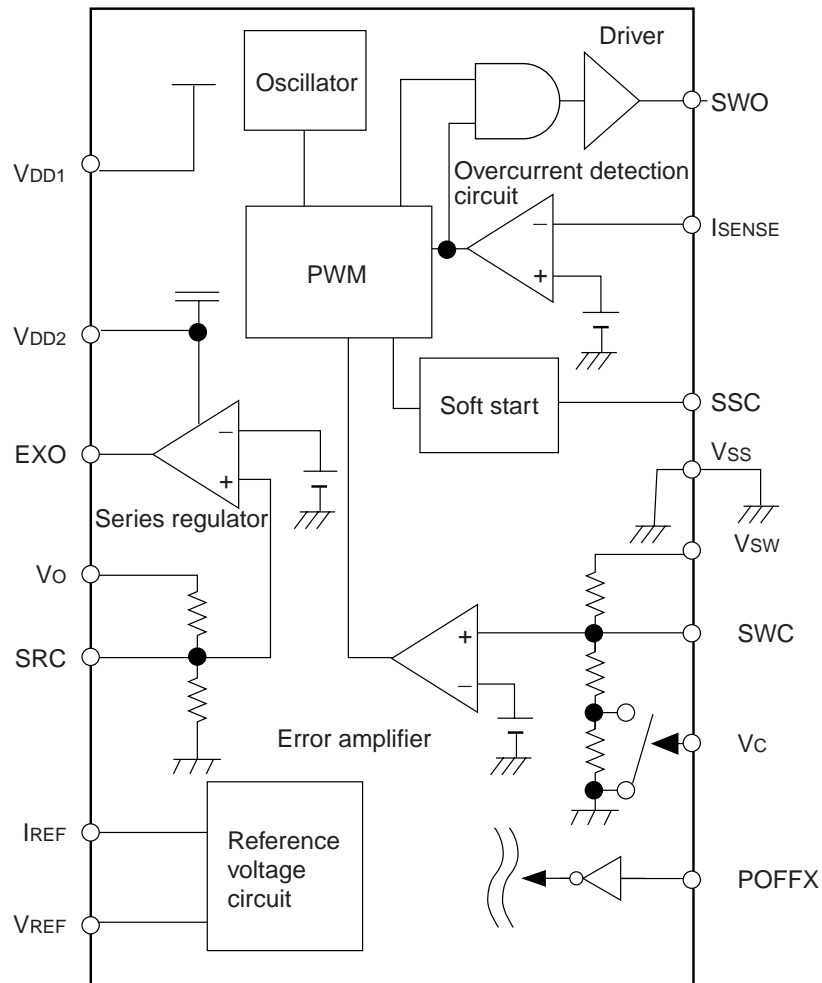
S1F71200 is also provided with an overcurrent protection circuit and a soft start circuit. When receiving external signals, S1F71200 can stop the oscillator and the switching circuit and turn off the power, so that it can reduce wasteful current consumption at the time of system halt.

FEATURES

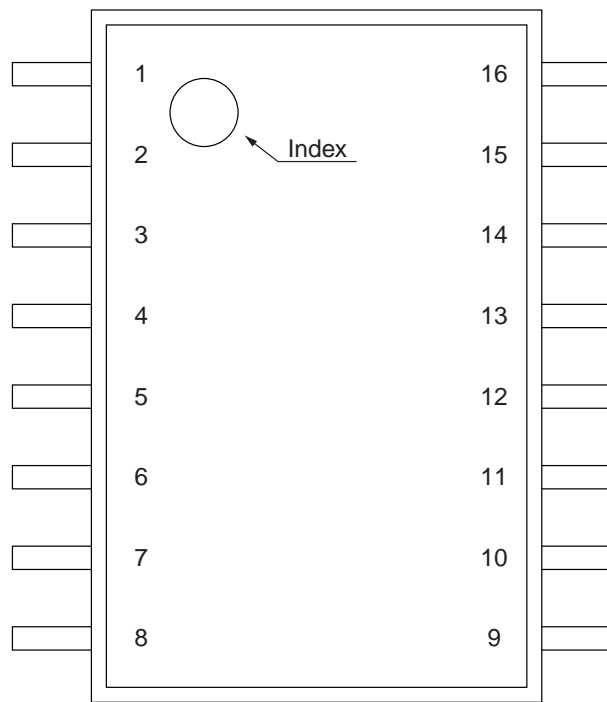
- Input voltage : 2.5V to 12.0V
- Output voltage : 5.0V (S1F71200M0A0)
3.3V (S1F71200M0B0)
- Power off current : 1.0 μ A
- Self current consumption : 150 μ A
(step-up portion)
15 μ A
(step-down portion)
- Frequency fixing (200kHz) PWM at step-up time
- Power off function (IC shutdown)
- Soft start function
- Overcurrent protection function
- Shipping pattern : plastic package
(SSOP2-16 pin)
- * Radiation-resistant design has not been provided for this specification.

S1F71200 Series

BLOCK DIAGRAM



PIN ASSIGNMENTS



SSOP2-16pin

S1F71200
Series

S1F71200 Series**PIN DESCRIPTIONS**

Pin No.	Pin name	Pin type	Power system	Description
1	VDD1	Power supply	VDD1	Power pin 1 (+), Input power pin
2	VDD2	Power supply	VDD2	Power pin 2 (+), Power pin for series regulator circuit
3	EXO	Output	VDD2	PNP transistor base drive pin for series regulator
4	Vo	—	—	Step-up/step-down output feedback pin
5	SRC	—	—	Series regulator phase compensation capacitor connection pin
6	IREF	Output	VDD1	Reference resistor connection pin. Connect a 100kΩ resistor between the Vss pins.
7	VREF	Output	VDD1	Reference voltage pin. Connect a 0.1μF capacitance between the Vss pins.
8	(N.C)	—	—	No connection
9	POFFX	Input	VDD1	Power off control pin. During normal operation : POFFX = VDD1 At power off time : POFFX = Vss
10	Vc	Input	VDD1	Step-up output voltage setting pin. For setting Vsw = Vo + 1.0V : Vc = VDD1 For setting Vsw = Vo + 0.5V : Vc = Vss
11	SWC	—	—	Switching regulator phase compensation capacitor connection pin
12	Vsw	—	—	Step-up output feedback pin
13	Vss	—	—	Power pin (-), Ground pin
14	SSC	—	VDD1	Capacitor connection pin for soft start
15	ISENSE	Input	VDD1	Overcurrent detection pin
16	SWO	Output	VDD1	Step-up switching power transistor drive pin

FUNCTIONAL DESCRIPTIONS

Description of Operation

S1F71200 is a switching regulator (step-up) and series regulator (step-down) control IC of pulse width modulation (PWM) system. When external parts such as transistor, inductor, capacitor, diode and resistor are connected, S1F71200 can constitute a step-up/step-down DC/DC converter.

When the input voltage is lower than the specified voltage value, S1F71200 raises the voltage to the set voltage (selectable at the VC pin) with the switching regulator and lowers the step-up voltage with the series regulator to stabilize the output voltage. On the other hand, when the input voltage is higher than the specified voltage value, S1F71200 stops the operation of the switching regulator (step-up) and operates the series regulator (step-down) only. Switching operations with input voltage makes constant voltage outputs possible all the time.

Operation of Switching Regulator

S1F71200 monitors voltage at the Vsw pin, i.e., the output voltage of the step-up switching regulator, and controls pulse width of the switching transistor. When the voltage at the Vsw pin drops below the step-up set voltage, S1F71200 changes the output level of the error amplifier and increases the on duty of the switching transistor for control.

On the other hand, when the voltage at the Vsw pin rises over the step-up set voltage, S1F71200 reduces the on duty for control. When voltages higher than the step-up set voltage is constantly supplied to the Vsw pin, S1F71200 stops operation of the step-up switching. When the switching stops completely, the input voltage is supplied to the Vsw pin through the coil and the diode. (The voltage at the Vsw pin comes to the one obtained by reducing V_F of the diode from the input voltage.)

Step-up Set Voltage

Step-up set voltage can be selected at the VC pin.

- ① VC = High VDD1 level :
Step-up set voltage = 6.0V (S1F71200M0A0)
4.3V (S1F71200M0B0)
- ② VC = Low VSS level :
Step-up set voltage = 5.5V (S1F71200M0A0)
3.8V (S1F71200M0B0)

In case of output stability and heavy load like ripple, ① is superior, but for the conversion efficiency at step-up operation, ② is superior. Characteristics vary with applicable external parts or voltage and load conditions. So, select a proper voltage after sufficient evaluation. The VC pin cannot be used in the open state.

Soft Start

When a capacitor is connected to the SSCAP pin, S1F71200 can set a soft start operation to prevent inrush current at the time when the power is turned on. The SSCAP pin is at the VSS level when the power is turned off (POFFX=VSS). When the operation state is set (POFFX=VDD1), the soft start capacitor starts being charged and the voltage at the SSCAP pin rises slowly. The step-up output voltage rises gradually as the voltage at the SSCAP pin rises. This operation is carried out when the power is turned on, when the power off is released or when the overcurrent detection is released and restrains surge current and output overshoot.

S1F71200 Series

Overcurrent Protection Circuit

The overcurrent protection circuit functions when an overcurrent flows through the current detection resistor during the step-up operation and the voltage at the ISENSE pin rises over the set voltage value. When the overcurrent protection function works, the transistor drive pin SWO comes to the VSS level and the switching transistor is turned off. Since the overcurrent protection circuit links to the soft start circuit, it drops the voltage at the SSCAP pin to the VSS level during overcurrent detection. When the overcurrent detection is released, the voltage at the SSCAP pin rises slowly and the soft start operation starts.

Power lost at the current detection resistor becomes a factor of lower efficiency. When the overcurrent protection circuit is not necessary, short-circuit the ISENSE pin to the VSS pin. The ISENSE pin cannot be used in an open state.

Operation of Series Regulator

S1F71200 has a built-in series regulator control circuit. When driving the PNP transistor as an external part, S1F71200 reduces voltage supplied to the VDD2 pin and constitutes a series regulator. The VDD2 pin is generally connected to the VSW pin of step-up output.

This series regulator operates monitoring voltage at the VO pin of step-up/step-down output. It controls the drive current (base current of the PNP transistor) at the EXO pin to stabilize voltage at the VO pin.

Power Off Function

S1F71200 can control circuit operations according to external signal control. When the POFFX pin is set to the VSS level, all circuits stop and their powers are turned off. The current consumption at the power off state is less than 1 μ A. When the power is off, the SWO pin is set to the VDD level, the EXO pin is set to the VDD2 level and respective external transistors are turned.

The voltage at the SSCAP pin comes to the VSS level, and the soft start circuit controls the step-up operation output voltage is controlled with the soft start circuit after the power off state is released. The soft start circuit controls step-up operations after power off release. When being set to the VDD level, the POFFX pin operates in general. The POFFX pin cannot be used in an open state. When the power off function is not used, connect the POFFX pin to the VDD1 pin.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Applicable Pin	Rating	Unit
Input voltage	V _{DD}	V _{DD1} V _{DD2}	15.0	V
Voltage at EXO pin	EXO	EXO	V _{SS} – 0.3 to V _{DD2} + 0.3	V
Voltage at Vo pin	V _O	V _O	V _{SS} – 0.3 to 15	V
Voltage at SRC pin	SRC	SRC	V _{SS} – 0.3 to 15	V
Voltage at IREF pin	IREF	IREF	V _{SS} – 0.3 to V _{DD1} + 0.3	V
Voltage at VREF pin	VREF	VREF	V _{SS} – 0.3 to V _{DD1} + 0.3	V
Voltage at POFFX pin	POFFX	POFFX	V _{SS} – 0.3 to V _{DD1} + 0.3	V
Voltage at Vc pin	V _C	V _C	V _{SS} – 0.3 to V _{DD1} + 0.3	V
Voltage at SWC pin	SWC	SWC	V _{SS} – 0.3 to 15	V
Voltage at Vsw pin	V _{SW}	V _{SW}	V _{SS} – 0.3 to 15	V
Voltage at SSC pin	SSC	SSC	V _{SS} – 0.3 to V _{DD1} + 0.3	V
I _{SENSE}	I _{SENSE}	I _{SENSE}	V _{SS} – 0.3 to V _{DD1} + 0.3	V
SWO	SWO	SWO	V _{SS} – 0.3 to V _{DD1} + 0.3	V
Package allowable loss	P _D	P _D	210 T _a ≤ 25°C	MW
Operating temperature	T _{opr}	—	–30 to +85	°C
Storage temperature	T _{stg}	—	–55 to +150	°C
Soldering temperature and time	T _{sol}	—	260 · 10	°C · s

Note

Any operation under conditions exceeding the above absolute maximum ratings may result in a malfunction or a permanent destruction. When even an item is more than the rating, a temporary normal operation is possible but with remarkably low reliability. So, be sure to keep all items below the ratings.

S1F71200 Series**ELECTRICAL CHARACTERISTICS****S1F71200M0A0** (Output : 5.0V)

DC Characteristics

Unless otherwise specified, Ta = 25°C.

Parameter	Symbol	Conditions	Rating			Unit
			Min.	Typ.	Max.	
Input supply voltage 1	V _{DD1}	V _{DD1} pin	2.5	—	12.0	V
Input supply voltage 2	V _{DD2}	V _{DD2} pin	—	—	12.0	V
Step-up set voltage	V _{SW}	V _{SW1} pin, V _C = V _{DD1} V _C = V _{SS}	—	6.0	—	V
			—	5.5	—	
Output voltage	V _O	V _{DD2} = 6V Ta = -30°C to +85°C	4.8	5.0	5.2	V
Operating time current consumption 1 (during step-up operation)	I _{VDD1-1} (V _{DD1} system)	V _{DD1} = 3V, V _{DD2} = 6V	—	150	250	μA
	I _{VDD2-1} (V _{DD2} system)	V _{DD1} = 3V, V _{DD2} = 6V	—	15	30	μA
Operating time current consumption 2 (operation for step-down only)	I _{VDD1-2} (V _{DD1} system)	V _{DD1} = 6V, V _{DD2} = 6V	—	100	200	μA
	I _{VDD2-2} (V _{DD2} system)	V _{DD1} = 6V, V _{DD2} = 6V	—	20	40	μA
Power off time current consumption	I _Q	V _{DD1} = 12V, V _{DD2} = 12V	—	—	1.0	μA
Output current at SWO pin	I _{OHSWO}	V _{DD1} = 3V, V _{DD2} = 6V V _{OH} = 50mV	-0.6	—	—	mA
	I _{OLSWO}	V _{DD1} = 3V, V _{DD2} = 6V V _{OL} = 50mV	1.0	—	—	mA
Input stability	ΔV _O	V _{DD} = 3V to 12V	—	50	—	mV*
Load stability	ΔV _O	I _L = 10mA to 100mA	—	50	—	mV*
Input voltage level at POFFX pin, at V _C pin	V _{IH}	—	0.8V _{DD1}	—	—	V
	V _{IL}	—	—	—	0.2V _{DD1}	V

DC Characteristics

Unless otherwise specified, Ta = 25°C.

Parameter	Symbol	Conditions	Rating			Unit
			Min.	Typ.	Max.	
Input pin leak current at POFFX pin, at Vc pin	I _{LINH}	V _{IN} = V _{DD1}	—	—	1.0	μA
	I _{LINL}	V _{IN} = V _{SS}	—	—	-1.0	μA
Step-up soft start time	T _{SS}	SSCAP = 0.1μF V _{DD1} = 3.0V, V _C = V _{DD1} I _o = 50mA	—	100	—	ms*
Step-up portion conversion efficiency	EFFI	V _{DD1} = 3.3V, V _C = V _{SS}	—	85	—	%*
Oscillation frequency	f _{OSC}	V _{DD1} = 3V (Measure it at the SWO pin.)	120	200	280	kHz
Overcurrent detection voltage	I _{DET}	V _{ISENSE}	0.10	0.15	0.20	V
Output voltage temperature coefficient	$\frac{\Delta V_o}{\Delta T_{opr}}$	Ta = -30°C to +85°C	—	0.015	—	%/°C

* These values are available when external parts are used in the example of circuit connection shown on the attached sheet.

The characteristics vary with applicable parts. Select proper parts after sufficient evaluation.

S1F71200 Series

S1F71200M0B0 (Output : 3.3V)

DC Characteristics

Unless otherwise specified, Ta = 25°C.

Parameter	Symbol	Conditions	Rating			Unit
			Min.	Typ.	Max.	
Input supply voltage 1	V _{DD1}	V _{DD1} pin	2.5	—	12.0	V
Input supply voltage 2	V _{DD2}	V _{DD2} pin	—	—	12.0	V
Step-up set voltage	V _{SW}	V _{SW1} pin, V _C = V _{DD1} V _C = V _{SS}	—	4.3	—	V
			—	3.8	—	
Output voltage	V _O	V _{DD2} = 4.3V Ta = -30°C to +85°C	3.15	3.3	3.45	V
Operating time current consumption 1 (during step-up operation)	IV _{DD1-1} (V _{DD1} system)	V _{DD1} = 3V, V _{DD2} = 4.3V	—	150	250	μA
	IV _{DD2-1} (V _{DD2} system)	V _{DD1} = 3V, V _{DD2} = 4.3V	—	15	30	μA
Operating time current consumption 2 (operation for step-down only)	IV _{DD1-2} (V _{DD1} system)	V _{DD1} = 5V, V _{DD2} = 5V	—	100	200	μA
	IV _{DD2-2} (V _{DD2} system)	V _{DD1} = 5V, V _{DD2} = 5V	—	20	40	μA
Power off time current consumption	I _Q	V _{DD1} = 12V, V _{DD2} = 12V	—	—	1.0	μA
Output current at SWO pin	I _{OHSWO}	V _{DD1} = 3V, V _{DD2} = 4.3V V _{OH} = 50mV	-0.6		—	mA
	I _{OLSWO}	V _{DD1} = 3V, V _{DD2} = 4.3V V _{OL} = 50mV	1.0		—	mA
Input stability	ΔV _O	V _{DD} = 3V to 12V	—	50	—	mV*
Load stability	ΔV _O	I _L = 10mA to 100mA	—	50	—	mV*
Input voltage level at POFFX pin, at V _C pin	V _{IH}	—	0.8V _{DD1}	—	—	V
	V _{IL}	—	—	—	0.2V _{DD1}	V

DC Characteristics

Unless otherwise specified, Ta = 25°C.

Parameter	Symbol	Conditions	Rating			Unit
			Min.	Typ.	Max.	
Input pin leak current at POFFX pin, at Vc pin	ILINH	VIN = VDD1	—	—	1.0	μA
	ILINL	VIN = VSS	—	—	-1.0	μA
Step-up soft start time	TSS	SSCAP = 0.1μF VDD1 = 3.0V, Vc = VDD1 Io = 50mA	—	70	—	ms*
Step-up portion conversion efficiency	EFFI	VDD1 = 3V, Vc = VSS	—	85	—	%*
Oscillation frequency	fosc	VDD = 3V (Measure it at the SWO pin.)	120	200	280	kHz
Overcurrent detection voltage	IDET	VISENSE	0.10	0.15	0.20	V
Output voltage temperature coefficient	$\frac{\Delta V_O}{\Delta T_{opr}}$	Ta = -30°C to +85°C	—	0.015	—	%/°C

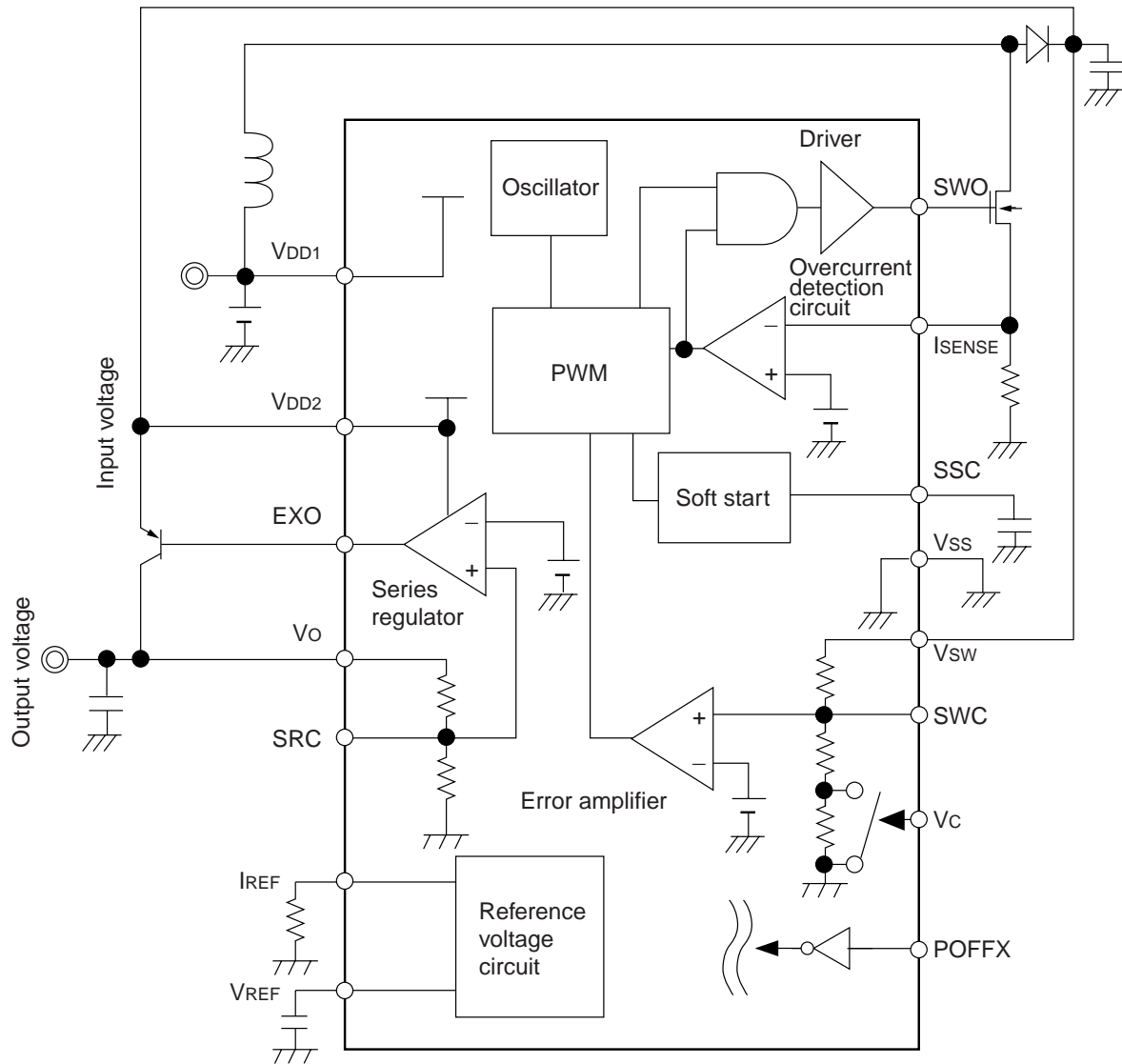
* These values are available when external parts are used in the example of circuit connection shown on the attached sheet.

The characteristics vary with applicable parts. Select proper parts after sufficient evaluation.

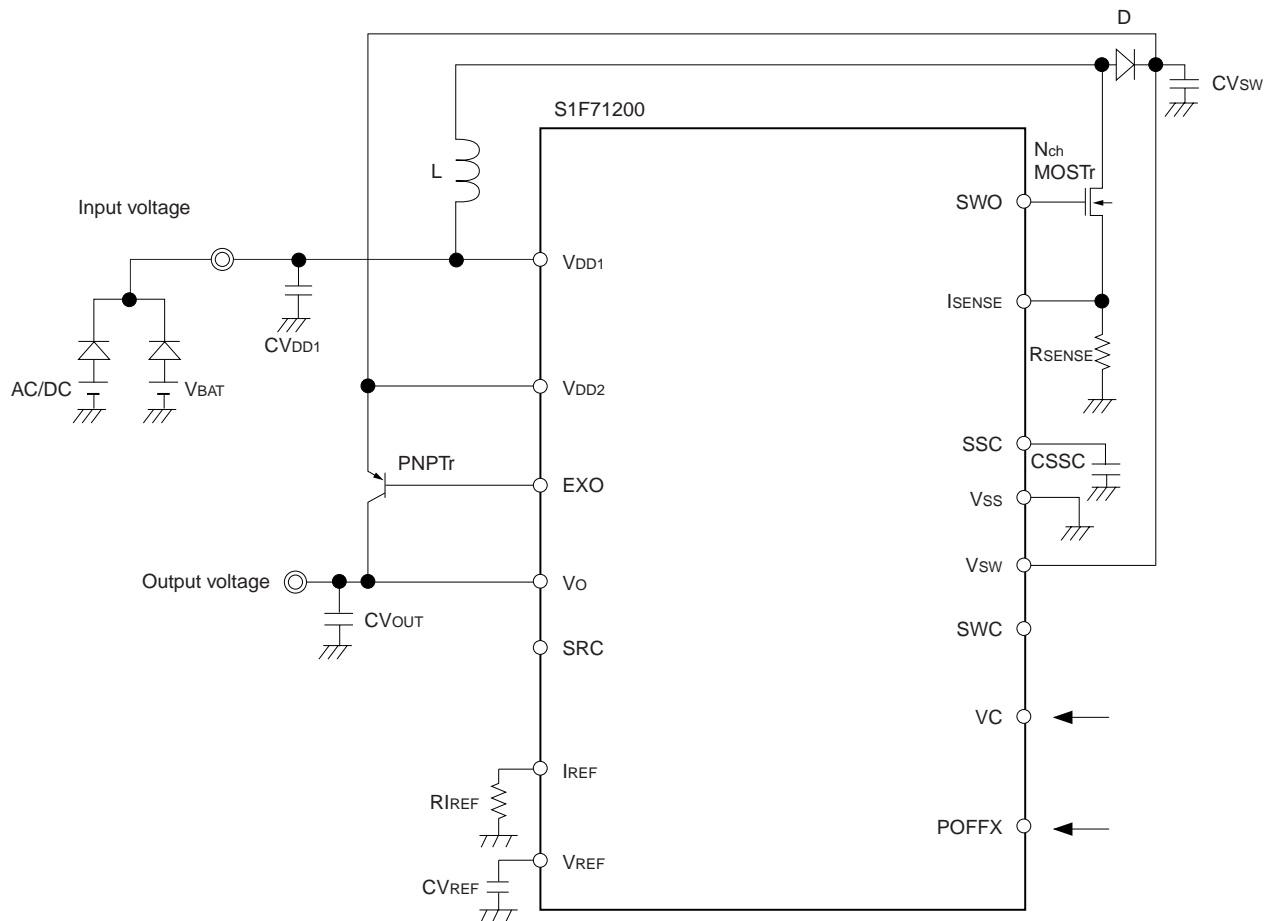
S1F71200 Series

EXAMPLE OF EXTERNAL CONNECTION OF REFERENCE CIRCUIT

Basic Circuit



Example of Parts Connection



CVDD1	47 μ F	Parts examples
NchTr		(Sanyo 16SA47M)
L	47 μ H	(Hitachi HAT2037T)
D	Schottky	(Sumida CR54)
CVSW	47 μ F	(Rohm RB161L-40)
PNPTr		(Sanyo 16SA47M)
CVOUT	22 μ F	(2SA1242)
RREF	100k Ω	(Sanyo 10SL22M)
CVREF	0.1 μ F	
CSSC	0.1 μ F	
RSENSE	0.1 Ω	

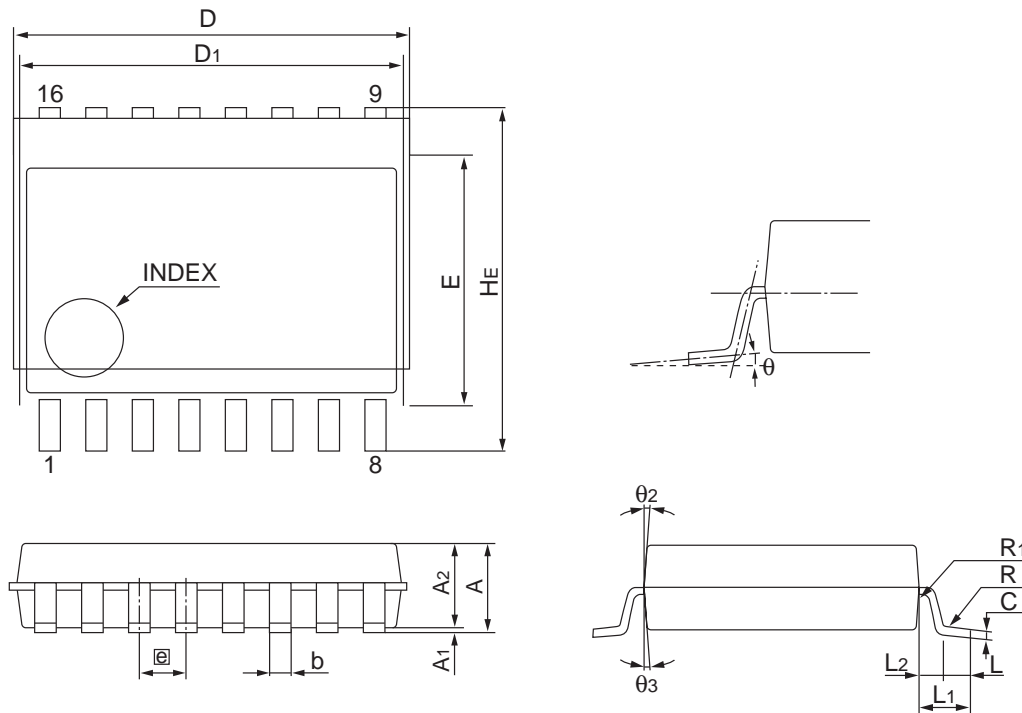
* Characteristics vary with applicable conditions and parts. Select proper parts after sufficient evaluation.

S1F71200 Series

MECHANICAL DATA

Plastic SSOP2-16pin

Reference



Lead type STD (SSOP2-16pin STD)

Symbol	Dimension in Millimeters			Dimension in Inches*		
	Min.	Nom.	Max.	Min.	Nom.	Max.
E	4.2	4.4	4.6	(0.166)	(0.173)	(0.181)
D1	6.4	6.6	6.8	(0.252)	(0.260)	(0.267)
A			1.7			(0.066)
A1		0.05			(0.002)	
A2	1.4	1.5	1.6	(0.056)	(0.059)	(0.062)
Ⓜ		0.8			(0.031)	
b	0.26	0.36	0.46	(0.011)	(0.014)	(0.018)
C	0.1	0.15	0.25	(0.004)	(0.006)	(0.009)
θ	0°		10°	(0°)		(10°)
L	0.3	0.5	0.7	(0.012)	(0.020)	(0.027)
L1		0.9			(0.035)	
L2		0.4			(0.016)	
HE	5.9	6.2	6.5	(0.233)	(0.244)	(0.255)
D			7			(0.275)
θ2						
θ3						
R						
R1						

* for reference

5. DC/DC Switching Regulators & Voltage Follower

S1F75300 Series Step-up Switching Regulator With Built-in Voltage Follower

DESCRIPTION

S1F75300 is a highly efficient and low power consumption step-up switching regulator with built-in voltage follower developed by using CMOS silicon gate processor. (For boosting, the external coil is used.)

The output voltage is adjustable with the 8-bit electronic volume.

This IC is optimum to power supply portions of medium and small liquid crystal panels for which high efficiency is requested.

FEATURES

- Boosting efficiency : 80%
- Low current consumption : Typ.200 μ A (without load)
- Output voltage (step-up output) : 30V Max., adjustable with the electronic volume.
- Optimum to small and medium liquid crystal panels
Input voltage : 2.7V to 5.5V
Output voltage : to 27V
- Reduction of current consumption at the time of standby with power-off function

LINE UP

Product	Amplified output voltage	Voltage at Vo2 pin	Temperature coefficient at Vo2 pin	Voltage follower duty
S1F75300M0A0	25V	22V	-0.06%/°C	1/160
S1F75300M0B0	27V	24V	-0.06%/°C	1/240

S1F75300 Series

BLOCK DIAGRAM

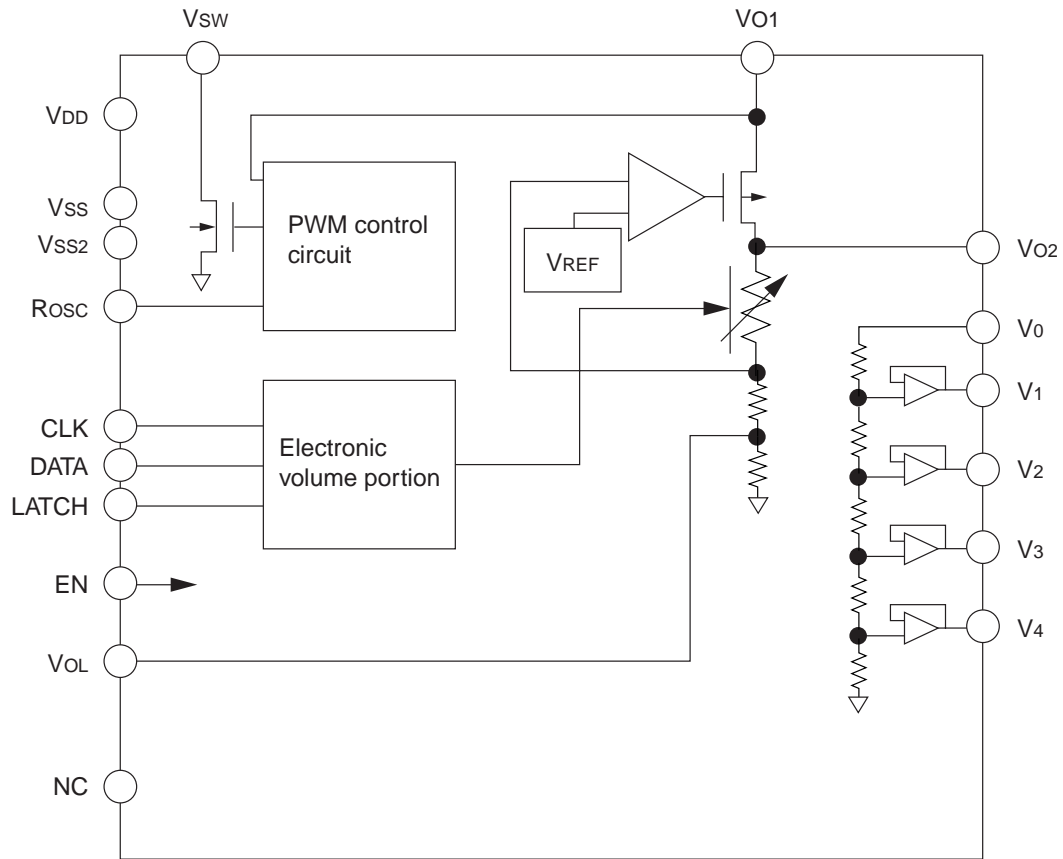


Figure 1 Block Diagram of S1F75300

PIN DESCRIPTIONS

Pin No.	Pin name	Description
1	DATA	Data input pin for adjusting electronic volume bias
2	CLK	Clock input pin for adjusting electronic volume bias
3	LATCH	Data latch input pin for adjusting electronic volume bias
4,9,16	NC	No connection
5,8	Vss, Vss2	GND pin
6	ROSC	External resistance connection pin for adjusting oscillation current
7	EN	Enable pin. HIGH : Normal operation, LOW : System operation stop
10	Vsw	External inductance drive pin
11	V4	Liquid crystal drive voltage pin 4
12	V3	Liquid crystal drive voltage pin 3
13	V2	Liquid crystal drive voltage pin 2
14	V1	Liquid crystal drive voltage pin 1
15	V0	Liquid crystal drive voltage pin 0
17	Vo2	Output voltage pin
18	Vo1	Output voltage monitor pin
19	VoL	Output voltage external adjustment pin
20	VDD	Power supply pin

PIN ASSIGNMENTS

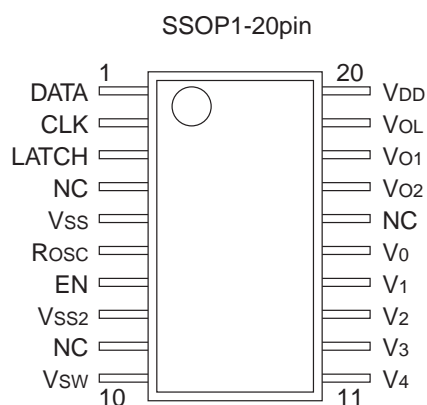


Figure 2 Pin Assignments

S1F75300 Series

FUNCTIONAL DESCRIPTIONS

Switching Regulator Portion

Operation of Basic Boosting Circuit

S1F75300 boosts using clock pulses generated in the PWM control circuit. Figure 3 shows the block diagram for explaining the principle of operation of the boosting circuit. This circuit stores energy in the inductance L when the switching transistor (Tr1) is on and can charge the capacitor C with the stored energy by passing it through the diode D for output when the switching transistor is off.

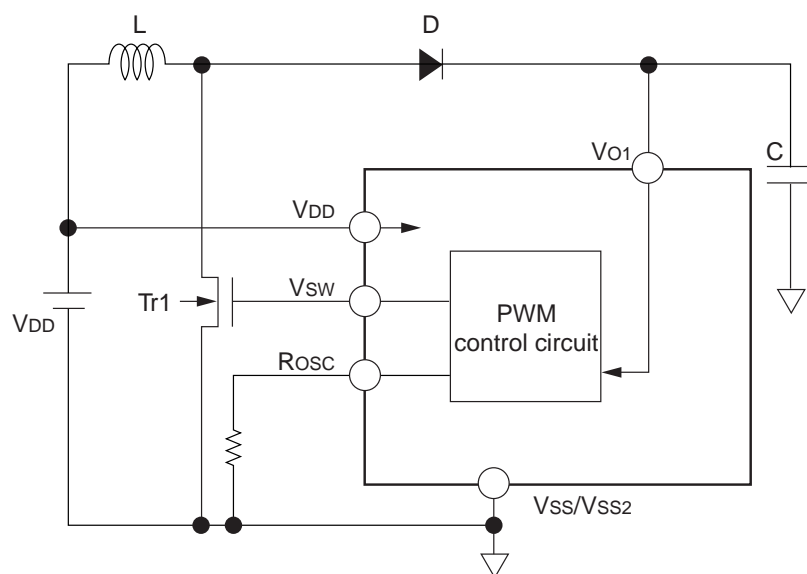


Figure 3 Block Diagram of Boosting Circuit

Reference Voltage Generator, Output Voltage Setting Stabilizing Circuit

- Reference Voltage Generator, Output Voltage Setting Stabilizing Circuit

The reference voltage generator is for generating stabilized voltage (reference voltage) not depending on input voltage necessary for the output voltage setting stabilizing circuit or the voltage detection circuit.

The reference voltage generator has a built-in temperature characteristic compensation circuit. For the temperature characteristic, any one temperature characteristics can be selected out of four temperature characteristics in the range from $-0.18\%/^{\circ}\text{C}$ to $-0.06\%/^{\circ}\text{C}$. (Selection with Mask Option.

The output voltage setting stabilizing circuit outputs the stabilized voltage VO_2 after receiving a boosted voltage. The output voltage VO_2 can be set to a specified voltage when the position of Point A on the intermediate tap of the resistor connected between the pin VO_2 and the pin GND as shown in Figure 4 is changed.

The variable resistor in Figure 4 has the function of electronic volume and can change the output VO_2 as the resistance value is changed as mentioned in Paragraph 5.1.3.

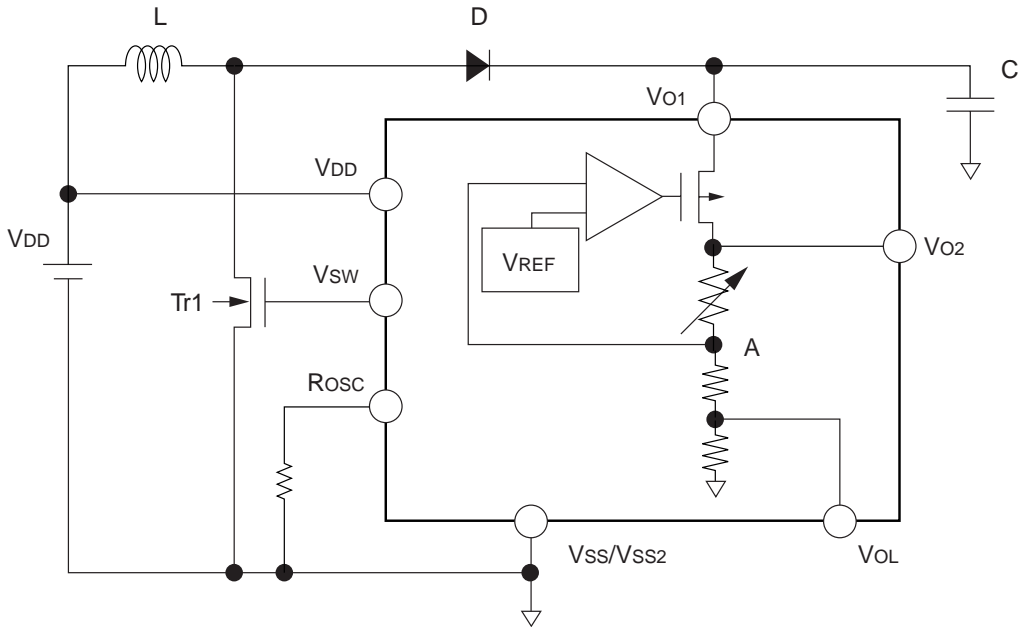


Figure 4 Stabilizing Circuit

Note

In the practical boosting state, a ripple voltage is superimposing the output setting voltage set as mentioned above. Since this ripple voltage is affected by applicable external parts and loading conditions, set the value of the coil through which the load current passes and check it before use.

- Output Voltage External Adjustment Pin (VOL)

The voltage VO_2 boosted and stabilized with the output voltage setting stabilizing circuit can slightly adjust output voltages when an external resistor is connected to the output voltage external adjustment pin VOL as shown in Figure 10 in Chapter 7, Example of External Connection.

S1F75300 Series

S1F75300 Series

Electronic Volume Portion

S1F75300 has a built-in 8-bit shift register and a built-in 8-bit latch so that it can vary the voltage VO2 when serial data is input. The 8-bit latch enables to vary the output voltage VO2. Data taken in the shift register is taken in the 8-bit latch as a synchronous strobe is input. The following shows the block diagram and the timing chart.

- DATA** : Serial data input pin for setting output voltage and bias value.
 "Data 1" is input at the High level and "Data 0" is input at the Low level. Data are input to (LSB) and (MSB) in this order.
- CLK** : Clock input to shift register pin
 When the clock starts, data at the DATA pin is taken in the shift register. Data to be taken in shift one after another for every clock. So, data input last becomes valid.
- LATCH** : Latch signal input pin
 When latch signal is set to High the content of the shift register is taken in the 8-bit latch.

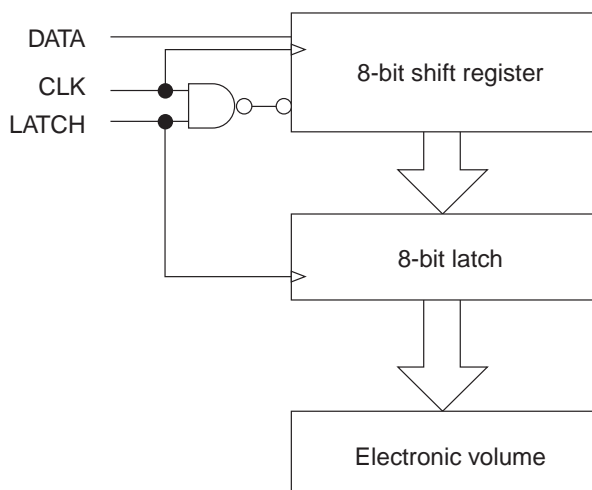


Figure 5-1 Block Diagram

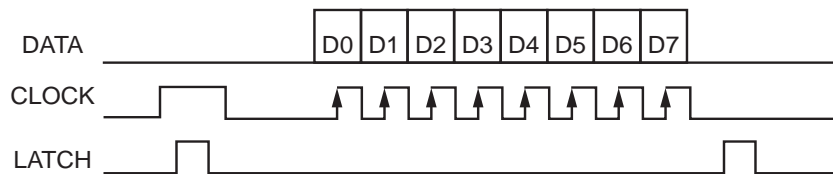


Figure 5-2 Timing Chart of 8-bit Latch Portion

Table 1 List of Electronic Volume Set Points

D7	D6	D5	D4	D3	D2	D1	D0	Electronic volume value
0	0	0	0	0	0	0	0	0
.....							
0	1	1	1	1	1	1	1	127
.....							
1	0	0	0	0	0	0	0	128
.....							
1	1	1	1	1	1	1	1	255

S1F75300 Series

S1F75300 Series

Voltage Follower Portion

The voltage follower portion of S1F75300 enables to adjust bias with the electronic volume as explained in Paragraph 5.1.3.

Figure 6 shows the block diagram of the voltage follower portion.

After the power is turned on, the resistance between V2 and V3 is set to nR. (The n value is selected optionally.) When n is 11 and 13 for example, the voltages at V1 to V4 are as follows after the power is turned on:

Table 2 Output Voltage of Voltage Follower

	n=11 (1/160 duty)	n=13 (1/240 duty)
V1	$13/14 \cdot V_0$	$16/17 \cdot V_0$
V2	$12/14 \cdot V_0$	$16/17 \cdot V_0$
V3	$2/14 \cdot V_0$	$2/17 \cdot V_0$
V4	$1/14 \cdot V_0$	$1/17 \cdot V_0$

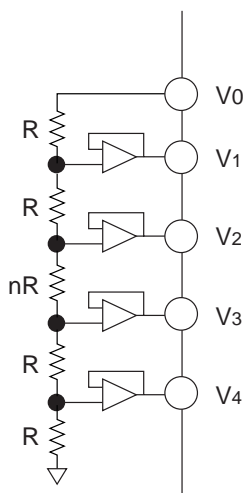


Figure 6 Block Diagram of Voltage Follower

EN Pin

This pin is for boosting action and for stopping and starting the voltage follower portion.

When the EN pin is set to Low level, the internal circuit action stops and the current consumption is restrained.

ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings

(V_{SS} = 0V, T_a=25°C)

Parameter	Symbol	Rating		Unit	Remarks
		Min.	Max.		
VSW pin voltage	V _{VSW}	V _{SS} - 0.3	33	V	—
VSW pin current	I _{VSW}	—	100	mA	—
Voltage of other pins	V*	V _{SS} - 0.3	7	V	—
Allowable loss	P _D	—	130	mW	—
Operating temperature	T _{opr}	-30	85	°C	—
Storage temperature	T _{stg}	-65	150	°C	—
Soldering temperature and time	T _{sol}	—	260 • 10	°C • s	At leads

S1F75300 Series**ELECTRICAL CHARACTERISTICS**
Step-up Switching Regulator and Voltage Follower Portion

DC Characteristics

Parameter	Symbol	Rating			Unit	Conditions
		Min.	Typ.	Max.		
Input voltage	V _{DD}	2.7	—	5.5	V	
Amplified output voltage	V _O	—	—	30	V	
Current consumption	I _{OPR}	—	200	—	μA	V _{DD} = 5.0V
Current consumption at enable time	I _{EN}	—	—	5	μA	
Switching transistor ON-state resistance	R _{SWON}	—	—	15	Ω	
Switching transistor leak current	I _{SWQ}	—	—	1	μA	
Input stability	ΔV _{O1}	—	0.5	—	%/V	V _{O2} =27V
Load stability		—	90	—	mV	V _{O2} =27V, I _{vout2} =-10mA
Output voltage / temperature coefficient	ΔV _{O1} / ΔT _a	—	-0.18	—	% / °C	
		—	-0.15	—		
		—	-0.10	—		
		—	-0.06	—		
Oscillation frequency	F _{CLK}	145	150	155	kHz	
Maximum duty ratio	F _{DUTY}	80	—	90	%	
Resistance between pins V _{OL} and V _{SS}	R _{VOL}	64	—	256	kΩ	
V _{O2} output current	I _{O2}	—	—	18	mA	
Efficiency	Eff	—	80	—	%	

Parameter	Symbol	Rating			Unit	Conditions
		Min.	Typ.	Max.		
V1 output current	V1OH	$V_1 + 70\text{mV}$	—	—	mA	$I_{OH} = 2\text{mA}$, $V_1 = \text{No-load voltage}$
	V1OL	—	—	$V_1 - 50\text{mV}$		$I_{OL} = -2\text{mA}$, $V_1 = \text{No-load voltage}$
V2 output current	V2OH	$V_2 + 50\text{mV}$	—	—	mA	$I_{OH} = 2\text{mA}$, $V_2 = \text{No-load voltage}$
	V2OL	—	—	$V_2 - 70\text{mV}$		$I_{OL} = -2\text{mA}$, $V_2 = \text{No-load voltage}$
V3 output current	V3OH	$V_3 + 70\text{mV}$	—	—	mA	$I_{OH} = 2\text{mA}$, $V_3 = \text{No-load voltage}$
	V3OL	—	—	$V_3 - 50\text{mV}$		$I_{OL} = -2\text{mA}$, $V_3 = \text{No-load voltage}$
V4 output current	V4OH	$V_4 + 50\text{mV}$	—	—	mA	$I_{OH} = 2\text{mA}$, $V_4 = \text{No-load voltage}$
	V4OL	—	—	$V_4 - 70\text{mV}$		$I_{OL} = -2\text{mA}$, $V_4 = \text{No-load voltage}$

S1F75300 Series

Electronic Volume

DC Characteristics

Parameter	Symbol	Rating			Unit	Conditions
		Min.	Typ.	Max.		
Output voltage range	V _{O2}		—	30	V	
Electronic volume resolution		—	1/256	—		
Linearity error		—	—	±1/2	LSB	
High level input voltage	V _{IH}	2.0	—	—	V	
Low level input voltage	V _{IL}	—	—	0.8	V	

AC Characteristics

Parameter	Symbol	Rating			Unit	Conditions
		Min.	Typ.	Max.		
CLK cycle	t _{CLK}	1	—	—	μs	
Data setup time	t _{CST}	0.5	—	—	μs	
Data hold time	t _{CHT}	0.5	—	—	μs	
Latch pulse width	t _{WLTC}	0.5	—	—	μs	
CLK power off → Latch start	t _{LST}	0.5	—	—	μs	
Latch power off → CLK start	t _{LHT}	0.5	—	—	μs	

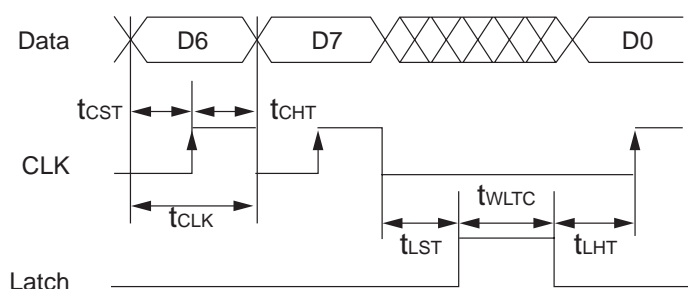


Figure 8 Electronic Volume Portion AC Characteristic Timing Chart

EXAMPLE OF EXTERNAL CONNECTION

(1) Connection Example 1

Figure 9 shows an example of the basic circuit of S1F75300.

(2) Connection Example 2

Figure 10 shows a connection example for connecting a variable resistor to the VOL pin so as to adjust VO2.

(3) Connection Example 3

Figure 11 shows a connection example for connecting a temperature compensation circuit between pins VO2 and VO so as to adjust temperature correction of voltage of the voltage follower portion with an external circuit.

Figure 12 shows an example of a temperature compensation circuit.

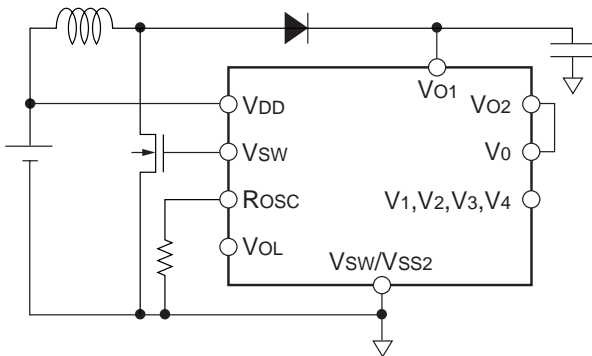


Figure 9 Connection Example 1

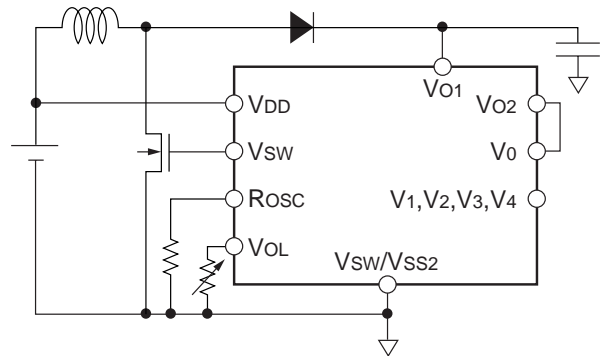


Figure 10 Connection Example 2

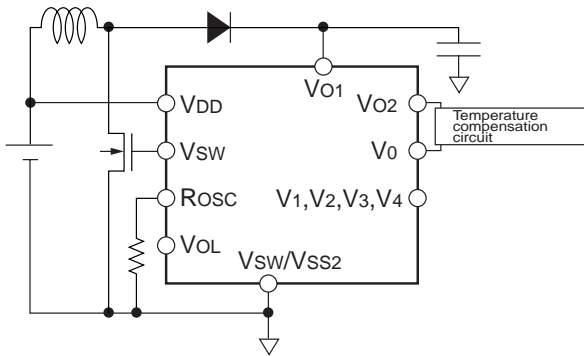


Figure 11 Connection Example 3

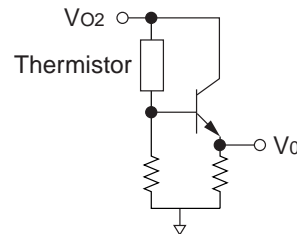


Figure 12 Example of Temperature Compensation Circuit

S1F75300 Series**EXAMPLE OF REFERENCE CIRCUIT**

The figure below shows an example of connection of this IC and a liquid crystal display panel.

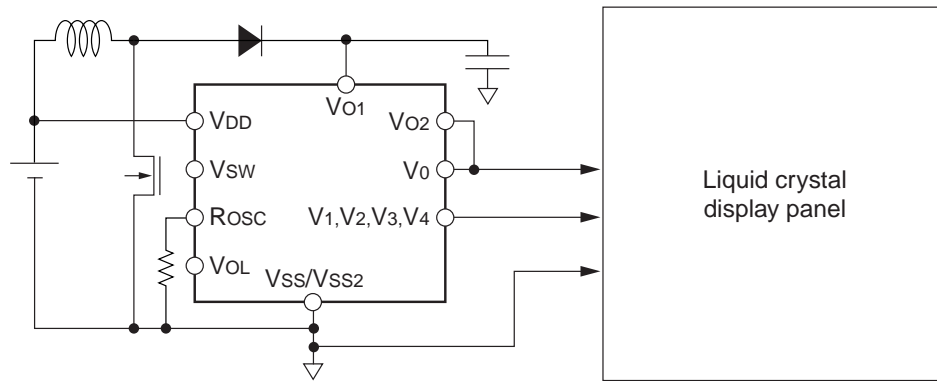


Figure 14 Example of Reference Circuit

6. Voltage Detector

S1F77200Y Series CMOS Voltage Detectors

DESCRIPTION

The S1F77200Y series products are non-adjusting voltage detectors being developed utilizing the base of the CMOS silicon gate process.

This voltage detector consists of the reference voltage circuit, voltage comparator, hysteresis circuit and output circuit, all operating on smaller current.

A voltage range to be detected is internally set on respective detectors. A wide variety of our standard products are grouped as shown below according to the output format employed for the voltage detector output pin. The S1F77200Y series employs N-channel open drain output approach. And the S1F77210Y series and S1F77220Y series employ the CMOS output and P-channel output, respectively.

The package used is the SOT89-3 pin plastic package. Our voltage detectors are used for determining battery life, and also for monitoring supply voltage fed to microcomputers and LSI systems.

FEATURES

- Full lineups: 19 types are prepared for the detection range between 2.0V to 5.0V.
For the detection range from 0.8V to 2.5V, 7 types are available (products designed for lower voltage detection).
- Low operating current: Typ. 2.0 μ A ($V_{DD} = 5.0V$).
- Low operating voltage: 1.5V at minimum.
- Absolute maximum rated voltage: 15V maximum.
- Highly stable built-in reference voltage source: Typ. 1.0V.
- Better temperature characteristics of output voltage: Typ. -100ppm/ $^{\circ}$ C.

S1F77200Y Series

LINEUP

Table 5-1

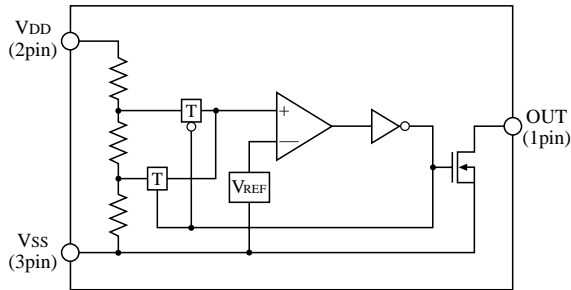
Product	Voltage detectable			Output type	Output phase	
	Min.	Typ.	Max.		Less than VDET	VDET or above
S1F77210Y1C0	2.10	2.15	2.20	CMOS	Low level	High level
S1F77210Y1P0	2.20	2.25	2.30	CMOS	Low level	High level
S1F77210Y1S0	2.30	2.35	2.40	CMOS	Low level	High level
S1F77210Y1E0	2.50	2.55	2.60	CMOS	Low level	High level
S1F77210Y1F0	2.60	2.65	2.70	CMOS	Low level	High level
S1F77210Y1R0	2.73	2.80	2.87	CMOS	Low level	High level
S1F77210Y1G0	2.93	3.00	3.07	CMOS	Low level	High level
S1F77210Y1H0	3.13	3.20	3.27	CMOS	Low level	High level
S1F77210Y130	3.43	3.50	3.57	CMOS	Low level	High level
S1F77210Y1T0	3.90	4.00	4.10	CMOS	Low level	High level
S1F77210Y1M0	4.10	4.20	4.30	CMOS	Low level	High level
S1F77210Y1J0	4.30	4.40	4.50	CMOS	Low level	High level
S1F77210Y120	4.50	4.60	4.70	CMOS	Low level	High level
S1F77210Y1K0	4.70	4.80	4.90	CMOS	Low level	High level
S1F77210Y1L0	4.90	5.00	5.10	CMOS	Low level	High level
S1F77210Y2C0	2.10	2.15	2.20	CMOS	High level	Low level
S1F77210Y2F0	2.60	2.65	2.70	CMOS	High level	Low level

Table 5-2

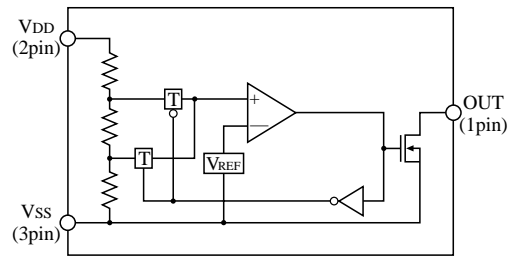
Product	Voltage detectable			Output type	Output phase	
	Min.	Typ.	Max.		Less than VDET	VDET or above
S1F77200Y1T0	3.90	4.00	4.10	N ch Open Drain	Low level	Hi-Z
S1F77200Y1F0	2.60	2.65	2.70	N ch Open Drain	Low level	Hi-Z
S1F77200Y1C0	2.10	2.15	2.20	N ch Open Drain	Low level	Hi-Z
S1F77200Y1N0	1.85	1.90	1.95	N ch Open Drain	Low level	Hi-Z
S1F77200Y1B0	1.10	1.15	1.20	N ch Open Drain	Low level	Hi-Z
S1F77200Y1Y0	1.05	1.10	1.15	N ch Open Drain	Low level	Hi-Z
S1F77200Y1A0	1.00	1.05	1.10	N ch Open Drain	Low level	Hi-Z
S1F77200Y1V0	0.90	0.95	1.00	N ch Open Drain	Low level	Hi-Z
S1F77220Y2D0	1.20	1.25	1.30	P ch Open Drain	High level	Hi-Z

BLOCK DIAGRAM

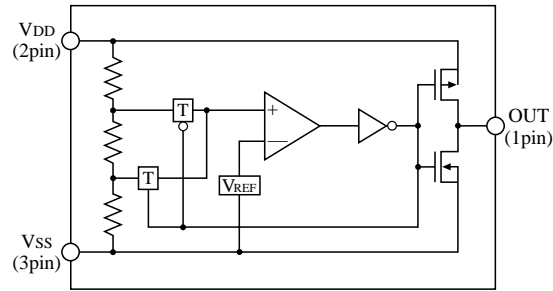
S1F77200Y1*0 Type



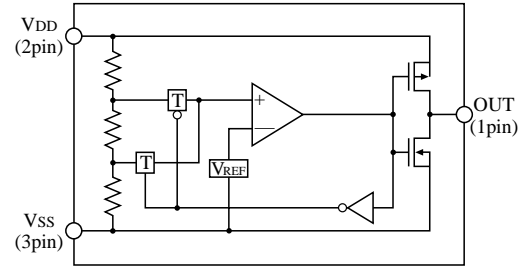
S1F77200Y2*0 Type



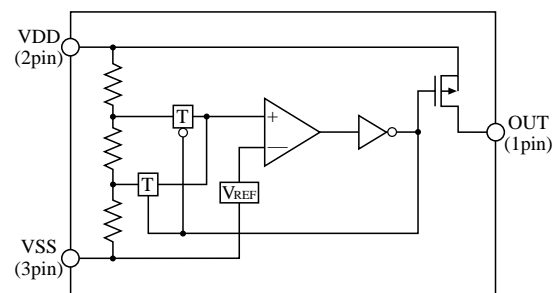
S1F77210Y1*0 Type



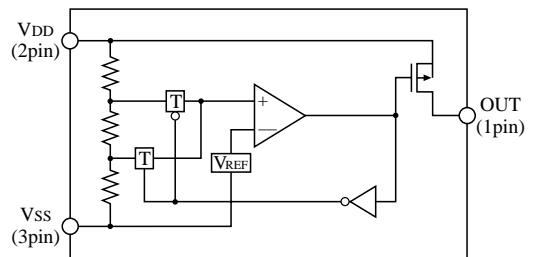
S1F77210Y2*0 Type



S1F77220Y1*0 Type



S1F77220Y2*0 Type



Note: A different code can be employed for the ones preceded by * marking depending on their detecting voltage specification.

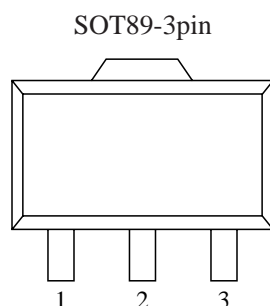
S1F77200Y Series

S1F77200Y Series

PIN DESCRIPTIONS

Pin No.	Pin name	Description
1	OUT	Voltage detection output pin
2	VDD	Input voltage pin (positive side)
3	VSS	Input voltage pin (negative side)

PIN ASSIGNMENTS



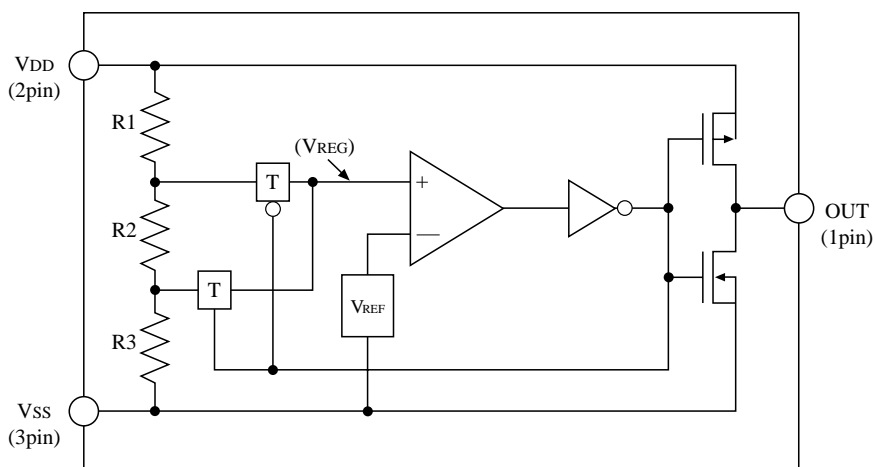
FUNCTIONAL DESCRIPTIONS

The S1F77200Y series has the circuit configuration as shown in the figure below. For the detection, divided potential (V_{REG}) across the resistors inserted across the power supply and the reference voltage (V_{REF}) generated on the IC are entered to the voltage comparator. Since the voltage comparator is designed to detect a target voltage even when potential difference between V_{REG} and V_{ref} minute, hysteresis is added so that the comparator may not fail due to noise on the power supply and such. In the example shown in the figure below,

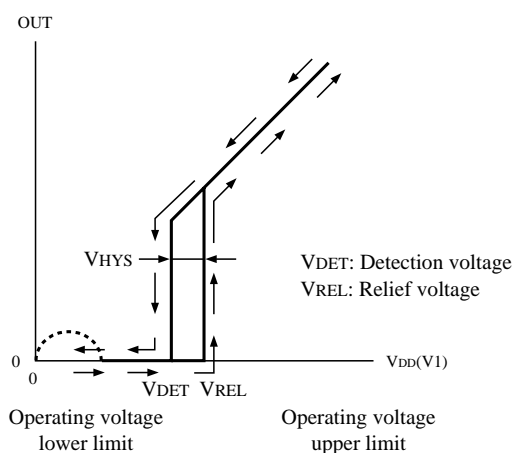
detection voltage (V_{DET}) for the input voltage drop and relief voltage (V_{REL}) for the increased input voltage are set based the following formula.

$$\text{Detection voltage: } V_{DET} = \frac{R1+R2+R3}{R2+R3} \cdot V_{REF}$$

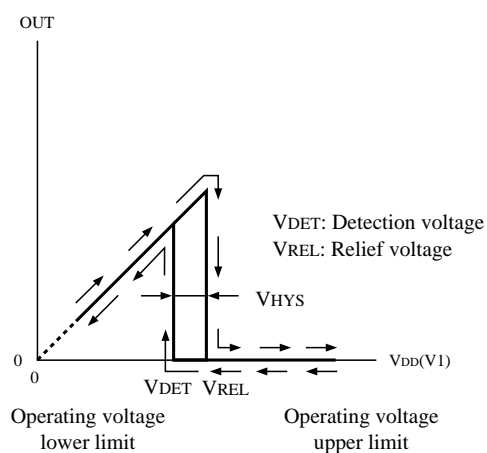
$$\text{Relief voltage: } V_{REL} = \frac{R1+R2+R3}{R3} \cdot V_{REF}$$



The following figures show the input and output characteristics of the S1F77200Y series.



[S1F772*0Y1*0 Type]



S1F772*0Y2*0 Type

Note: The above input/output characteristics assumes that the pull up resistor is connected to the output pin for the S1F77200Y series. For the S1F77220 series, it assumes that the pull down resistor is connected between the OUT and VDD pins.

If the input voltage that is applied between VDD and VSS terminals drops below the lower limit of voltage for IC operation, the output condition of the OUT terminal may become unsteady.

Ensure to prevent problems from occurring in circuit operation.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rating	Unit
Supply voltage range	$V_{DD} - V_{SS}$	15	V
Output voltage	V_O	$V_{DD} + 0.3$ to $V_{SS} - 0.3$ (S1F77210)	V
		15 to $V_{SS} - 0.3$ (S1F77200)	
		$V_{DD} + 0.3$ to $V_{DD} - 15$ (S1F77220)	
Output current	I_O	50	mA
Allowable dissipation	P_D	200	mW
Operating temperature	T_{opr}	-40 to +85	°C
		-30 to +85 (designed for lower voltage operation)	
Storage temperature	T_{stg}	-65 to +150	°C
Soldering temperature and time	T_{sol}	260 · 10 (at leads)	°C · s

S1F77200Y Series**ELECTRIC CHARACTERISTICS****S1F77210Y1C0**

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.50	—	12.0	V
Detection voltage	VDET	Ta = 25°C	2.10	2.15	2.20	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.05	0.10	0.15	V
Operating current	IDD	VDD = 3.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
High level output current	IOH	VDD = 3.0V OUT = 2.7V	—	-1.00	-0.25	mA
Low level output current	IOL	VDD = 2.0V OUT = 0.2V	0.20	1.00	—	mA
Detection voltage response time	T _{PHL}	VDD = 3V→2V Ta = 25°C	—	8	40	μs
		VDD = 3V→2V Ta = -30°C to +85°C	—	—	200	μs

S1F77210Y1P0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.50	—	12.0	V
Detection voltage	VDET	Ta = 25°C	2.20	2.25	2.30	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.05	0.10	0.15	V
Operating current	IDD	VDD = 3.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
High level output current	IOH	VDD = 3.0V OUT = 2.7V	—	-1.00	-0.25	mA
Low level output current	IOL	VDD = 2.0V OUT = 0.2V	0.20	1.00	—	mA
Detection voltage response time	T _{PHL}	VDD = 3V→2V Ta = 25°C	—	8	40	μs
		VDD = 3V→2V Ta = -30°C to +85°C	—	—	200	μs

S1F77210Y1S0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.50	—	12.0	V
Detection voltage	VDET	Ta = 25°C	2.30	2.35	2.40	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.05	0.10	0.15	V
Operating current	IDD	VDD = 3.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
High level output current	IOH	VDD = 3.0V OUT = 2.7V	—	-1.00	-0.25	mA
Low level output current	IOL	VDD = 2.0V OUT = 0.2V	0.20	1.00	—	mA
Detection voltage response time	TPHL	VDD = 3V → 2V Ta = 25°C	—	8	40	μs
		VDD = 3V → 2V Ta = -30°C to +85°C	—	—	200	μs

S1F77210Y1E0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.50	—	12.0	V
Detection voltage	VDET	Ta = 25°C	2.50	2.55	2.60	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.05	0.10	0.15	V
Operating current	IDD	VDD = 3.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
High level output current	IOH	VDD = 3.0V OUT = 2.7V	—	-1.00	-0.25	mA
Low level output current	IOL	VDD = 2.0V OUT = 0.2V	0.20	1.00	—	mA
Detection voltage response time	TPHL	VDD = 3V → 2V Ta = 25°C	—	8	40	μs
		VDD = 3V → 2V Ta = -30°C to +85°C	—	—	200	μs

S1F77200Y Series**S1F77210Y1F0**

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.50	—	12.0	V
Detection voltage	VDET	Ta = 25°C	2.60	2.65	2.70	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.05	0.10	0.15	V
Operating current	IDD	VDD = 3.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
High level output current	IOH	VDD = 3.0V OUT = 2.7V	—	-1.00	-0.25	mA
Low level output current	IOL	VDD = 2.0V OUT = 0.2V	0.20	1.00	—	mA
Detection voltage response time	T _{PHL}	VDD = 3V→2V Ta = 25°C	—	8	40	μs
		VDD = 3V→2V Ta = -30°C to +85°C	—	—	200	μs

S1F77210Y1R0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.50	—	12.0	V
Detection voltage	VDET	Ta = 25°C	2.73	2.80	2.87	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.05	0.10	0.15	V
Operating current	IDD	VDD = 3.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
High level output current	IOH	VDD = 3.0V OUT = 2.7V	—	-1.00	-0.25	mA
Low level output current	IOL	VDD = 2.0V OUT = 0.2V	0.20	1.00	—	mA
Detection voltage response time	T _{PHL}	VDD = 3V→2V Ta = 25°C	—	8	40	μs
		VDD = 3V→2V Ta = -30°C to +85°C	—	—	200	μs

S1F77210Y1G0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.50	—	12.0	V
Detection voltage	VDET	Ta = 25°C	2.93	3.00	3.07	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.09	0.15	0.21	V
Operating current	IDD	VDD = 4.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
High level output current	IOH	VDD = 4.0V OUT = 3.6V	—	-1.60	-0.40	mA
Low level output current	IOL	VDD = 2.0V OUT = 0.2V	0.20	1.00	—	mA
Detection voltage response time	TPHL	VDD = 4V → 3V Ta = 25°C	—	8	40	μs
		VDD = 4V → 3V Ta = -30°C to +85°C	—	—	200	μs

S1F77210Y1H0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.50	—	12.0	V
Detection voltage	VDET	Ta = 25°C	3.13	3.20	3.27	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.09	0.15	0.21	V
Operating current	IDD	VDD = 4.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
High level output current	IOH	VDD = 4.0V OUT = 3.6V	—	-1.60	-0.40	mA
Low level output current	IOL	VDD = 2.0V OUT = 0.2V	0.20	1.00	—	mA
Detection voltage response time	TPHL	VDD = 4V → 3V Ta = 25°C	—	8	40	μs
		VDD = 4V → 3V Ta = -30°C to +85°C	—	—	200	μs

S1F77200Y Series**S1F77210Y130**

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.50	—	12.0	V
Detection voltage	VDET	Ta = 25°C	3.43	3.50	3.57	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.09	0.15	0.21	V
Operating current	IDD	VDD = 4.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
High level output current	IOH	VDD = 4.0V OUT = 3.6V	—	-1.60	-0.40	mA
Low level output current	IOL	VDD = 2.0V OUT = 0.2V	0.20	1.00	—	mA
Detection voltage response time	T _{PHL}	VDD = 4V→3V Ta = 25°C	—	8	40	μs
		VDD = 4V→3V Ta = -30°C to +85°C	—	—	200	μs

S1F77210Y1T0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.50	—	12.0	V
Detection voltage	VDET	Ta = 25°C	3.90	4.00	4.10	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.13	0.20	0.27	V
Operating current	IDD	VDD = 5.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
High level output current	IOH	VDD = 5.0V OUT = 4.5V	—	-2.00	-0.50	mA
Low level output current	IOL	VDD = 2.0V OUT = 0.2V	0.20	1.00	—	mA
Detection voltage response time	T _{PHL}	VDD = 5V→4V Ta = 25°C	—	8	40	μs
		VDD = 5V→4V Ta = -30°C to +85°C	—	—	200	μs

S1F77210Y1M0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.50	—	12.0	V
Detection voltage	VDET	Ta = 25°C	4.10	4.20	4.30	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.13	0.20	0.27	V
Operating current	IDD	VDD = 5.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
High level output current	IOH	VDD = 5.0V OUT = 4.5V	—	-2.00	-0.50	mA
Low level output current	IOL	VDD = 2.0V OUT = 0.2V	0.20	1.00	—	mA
Detection voltage response time	TPHL	VDD = 5V → 4V Ta = 25°C	—	8	40	μs
		VDD = 5V → 4V Ta = -30°C to +85°C	—	—	200	μs

S1F77210Y1J0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.50	—	12.0	V
Detection voltage	VDET	Ta = 25°C	4.30	4.40	4.50	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.13	0.20	0.27	V
Operating current	IDD	VDD = 5.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
High level output current	IOH	VDD = 5.0V OUT = 4.5V	—	-2.00	-0.50	mA
Low level output current	IOL	VDD = 2.0V OUT = 0.2V	0.20	1.00	—	mA
Detection voltage response time	TPHL	VDD = 5V → 4V Ta = 25°C	—	8	40	μs
		VDD = 5V → 4V Ta = -30°C to +85°C	—	—	200	μs

S1F77200Y Series**S1F77210Y120**

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.50	—	12.0	V
Detection voltage	VDET	Ta = 25°C	4.50	4.60	4.70	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.08	0.15	0.22	V
Operating current	IDD	VDD = 5.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
High level output current	IOH	VDD = 5.0V OUT = 4.5V	—	-2.00	-0.50	mA
Low level output current	IOL	VDD = 2.0V OUT = 0.2V	0.20	1.00	—	mA
Detection voltage response time	T _{PHL}	VDD = 5V→4V Ta = 25°C	—	8	40	μs
		VDD = 5V→4V Ta = -30°C to +85°C	—	—	200	μs

S1F77210Y1K0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.50	—	12.0	V
Detection voltage	VDET	Ta = 25°C	4.70	4.80	4.90	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.13	0.20	0.27	V
Operating current	IDD	VDD = 5.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
High level output current	IOH	VDD = 5.0V OUT = 4.5V	—	-2.00	-0.50	mA
Low level output current	IOL	VDD = 2.0V OUT = 0.2V	0.20	1.00	—	mA
Detection voltage response time	T _{PHL}	VDD = 5V→4V Ta = 25°C	—	8	40	μs
		VDD = 5V→4V Ta = -30°C to +85°C	—	—	200	μs

S1F77210Y1L0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.50	—	12.0	V
Detection voltage	VDET	Ta = 25°C	4.90	5.00	5.10	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.13	0.20	0.27	V
Operating current	IDD	VDD = 6.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
High level output current	IOH	VDD = 6.0V OUT = 5.4V	—	-2.40	-0.60	mA
Low level output current	IOL	VDD = 2.0V OUT = 0.2V	0.20	1.00	—	mA
Detection voltage response time	TPHL	VDD = 6V → 4V Ta = 25°C	—	8	40	μs
		VDD = 6V → 4V Ta = -30°C to +85°C	—	—	200	μs

S1F77210Y1C0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.50	—	12.0	V
Detection voltage	VDET	Ta = 25°C	2.10	2.15	2.20	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.05	0.10	0.15	V
Operating current	IDD	VDD = 3.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
High level output current	IOH	VDD = 2.0V OUT = 1.8V	—	-0.40	-0.10	mA
Low level output current	IOL	VDD = 3.0V OUT = 0.3V	0.50	2.00	—	mA
Detection voltage response time	TPHL	VDD = 3V → 2V Ta = 25°C	—	8	40	μs
		VDD = 3V → 2V Ta = -30°C to +85°C	—	—	200	μs

S1F77200Y Series**S1F77210Y1F0**

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (V _{SS} = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	V _{DD}	—	1.50	—	12.0	V
Detection voltage	V _{DET}	Ta = 25°C	2.60	2.65	2.70	V
Hysteresis width	V _{HYS}	V _{HYS} = V _{REL} - V _{DET}	0.05	0.10	0.15	V
Operating current	I _{DD}	V _{DD} = 3.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
High level output current	I _{OH}	V _{DD} = 2.0V OUT = 1.8V	—	-0.40	-0.10	mA
Low level output current	I _{OL}	V _{DD} = 3.0V OUT = 0.3V	0.50	2.00	—	mA
Detection voltage response time	T _{PHL}	V _{DD} = 3V→2V Ta = 25°C	—	8	40	μs
		V _{DD} = 3V→2V Ta = -30°C to +85°C	—	—	200	μs

S1F77200Y1T0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (V _{SS} = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	V _{DD}	—	1.50	—	12.0	V
Detection voltage	V _{DET}	Ta = 25°C	3.90	4.00	4.10	V
Hysteresis width	V _{HYS}	V _{HYS} = V _{REL} - V _{DET}	0.13	0.20	0.27	V
Operating current	I _{DD}	V _{DD} = 5.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
Low level output current	I _{OL}	V _{DD} = 2.0V OUT = 0.2V	0.20	1.00	—	mA
Detection voltage response time	T _{PHL}	V _{DD} = 5V→4V Ta = 25°C	—	8	40	μs
		V _{DD} = 5V→4V Ta = -30°C to +85°C	—	—	200	μs

S1F77200Y1F0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.50	—	12.0	V
Detection voltage	VDET	Ta = 25°C	2.60	2.65	2.70	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.05	0.10	0.15	V
Operating current	IDD	VDD = 3.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
Low level output current	IOL	VDD = 2.0V OUT = 0.2V	0.20	1.00	—	mA
Detection voltage response time	T _{PHL}	VDD = 3V → 2V Ta = 25°C	—	8	40	μs
		VDD = 3V → 2V Ta = -30°C to +85°C	—	—	200	μs

S1F77200Y1C0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	0.80	—	10.0	V
Detection voltage	VDET	Ta = 25°C	2.10	2.15	2.20	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.05	0.10	0.15	V
Operating current	IDD	VDD = 3.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
Low level output current	IOL	VDD = 1.5V OUT = 0.15V	0.15	0.75	—	mA
Detection voltage response time	T _{PHL}	VDD = 3V → 2V Ta = 25°C	—	8	40	μs
		VDD = 3V → 2V Ta = -30°C to +85°C	—	—	200	μs

S1F77200Y Series**S1F77200Y1N0**

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (V _{SS} = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	V _{DD}	—	0.80	—	10.0	V
Detection voltage	V _{DET}	Ta = 25°C	1.85	1.90	1.95	V
Hysteresis width	V _{HYS}	V _{HYS} = V _{REL} - V _{DET}	0.03	0.05	0.08	V
Operating current	I _{DD}	V _{DD} = 3.0V	—	2.00	5.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
Low level output current	I _{OL}	V _{DD} = 1.5V OUT = 0.15V	0.15	0.75	—	mA
Detection voltage response time	T _{PHL}	V _{DD} = 2V→1V Ta = 25°C	—	8	40	μs
		V _{DD} = 2V→1V Ta = -30°C to +85°C	—	—	200	μs

S1F77200Y1B0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (V _{SS} = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	V _{DD}	—	0.80	—	10.0	V
Detection voltage	V _{DET}	Ta = 25°C	1.10	1.15	1.20	V
Hysteresis width	V _{HYS}	V _{HYS} = V _{REL} - V _{DET}	0.03	0.05	0.08	V
Operating current	I _{DD}	V _{DD} = 1.5V	—	1.50	4.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
Low level output current	I _{OL}	V _{DD} = 0.8V OUT = 0.16V	0.05	0.40	—	mA
Detection voltage response time	T _{PHL}	V _{DD} = 1.5V→0.8V Ta = 25°C	—	8	40	μs
		V _{DD} = 1.5V→0.8V Ta = -30°C to +85°C	—	—	200	μs

S1F77200Y1Y0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (V _{SS} = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	V _{DD}	—	0.80	—	10.0	V
Detection voltage	V _{DET}	Ta = 25°C	1.05	1.10	1.15	V
Hysteresis width	V _{HYS}	V _{HYS} = V _{REL} - V _{DET}	0.03	0.05	0.08	V
Operating current	I _{DD}	V _{DD} = 1.5V	—	1.50	4.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
Low level output current	I _{OL}	V _{DD} = 0.8V OUT = 0.16V	0.05	0.40	—	mA
Detection voltage response time	T _{PHL}	V _{DD} = 1.5V → 0.8V Ta = 25°C	—	8	40	μs
		V _{DD} = 1.5V → 0.8V Ta = -30°C to +85°C	—	—	200	μs

S1F77200Y1A0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (V _{SS} = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	V _{DD}	—	0.80	—	10.0	V
Detection voltage	V _{DET}	Ta = 25°C	1.00	1.05	1.10	V
Hysteresis width	V _{HYS}	V _{HYS} = V _{REL} - V _{DET}	0.03	0.05	0.08	V
Operating current	I _{DD}	V _{DD} = 1.5V	—	1.50	4.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
Low level output current	I _{OL}	V _{DD} = 0.8V OUT = 0.16V	0.05	0.40	—	mA
Detection voltage response time	T _{PHL}	V _{DD} = 1.5V → 0.8V Ta = 25°C	—	8	40	μs
		V _{DD} = 1.5V → 0.8V Ta = -30°C to +85°C	—	—	200	μs

S1F77200Y Series**S1F77200Y1V0**

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

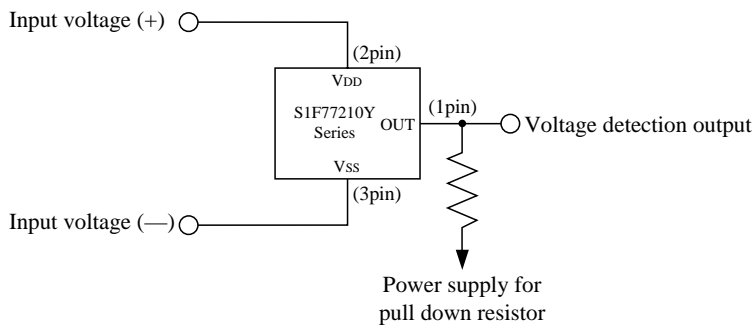
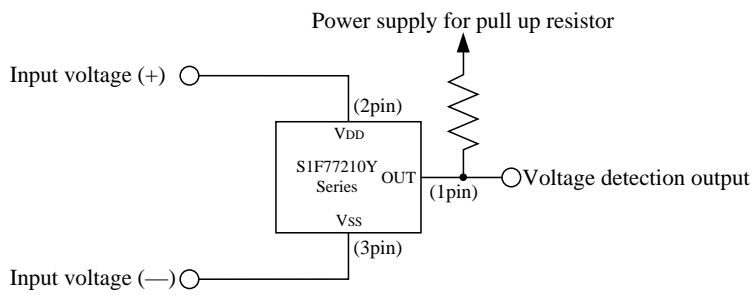
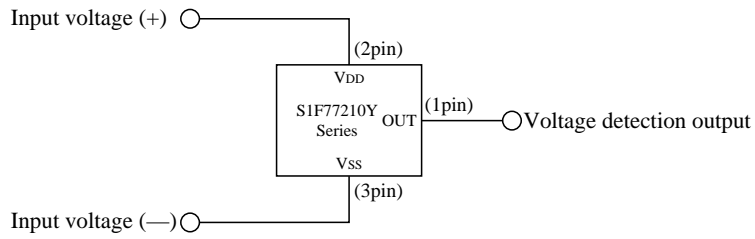
Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	0.80	—	10.0	V
Detection voltage	VDET	Ta = 25°C	0.90	0.95	1.00	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.03	0.05	0.08	V
Operating current	IDD	VDD = 1.5V	—	1.50	4.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
Low level output current	IOL	VDD = 0.8V OUT = 0.16V	0.05	0.40	—	mA
Detection voltage response time	T _{PHL}	VDD = 1.5V → 0.8V Ta = 25°C	—	8	40	μs
		VDD = 1.5V → 0.8V Ta = -30°C to +85°C	—	—	200	μs

S1F77220Y2D0

(Ta = -30°C to +85°C is assumed except where otherwise specified.)

Parameter	Symbol	Conditions (Vss = 0.0V)	Min.	Typ.	Max.	Unit
Operating voltage	VDD	—	1.5	—	12.0	V
Detection voltage	VDET	Ta = 25°C	1.20	1.25	1.30	V
Hysteresis width	VHYS	VHYS = VREL - VDET	0.03	0.05	0.08	V
Operating current	IDD	VDD = 3.0V	—	1.50	4.00	μA
Detection voltage temperature characteristics	$\frac{\Delta V_{DET}}{V_{DET}}$	—	-300	-100	+100	ppm/°C
Low level output current	IOL	VDD = 1.5V OUT = 0.64V	—	-0.03	-0.06	mA
Detection voltage response time	T _{PHL}	VDD = 1.5V → 0.8V Ta = 25°C	—	8	40	μs
		VDD = 1.5V → 0.8V Ta = -30°C to +85°C	—	—	200	μs

EXAMPLES OF EXTERNAL CONNECTION



S1F77200Y Series

S1F77200Y Series

SAMPLE CIRCUITS (S1F77210Y Series)

CR timer circuit

When the S1F77210Y circuit configured as shown in Figure 5-14, it can be used as a CR timer circuit.

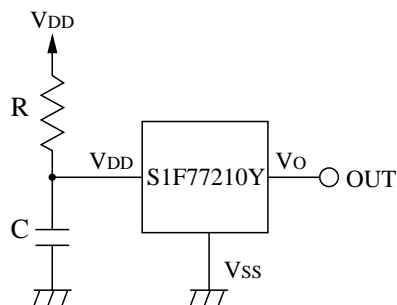


Figure 5-14 CR timer circuit

Battery backup circuit

The following is an example of the supply voltage switching circuit for the battery backup supply configured featuring the S1F77210Y series.

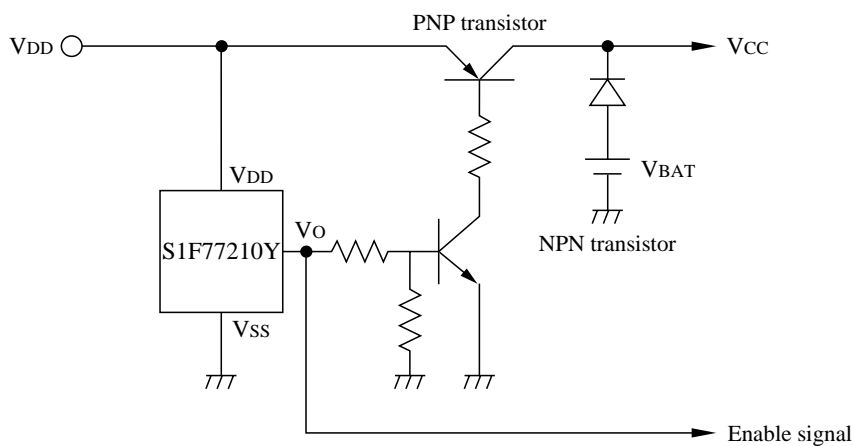


Figure 5-15 Battery backup circuit

SAMPLE CIRCUITS (S1F77200Y Series)

CR timer circuit

When the S1F77200Y circuit is configured as shown in Figure 5-16, it can be used as a CR timer circuit.

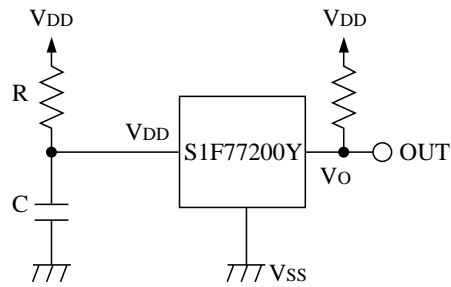


Figure 5-16 CR timer circuit

Battery backup circuit

The following is an example of the supply voltage switching circuit for the battery backup configured featuring the S1F77200Y series.

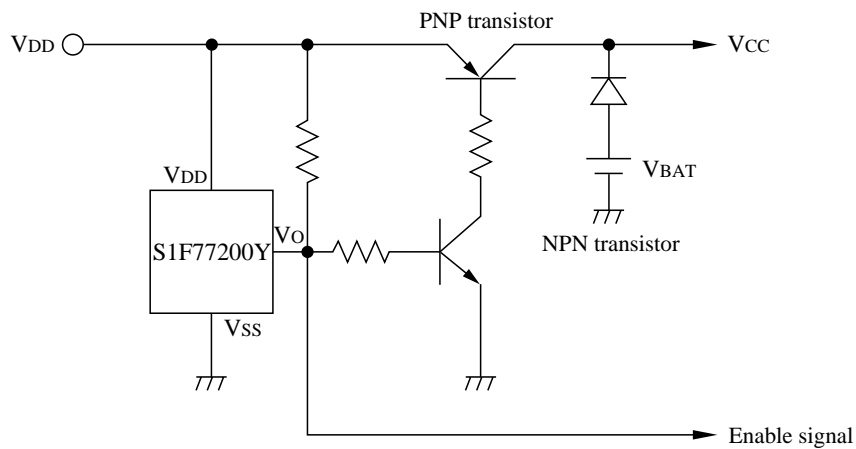


Figure 5-17 Battery backup circuit

S1F77200Y Series

S1F77200Y Series

PRECAUTIONS

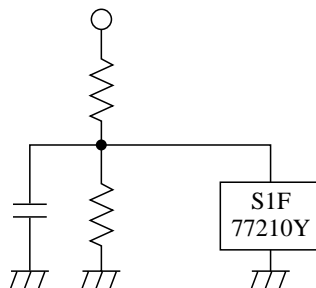
Short cut current on the S1F77210 (CMOS output voltage detector)

Since the S1F77200Y series employs CMOS output, as an input voltage nears the detection voltage range, short cut current is flown between VDD and VSS. The short cut current is voltage sensitive, and approximately 2 mA flows at 5V level or so (our products are not check for short cut current after volume production has been started).

Although duration of the short cut current depends on operating conditions (such as type the circuit used and supply impedance), normally it is assumed to continue several usec to several dozens of usec.

If a load with high impedance is inserted across the power supply, oscillation can be introduced by the short cut current. In order to reject this trouble, the following measures should be considered:

- (1) Reduce the resistance value.
- (2) Insert a capacitor.
- (3) Replace with the S1F77200Y series (it employs N-channel open drain approach).



7. Appendix

ABSOLUTE MAXIMUM RATINGS

Absolute maximum ratings are the maximum physical and electrical ratings of a device beyond which performance degradation or damage will occur. Always check circuit conditions before using a device to avoid exceeding these ratings. Typically, absolute maximum ratings include the following parameters.

1. Power supply voltage
Steady state applied voltages, noise, reverse voltage transients and power-on-transients can degrade or damage the integrated circuit if they exceed the maximum power supply voltage rating.
2. Input signal voltage
Input signals exceeding this rate can damage input protection circuits
3. Output current
Generally, specifications are not set for CMOS devices with small output currents. Devices that provide large drive currents will have output current specifications.
4. Power dissipation
The maximum power dissipation of a device is limited by its construction and package type. Maximum output current limits are set to prevent thermal damage.
5. Operating temperature range
The temperature range for normal device operation with no change in performance characteristics.
6. Storage temperature range
The temperature range for device storage with no degradation or damage. This specification is particularly important when ICs are being transported by air.
7. Soldering temperature and the duration
The maximum soldering temperature and the time for which the leads can be at this temperature.

RECOMMENDED OPERATING CONDITIONS

Recommended operating conditions are the conditions under which a device functions correctly. These include power supply voltage, input conditions and output current. These conditions are sometimes listed as part of the electrical characteristics.

ELECTRICAL CHARACTERISTICS

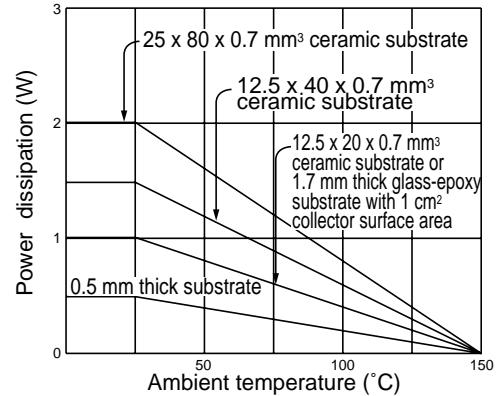
Electrical characteristics specify the DC and AC characteristics of a device under the worst measurement conditions.

POWER DISSIPATION CONDITIONS

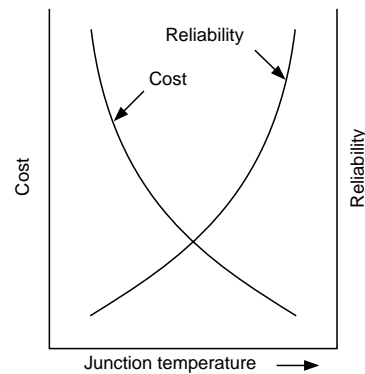
To prevent damage always consider the following points when designing with power regulation ICs.

1. A precise thermal design is necessary to ensure adequate heat dissipation.

The following figure shows the power dissipation capacity in relation to ambient temperature.

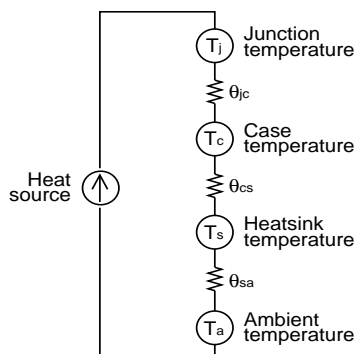


The following figure shows the cost and reliability of a product and is significant when designing a system.



Appendix

The following figure shows a thermal design model which can be used to determine heatsink capacity.



2. Ensure that the regulator common pin is a single-point ground to prevent earth loops. Make ground lines as thick and short as possible. Use the specified bypass capacitors for inputs and outputs. If there is a switching load, use a tantalum or ceramic capacitor, as these devices have a high frequency response between the power supply and ground.

PARAMETER SUMMARY

Symbol	Parameter
C_D	Drain capacitance
C_{F8}	Field slew capacitance
C_G	Gate capacitance
C_I	Input capacitance
C_n	Capacitance
CT	Crosstalk
CT_n	Temperature gradient
f_{CLK}	Clock frequency
f_{max}	Maximum clock frequency
f_{OSC}	Oscillator frequency
FT	Field through (channel OFF)
I_{BSQ}	Backup switching leakage current
I_{DDO}	Operating current
I_{DDS}	Standby current
I_{DD}	Power supply current
I_{IH}	High-level input current
I_{IL}	Low-level input current
I_{LKI}	input leakage current
I_{MAX}	Maximum current
I_O	Output current
I_{OH}	High-level output current
I_{OL}	Low-level output current
I_{OPR1}	Multiplier circuit power dissipation

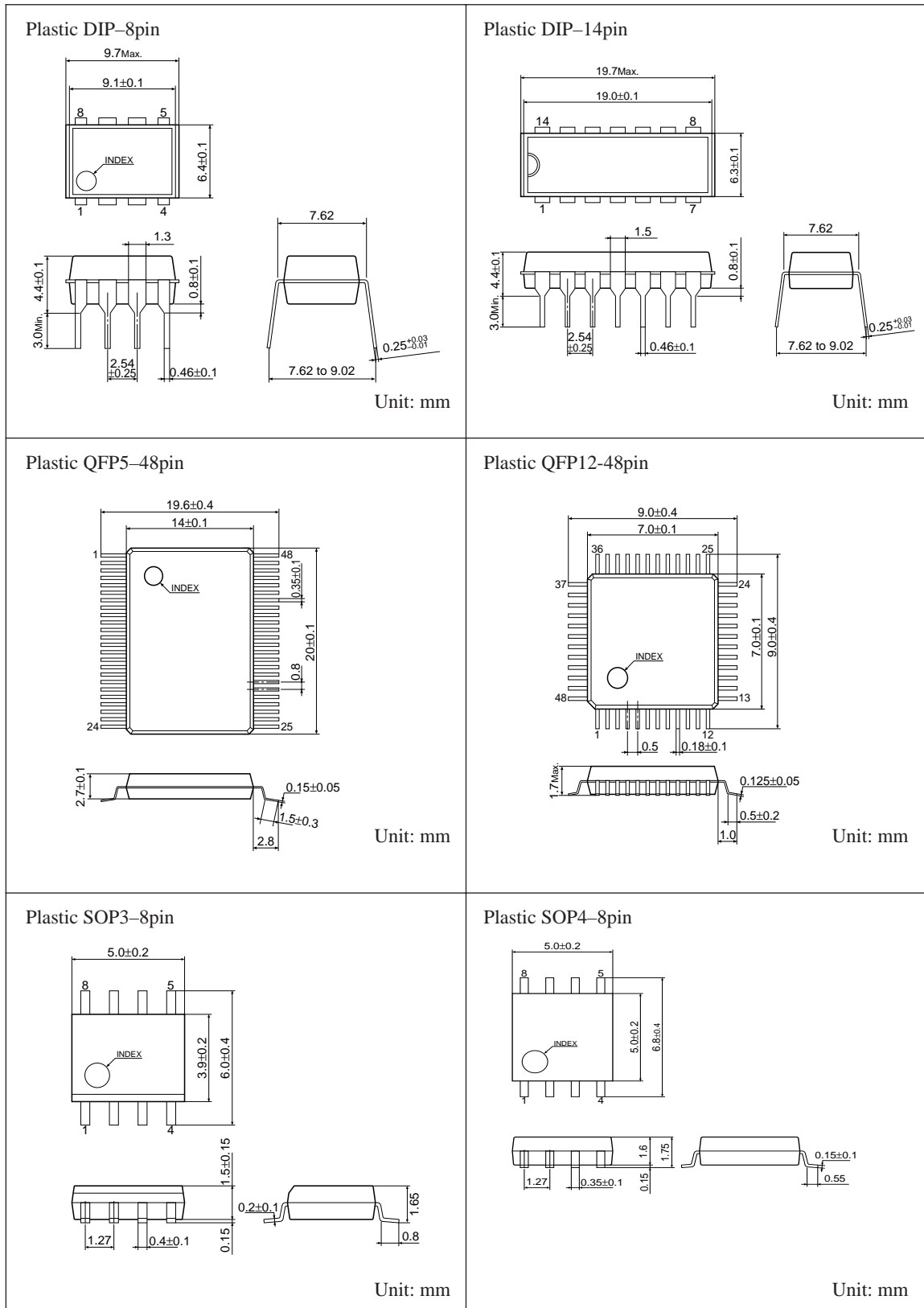
Symbol	Parameter
I_{OPR2}	Stabilization circuit power dissipation
I_Q	Quiescent current
I_R	Reverse current
I_{SWQ}	Switching transistor leakage current
K_I	Output voltage temperature gradient
P_D	Power dissipation
P_{eff}	Voltage multiplication efficiency
R_{BSON}	Backup switch ON resistance
R_L	Load resistance
R_O	Output impedance
R_{ON}	ON resistance
R_{OSC}	Oscillator network resistor
R_{RV}	Stabilization voltage sensing resistor
R_{RVn}	Reference voltage
R_{SAT}	Stabilization output saturation resistance
R_{SWON}	Switching transistor ON resistance
T_a	Ambient temperature
t_{AE}	Minimum pulsewidth
t_{HA}	Address hold time
t_{HD}	Data hold time
THD	Total harmonic distortion
θ_{jn}	Thermal resistance
t_{MRR}	Memory reset recovery time

Symbol	Parameter
t _{MR}	Memory reset
T _{opr}	Operating temperature
t _{PAE}	Propagation delay
t _{PHL}	Low-level transition time
t _{PLH}	High-level transition time
t _{PLS}	Propagation delay
t _{POP}	Propagation delay
t _{PS}	Propagation delay
t _{SA}	Address setup time
t _{SD}	Data setup time
T _{sol}	Soldering temperature and time
T _{stg}	Storage temperature
V _{DD}	Power supply voltage
V _{DET}	Detection voltage
V _F	Forward voltage

Symbol	Parameter
V _I	Input voltage
V _{IH}	High-level input voltage
V _{IL}	Low-level input voltage
V _I	Input voltage
V _O	Output voltage
V _{off}	Input offset voltage
V _{op+}	Input voltage range
V _{OPMAX}	Maximum output voltage
V _{OPMIN}	Minimum output voltage
V _{REF}	Reference voltage
V _{REG}	Output voltage (regulated)
V _{SS}	Power supply voltage
V _{SSn}	Power supply voltage
V _{STA}	Oscillator start-up voltage
V _{STP}	Oscillator shut-down voltage

Appendix

MECHANICAL DATA



<p>Plastic SOP5-14pin</p> <p>10.5Max. 10.2±0.2 14 8 INDEX 5.5±0.2 8.0±0.3 6.8 1.27±0.1 0.4±0.1 0.1±0.08 2.2Max. 2.3 0.15±0.1 0.4</p> <p>Unit: mm</p>	<p>SOT 89-3pin</p> <p>4.5±0.1 1.8Max. 0.4 2.5±0.1 4.25Max. 0.8 Min. 1.5 1.5 0.44Max. 0.44Max. 1.5±0.1 0.48Max. 0.53Max. 0.48Max.</p> <p>Unit: mm</p>
<p>Plastic SOP2-24pin</p> <p>15.5Max. 15.2±0.1 24 12 INDEX 8.4±0.1 11.8±0.3 1.27 0.4±0.1 0.2 2.5±0.15 2.7 0.15±0.05 1.0</p> <p>Unit: mm</p>	<p>Plastic SOP2-28pin</p> <p>18.1Max. 17.8±0.1 28 14 INDEX 8.4±0.1 11.8±0.3 1.27 0.4±0.1 0.2 2.5±0.15 2.7 0.15±0.05 1.0</p> <p>Unit: mm</p>
<p>Plastic SSOP2-16pin</p> <p>6.8±0.2 6.6±0.2 16 9 INDEX 4.4±0.2 6.2±0.3 0.8 0.36±0.1 0.09 1.5 1.7Max. 0.15 0.5±0.2 0.9</p> <p>Unit: mm</p>	<p>Plastic SSOP1-20pin</p> <p>6.5±0.1 20 11 INDEX 4.4±0.1 6.4±0.3 0.65 0.22±0.1 0.1±0.05 1.2Max. 0.15 0.5±0.2 1</p> <p>Unit: mm</p>

Appendix

EMBOSS CARRIER TAPING STANDARD (SOT89-3pin)

TAPING INFORMATION

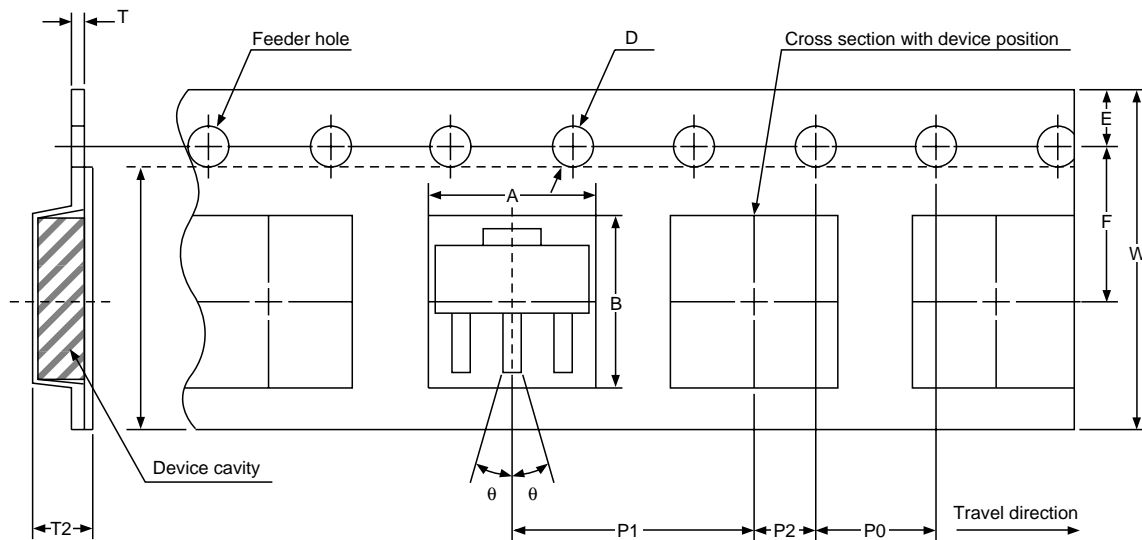
The emboss carrier taping standard is shown in the following table and figure. This standard conforms to

Dimension code	Dimensions/angles (mm/°)
A	5.0
B	4.6
D	1.5 +0.1, -0.05
E	1.50 ±0.1
F	5.65 ±0.05
P1	8.0 ±0.1
P0	4.0 ±0.1

the EIAJ RCI00B electronic parts taping specification. Each tape holds 1,000 devices.

Dimension code	Dimensions/angles (mm/°)
P2	2.0 ±0.05
T	0.3
T2	2.3
W	12.0 ±0.2
W1	9.5
θ	30°Max.

Note
The tape thickness is 0.1 mm Max.



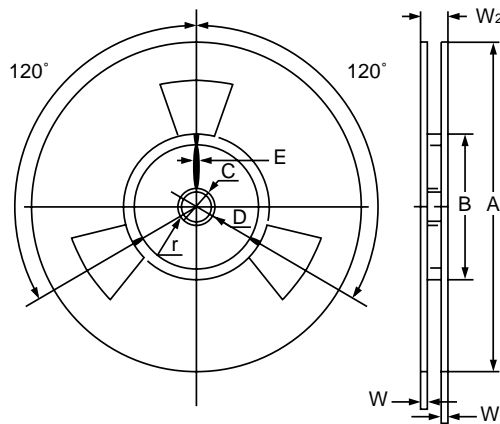
There are no joints in either the cover or carrier tapes. Less than 0.2% of the total device count is comprised of non-sequential blanks. There are no sequential

blanks. This does not apply to the tape leader and trailer.

REEL SPECIFICATIONS

The reel specifications are shown in the following table and figure. The reel is made of paperboard.

Dimension code	Dimensions (mm)
A	178 ±2.0
B	80 ±1.0
C	13.0 ±0.5
D	21.0 ±1.0
E	2.0 ±0.5
W	14.0 (See note.)
W1	1.5 ±0.1
W2	17 (See note.)
r	1.0

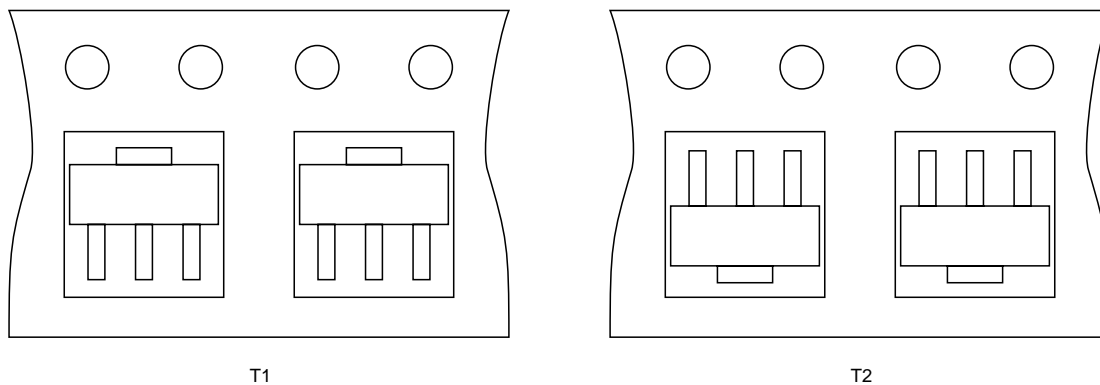


Note

W and W2 are measured at the reel core.

DEVICE POSITIONING

Small molded power IC devices are positioned as shown in the following figure.



Appendix

EMBOSS CARRIER TAPING STANDARD (SOP3-8pin)

TAPING INFORMATION

The emboss carrier taping standard is shown in the following table and figure. This standard conforms to

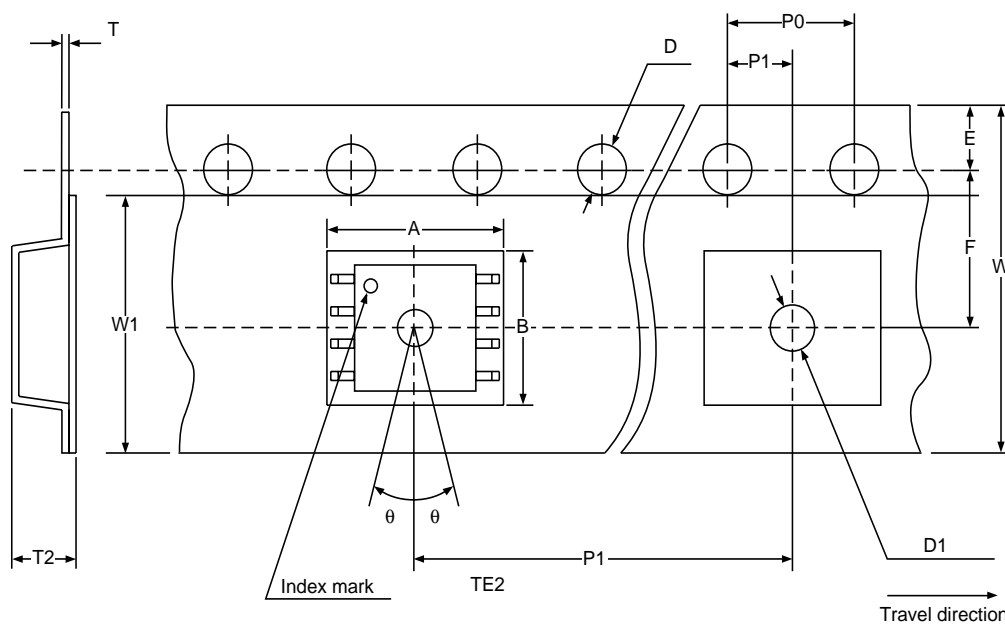
Dimension code	Dimensions/angles (mm/°)
A	6.7
B	5.4
D	1.55 +0.05, -0
D1	1.55 ±0.05
E	1.75 ±0.1
F	5.5 ±0.1
P1	8.0 ±0.1
P0	4.0 ±0.1

the EIAJ RCI009B electronic parts taping specification. Each tape holds 2,000 devices.

Dimension code	Dimensions/angles (mm/°)
P2	2.0 ±0.05
T	0.3 ±0.05
T2	2.5
W	12.0 ±0.3
W1	9.5
θ	15°Max.

Note

The tape thickness is 0.1 mm Max.



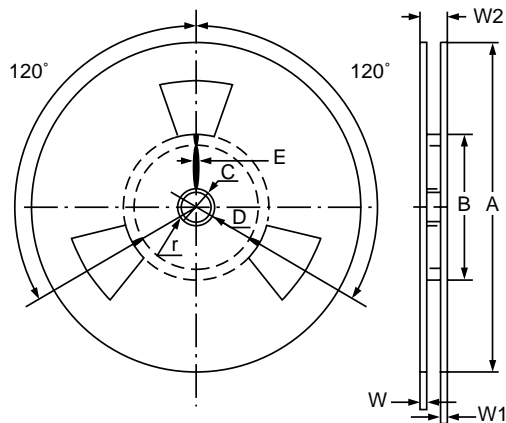
There are no joints in either the cover or carrier tapes. Less than 0.2% of the total device count is comprised of non-sequential blanks. There are no sequential

blanks. This does not apply to the tape leader and trailer.

REEL SPECIFICATIONS

The reel specifications are shown in the following table and figure. The reel is made of paperboard.

Dimension code	Dimensions (mm)
A	330 ±2.0
B	80 ±1.0
C	13.0 ±0.5
D	21.0 ±0.5
E	2.0 ±0.5
W	15.4 ±1.0 (See note.)
W1	2.0 ±0.5
W2	23.4 (See note.)
r	1.0

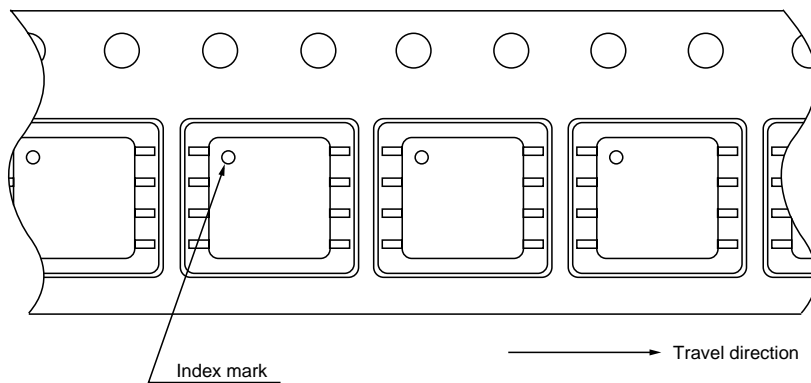


Note

W and W2 are measured at the reel core.

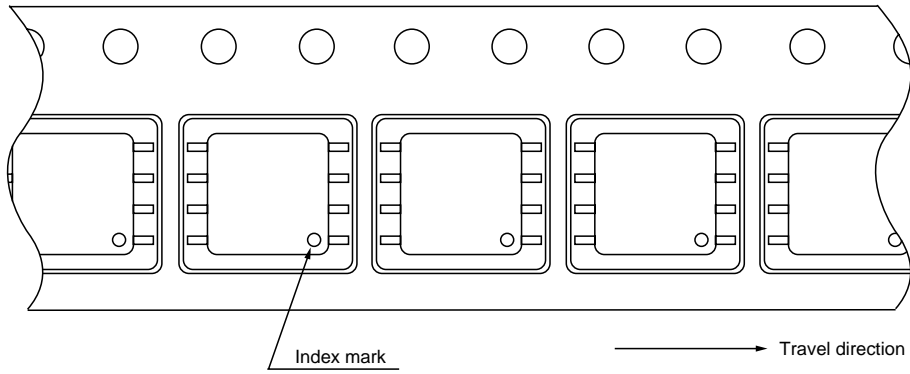
DEVICE POSITIONING

Type B products are positioned so that the index mark is on the sprocket hole side of the tape, as shown in the following figure.



Appendix

Type F product are positioned so that the index mark is on the opposite side to the sprocket holes, as shown in the following figure.



EMBOSS CARRIER TAPING STANDARD (SOP5-14pin)

TAPING INFORMATION

The emboss carrier taping standard is shown in the following table and figure. This standard conforms to

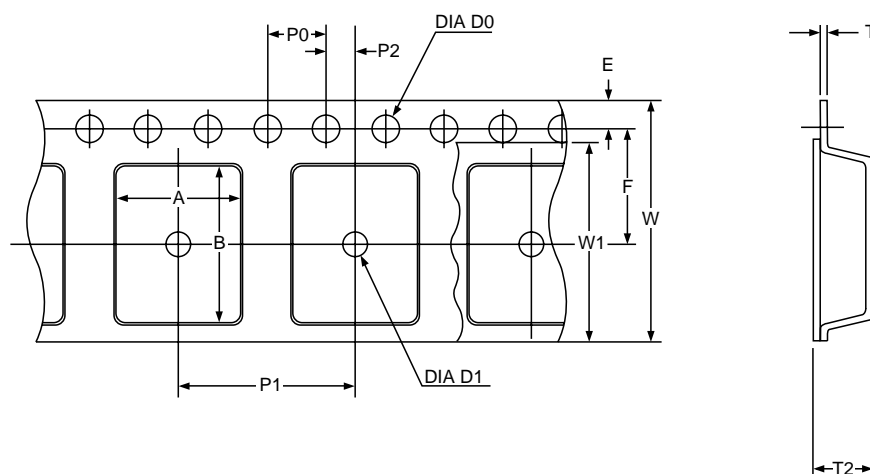
Dimension code	Dimensions (mm/°)
A	8.4
B	10.6
D0	1.55 ±0.05
D1	1.55 ±0.05
E	1.75 ±0.1
F	7.5 ±0.1
P1	12 ±0.1
P0	4.0 ±0.1

the EIAJ RCI009B electronic parts taping specification. Each tape holds 2,000 devices.

Dimension code	Dimensions (mm/°)
P2	2.0 ±0.1
T	0.3 ±0.05
T2	3.0
W	16.0 ±0.3
W1	13.5

Note

The tape thickness is 0.1 mm Max.



There are no joints in either the cover or carrier tapes. Less than 0.1% of the total device count is comprised of non-sequential blanks. There are no sequential

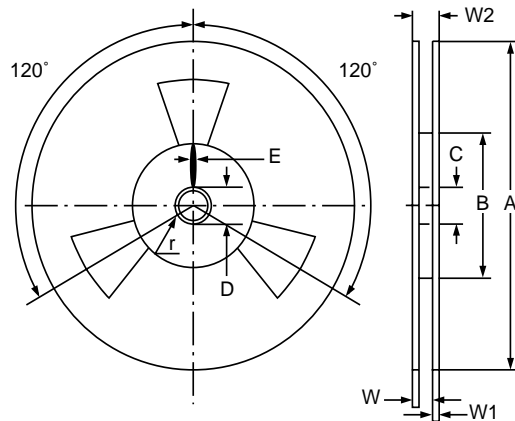
blanks. This does not apply to the tape leader and trailer.

Appendix

REEL SPECIFICATIONS

The reel specifications are shown in the following table and figure. The reel is made of paperboard.

Dimension code	Dimensions (mm)
A	330 ±2.0
B	80 ±1.0
C	13.0 ±0.5
D	21.0 ±1.0
E	2.0 ±0.5
W	14.0 ±1.5 (See note.)
W1	2.0 ±0.5
W2	20.5 max (See note.)
r	1.0

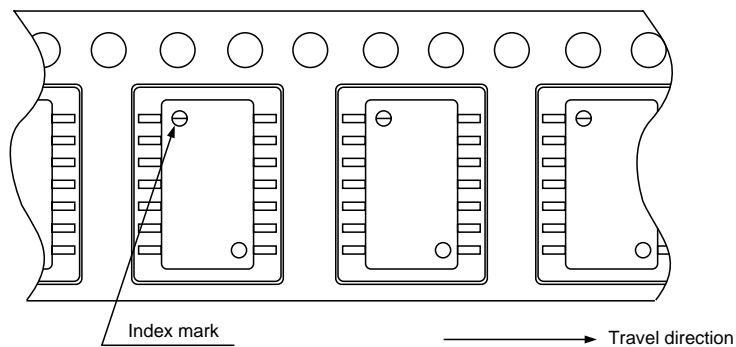


Note

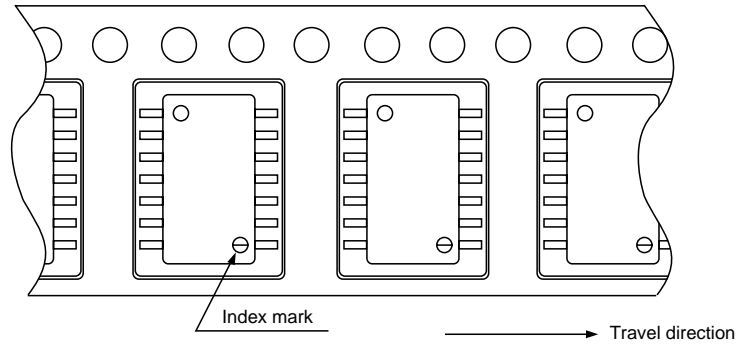
W and W2 are measured at the reel core.

DEVICE POSITIONING

Type B products are positioned so that the index mark is on the sprocket hole side of the tape, as shown in the following figure.



Type F products are positioned so that the index mark is on the opposite side to the sprocket holes, as shown in the following figure.



Appendix

EMBOSS CARRIER TAPING STANDARD (SOP2-24pin)

TAPING INFORMATION

The emboss carrier taping standard is shown in the following table and figure. This standard conforms to

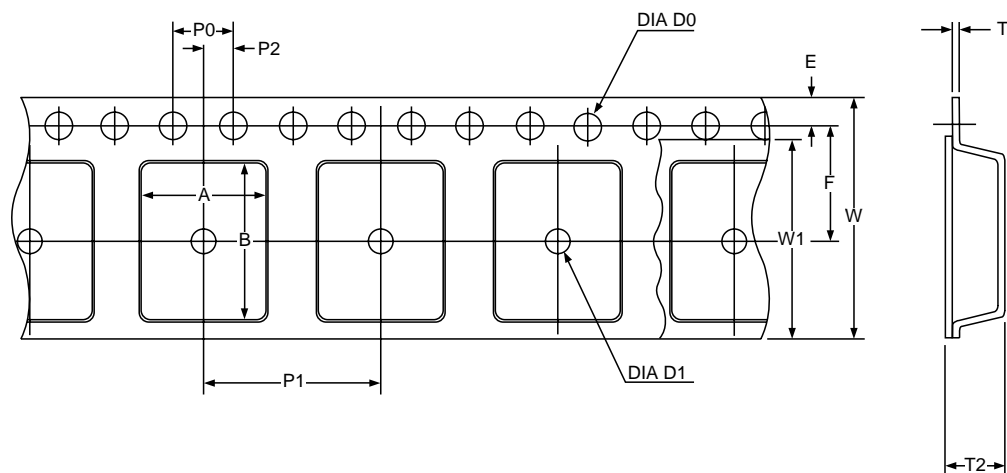
Dimension code	Dimensions (mm)
A	12.4
B	15.6
D0	1.55 +0.1, -0
D1	2.0 +0.1, -0
E	1.75 ±0.1
F	11.5 ±0.1
P1	16 ±0.1

the EIAJ RCI009B electronic parts taping specification. Each tape holds 1,000 devices.

Dimension code	Dimensions (mm)
P0	4.0 ±0.1
P2	2.0 ±0.1
T	0.3 ±0.05
T2	3.0 ±0.1
W	24 ±0.2
W1	21.5 Typ.

Note

The tape thickness is 0.1 mm Max.



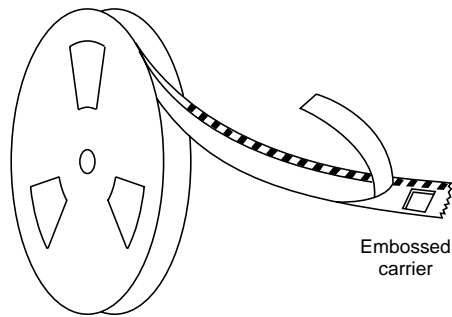
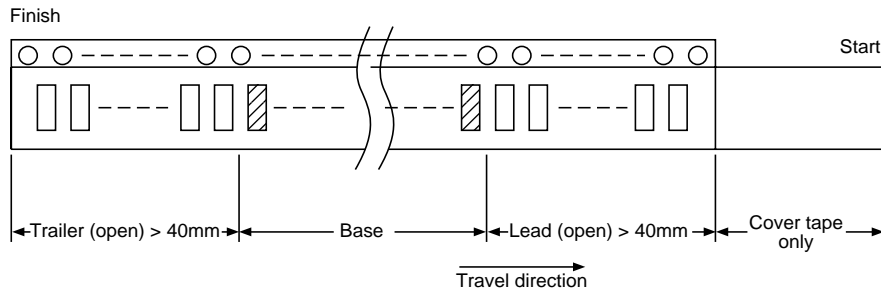
There are no joints in either the cover or carrier tapes. Less than 0.2% of the total device count is comprised of non-sequential blanks. There are no sequential blanks. This does not apply to the tape leader and

trailer. The tape tension should be approximately 10 N (1 kgf). A label indicates the part name, quantity and lot number.

Tape configuration

The tape configuration is shown in the following figure. Blank sections are provided as a leader and trailer, with 1,000 SOP2 packages fitted into the component mounting section between them. At the begin-

ning of the leader section there is an extra section of tape which contains the cover tape only.

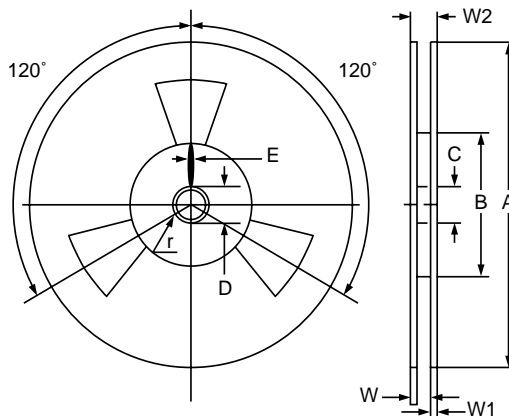


Appendix

REEL SPECIFICATIONS

The reel specifications are shown in the following table and figure. The reel is made of conductive PVC.

Dimension code	Dimensions (mm)
A	330 ±2.0
B	80 ±1.0
C	13.0 ±0.5
D	21.0 ±1.0
E	2.0 ±0.5
W	24.4 +2, -0 (See note.)
W1	2.0 ±0.5
W2	31.4 Max. (See note.)
r	1.0

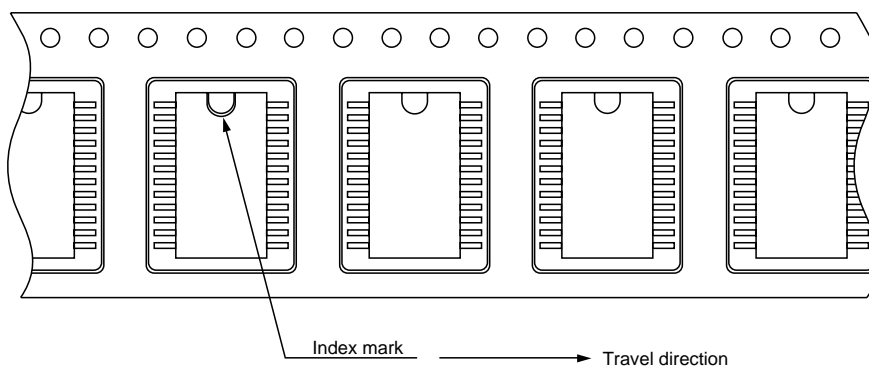


Note

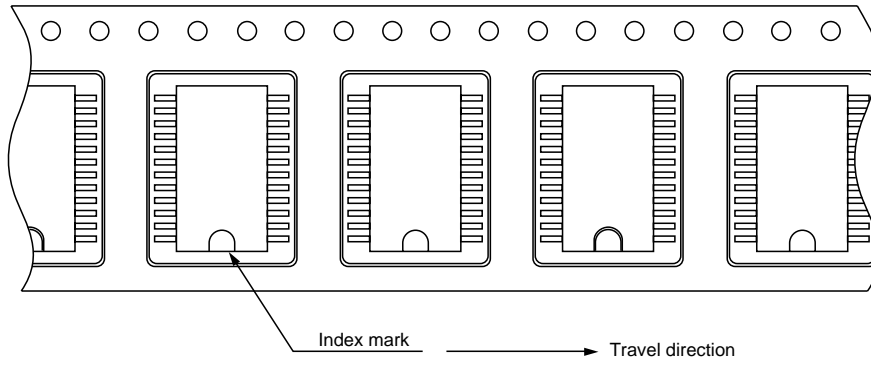
W and W2 are measured at the reel core.

DEVICE POSITIONING

Type B products are positioned so that the index mark is on the sprocket hole side of the tape, as shown in the following figure.



Type F products are positioned so that the index mark is on the opposite side to the sprocket holes, as shown in the following figure.



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